ELECTRON/PROTON SPECTROMETER CERTIFICATION DOCUMENTATION ANALYSES

Document Number EPS-779

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Prepared by

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Houston, Texas
Under Contract NAS 9-11373

for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

(NASA-CR-128/03) LEGICATION DOCUMENTATION SPECTROMETER CERTIFICATION DOCUMENTATION ANALYSES (Lockheed Electronics Co.)

N73-1757

ELECTRON/PROTON SPECTROMETER CERTIFICATION DOCUMENTATION ANALYSES

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ELECTRON/PROTON SPECTROMETER CERTIFICATION DOCUMENTATION: ANALYSES

1.0 INTRODUCTION

This document contains a compilation of analyses generated throughout the progressive development of the Electron/Proton Spectrometer (EPS) for Skylab. The purpose of the compilation of these data is to document the analyses required by the "EPS Verification Plan" (LEC Document No. EPS-435). The "EPS Verification Plan" was generated to satisfy the "Apollo Applications Program Ancillary Hardware General Requirements" (MSC Document No. MSC-KA-D-69-44, Revision A), and the NASA Contract, "Electron/Proton Spectrometer for Skylab", NAS 9-11373.

2.0 CERTIFICATION OF THE EPS

The certification of the EPS requires that the various tests, inspections, and analyses be documented and approved/accepted by the cognizant Reliability and Quality Assurance personnel for the EPS program. The certification is to be accomplished in three parts in accordance with the "EPS Verification Plan".

- e Evaluation and review of the "Qualification Test Procedure", the records of the qualification testing of the EPS Qualification Test Unit, the "Qualification Test Report", and the acceptance test procedures.
- data points defined by the "EPS Verification Plan", and the results of the various inspections.

2.0 Continued

e Evaluation and review of the various analyses performed during the development and testing of the EPS.

2.1 Qualification Verification

The "Qualification Test Procedure", the records of the qualification testing of the EPS Qualification Test Unit, the "Qualification Test Report", and the acceptance test procedures have been reviewed and accepted by NASA/MSC.

2.2 Inspection Verification

The inspection procedures and data points, as defined by the "EPS Verification Plan", and the results of the various inspections have been reviewed and accepted by NASA/MSC.

2.3 Analyses Verification

The collection and identification of the various analyses performed during the development of the EPS are contained within this document to facilitate their evaluation and review. Analyses made during the early development stages of the EPS program are not necessarily correct for the final item. The early analyses, however, provided the basis for arriving at the final configuration of the EPS, and reflect the progression of scientific and engineering skills in the development of a superior product.

3.0 VERIFICATION MATRIX

The "Verification Matrix", a sub-section of the "EPS Verification Plan", provides, in matrix form, a listing of the various EPS functions to test, inspect, and analyze, in order to comply with the requirements of the EPS contract NAS 9-11373

3.0 Continued

and the "AAP Ancillary Hardware General Requirements". The contents of this document, therefore, is a representative cross-section of the various analyses made during the development of the EPS, and are arranged in section order as found in the "Verification Matrix" (see Table 1 - "EPS Verification Plan - Verification Matrix").

TABLE I - EPS VERIFICATION PLAN - VERIFICATION MATRIX

· · · ·	
VERIFICATION METHOD:	TEST TYPE
1. TEST	NR - NO REQUIREMENT
2. ASSESSMENT	A - DEVELOPMENT
A. SIMILARITY	B - QUALIFICATION
B. ANALYSIS	C - ACCEPTANCE
C. INSPECTION	D - PRE-INSTALLATION
D. DEMONSTRATION	E - INTEGRATED SYSTEMS
	F - PRELAUNCH
	G - OTHER

Section 3.0 End Item	,	VER	IFIC	OITA	Verification Plan				
Specification Reference	NR	А	В	С	D	E	F	G	Reference
3.0 3.1	X X		,						
3.1.1	X X								
3.1.1.1 3.1.1.1A 3.1.1.1B 3.1.1.1C 3.1.1.1D 3.1.1.1E 3.1.1.1F 3.1.1.1G 3.1.1.2 3.1.1.2.1 3.1.1.2.2	x	1 1 1 1 1	1 1 1	1					2.3.4 2.3.4 2.3.4 2.3.4 3.1 2.3.4 2.1 & 3.1 2.3.4, 3.1.8 & 4.2

	:	٠.							
Section 3.0 End Item		VER	IFIC	ATIC	N !1E	тноі	D		Verification Plan
Specification Reference	NR	A	В	С	D	E	F	G	Reference
3.1.2.2 3.1.2.2.1a 3.1.2.2.1b 3.1.2.2.1d 3.1.2.3 3.1.2.4 3.1.2.5 3.1.2.6 3.1.2.7 3.1.2.8 3.2 3.2.1 3.2.1.1 3.2.1.1.1 3.2.1.1.1 3.2.1.1.6 3.2.1.5 3.2.1.5 3.2.1.6	X X X X	2C 2C 2B 2B	1 1 2C 2B 2B 2B			E			3.1.2 thru 3.1.7 3.1.2 thru 3.1.7 3.1.2 & 3.1.3
3.3 3.3.1 3.3.1.6 3.3.1.7	x x		20						
3.3.1.7.1 3.3.1.8 3.3.2	x x		21	3					

TABLE I - EPS VERIFICATION PLAN - VERIFICATION MATRIX (Continued)

Section 3.0 End Item		VER	IFIC	OITA	Verification Plan				
Specification Reference	NR	Α	В	С	D	E	F	G	Reference
			2C						
3.3.2.3	Ì	1 13	2B			•			
3.3.2.4		2B	2C						
3.3.2.5		2.0	2B						•
3.3.2.6		. 2B	ļ						
3.3.2.7		2B	2B						
3.3.2.9		2B	2B						2.3.3 & 3.1.6
3.3.2.10		1	1		<u> </u>				3.1.2
3.3.2.11			1						3.1.2
3.3.2.12	X				İ				3.1.8 & 4.2
3.3.2.13			1	1					i i
3.3.2.14		1	1						2.3.3 & 3.1.6
3.3.2.15				2C					
3.3.2.16				2C		1			
3.3.4	х								
3.3.4a			2B						
3.3.4b			2B						
3.3.4d] .		2B						
3.3.5	1		2C	2C					
3.3.6	х								
3.3.6.1	1	2B	2C						
3.3.6.2		2B	2D	2D					
3.3.7	1	2B	23			•			
3.3.8	x								
3.3.8.1	х								
		1	i	1	ı	1	1	1	
	X				1	1	1		
3.3.8.2 3.3.9	x	2B	2B						

TABLE I - EPS VERIFICATION PLAN - VERIFICATION MATRIX (Concluded)

Section 3.0		VER	IFIC.						
End Item Specification Reference	NR	A	В	С	D	Е	F	G	Verification Plan Reference
3.3.10.1	х								
3.3.10.2	·	2В	2B						
3.3.10.3		2 B	2C	2C			ľ		
3.3.10.4		2B	2C	2C					·
3.3.10.5	•		2C	2C					
3.3.10.6			2C	2C					
3.3.10.7		2B	2C	2C					
3.3.10.8				2C					:
3.3.10.9		2В	2B						
3.3.10.9.1		2В	2B						
3.3.11		2B	2B						
3.3.12		2B	2B						· .
3.3.13		2B	2C						
3.3.14		2B	2C						
3.3.15		2C	2C	2C					
3.3.16		1	1						2.3.1 & 3.1.7
3.3.17		2C	2C	2C					
3.3.18			2В						
3.3.19	X.				1	1			

VERIFICATION MATRIX'S SECTIONS APPLICABLE TO ASSESSMENT ANALYSIS (INDEX)

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3.1.2.3 Minimum Useful Life

The detectors are the only items on the EPS having a limited life expectancy. The detectors, therefore, are subjected to a special screen and burn-in program to determine their operating parameters, their statistical useful life, and their reliability. Also, because of the limited life expectancy of the detectors, the EPS flight units will be delivered to NASA/MSC with diodes mounted in place of detectors. The flight detectors will be installed on the EPS flight units shortly before launch.

3.1.2.8 Safety

The document "Safety Assessment for EPS Electron-Proton Spectrometer", EPS-425, included herein, presents the safety analyses.

SAFETY ASSESSMENT

FOR

EPS ELECTRON-PROTON SPECTROMETER

LEC Document Number EPS-425

Prepared by

Lockheed Electronics Company, Inc.
Houston Aerospace Systems Division
Houston, Texas

Under Contract NAS 9-11373

For

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

August 1971

SAFETY ASSESSMENT

FOR

EPS ELECTRON-PROTON SPECTROMETER

Prepared by:

Reliability and Quality Assurance Engineer

Approved by:

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Approved by:

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Program Manager

Electron-Proton Spectrometer Program Advanced Programs Department

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SAFETY ASSESSMENT

1. PURPOSE

The purpose of this safety analysis is to identify the efforts required to assure relatively hazard free operation of the EPS and to meet the safety requirements of the program.

Safety engineering criteria, principles, and techniques in applicable disciplines is stressed in the performance of system and subsystem studies; in test planning, and in the design, development, test, evaluation, and checkout of the equipment, and the operating procedures for the EPS program.

2. DATA

There are no formal data submittal requirements specifically associated with the EPS system safety engineering program listed in the contract. However, letter reports and safety assessment requiring the attention of NASA/MSC will be transmitted when appropriate and any accident/incident reports prepared in response to NASA/MSC direction will be submitted.

3. SYSTEM SAFETY ASSESSMENT

3.1 TOXIC FLUIDS OR MATERIALS

No toxic fluids or materials will be used during the processes of manufacturing, testing, or handling of the EPS.

3.2 FLAMMABLE FLUIDS AND MATERIALS

No flammable fluids or material will be used in the manufacturing, testing, or handling processes of the EPS, except isopropyl alcohol for cleaning the electronic subassemblies:

3.3 NUCLEAR COMPONENTS/RADIATION

The EPS instrument itself does not contain any nuclear components; however, the laboratory equipment will contain radiation sources. LEC has been licensed to use radioactive sources.

3.4 RADIOACTIVE SOURCES

Radioactive Mater	rial		Quantity	
Barium-133*		Elemental	2 sources not to 100 microcuries e	acn
Cesium-137*	Solid,	Elemental	4 sources, each on not to exceed 100 curies, one not the language of the langu	MTCIO-
Bismuth-207*	Solid,	Elemental	4 sources, each of not to exceed 100 curies, one not to microcurie) MICIO-
Americium-241**	Solid	, Elemental	l source not to e	exceed
			l Inches	

^{*}Evaporated onto plastic film (Typical Bionuclear Inc., Houston, Texas.)

These radioactive sources will be used for routine checks and calibrations of lithium-drifted silicon detectors, either in air or in a vacuum chamber. Because of their solid form and low activity, it is necessary to handle the sources with only a pair of small tongs.

3.4.1 Radiation Protection Program

The sources will be stored in locked, appropriately marked cabinets when not in use, with access to authorized users only. While the sources are not in use, they will be stored in a locked cabinet such that the dose level at the surface of the cabinet is < 2 mr/hr. While in use, appropriate radiation signs will be placed at the 2 mr/hr locations.

^{**}Electrodeposited onto platinum foil (Typical Ortec Inc.)

In addition, personnel using the sources on a routine basis will wear film badges available from R. S. Laudauer, Jr. and Company.

3.4.2 Waste Disposal

At the end of the EPS program, the sources will be turned over to the NASA/MSC Health Physics Group for either storage or disposal. No wastes or disposal are expected to be necessary for these sources during the duration of the EPS program.

3.5 VAN DE GRAAFF FACILITY

An adequate safety program is already in existance at the Van de Graaff facility, and consists of the following:

- (1) The first time the accelerator is operated in each of the three modes, (low energy proton, high energy proton, and electron mode) Health Physics will be notified to perform a radiation survey for that mode.
- (2) Prior to each accelerator startup, the operating supervisor or his alternate shall be responsible to see that the following control procedure is accomplished:
- a. Physically check each entrance into the target area to insure that the interlock system is functioning correctly.
- b. Inspect the target room before each accelerator startup to verify that no one is present.
- c. Check the visual warning system to insure that all units are operating correctly.
- d. Check the area monitoring system panel to insure that all monitors are operating.

- e. Announce over the building intercom system, two (2) minutes prior to each startup, that accelerator operations will commence immediately.
- f. Check the roof area for occupancy restrictions when required for a particular mode of operation.
- g. Insure that an approved operator is at the console panel during accelerator operation.
- 3. It shall be the responsibility of the facility supervisor to maintain an OPERATION LOG. This record will indicate modes of operation and duration of each operation, e.g., target used, current, voltage and time spent on each mode of operation.
- 4. Approval must be received from the Radiological Control Officer (RCO) before anyone is allowed in the target room during radiation producing operations.
- 5. During the period covered by Machine Use Request 000225 (April 15, 1971 to February 1, 1972), no modifications will be performed on the accelerator facilities without authorization from the RCO.
- 6. In the event of a <u>RADIOLOGICAL EMERGENCY</u>, operations will be suspended and Health Physics notified immediately.
- 7. The roof area will be roped off and posted "Caution Radiation Area" during electron, proton and neutron production.
- 8. The doors to the accelerator target room will be posted as restricted areas at all times and will be posted "Caution High Radiation Area."

3.6 ENVIRONMENTAL CHAMBERS FACILITIES

NASA/MSC Environmental Facilities will be used for Qualification Testing and other environmental testing. These facilities have their own safety program approved by NASA/MSC.

3.7 CONTROL SYSTEM TEST FACILITIES

All environmental chambers located in the Lockheed Facility test area have been checked for safety features, and personnel using these facilities are aware of the procedures and cautions.

3.8 END ITEM ASSEMBLY

Maximum efforts have been made during design to ensure that the optimum degree of inherent safety has been included in all equipment designed, procured, or leased for the EPS Program through the selection of appropriate equipment components and design features, and through the use of materials which are known to be hazard free.

Appropriate action has been taken to assure that necessary functions of the system will occur as required, and that no primary failures will cause a chain of dependent failures which would degrade system safety and create hazardous conditions.

The environmental and acceptance test procedures will be designed to reflect safety considerations in their testing operations. The safety of the operations as well as the ability of the procedures to enhance the inherent safety achieved in the subsystems and equipment is a prime consideration.

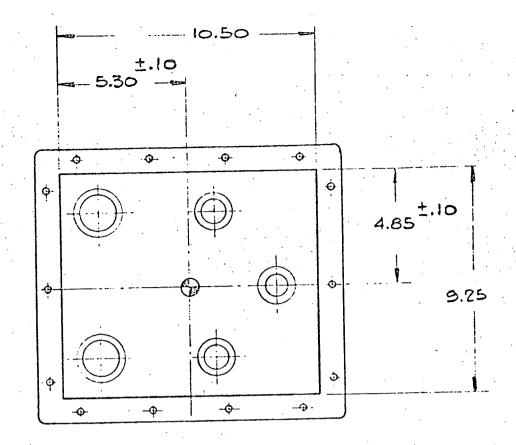
3.9 RADIO FREQUENCY (RF) RADIATION HAZARDS

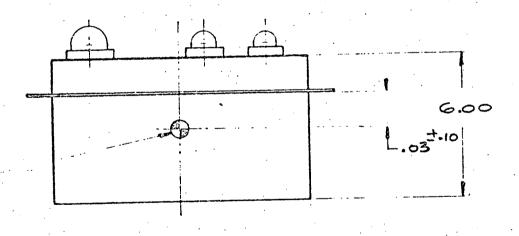
The limit for equipment exposure to RF radiation has been established at 0.01 watt/square centimeter (CM2) at any It is possible to encounter even higher power frequency. densities than this established safe maximum limit during the tests required by the Radio Frequency interference (RFI) tests; however, these high densities are localized. Susceptibility to fields and voltages from other circuits and equipment in the spacecraft was reduced to a practical minimum in the basic design of each assembly and sub-assembly. Primary consideration was given to components and circuits that are inherently free of susceptibility to magnetic fields at dc and audio frequencies. Preference was also given to circuits and components which are optimally free of susceptibility to transient voltage fluctuations and response to signals outside the intended operating frequency bands. The EPS is designed to withstand the transient supply voltage changes caused by the operation of other equipment in the spacecraft without degradation of operation. All digital logic has been designed to operate at as high a triggering voltage as feasible, definitely above the millivolt level. This design objective will provide optimum freedom from inadvertent operation due to stray pulses.

3.2.1.1.1 Location, Envelope Weight and Center-of-Gravity

The EPS was initially designated to be located on the Skylab Multiple Docking Adapter at which time a 15-pound maximum weight limitation was imposed on the design. Within approximately two months after the award of the EPS contract, however, notification was received that the EPS was to be relocated to the Command Service Module in the sector No. 3 fairing area by radial beam No. 2. At that time, a maximum weight limitation of 20 pounds was imposed. The relocation also dictated two major changes in the structural design of the envelope: 1) The mounting flange was to be about the mid-section of the EPS instead of at the base of the EPS, and 2) A structurally stronger envelope was required to withstand the exceptionally higher shock and acceleration g-forces associated with the new The resulting envelope weight for the Structural location. Test Unit was 21 pounds, the Engineering Test Unit, 22.5 pounds, and the Qualification Test Unit, 22.53 pounds.

The center-of-gravity, which remained at essentially the same point throughout the several packaging designs, is essentially the same as that for the Qualification Test Unit (see figure 1).





POSITION | OF C.S.

FIG. 1. MASS PROPERTIES STATUS
- POSITION OF C.G.

3.2.1.1.2 Structural

The following are documents applicable to the assessment of the structural requirements of the EPS.

Subject Title	Page
EPS Packaging Design Specification (Goals) (EPS-19)	25
Hermetic Sealing of EPS (EPS-5)	27
EPS Thermal Packaging Design (EPS-11)	29
Thermally Conductive Substrates for Printed Circuit Boards (EPS-71)	30
Interface of EPS with CSM (EPS-92)	32
Results of the EPS/CSM Interface Meeting Held at North American Rockwell on 1-12-71 (EPS-104)	35
Preliminary Results of Thermal Analysis (EPS-174)	40
Comments on the Thermal Design Analysis (TXA 50-131) from LMSC - April 1, 1971 (EPS-194)	. 43
Additional Thermal Analysis Results (EPS-200)	46
Random Vibration Criteria for EPS (EPS-123)	47
EPS Sensor - Qualification Model	52
EPS Baseplate - Qualification Model (EPS-855)	71

Subject Title		Page
EPS Proposed Increase in Qualification Vibration		73
Level		
Proposed Increase in Qualification Vibration	-	80
Levels for the EPS (EPS-675)		. 1
Comparison of Acceleration Levels to Other Dynamic Test Levels for the EPS (EPS-592)		84
Statement of Work: Barry Vibration Isolators for EPS (EPS-670)		91
Vibration Testing of the EPS Electronics (EPS-722)		92
EPS Combined Pressure and Random Vibration		94
Vibration Test Report (Interim) on Solid State Radiation, Inc's. Lithium Ion Drift		98
Detectors		•

ELECTRON-PROTON SPECTROMETER PACKAGING DESIGN SPECIFICATION (GOALS)

- 1. Location Mounted on multiple docking adaptor.
- 2. Instrument will be thermally isolated from vehicle skin.
- 3. Temperature Range, External -180°F to +277°F.
- 4. Temperature Range, Internal -

Operating Mode Standby Mode

Detectors -58°F to +32°F -58°F to +95°F
Electronics -13°F to +77°F -13°F to +158°F

5. Power

Electronics - 12 watts
Heaters - 3 watts available.

- 6. Package Size 10" x 8" x 5" (400 cubic inches). (Detectors will protrude beyond 5" package height).
- 7. Weight 15 lbs.
- 8. Operating Pressure 10⁻⁸ torr.
- 9. General
 - a. Information on other environmental requirements is contained in MSC-01159, Rev. C "Flight Hardware Environmental Design Requirements", September 1, 1970.
 - b. It is presently planned that the detectors will be sealed units.
 - c. It is presently planned that the packaging design will provide conductive paths to the external walls of the package, to transmit heat from the electronics.
 - d. Electronics Analog electronics will use P/C board techniques; digital and power supplies will most probably utilize welded cordwood modular techniques.
 - Ref. B Temp. Range, Internal Mode: "-58°F to +32°F"was "-13°F to +77°F" and "-13°F to +77°F" was "+32°F to +122°F".

- Perform evaluation and initial analysis of existing design concept.
- II. Select suitable thermal coatings, investigate applicable thermal insulations.
- III. Based on specs and initial analysis of existing design, make recommendations to finalize design concept.
- IV. Provide liaison to LEC/HASD design engineering throughout the entire design phase.
- V. Perform thermal analysis of final thermal design and write report on results.

INTERDEPARTMENTAL COMMUNICATION

B. C. Hall

DEPT./673-10 BIDG. Beta FAC. HASD EPS-5

FROM

Tarm LAC 201

D. L. Vincent

ORGN. 673-10 ZONE Beta FAC. HASD EXT. 481

SUBJECT. Hermetic Sealing of EPS

It has been suggested that the EPS experiment be a completely hermetically sealed unit, so that it will not require documentation covering non-metallic materials, flammability, outgassing constituents, etc.

It is felt that this is a rather expensive way to avoid some documentation requirements. To design on the basis of a completely hermetically sealed unit will involve impact to the EPS program in several areas, such as:

- a. Invalidation of all previous design concepts studied.
 - b. Need for investigation into suitable sealing techniques and seal testing that was not included in the original proposal. The difficulty of sealing for a five year period (one year operational) has not yet been established, but true hermetic sealing is both costly and time consuming to design and produce.
- c. Invalidation of all preliminary thermal analysis undertaken by LMSC.
 - d. Elimination of multilayer insulation as a possible insulation technique. This material is only satisfactory under vacuum conditions.
 - e. Weight the casing would now have to withstand a differential pressure of 15 psi. This would possibly lead to an increase in weight.
 - f. Additional machining for seal(s) and sealing bolts would involve additional costs, as would the seal itself.

11-12-70 Page 2

> If permanent (solder, welding) sealing techniques are used, then increased difficulty of access to internal structure and circuitry would seriously hamper rework if and when required.

While the above may not be exhaustive, it gives a measure of the impact associated with this decision. In contrast to this, it is felt that if the materials used in the construction of the EPS are selected from materials already approved for use in the Apollo program (ref. 1, 2 and 3), much of the documentation and testing is already covered.

Experience has shown that the outgassing from the average experiment electronics is not excessive, where care has been exercised in the selection of materials used. Also, even when no attempt has been made to stabilize materials such as potting compounds, encapsulations and conformal coatings - sources of the major portion of the outgassing - the outgassing tends to stabilize itself in a short period of time. Should certain materials required to be used be a cause of excessive outgassing, it would probably be more economic to provide individual sealed containers at a component or subassembly level rather than at the general assembly level.

Finally, the EPS experiment will probably be a very small source of outgassing compared to that from the spacecraft itself.

Determination of whether the design should provide total hermetic sealing unit must be made very soon to avoid major schedule impact to the EPS project.

- Grumman document LIS-360-22101 1.
- North Americal document MC 999-0058 2.
- Bendix document ATM 242.

Vincent

B. E. Curtsinger cc:

R. S. Lindsey

R. P. Dunn

P. Gleeson

INTERDEPARTMENTAL COMMUNICATION

D. L. Vincent TO

R. P. Dunn

DEPT./ 673-10 BLDG/Beta PLANT/HASD DATE 11-17-70 ORON.

EPS-11

FROM

B. C. Hall

DEPT./ PLANT/ PLANT/ PAGE HASD

Electron-Proton Spectrometer Thermal/Packaging Design SUBJECT

In order to achieve maximum progress in the thermal/packaging design of the EPS instrument, the following requirements will be considered firm and will be utilized until further notice.

- Temperature Range, External: -180°F to +277°F l.
- Temperature Range, Internal: Design goals 2.

Standby Mode Operate Mode Instrument Subassembly -50°C to +35°C 0 + 25°C Detectors -25°C to +70°C 25°C + 25°C Electronics

- Mounting Location MDA
- Instrument will be thermally isolated from vehicle skin.
- Weight: 15 lbs. 5.
- Vacuum seal Not mandatory, design for thermally conductive paths from electronic components to a common heat sink using suitable encapsulating techniques.
- Electronics 12 watts 7. Power: Heater - 3 watts
- Will be hermetically sealed in TO-5 transistor Detectors: 8. package.
- Packaging:
 - Analog electronics use PC boards. a.
 - Digital and power electronics use welded cordwood modular techniques.
- 10. Information on other environmental requirements can be found in MSC-01159 Rev. C "Flight Hardware Environmental Design Requirements", dated September 1, 1970.

B. E. Curtsinger CC:

R. S. Lindsey

DEPT./673-10 RIDG. Beta PLANT/HASD PATE 12-16-70 Ref: EPS-71

B. C. Hall

FROM D. L. Vincent

DEPT. 673-10 BLDG Beta PLANT/HASD EXT. 422

SUBJECT. Thermally Conductive Substrates for Printed Circuit Boards (Action Item 1, 12-14-70)

Investigation of thermally conductive substrates for printed circuit boards indicates that apart from the conventional glass-epoxy (a very poor thermal conductor) the choice resolves itself into one between the pure oxide ceramics and aluminum alloy.

The International Electronic Research Corp. markets a "metal core circuit board" consisting of an aluminum alloy (6061-T6) core, an "Insulube 448" insulation and copper conductor. This type of board is being used in many avionics applications (e.g. by Lockheed in the S3A). Generally, such a board is capable of providing five times the power dissipation of the glass-epoxy equivalent board. When a board is attached to a good "thermal ground", this power dissipation could rise to 12-15 times that of a glass-epoxy board.

National Beryllia Corp. are manufacturers of pure oxide ceramics, including alumina and berryllia substrates. Their Cermetrol Division has the capacity to manufacture a complete "printed circuit board".

The thermal conductivities of the substrates are:

Glass-Epoxy (G-10 Typical) .0026 watts/cm-°C Aluminum Alloy (6061-T6) 1.55 watts/cm-°C Alumina (99.7% Al₂O₃) .35 watts/cm-°C Beryllia (Berlox Kl20) 2.08 watts/cm-°C

However, the thermal conductivity is not a very good comparison of the relative efficiencies of the above materials as a thermally conductive substrate. Aluminum alloy, being an electrical conductor, needs a 4-5 mil insulating layer between it and the conductor.

12-16-70 EPS-71 Page 2

A common concept for plates or sheets of material such as PC boards is resistance per square, and comparing these materials on this basis is a factual measure of their capabilities. Assuming, for comparison, a 1/16 inch thick board

Glass-Epoxy 2860 °C/watt Aluminum (6061-T6) 4.06 °C/watt Alumina 17.98°C/watt Berlox K.120 3.309°C/watt

It can be seen that either the metal core circuit board or beryllia give the greatest improvement in heat dissipation over glass-epoxy. However, the aluminum board may have undesirable characteristics for use in some circuitry (such as capacitance in the op. amp. for EPS).

Ball park figures for cost are:

Aluminum Alloy Board (MCCB)

\$200 - \$300 for prototype board (about 3-1/2"x 2-1/4"-75 holes)

\$ 50 - \$100 for quantities ~ 25 (delivery ~10-12 weeks)

Beryllia

No cost figures available. Anticipate costs similar to aluminum alloy board above. (delivery ~ 8-10 weeks)

There is obviously no problem mechanically in using MCCB's, and preliminary calculations show that beryllia would be satisfactory.

D. L. Vincent

cc: Curtsinger

Dunn Lindsey

INTERDEPARTMENTAL COMMUNICATION

B. C. Hall

073-102003/Beta FAC HASD DATE 12-30-70

Ref: EPS-92

D. L. Vincent

CASH 673-10 FOR Beta PART HASD

SUBJECT: Interface of EPS with CSM

The writer received a telephone call from North American Rockwell, regarding interface information on mounting the EPS into the CSM. Discussion took place on the thermal and structural conditions, and they will be contacting B. E. Curtsinger and/or R. S. Lindsey to come to an agreement regarding the electrical interface. is important to them.

They provided some general information regarding the temperature of the spacecraft in the immediate area for mounting the EPS, and the proposed concept for attaching us to the spacecraft.

Mr. Ed Schlessinger gave the following details.

- We will be mounted on the shadow side of the spacecraft, though there exists the possibility that we may see the sun for a short period of time in one particular attitude of the spacecraft.
- Temperatures of the access panel that we would be mounted in place of are:

for varying β angle (angle between sun line and orbit plane)

0°	Temperature fashion bet	will vary ween -70°F	in a sinu and +25°F	soidal •
+73 1/2°	-80°F			
-73 1/2°	-65°F			
β angle	Panel Tempe	rature		•

Within the spacecraft structure cavity the cavity wall temperature will range from 0°F to +50°F.

12-30-70 Ref: EPS-92 Page 2

Mr. Squigley gave the following structural information.

- 1. We would be mounted on a flange on the access panel.
- 2. The EPS top plate would be 1-1/2" 2" above the panel.
- 3. The approximate dimensions of the cavity are 14-1/2" x 12-1/2" x 7-1/2" deep. A more up-to-date sketch of the proposed mounting and cavity will be transmitted to NAR's Houston representative to pass on to us (it appears that the cavity is not a full rectangular box).

The writer informed them that our envelope would be smaller than the 12" \times 10" that they had allowed for, and gave a provisional size of 10"- 10-1/2" \times 9" \times 6" high (exclusive of the detectors).

It appears that there would be space to provide some thermal insulation within the cavity should we find that we require it to keep within our thermal parameters.

They had been given to understand that at least one of the detector shields was only about 2-3 mils thick, and were a little concerned about the possible susceptibility to damage this would mean. The writer advised them that the thinnest shields are 14 and 71 mils thick aluminum.

The writer also inquired about the type of mating connector they might wish us to use, mentioning that we had planned to use a connector of the type covered by a MSFC specification. It would appear that they have some requirements regarding the connector, and its location, but preferred to leave this until they had spoken about the electrical interface.

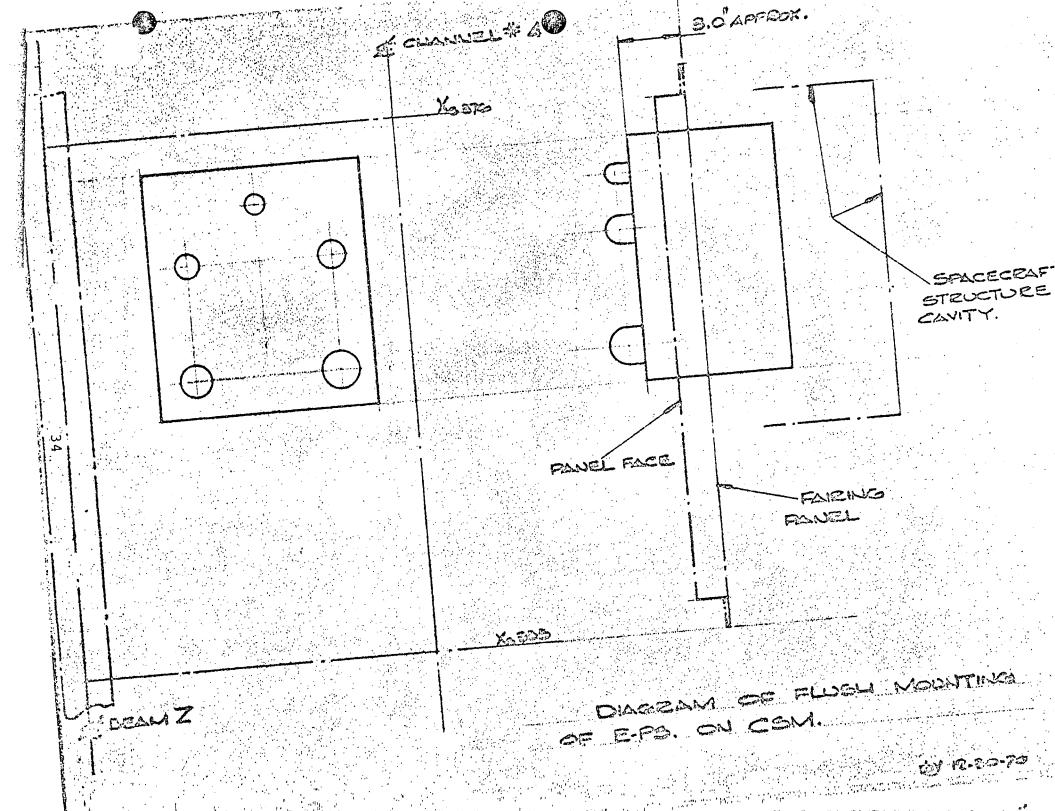
Finally, it does not appear that they have been officially "turned on" by NASA to mount us on the CSM as yet, but understand that the official "turn-on" is "in the mill".

D. L. Vincent

cc: B. E. Curtsinger

R. P. Dunn

R. S. Lindsey



INTERDEPARTMENTAL COMMUNICATION

B. C. Hall

DEFT./ 673-10 BLDD./Beta FLANT/HASD DATE 1-13-71 COOM! Ref: EPS-104

FROM B. E. Curtsinger

D. L. Vincent

DEFT./ 673-10 PLANT/Beta PLANT/HASD EXT. 422

SUMPECT. Results of the EPS/CSM Interface Meeting Held at North American Rockwell (NR) on 1-12-71

List of Attendees:

A. Farkas NASA/MSC
P. Liles NR/Downey

B. Curtsinger LEC
D. Vincent LEC

Various other NR personnel.

Results:

After the North American Rockwell and Lockheed organizations and the basic operation of the EPS had been discussed, the four instrument to spacecraft interfaces were discussed in detail. These four interfaces are:

- A. Installation and Envelope
- B. Electrical and Functional
- C. Environmental
- D. Ground/Bench Test Equipment

Each of these interfaces will require an Interface Control Document which will be, in effect, a contractual agreement between NR and NASA/LEC.

Installation and Envelope:

LEC presented the drawing no. SMC39106411, "Outline Drawing - Electron Proton Spectrometer" for discussion and review. This drawing defines the overall size of the package and position and maximum projection of the detector housings. Despite the increase in size from the provisional size of 10" x 9" x 6" given approximately two weeks ago to the present size of 10-1/2" x 9-1/4" x 6", North American personnel were able to confirm that they can mount and install this size package, and provided a sketch of the required hole pattern in the mounting flange around the instrument.

The present maximum allowable weight of the instrument was given (20 lbs), and it was indicated that while we anticipated that we would be a little below this, no firm estimate was available at this date.

The type of connector mating with the spacecraft, and its position, was discussed. Agreement was reached on a ME 414-0096-0053 connector for the instrument with the mating connector being ME 414-0095-0061. North American said that these were available from Kierulf Electronics in Los Angeles (telephone no. 213-685-5511). suggested contacting Miss Mildred Haller of that company. be that Kierulf has some of these connectors in stock, though normal delivery is 4-5 weeks. Regarding the connector position, LEC stated its preference for it to be at the bottom of the instrument, close to one of the 9-1/4" sides and to one side of the centerline of the instrument. North American needed to look into their wiring and connector layouts more closely before they could give a definite answer, but generally thought that this position would be acceptable to them. Some questions were raised regarding the projection of the connector below the base of the instrument. LEC indicated that we had some leeway in this area and would attempt to accommodate their needs as far as we could. NR will send their suggested position for the connector and its projection to A. Farkas (NASA/MSC) by the end of the week.

Installation into the spacecraft was discussed generally, and apart from some question of access to some components in the region of the instrument, did not appear to present any problems. The need for a handling container for the instrument and a protective shield for the detector if installation takes place at KSC was discussed, but no resolution was made.

All in all, the installation and envelope discussion was remarkably free of any problem areas.

Electrical and Functional:

A proposal was made by LEC to include an Analog to Digital converter in the EPS, thereby deleting the requirements for the two analog channels and the 1 pps sync signal. NR was very agreeable to this due to schedule and telemetry channel availability restrictions. Therefore, for the remainder of the discussion, it was assumed that an A/D converter would be included in the EPS.

NR had performed tests to determine if the tape recorder/VCO telemetry channel had sufficient bandwidth to accept a serial 220 bit per second, bi-phase-level PCM signal. The results of these tests indicated that this was acceptable. It is not known, at this time, whether the existing Skylab ground telemetry stations will accept this signal.

The power interface (including the uplink command control requirement) was discussed and is agreeable to both groups.

North American Rockwell has a specification for RFI/EMI and will include this document in the ICD. This specification has not been reviewed for compatibility with existing requirements.

The availability of an EPS for spacecraft functional tests (on 6-21-71) was discussed. Mr. Farkas suggested that the Engineering Test Unit be used for these tests. It was pointed out by LEC that the Engineering Test Unit will not have QA coverage during fabrication, and this would probably prevent the unit from being connected to the spacecraft. NR agreed. It was decided that NASA and NR would resolve this problem.

Environmental:

This discussion centered around the Environmental ICD and its format. The environmental requirements covered were:

- 1. Thermal
- 2. Shock and Vibration
- 3. Nuclear Radiation
- 4. Pressure
- 5. Magnetic Field
- 6. Other environmental factors.

These areas were discussed, primarily from the point of view of NR's need-to-know in terms of integration into the spacecraft as a system, and the EPS possible interaction with other instrumentation.

Thermal:

This covers surface materials and properties, thermal coating characteristics, temperature control means, range and set points, thermal analytical model, heat sources and/or sinks and conductance values.

The primary need for control of this information is integration into the thermal engineering of the spacecraft plus the need for knowledge of the type of materials and surface coatings that would be handled on installation in the spacecraft. Most of the information required could well be supplied by direct liaison between E. Schlessinger (NR's Thermal Engineer) and Don Smith (LMSC), particularly in the area of the analytical model (a very simple model).

LEC raised the possible need to heat sink the experiment to the spacecraft and possibly insulate the instrument from the cavity within the spacecraft skin. There appears to be no problem in this approach if needed.

From discussion of the Functional ICD, there is a need to define any temperature requirements in terms of time also, as in two modes of spacecraft operations, we could be on the sunward side of the spacecraft. One of these is during the docking maneuver, the other is during an "earth resources" mode.

Shock and Vibration:

NA will supply the shock and vibration levels at the mounting surface of the instrument in the near future.

Nuclear Radiation:

It was accepted that we had no radiation source, and that we measured electron and proton radiation levels. A statement to this effect will be included.

Pressure:

This covers any limitations on the instrument operation due to gas release, RCS burns, etc. The primary effect would be slight degradation of the thermal coating surfaces. LEC confirmed that we would be looking at the instrument for the need to vent any internal atmospheric pressure during the launch and orbit insertion sequences.

Magnetic Fields:

This would cover transient magnetic fields, and LEC could give no definite figures at this time.

Other Environmental Factors:

This would cover any other needs of the instrument not covered elsewhere. At this time neither LEC nor NR had any items to include under this heading. The question of accoustics was raised by A. Farkas. NR replied that this was normally included in the vibration levels to the instrument.

Ground/Bench Test Equipment:

Since the EPS instruments are not to be installed on the Space-craft at the North American plant at Downey, there is no requirement for tests or equipment at that location. However, NR strongly recommends that several tests be performed at Cape Kennedy.

Immediately after the EPS arrives at KSC, the unit should be subjected to a pre-installation test. This test would require bench test equipment and QA coverage.

Since the time between installation of the instrument on the spacecraft and launch could be as long as four months, NR recommends that equipment be provided to allow for functional tests of the EPS while installed on the CSM. This would require GSE and QA coverage.

Summary:

From the information obtained at this meeting, and from possible phone conversations in the future, North American Rockwell will prepare the ICD's for each interface. These will be sent to NASA and LEC for concurrence before the final drafts are prepared.

D. L. VI

cc: B. E. Cash

R. P. Dunn

c. L. Fletcher

P. Gleeson

R. B. Hendrix

R. S. Lindsey

T. D. Lyons

W. A. Oliveira

R. W. O'Neill

C. J. Spahn

INTERDEPARTMENTAL COMMUNICATION

B. C. Hall

DEPT./ 673-10 LONE Beta PLANT/ HASD DATE 3-23-71 OFFI. Ref: EPS-174

FROM

D. L. Vincent

OKON. 673-10 DEDG. Beta FAC. HASD EXT. 422

SUBJECT: Preliminary Results of Thermal Analysis

The advance results from LMSC regarding the temperatures of the EPS show that these fall within the range of the packaging design specification (EPS-19, Rev. B) provided.

Cold orbit temperatures were predicated on 15.9W (12.9W electronics power + 3.0W heater power) while hot orbit temperatures are based on 12.9W electronics power only. The experiment is considered as mounted on the spacecraft structure via a glass-fiber mounting flange, or isolated in a manner to provide an equivalent thermal resistance at this point.

The specified temperature limits and the analysis results are tabulated below.

	Detectors	Electronics	
Specified Limits	-58°F to +32°F (-50°C to +0°C)	-13°F to +77°F (-25°C to +25°C)	
Hot Orbit			
Orbit Average	+12°F (-11.1°C)	+35°F (+1.7°C)	
Temperature Range	+27°F to +1°F (-2.8°C to -17.2°C)	+37°F to +32°F (+2.8°C to +0°C)	
Cold Orbit			
Orbit Average	-24°F (-31.1°C)	+2°F (-16.7°C)	
Temperature Range	-22°F to -26°F (-30°C to -32.2°C)	+1°F (+1/2°C)	

		Detectors	Electronics
Γ	*Cold Orbit (18.9W)		
	Orbit Average	-12°F (-24.4°C)	+12°F (-11.1°C)
	Temperature Range	-10°F to -14°F (-23.3°C to -25.6°C)	+1°F (+1/2°C)

^{*}Estimated temperatures based on 6 watts of heater power in cold orbit.

An examination of these results shows that for the hot orbit, the detector and electronics temperatures fluctuate more widely than for the cold orbit. The detector temperature can rise to within 5°F of the maximum specified temperature, whereas the electronics are about 3°F above the mean (or nominal) specified temperature. In the cold orbit, the detectors are about 9°F below the mean specified temperature and the electronics are 13°F above the minimum specified temperature. The electronics temperature could be raised 10°F in the cold mode by the addition of an extra 3.0W of heater power, and this would raise the detector temperature by about the same amount. Figure 1 shows these results in a tabular form.

As a rough estimation of the thermal advantage of changing to a glass-fiber mounting flange, it would require a total power consumption 25.9W to maintain the cold mode temperatures at those for 15.9W.

D. L. Vincent

cc: B. L. Cash

B. E. Curtsinger

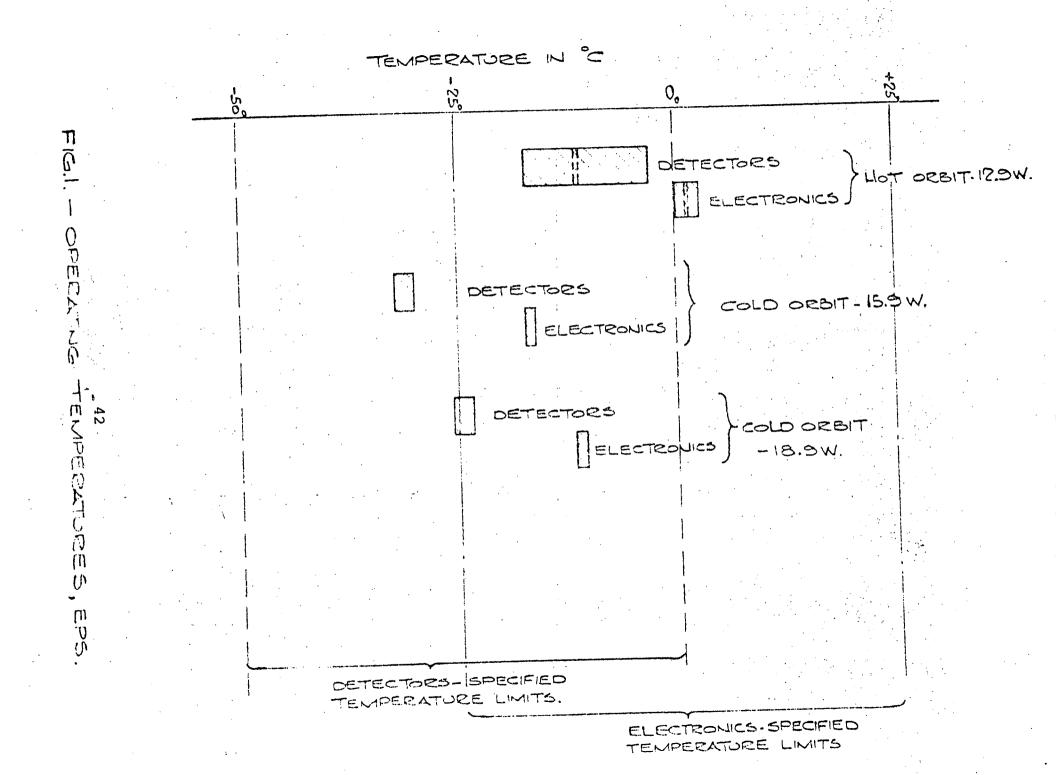
R. P. Dunn

P. Gleeson

R. B. Hendrix

R. S. Lindsey

C. J. Spahn



VB. C. Hall

DEPT./ DECOM Beta FLANT/ BATE 4-9-71
Ref: EPS-194

OBOT 673-10 FIRE Beta FAC HASD EXT. 422

D. L. Vincent

SUBJECT: Comments on the Thermal Design Analysis (TXA 50-131) from LMSC - April 1, 1971

An initial perusal of the above thermal design analysis report has presented no surprises or major deviation from information provided to the writer by D. H. Morton (LMSC) by phone.

Specific comments on the recommended thermal design provisions are as follows.

1. Thermal control surfaces

The proposed use of the White thermatrol paint and Mystic tape had been made known to us, and the design caters for this. D. Morton has provided the writer with LMSC's Material Specification, Process Bulletin and Process Specification (for protection of thermal control surfaces) for this material.

2. Electronics/Baseplate Interface

The change from 1/16" thick x 20.10 sq. ins. to 1/8" thick x 15.20 sq. ins. of fiberglass, providing approximately a 20°F increase in the electronics operating temperature, was provided by D. Morton and the necessary details are in the process of being modified. The proposal for the connecting screws is already incorporated in the design.

EPS/Spacecraft Interface

The proposal of a fiberglass flange came from LEC (as an alternative to a multitude of spacers and a possible requirement for NAR to isolate the hold-down bolts from the spacecraft structure). The present design incorporates this flange and the conduction path length is as recommended.

4. Heater Power Requirements

This paragraph did contain information not previously transmitted. The writer had advised LMSC that we monitored the temperatures, but that there was no provision to turn the instrument off, except through ground command. Possibly, this can be loosely interpreted as thermostatic control. The recommended "turn-on" temperatures for the heaters had not been transmitted, and the writer understands from B. Curtsinger that the heater control circuit is designed for "turn-on" at 0°C (32°F) and "turn-off" at $+10^{\circ}C (+50^{\circ}F)$.

The request to examine the possibility of leaving the smallest detector dome unpainted was made due to the required thickness of the paint coating (4-6 mils). Discussion with B. Cash indicated that this thickness of paint on a dome of only 14 mils thickness would lead to either alteration of the energy levels measured by that detector or reduction of the required thickness of the dome by some amount that would, of necessity, thickness of the dome by some amount that would, of necessity, have to await the results of test investigation of the effect of the paint coating. LMSC evaluated the thermal effect of leaving this dome unpainted, with the result that the change in temperature was insignificant. Therefore, the design does not require this dome to be painted.

Regarding the "stand-by" case (presumed to reflect possible rendezvous and docking situation; the report clearly indicates that these are worst-case situations. And the final sentence indicates that once again NAE has "backed off" from their initial input on the worst case parameters for the rendezvous and docking mode, which was in the order of potentially 7-10 days - with the EPS facing the sun - as a design a quarement!

4-9-71 EPS-194 Page 3

Comparing the temperature results with those given in "Preliminary Results of Thermal Analysis" EPS-174 (3-23-71) written prior to the change in the electronics/baseplate interface, we have:

Hot Orbit

Orbit average and temperature range Detectors:

remain the same.

Orbit average 62°F (16.7°C) Electronics:

Temperature range ≈ ± 1°C

Cold Orbit (3W heater power)

Orbit average and temperature range Detectors:

remain the same.

Orbit average +17°F (-8.3°C) Electronics:

Temperature range = 1/2°C

Cold Orbit (6W heater power)

Orbit average and temperature range Detectors:

remain the same.

Orbit average +37°F (+2.8°C) Electronics:

Temperature Range : 1/2°C

These results show that the alteration in the electronics/baseplate interface has provided an increase in the electronics operating temperatures without any significant change in the equivalent detector operating temperatures. The only outstanding item in the design (from a thermal standpoint) is the determination of the desired heater power. There is no obstacle in the present design to prevent the use of 3W or 6W, and as it seems to be desirable that the electronics operate at as warm a temperature as possible in the cold mode then, power allotment permitting, the writer suggests that we use 6W heater power.

B. L. Cash cc:

B. E. Curtsinger

R. P. Dunn

P. Gleeson

R. B. Hendrix

R. S. Lindsey

C. J. Spahn

INTERDEPARTMENTAL COMMUNICATION



B. E. Curtsinger

DEPT./ 673-10 ZONE Beta FAC. HASD DATE 4-15-71
Ref: EPS-200

FROM

D. L. Vincent

DEPT./ 673-10 EDG./ Beta PLANT/ HASD EXT. 422

SUBJECT: Additional Thermal Analysis Results

At the time the thermal report was discussed, it was noticed that two previous points raised had been omitted. These were:

- a. What is the minimum temperature of the electronics with all power off?
- b. What is the minimum temperature of the electronics with 6W of heater power only? If this is below -50°C, what is the minimum power requirement to maintain the electronics at or above -50°C?

The answer to these questions was given by LMSC as:

a. All power off:

Electronics Temp -100°F (-73.3°C) Detector Temp -103°F (-75°C)

b. 6W heater power only:

Electronics Temp -54°F (-47.8°C) Detector Temp -71°F (-57.2°C)

As the 6W of heater power maintains the electronics at or slightly above -50°C, no attempt was made to find the power required to maintain the electronics at -50°C. Additional information provided was the detector temperature in these particular modes.

D. L. Vincent

cc: B. C. Hall

B. L. Cash

R. P. Dunn

P. Gleeson

T. L. Knox

R. S. Lindsey

C. J. Spahn

Guran

INTERDEPARTMENTAL COMMUNICATION

B. C. Hall

DEPT./ 673-10 ELDO./Beta PLANT/HASD DATE 2-8-71 Ref: EPS-123

FPOM

D. L. Vincent

DEPT./ 673-10 BIDS./Beta FLANT/HASD EXT. 422

SUBJECT:

Random Vibration Criteria for EPS

The vibration criteria for the EPS when mounted into the CSM fairing was received from Mr. A. Farkas (NASA/MSC) on 2-4-71. This information had been provided by North American in a telefax.

Review of the information led to an immediate query of the very high power spectral density levels involved. Mr. Paul Liles (NAR) confirmed the 6.0 g 2 /Hz level to Mr. Farkas, and these levels were confirmed independently of NAR by Mr. Farkas. These levels are apparently factual levels based on the monitored results of two tests, and are applicable to the EPS for any mounting position in the CSM fairing. Mr. Farkas states that these levels would be the test levels for the EPS, though the writer can find no indication in the telefax that these are other than flight environment levels. If they are flight levels or acceptance test levels, then the qualification test levels would be significantly higher (e.g. 6 g 2 /Hz x 1.3 2 = 10.14 g 2 /Hz). The question of what levels we will be contractually obligated to test to needs some clarification.

It is obvious that these high levels will have an impact on the design of the EPS. Not only is it necessary to reexamine the structural design in the light of the new criteria, but it will also be necessary to investigate the internal packaging of all of the electronics in each slice. vibration spectrum has its peak power levels between 100 -1000 Hz; the natural frequency of the EPS will be somewhere between 100 - 350 Hz in all probability, as will that of the majority of components. The peak power input bandwidth is so wide that it is virtually impossible to design so that the instrument will not have a resonant frequency in this range. An investigation of the full impact of this to the packaging design must be made, but has not yet been started. If the writer had to hazard a guess, it would be that we will be extremely lucky if we avoid having to modify the design appreciably from its present size and weight.

2-8-71 EPS-123 Page 2

At this point, a review of the history of the vibration criteria for the EPS is not amiss. Figure 1 shows the variety of random vibration criteria that we have received as design requirements.

The first was that contained in MSC-02814, Preliminary Requirements Review, Electron-Proton Spectrometer (11-6-70):

80 Hz @ 3 dB/Octave increase

Curve "A" Acceptance Test levels.

 $350 \text{ Hz} @ .067 \text{ g}^2/\text{Hz}$ 80 -

5 mins/axis

350 - 2000 Hz @ 3 dB/Octave Decrease

* 8.1 q r.m.s.

At this point in time, there was some uncertainty as to the location of the experiment on the MDA, and it was felt that the above specification was a fairly low one to design to. Therefore, the general specification for the MDA skin was selected from MSC-01159, Rev. C, "Flight Hardware, Environmental Design Requirements:

MDA Skin, Subzone 11-2

 $130 \text{ Hz} @ .30 \text{ g}^2/\text{Hz}$

220 Hz @ -6 dB/Octave 130 -

 $800 \text{ Hz} @ .10 \text{ g}^2/\text{Hz}$ 220 -

800 - 1400 Hz @ -12 dB/Octave

 $1400 - 2000 \text{ Hz} @ .010 \text{ g}^2/\text{Hz}$

Curve "B" 1 min/axis

11.6 g r.m.s.

Detectors were vibration tested to these levels, and also the levels for the OWS LH2 cylinder tank general specifications, subzone 4-3 (between 12-2-70 and 12-7-70 - see EPS 33 and 67).

20 Hz $@.010 g^2/Hz$

90 Hz @ +12 dB/Octave 20 -

200 Hz @ $3.7 g^2/Hz$ 90 -

500 Hz @ -12 dB/Octave 200 -

 $500 - 2000 \text{ Hz} @ .095 \text{ g}^2/\text{Hz}$

Curve "C" l min/axis

29.1 g r.m.s.

2-8-71 EPS-123 Page 3

The detectors successfully completed testing to both these levels. The OWS spectrum was run, as the workshop was being considered as an alternative location for the EPS. However, design was based on the MDA skin criteria, though it was recognized that these levels might be increased a little, dependent on the location of the experiment, so somewhat larger factors of safety were used in the initial design than would normally be called for to achieve an economical, lightweight design.

On 12-16-70, an interface meeting was held between LEC, NASA and Martin-Denver. At this time we were given a location on the MDA - the L-Band Radiometer Truss - and its accompanying vibration requirements.

 $20 - 183 \text{ Hz} @ 1.0 \text{ g}^2/\text{Hz}$

183 - 554 Hz @ -12 dB/Octave

 $554 - 750 \text{ Hz} @ .012 \text{ g}^2/\text{Hz}$

750 - 1300 Hz @ -12 dB/Octave

1300 - 2000 Hz @ $.0013 \text{ g}^2/\text{Hz}$

Curve "D" l min/axis

15.1 g r.m.s.

Investigation indicated that our design could accommodate this new criteria without significant impact on the detail design (EPS)72), mainly due to the large factors of safety used - as mentioned previously.

Approximately one week later, we were advised that the EPS would not be mounted on the MDA! A possible alternative position on the CSM was mentioned, and this was welcomed as probably leading to a reduction in the vibration criteria. General opinion was that the CSM vibration levels would be significantly lower than for the MDA. Even at the interface meeting with NAR, no mention was made of high vibration levels (EPS-104, 1-13-71).

CSM

20 - 175 Hz @ +6 dB/Octave

175 - 350 Hz @ 6.0 g^2/Hz

350 - 2000 Hz @ -3 dB/Octave

Curve "E"
80 secs + 10 secs
@ 4 dB above nominal

≈ 85.99 g r.m.s.

2-8-71 EPS-123 Page 4

As can be seen from Curve "E", the power levels involved are considerably higher than any previous specification given, and certainly we have no large factors of safety now involved to offset the impact on the design.

The environment of this location on the CSM is not an ideal one for a sensitive instrument, and will almost certainly have an effect on our present design. Examination of the curves shows that the CSM criteria is significantly greater than the OWS spectrum to which we subjected the detectors (as a "worst case" test), and it is interesting to note how the vibration level requirements have increased steadily since the project was first started. From the information that was first provided for design, it would have been impossible to forecast the levels now imposed.

D. L. Vincent

cc: B. E. Curtsinger

R. P. Dunn

P. Gleeson

R. B. Hendrix

R. S. Lindsey

C. J. Spahn

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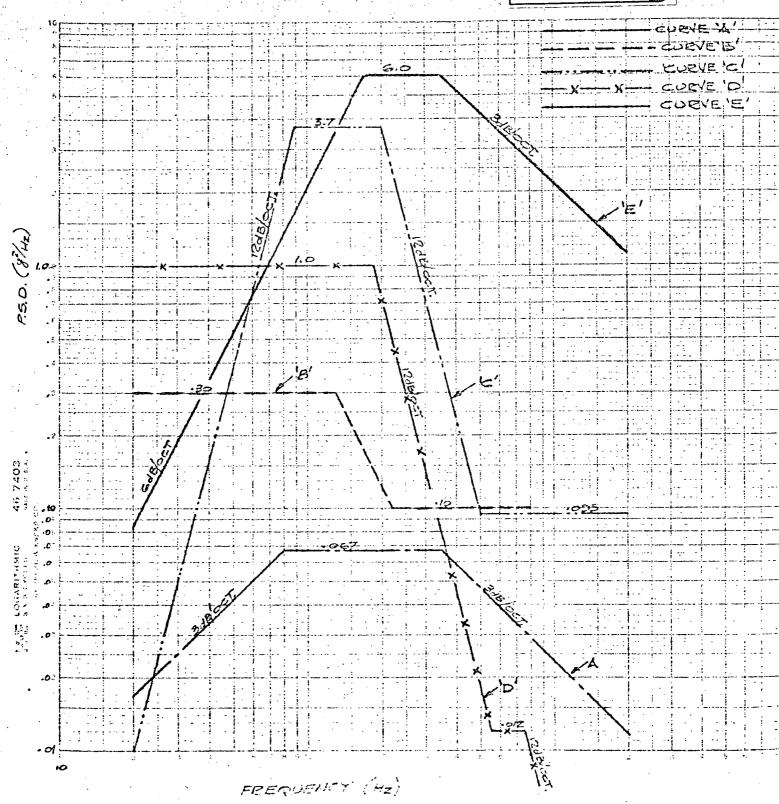


FIG. 1_ RANDOM VISUATION CRITERIA FOR EPS.

CURVE A' - PRELIM. REQUERNER TO TEVEN 11-6-70 CURVE B' - MOA CYLINDER CHUI, GOV. SPEC. CURVE C' - OWS LAG CYLINDER TAUK SECTION

CUEVE D'- MOA L-RAND ENDIOMETE TRUES - MARTILIDEN/ER-12- CONFAIRING - 1.48-2-4-7

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01 0 10/18/21	CHOISCT E/P SENSOR	SHEET NOOFOF
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ELECTRON / PROTON SENSOR COMBINED PRESSURE AND RANDOM VIBRATION

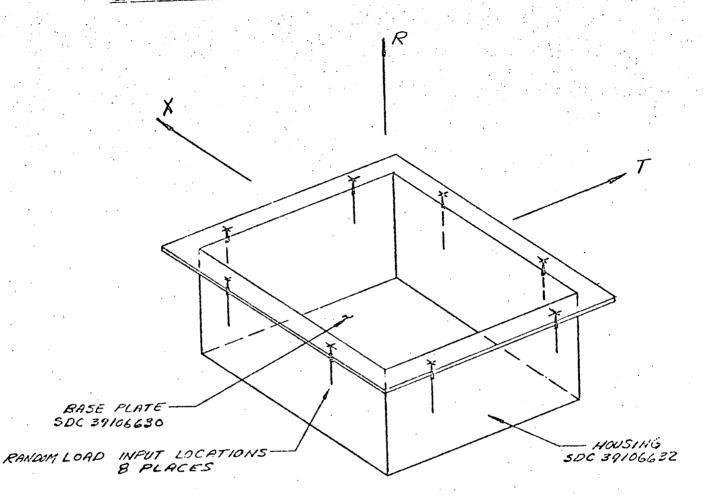
THE STRUCTURAL INTEGRITY OF THE E/P SENSOR
HARDWARE HAS BEEN DEMONSTRATED BY A SERIES
OF SINUSDIDAL, RANDOM, AND SHOCK TEST ENVIRONMENTS BEING APPLIED TO THE ENGINEERING TEST
MODEL. THE ACTUAL FLIGHT ENVIRONMENT WHL
SUBJECT THE INSTRUMENT TO A LOAD COMBINATION
WHICH WOULD BE BOTH DIFFICULT AND EXPENSIVE TO
DUPLICATE. THIS LOADING IS A SUPERPOSITION OF
PRESSURE ON THE INSTRUMENT BASE PLATE AND
A MAXIMUM RANDOM VIBRATION SPECTRUM APPIED
THROUGH THE EIGHT MOUNTING LOCATIONS.

THE ENCLOSED STRESS ANALYSIS IS PRESENTED TO VERIFY THE ADEQUACY OF THE EIP SENSOR TO THE COMBINED PRESSURE AND VIBRATION LOADING.

MINIMUM MARSINS OF SAFETY WERE FOUND ON THE ENCLOSURE BASE PLATE (SOC 39106630). THE LOWEST MARGIN WAS +.08 ON ULTIMATE LOADING

BY DGP DATE 10/5/71 SUBJECT ELP SENSOR	SHEET NOOF
CHKD. BY DATE QURL MODEL	JOS NO
CHKD. BY DATE	

STRESS CALCULATIONS FOR HARD MOUNTED



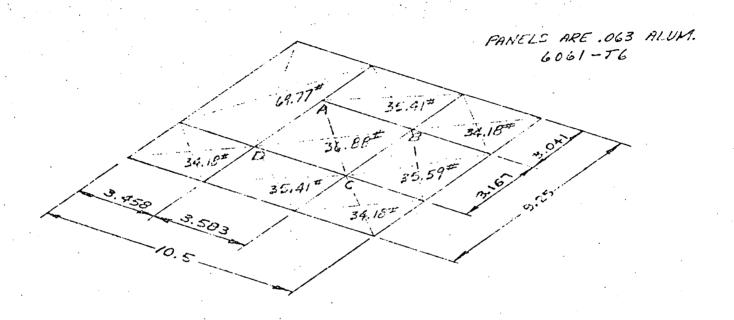
OUTER HOUSING ASSEMBLY SEC 39107462

D. C. P. DATE 10/6/71	BUBJECT ELP SENSOR
DILLALIMILLA	QUAL MODEL
CHRD. BT DATE	BASE PLATE

SHEET NO. ____OF ___



CALCULATION OF PRESSURE LONDS ON PANELS &



A MAXIMUM PRESSURE OF 3.25 PSI WAS READ FROM NAR ENVIRONMENTAL SPEC MHO4 -02120 - 434

PANEL PRESSURE LEADS (LIMIT)

$$3.25 \times 3.456 \times 3.091 = 34.18^{\pm}$$
 (2) 102.54
 $3.25 \times 3.456 \times 3.167 = 35.59$ (1) 35.59
 $3.25 \times 3.456 \times 6.208 = 69.77$ (1) 69.77
 $3.25 \times 3.583 \times 3.041 = 35.41$ (2) 70.82
 $3.25 \times 3.533 \times 3.167 = 36.86$ (1) 36.86
 $70796.$ 315.60^{\pm}
 $3.25 \times 10.5 \times 9.25 = 315.66^{\pm}$ CHECK

DISTRIBUTE 1/4 OF TOTAL PANEL LOAD TO EACH

7.6.	P DATE 10/6/71	SUBJECT_FIR_FENGER	_ SHEET NO 2
	DATE	QUAL MODEL	_ JOB NO
CHIRD, BT		ROSS PLETE	
	PRESSURE	LOAD CALCULATION (CONT'S)	
	•		
		MICHE BEAM WILL BE BEA	M AD" AS
	SHOWN BE	ELEN.	
	10	NEGLECT REACTION	97"0" 1Pp
		D A	X-
		and the first terminal of the first terminal	
		9.17 PA	-3.00/
		DISTRIBUTED LOND ON BEAR	
	W = (6)	9.77 + 35.41 + 36.88 +34.18+ = 52.91=	-35.41) ×.25
	w	= 52.91 / 9.17 = 5.77	T/1N.
	READ	TIDIL PARTY	
		Re (NEGLECT)	
· · · · · · · · · · · · · · · · · · ·		- 7.001	•
		W/ = (35.41+ 34. E-36.88	+ 35.59) Y. 25

$$W = (35.4) + 34.8 - 36.88 + 35.59) \times .25$$
$$= 35.51$$
$$R_{A} = W / 2 = .7.72$$

BY PGP DATE 10/9/21 SUBJECT FIR SENSOF

PRESSURE LOAD (NECHENTION (CONT'D)

Reproduced from best available copy.

DETERMINE MOMENT AT VARIOUS SECTIONS ALONG

X BETWEEN R. AND A

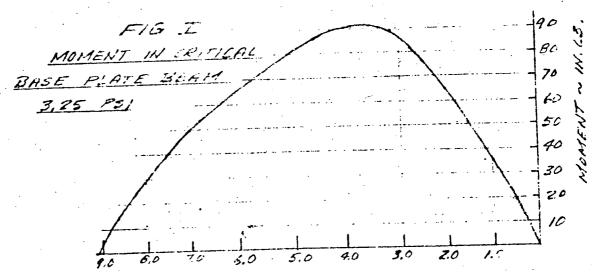
$$M = R_{p} \times -\frac{1}{2} W X^{2}$$

$$R_{p} = \left[\left(2.91 \times \frac{9.17}{2} \right) + \left(17.76 \times 6.129 \right) \right] / 9.17$$

SECTION	X	FX	XZ	WXZ	MOMENT
-JEC11011	.5	19.16	.25	1.44	18.44
1			. —	5.77	35.44
Z	1.0	38.32		}	50.99
3	ستنادير	57,48		17.98	
4	2.0	76.64	4.0	23.08	65.10
		95.8	£ .	36.06	77.77
5				1	89.21
6	3.001	14.99	3,000	12/10/6/	

X BETWEEN A NNE D

	•		x-3.001	7	،سسر را
				10/220011	1277000000
			1 2 2 /1//	トレバス・コンフロ	<i>プラングラとフィー</i>
			$1 \times -2 \times 000$	1000	
	7 4.585 175.76	- · ·		Τ	i
			1 .	1	1 0/ 25
			1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	1 225 1.5	1 06.73
- 1	1 1 - 0 - 1	ツェカン モノとた こ	ひしんつごを	1 201.	
	1 A 5 8 3 1 / /3 . /c !	21,04 100	- 1		
1					
	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1				
	- Commence of the same of the				



X DISTANCE FROM PR ~IN

BY DGP DATE 19/9/7/4 SUBJECT GIP ROME NOSE	SHEET NOOF
BY DATE DATE OUNC NOSE	JOB NO
TRASE PART	

64 g RMS LOND PRICULATION

R" AXIS VIEXNITION

THE RINGS PRODUCT VIERATION TEST WAS RUN

AT A SEG RIAS LEVEL (TEST SPEC, CALLED FOR

643 MAS). THE BOTTOM PLATE INSTRUMENTATION

CONSISTED OF ONLY ONE ACCELERAMETER WHICH

WAS LOCATED APPROXIMATELY IN THE CENTER OF THE

BOTTOM PLATE, THE ACCELEROMETER WAS

FOSITIONED TO MEASURE R' AND RESPONSE.

BECAUSE OF THE CHAITED INSTRUMENTATION THE ACCESSATION LEVELS OF SPECIFIC MODES COMIST BE ISOLATED:

A CONSERTATIVE APPRIMENT IS TAKEN IN THE FOLLOWING CALCULATIONS TO ESTIMATE THE SHEARS AND MOMENTS OCCURRING IN THE BASE PLATE DOGMES 649 PLAS & AKIS EXCITATION.

10 PMS $y'''' = 143 \times \frac{64}{55} = 166.7 g''''' PMS$ (143 g was -10 PMS ACCULERATION FROM THE 559 PMS PMS IMPORT TEST)

30 ACCELERATION PERSON WILL GO TO

THE METHON TO BE USED TO CHLOCKTE BASE

PLATT LOND WILL BE TO ACCOME THAT THE

499 9 RESERVEDE TO THAT OF THE FIRST MISE

AND ONLY THE FIRST MIDE IS INDOCTIVITY THE

ACCELERATION WILL BE APPLIED UNITERMLY TO

THE OVERPLY BASE FUNTE TO SIMPLIFY THE

CHLOUR ATTENS.

SHEET NO. _ Jo___OF --

649 VIERATIME TEST LENOING (CONTE)

Reproduced from available copy.

- POTTOM PLATE

	VOLUME	.,
5xIN 9.25 × 10.5 x .062 =	6.022	IN 3
CENTER RIES		** 5
4 x 3.583 x . 287 x . 08 =	. 323	
4 x 3.16/ 1.282 x .08 =	286	
TAPERED RIES		
8 x 2.499 x 125 x . 12 x /2=	.150	
8 x 2.773 x .219 x . 08 x /2 =	.194	
5 x 2.916 x 125 x.12 x 1/2 =	.109	
5 x 2.539 x.219 x.08 x 1/2 =	.111	
EDGE 39.5 x 1(154 x,234) - (.085 x,094) =	1.126	
INTERSECTIONS	.333	:
Ex. 196 x . 696 x . 344 =	.147	
+. 696 x. 6/6 x . 344 =	,236	•
+. 396 × 457 x . 344 =	• • •	
- 4 x 3/19/6 x 1/25 x 244 =	068	
CONNECTOR BOSS & RIB		
.75 x 1.628 x .16 x /2 =	.098	
1.562 X.17 X.08 X/2 =	.011	
2.956 x 1/25 x 481 x /2 =	.089	
FULLETT THE		
28/4 x . 126 x . 375 (1-4) =	.026	
42/4 x. ZEIX 315' (1-7/4) =	,317	
		•

TOTAL YOLUME 9.5/ IN3

DENSITY OF GOGI-TE PLUMINANT = .098 =/1N3

TOTAL WE SO FOR BASE PLATE

WT = 4.51 x .098 = .93

649 VIBRATION TEST LOADING (CONTID)

NOW THE EQUIPALENT TOTAL LOAD FROM VIERATION

499.2 1.93 = 464

UNIT LOAD IS

THE TOTAL CIMIT DESIGN LOAD BY MAY SECTION

CAN NOW BE DETERMINED BY USING FIG I

FOR OBTAINING THE PRESSURE MOMENT AT

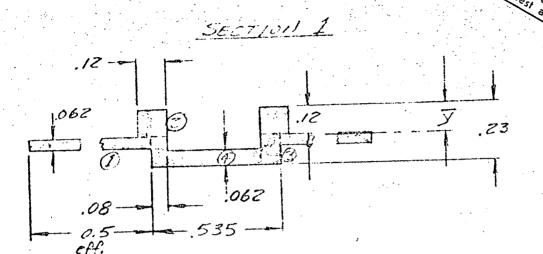
ANY DESIRED SECTION ON BEAM "AD", OUR

ASSUMED CRITICAL BEAM, AND MULTIPLYING THE

MOMENT FROM THE CURVE BY:

		-	(LIMIT)
SECTION	PRESS. MOM.	VIB. MOM.	TOTAL MOMENT
/	18.44	27.11	45.55 IN LE.
2	35.44	52.10	87.54
3	50.99	74.96	125.95
. 4	65.10	95.7	160.80
5	77.77	114.32	192.09
6	89.01	130.84	219.85
7	86.92	127.77	214.69

BEAM "NO" DECTION PROPERTIES



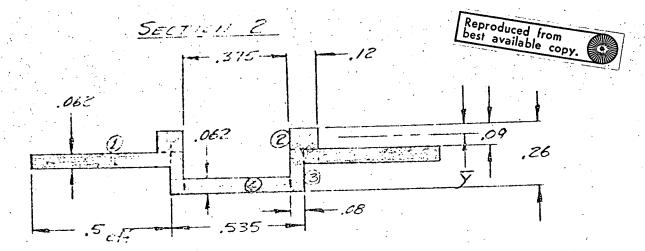
	the state of the s						
ſ	ELEM	A	V	A	Ayz	To	TOT
1	2.2677	2/2	151	.00935	.00141	.00002	.00143
Ì	2	0200	26	00173	,00010	.00003	.00013
	· · · Z	.0286	,00	00302	,00054		.00056
	3	.0116	.//5	20200	00092	.00001	.00093
-			1	,00404			.00305
- [Tor	1517		,01001	.00277	1.0-1-0	L

$$\overline{y} = \frac{.01881}{.1317} = .1428 \text{ IN} \qquad \overline{y} = .0204 \text{ IN}$$

$$T_{yy} = .00305 - .1317(.0204) = .00036 \text{ IN}^4$$

$$Z_{yy} = .00254 \text{ IN}^3$$

BEAM "HO" SECTION PROPERTIES (CONTO)



5 = 1 6 1 1	1 0		A.	Ayz	70	Tor.
	.068	121	,00750	.00091	1.00000	,00093
2	0211	015	000?	00004	.00001	.0000
3	2275	175	.00476	.00083	,00007	.00090
4	0233	779	.00534	,00122	.00001	.00123
			.01857		.00011	.00311

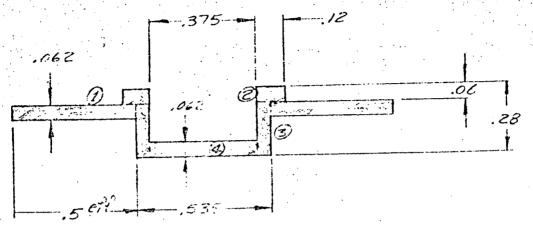
$$\frac{y}{y} = \frac{.01857}{.1321} = .1385 \text{ IN} \qquad y^{2} = .0192 \text{ IN}^{2}$$

$$T_{yy} = .00311 - .1341(.0192) = .00054 \text{ IN}^{4}$$

$$Z_{yy} = \frac{.00054}{1.1385} = .0039 \text{ IN}^{3}$$

BEAM "AL" SECTION PROFERTIES (CONT'S)

SECTEN 3



ELEM		\ <u>`</u>	RY	Ay	To	TOT
	.062	.091	.00664	.0005/	.00002	.00053
7	0141	.03	1.00043	.00001		.00001
3	030.2	.17	20528	.00102	.00020	
. 1	1223	249	.00580	.00144	,00001	.00145
TOT	1349		.01785	,00298	,00072	.00321

$$\overline{y} = \frac{.01785}{.1349} = .1323 \text{ III.} \qquad \overline{y}^2 = .0175 \text{ III}^3$$

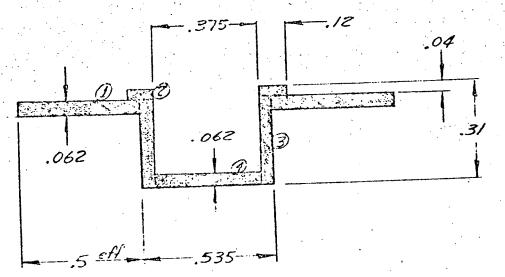
$$\overline{I}_{yy} = .00321 - .1349(.0175) = .00085 \text{ III}^4$$

$$\overline{I}_{yy} = \frac{.00685}{.1477} = .00575 \text{ III}^3$$

BEAM 'AS SECTION PROPERTIES

(CONTID)

SECTION 4



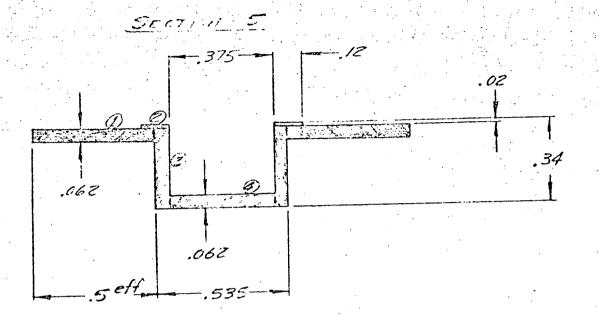
				<u> </u>		707
ELEM	A	y	1 1 1	Ayz	4	
,	.068	.07/	.0046	.00031	1.0000	.00033
. 2	<u> </u>	27	00019	.00000	.00000	.00000
2	.0796	1000	2437	00127	.00026	,00158
3	. 0432	.175	1.00136	.00137	20201	.00182
4	.0233	779	1.00633	1.00181	,00007	1.00.02
	./38/		.01865	.00344	.000 29	.00373
101	1.75 67	<u> </u>			J	

$$\overline{y} = \frac{.01865}{.138!} = .1350 \text{ IN.} \qquad \overline{y}^2 = .0182 \text{ IN.}^2$$

$$T_{yy} = .00373 - .1381(.0182) = .00121 \text{ IN.}^4$$

$$Z_{yy} = \frac{.00121}{.175} = .00691 \text{ IN.}^3$$

BERIT "AD" SECTION PROPERTIES (CONT'S)



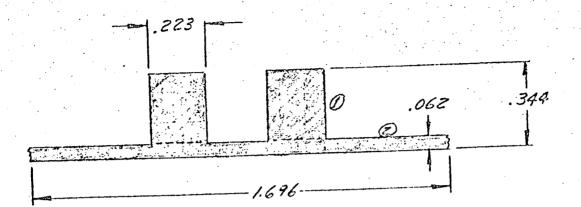
ELEM	a	V	BY	Ryz	Io	TOT
CLEM	062			.00016	7	.00018
7	.0048			.00000	.00000	.00000
.3	.0512			.00166	.00040	.00206
_	.0233		1	,00222	li .	.00223
TOT	.1413	r 			.00043	.00447

$$\frac{y}{y} = \frac{.01963}{.1413} = .1389 \text{ IN.} \qquad \overline{y}^2 = .01919 \text{ IN}^2$$

$$T_{yy} = .00447 - .1413(.01919) = .00176 \text{ IN}^4$$

$$Z_{yy} = \frac{.00176}{.2011} = .00875 \text{ IN}^3$$

BEAM "AD" SECTION PROPERTIES (CONT'D)



				<u>-</u>		
		· · ·	Av	Ayz	Io	TOT
ELEM	77	101	11773	,00250	.00114	,00364
/	.12577	.141	,0///	01050	00003	,01033
2	.10515	,3/3	,03291	,0,000	100000	,01033
TOT	23092		P5064	.01280	1.00111	.01397

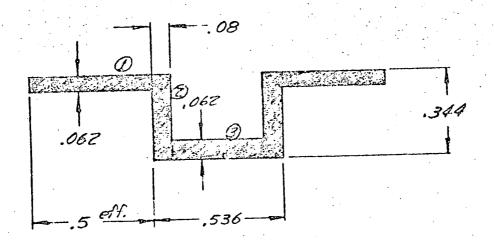
$$\overline{y} = \frac{.05064}{.23092} = .2193 \text{ IN.} \quad \overline{y}^2 = .04809 \text{ IN}^2$$

$$T_{yy} = .01397 - .23092(.04809) = .00287 III^{4}$$

$$Z_{yy} = \frac{.00287}{.2193} = .01309 III^{3}$$

BEAM AD" SECTION PROPERTIES

SECTION Z



			1 0	Aye	7	TOT
ELEM	\mathcal{A}		Ay	· · · · · · · · · · · · · · · · · · ·	1 20	
	.062	.031	.00192	.00006	.00002	.00008
	05504	172	.00947	.00163	,00054	,00217
6	02225	2/3	00728	00228	.00001	,00229
3		·	1.00720	00707	.00057	00050
TOT.	.14029		.01861	1.00397	1.00037	1.00,07

$$\frac{.01867}{y} = \frac{.01867}{.14029} = .13308$$
 $y^2 = .01771$

$$I_{yy} = .00454 - .14029(.01771) = .00206 IH^4$$

$$\frac{2}{3} = \frac{.00206}{.2109} = .009767 IN^3$$

SHEET NO. ___O__OF ___

BASE PLATE

BEAM AD STRESSES

$$F_{t_y} = 35,000 \text{ psi}$$

 $F_{t_u} = 38,000$
 $ULT = 1.5 \times LIM.$

SECTION	MOMENT	Z-1N.3	BENDING STRESS	M. S.LIM	M.S. ULT.
1	45.55 IN.LB.	_	17,930 psi	+.49	+.29.
Z	87.54	.0039	22,450	r.36	+ . //
3	125.95	.00575	21,900	¥.375	+.14
4	160.80	.00691	23, 270	+.34	+.08
5	192.09	.00875	21,950	4.37	+,13
6	219.85	.01309	16,795	+.52	+,34
フ <i>*</i>	227.24	.00977	23, 260	+.34	+.08

* ESTIMATED MAX. MOMENT SECTION

THE PRECEDING SOMEWHAT CONSERVATIVE ANALYSIS
REVEALS NO PROBLEMS STRUCTURALLY WITH THE
LOWER ENCLOSURE PLATE. THE FIXIDY AT THE
PLATE EDGE HAS BEEN IGNORED BECAUSE IT WILL
BE SMALL HID WILL LOWER THE PRESSURE STRESSES
INCREASED ALLOWABLES FOR PLASTIC BENDING HAVE NOT
BEEN USED. THIER USE WOULD EFFECT EACH SECTION
OIFFERENTLY BUT THE USE WOULD INCREASE ALL
MARGINS OF SAFETY. RESONANT FREQUENCIES OF
THE SMALL SUB PLATE AREAS FALL ABOVE 2000 CP

FROM ROARKE 3RD ED. pg 203

3.583 $\int_{0.02^{\infty} THK} \int_{0.062^{\infty} THK} \int_{0.02^{\infty} THK} \int$

E = 10 psi

6 = 10.03

CHKD. BY ___ DATE ____ JOB NO.____

SIDE FLATE

CALCULATION OF PRESSURE AND ACCELERATION LOADS

THE TOTAL LOAD ON THE ENCLOSURE SIDES WILL BE
CALCULATED IN A SIMILAR MANNER AS THOSE ON THE
BOTTOM PLATE, THAT IS, THE ACCELEROMETER RMS
LEVELS READ FROM THE 55g RMS RANDOM
VIBRATION TEST WILL BE APPLIED TO THE TOTAL
PLATE AREA TO CALCULATE AN EQUIVALENT PRESSURE
WHICH WILL BE ADDED TO THE DESIGN PRESSURE
DIRECTLY.

10 RMS g'D $111.3 \times \frac{64}{55} = 129. \text{ g'D}$ 36 PEAKS WILL GO TO 388. g'D

WILL BE.

.04 x .098 x 388. = 1.52 psi

LIMIT DESIGN LOAD ON SIDE PLATE IS:

3.25 + 1.52 = 4.77 psi

THE LARGEST SIDE WILL BE USED FOR THE

ANALYSIS (10.5 X 3.456). A UNIFORM THICK
NESS OF .04" WILL BE ASSUMED. THIS IGNORE.

STIFFENING RIBS AIDING IN PANEL SUPPORT. THE

PANEL DEFLECTION IS EXPECTED TO BE LARGER

THAN 1/2 THICKNESS THEREFORE A DIAPHRAM

ANALYSIS WILL BE USED. SEE ROARKE 3RD ED

PQ 222.

CHKD. BY ____ DATE _____ SUBJECT _____ CLASS _____ OUAL MODEL ______ SIDE PLATE

14 = 147.09

JOB NO.

CALCULATION OF PRESSURE AND ACCELERATION
LOADS AND STRESSES ON ENCLOSE SIDE PLATE.

ROARKE BRO ED. Pg 222

$$t^2 = .0016$$
 $t^4 = .00000256$
 $t^2 = 11.92$
 $t^{10.5}$
 $t^{2} = .0016$
 $t^{2} = 11.92$
 $t^{2} = .00000256$
 $t^{3} = 3.$

$$Et^2/b^2 = \frac{10^7 \times .0016}{11.92} = 1.342 \times 10^3$$

$$\frac{sb^{2}}{Et^{2}} = 7.16^{\circ} + .06(10.3 - 7.16) = 7.35$$

$$S = 1.342 \times 7.35 \times 10^{3} = 9865 \text{ psi G CE}$$

69

		SHEET NO LOLLOF
10/10/7/	SUBJECT E/P SENSOR	SHEET WORLD
BY DATE DATE DATE	QUAL MODEL	JOB NO
CHKD BY DATE		

INTERDEPARTMENTAL COMMUNICATION

B. C. Hall

FROM

DEPT./ 625-40 EDO./ Beta FAC. HASD 1-14-72
EPS-855

D. L. Vincent

ORON. 625-40 Beta FAC. HASD EXT. 422

SUBJECT: EPS Baseplate: Qualification Model

An analysis of the baseplate under combined pressure and random vibration was made ("Electron/Proton Sensor, Combined Pressure and Random Vibration, 10/18/71; D.G. Probe") based on 'R' Axis random vibration as specified in NAR's ICD.

It has now been proposed that the 'R' Axis random vibration criteria be:

Max. g and lift-off simulation - 80 secs.

20 - 175 Hz +9 dB/oct increase

 $175 - 350 \text{ Hz} \qquad 6.0 \text{ g}^2/\text{Hz}$

350 - 2000 Hz -3 dB/oct decrease (70.5 g rms)

Transonic/Mach I Simulation - 10 secs

20 - 175 Hz +9 dB/oct increase

 $175 - 350 \text{ Hz} \quad 10.0 \text{ g}^2/\text{Hz}$

350 - 2000 Hz -3 dB/oct decrease (91.0 g rms)

It is therefore necessary to re-examine the integrity of the baseplate when subjected to the proposed vibration levels

Vibration Test level achieved, 55 g rms in 'R' Axis monitored response on baseplate = 143 g rms.

Hence, rms vibration of baseplate at new level:

 $= 143 \times \frac{91}{55} = 236.6 \text{ g rms}$

and peak level (3 σ) will not exceed 3 x 236.6 = 709.8 g

From previous analysis:

Equiv. Unit Load @ 499.2 g = 4.78 lbs/sq. in.

Hence, Equiv. Unit Load @ 709.8 g =

4.78 x $\frac{709.8}{499.2}$ = 6.8 lbs/sq. in.

and moment factor (vibration)

$$=\frac{6.8}{3.25}=2.092$$

Again, from previous analysis, maximum pressure moment is 92 lbs-ins @ section 7.

Max. vibration moment = $92 \times 2.092 = 192.46$ lbs-ins Section modulus, section 7 = .00977

$$f_b = \frac{M}{Z}$$
 $F_{Oy} = 35,000$ PSI $F_{Ou} = 42,000$ PSI $f_b = \frac{192.46}{.00977} = 19,699$ PSI $f_b = \frac{35,000}{19,699} = 1.78$ $f_b = \frac{35,000}{19,699} = 1.78$ $f_b = \frac{42,000}{1.5 \times 19,699} = 1.42$ M.S. $f_b = \frac{42,000}{1.5 \times 19,699} = 1.42$ M.S. $f_b = \frac{42,000}{1.5 \times 19,699} = 1.42$

The above values are based on vibration only, as when the baseplate is subjected to qualification testing.

Consider with 3.25 PSI pressure added, then:

$$f_{b} = \frac{192.46 + 92}{.00977} = 29,116 \text{ PSI}$$

$$F \text{ of } S_{\text{Lim}} = \frac{35,000}{29,116} = 1.20 \qquad M.S._{\text{Lim}} = +.20$$

$$F \text{ of } S_{\text{Ult}} = \frac{42,000}{1.5 \times 29116} = .96 \qquad M.S._{\text{Ult}} = -.04$$

These figures indicate that the baseplate is marginal when subjected to the proposed peak vibration and pressure levels, but appears to present no problems if subjected to the vibration levels only.

The preceding is a somewhat conservative analysis, as was the analysis previously prepared. The notes on P. 15 of D. G. Probe's analysis apply here also.

The calculations show that the baseplate will meet the new vibration levels in qualification testing, if imposed. However, there is no real margin of safety for the combined pressure and vibration condition. Considering the increase in the vibration level, this is not surprising.

Failure of the baseplate, should it occur, would not be dramatic, but would probably consist of some cracking in the region of section 4 and/or 7.

IT HAS BEEN PROPOSED TO RAISE THE EPS
QUALIFICATION RANDOM VIBRATION CRITERIA TO:-

MAX. 9 AND L'FT-OFF SIMULATION.

20-175 Hz +9dB/OCTAVE 175-350 Hz 6.0 32/Hz 350-2000 Hz -3dB/OCTAVE

(70.5g r.m.s.)

TRANSONIC/MACH! SIMULATION.

20-175 Hz +9dB/OCTAVE 175-350 Hz 10.0 g2/Hz 350-2000 Hz -3dB/OCTAVE

(91.0 g r.m.s.)

IT IS THEREFORE NECESSARY TO RE-EXAMINE
THE BASEPLATE, OUTER HOUSING AND THE RESPONSE OF THE
VIBRATION ISOLATORS TO THIS INCREASE IN RANDOM
VIBRATION LEVELS.

AN ANALYSIS OF THE BASEPLATE UNDER COMBINED DIFFERENTIAL PRESSURE AND RANDOM VIBRATION WAS MADE (ELECTRON/PROTON SENSOR, COMBINED PRESSURE AND RANDOM VIBRATION, 10/18/71, D.G. PROBE) BASED ON THE 'R'AXIS RANDOM VIBRATION AS SPECIFIED IN N.A.R'S I.C.D. THE FOLLOWING PAGES UP-DATE THAT ANALYSIS TO APPLY TO THE NEW VIBRATION CRITERIA.

CHKD. BY ____ DATE ____

STRUCTURAL TEST UNIT, 'R' AXIS RANDOM VIBRATION:

RANDOM VIBRATION TEST INPUT = 55.09 r.m.s.

BASEPLATE RESPONSE = 143 g r.m.s.

BASEPLATE RESPONSE AT Slig (M.S = 143.0 x 51 = 236.69.

AT PEAK LEVEL (30), RESPONSE WILL NOT EXCEED 3x 236.6 = 709.89.

WEIGHT OF BASEPLATE = .93 LBS.

EQUIVALENT TOTAL LOAD ON BASEPLATE = 709.8 x .93 = 660.114.

= 660.114 = 6.797 LBS/SQ.IN.

INCLUDING 3.25 P.S.I. PRESSURE DIFFERENTIAL,

TOTAL PRESSURE EQUIVALENT = 6.8 + 3.25

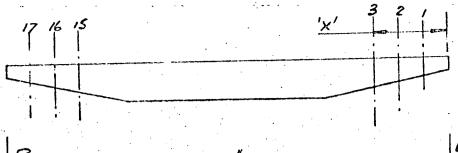
= 10.05 LB./5Q.IN.

FROM PREVIOUS ANALYSIS, BEAM AD IS CRITICAL BEAM; AND DISTRIBUTED LOAD ON BEAM WAS 5.77 LB/IN. FOR 3.25 LB/SQ.IN. PRESSURE, AND RA WAS 17.76 LB.

UNDER NEW LOADING, DISTRIBUTED LOAD $\omega = 5.77 \times 10.05 = 17.84 \, \text{LB/iN}.$ 3.25

AND $R_A = 17.76 \times 10.05 = 54.92 LB.$ 3.25

SECTIONS TAKEN EVERY .5 ALONG LENGTH OF BEAM.



W= 17.84 LB/W., Ra= 54.92 LB.

$$P_{R} = \left[\frac{\left(\frac{17.64 \times 9 \times 9}{2} \right) + \left(54.92 \times 6 \right)}{9} \right] = \left[\frac{722.52 + 329.52}{9} \right]$$

= 116.89 LB.

TO DETERMINE BENDING MOMENT AT STATIONS EVERY .5"
ALONG BEAM :-

WHEN 'X' LIES BETWEEN RE AND RA,
BENDING MOMENT, M = Rex - WX2

WHEN 'X' LIES BETWEEN RA AND R., $M = R_{e} \times - \frac{\omega}{2} x^{2} - R_{a} (x-3.0)$

BY EV DATE 8:2:22

SUBJECT EPS - PROPUSED

INCREASE IN QUAL. VIB. TION

LEVELS

бнеет NO._----ОГ ___-Јов NO.____-

Re= 116.89, W= 17.84, R= 54.92

	•						
STATION	'X'	PRX	X²	$\frac{\omega x^2}{2}$	X-3	P _A (x-3)	M
0	0	0	0	0			0
1	.5	58.445	. 25	2.23			56.215
2	1.0.	116.83	1.00	8.92		graph (Challege	107.97
3	1.5	175.335	2.25	20.07	-	ويديني -	155.265
4	2.0	233.78	1.00	35.68			198.10
5	2.5	292.225	6.25	55.75	Green and the second		236.175
6	3.0	330.67	9.00	80.28	0	0	270.39
フ	3.5	109.115	12.25	109.27	.5	27.46	272.385
B	1.0	467.56	16.00	142.72	1.0	54.92	269.92
9	4.5	526.005	20.25	180.63	1.5	82.58	262.995
10	5.0	584.45	25.00	223.00	2.0	109.84	251.61
11.	5.5	642.895	30.25	269.83	2.5	137.30	235.765
12	6.0	701.34	36.00	321.18	3.0	164.76	215.46
13	6.5	759.785	42.25	376.87	3.5	192.22	120.695
14	7.0	B18.23	49.00	437.08	4.0	219.68	161.47
15	7.5	E76.675	56.25	501.75	4.5	247.14	127.785
16	8.0	935.12	64.00	570.88	5.0	274.60	89.64
17	8.5	993.565	72.25	644.47	5.5	302.06	47.035
18	9.0	1052.01	81.00	722.52	6.0	329.52	03

MAX. M = 272.391 OCCURS AT X = 3.473".

TABLE OF BENDING MOMENTS.

BY _ PL	date 2:2:72
muse by	DAYE

SUBJECT EPS-PROPOSED

INCREASE IN QUAL. VIBL. FION

LEVELS.

SHEET NO._ 22__OF ___.

JOB NO._____

STATION	MOMENT LBS-INS.	I NS	Z 1N5 ³	STLESS LB/SQ.IN.	
1	56.215	.00036	.00254	20,557	
2	107.97	.00054	.0039	27,685	
3	155.265	.00085	100575	27,003	
4	198.100	.00121	.00691	28,669	沿
5	236.475	100176	.00875	27,026	
6	270.39	.00287	.01309	20,656	
7	272.385	.00206	.009767	27,888	
8	269.92	.00206	.009767	27,636	
9	262.995	.00206	.009767	26,527	
10	251.61	.00206	.009767	25,761	
11	235.765	.00206	.009767	24, 139	
12	215.46	.00287	.01309	16,460	
/3	190.695	100176	·00875	21,794	
14	161.47	100121	100691	23,368	
15	127.785	100085	.00575	22,223	
16	89.64	.00054	10039	22,215	
17	17.035	.00036	.00254	18,518	ل

* POINT OF MAX. STRESS IN BEAM.

TABLE OF BENDING STRESS.

MAX. BENDING STRESS = 28,669 LB/SQ.IN.

BEAM MATL. - ALUM. ALLOY, 6061-TG.

Fty = 35,000 LB/SQ.IN

Ftm = 42,000 L8/5Q. IN.

FACTOR OF SAFETY :-

$$M.5_{ULT} = -.023$$

AT EDGES OF BEAM, BENDING STRESS IS COMBINED WITH BENDING STRESS INDUCED IN PANELS. MAXIMUM COMBINATION IS AT STN. 3.

BENDING STRESS (BEAM) = 27,003 LB/SQ.IN.

ASSUME PANEL 2.75 SQUARE. $t = .063 \qquad \frac{\alpha}{L} = 1.0$

(Roark, Table 10,)
case 41

β= .3078 , ω=10.05 P.S.I. $S_{l} = \beta \underline{\omega b}^{2}$ = .3078 × 10.05 × 2.75 = 5894 LE/5Q.W.

COMBINED STRESS = 27003 - (-5894) = 16,449 LB/SQ.IN.

FOR GOGI-TG, F. = 27,000 LE/SQ.IN. FS.y = 20,000 LB/SQ.IN.

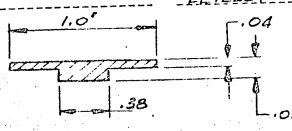
M.S. LIM = +.216 F.S.LIM = 20,000 = 1.216

M.S. ULT. = +.09 F.5. ULT. = 27000 = 1.09

CONSIDER EFFECT OF BASEPLATE BENDING ON ELECTRON BEAM WELD AROUND EDGE.

MAX. SLOPE AT END OF BEAM = . 058 RADIANS.

CONSIDER SIDE RIB AS CANTILEVER BEAM UNDER END MOMENT.



RIB SECTION

:.
$$M_0 = \frac{QEI}{L} = \frac{.058 \times 10 \times 10^6 \times 28.45 \times 10^6}{3.38}$$

= 4.48 LB-INS.

STRESS IN WELD:-

ASSUME LENGTH OF WELD = 1.5 x .38 = .57"

THEN STRESS IN WELD OUE TO BENDING
$$= \frac{GM}{bt^2} = \frac{G \times 4.28}{.57 \times .08^2} = 7,368 LB/SQ.IN.$$

DEPT. 625-40,150. Beta PLANT HASD DATE 2-8-72
DOON. EPS-67!

B. C. Hall

D. L. Vincent

DSPT. 625-40 Beta FAC. HASD EXT. 422

10 seconds

SUBJICT: Proposed Increase in Qualification Vibration Levels for the EPS

It has been proposed to increase the EPS 'R' axis qualification random vibration criteria from:

Max g and Lift-off Simulation 80 seconds

20 - 125 Hz @ 12 dB/Oct Increasing

 $125 - 500 \text{ Hz} - 2.0 \text{ g}^2/\text{Hz}$

500 - 675 Hz - -9 dB/Oct

 $675 - 1100 \text{ Hz} - .80 \text{ g}^2/\text{Hz}$

1100 - 2000 Hz - -9 dB/Oct (overall - 41 g rms)

Transonic/MACH 1 Simulation 10 seconds

20 - 125 Hz @ 12 dB/Octave increasing

 $125 - 500 \text{ Hz} - 5.0 \text{ g}^2/\text{Hz}$

500 - 675 Hz - -9 dB/Octave

 $675 - 1100 \text{ Hz} - 2.0 \text{ g}^2/\text{Hz}$

1100 - 2000 Hz - -9 dB/Octave (overall = 64 g rms)

to the following levels:

Max. g and Lift-off Simulation 80 seconds

20 - 175 Hz - +9 dB/Octave

 $175 - 350 \text{ Hz} - 6.0 \text{ g}^2/\text{Hz}$

350 - 200 Hz - -3 dB/Octave (overall = 70.5 g rms)

Transonic/MACH 1 Simulation

20 - 175 Hz - +9 dB/Octave

 $175 - 350 \text{ Hz} - 10.0 \text{ g}^2/\text{Hz}$

350 - 2000 Hz - -3 dB/Octave (overall - 91.0 g rms)

Test time has not been changed.

These new levels represent a considerable increase in the vibration input to the EPS in the 'R' axis, which has always been the most severe axis for vibration response.

The effect of the proposed levels on an EPS test unit was considered in two ways:

- What increase in vibration response and stress levels would be seen on the hard-mounted outer housing?
- 2. What increase in vibration input would the electronics package receive from the vibration isolators?

From the EPS Structural Test Unit results, we know that the baseplate is probably the most highly stressed part in the unit. A prior stress analysis was undertaken to verify the integrity of the baseplate under combined pressure and random vibration. This analysis has been updated to reflect the new vibration levels, and both are included as attachments to this memo.

These analyses are hand calculated. A number of assumptions have been made in them, and these assumptions probably err on the side of conservatism in the approach, but not necessarily so. It is usual in such cases to apply a factor of safety to such hand-calculated results. No such factors of safety have been used in the accompanying analyses.

The analysis of the baseplate shows that its integrity under a combination 3.25 p.s.i. differential pressure and the proposed transonic/Mach I simulation random vibration cannot be verified. Stresses at several sections are too high, and in one case we have a negative margin of safety occurring on ultimate loading. While the stress levels would be about 30% lower for the random vibration criteria alone, no account has been taken of potential stress concentration areas - of which the baseplate has several.

It should perhaps be mentioned that if the initial design and stress check had been performed using the presently proposed vibration criteria, the resulting baseplate would not be to the present configuration. It would be stronger, stiffer and probably 20 - 25 % heavier.

Investigation of the response of the vibration isolators to the proposed vibration levels gives a new input level of 6.75 g rms compared to 6.1 g rms for the old, and a deflection requirement of .127" compared to .115". These are based on hand calculations by the writer.

Barry Controls, manufacturers of the vibration isolators, have carried out a computer analysis of the isolator response to the new levels which confirms these hand calculations.

Obviously, the response levels of the electronics components will increase over the response to the previous level, but not excessively so and will probably not be critical.

D. J. Vincent

VIBRATION ISOLATOR RESPONSE (BARRY CONTROLS ANALYSIS)

'R' Axis

Max. g and Lift-off.

	3 Sigma	3 Sigma
	RMS (g's)	RMS Displ. (inches)
35 Hz	12.10	.084"
•	(7.47)	(.051)
50 Hz	23.20	.085"
	(15.57)	(.059)
en e		
Transonic/MACH 1		
35 Hz	15.6	.110"
	(11.79)	(.0804)
50 Hz	29.9	.110"
	(24.63)	(.0882)

Note: Values in parenthesis are for previous test criteria.

REPORT: COMPARISON OF ACCELERATION LEVELS TO OTHER DYNAMIC TEST LEVELS FOR THE ELECTRON-PROTON SPECTROMETER

LEC Document Number EPS-592

Prepared by

D. L. Vincent Mech. Engineer

Approved by:

B. C. Hall

Program Manager

COMPARISON OF ACCELERATION LEVELS TO OTHER
DYNAMIC TEST LEVELS FOR THE ELECTRON-PROTON SPECTROMETER

Preface

At the Critical Design Review of the Electron-Proton Spectrometer (EPS) held 19th - 20th October 1971, the absence of any acceleration testing for the EPS caused concern to some participants. As a result of this conern, RID T-4 was generated requiring that LEC do an analysis to verify the integrity of the EPS to a 'qualification' level of acceleration and compare this with other dynamic test levels. This report has been written to comply with this requirement.

Introduction

The boost acceleration occurs only in the +X direction of the EPS and reaches a peak value of 4.9 g, hence an ultimate 'qualification' test level would be $4.9 \times 1.5 = 7.35 \text{ g}$.

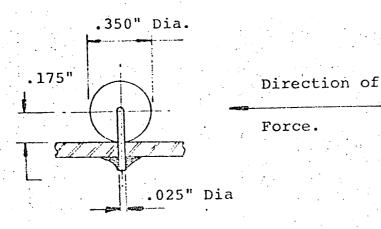
A 20 g, 11 millisecond terminal sawtooth basic design shock and qualification level random vibration test has already been carried out on the EPS Structural and Engineering Test Units. The attached figure shows that, in the 'X' axis, both these tests expose the EPS to higher 'g' levels than the proposed acceleration level. Additionally, the response of the EPS electronic package upon its vibration isolators exceeds this proposed acceleration level between the range of 30 - 80 cps.

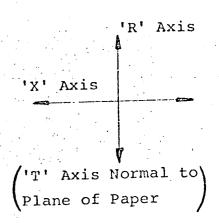
Consideration of the type of loading induced by each of the test methods assists in an evaluation of the relative severity of each of the tests. Acceleration will produce in the EPS and its component parts a unidirectional steady state load; failure will occur when this load exceeds the ultimate load that the part can withstand. Shock also produces an essentially unidirectional force, suddenly applied and of short duration. Shock induces loading which has approximately twice the effect of the same 'g' loading steadily applied. In this instance failure could occur at a level substantially below that causing a failure in an acceleration mode. Random vibration produces a continually varying bi-directional force which produces an alternating load of varying magnitude; failure can occur from overloading the component or from fatigue. A component can fatigue at a substantially lower loading than that required for failure under steady state conditions.

Hence, it can be seen that for an equal load situation, both vibration and shock are more severe than acceleration. On this basis, an analysis was made of the stress levels induced by the various test conditions in the leads of a typical EPS component. The factors of safety for each test mode were then compared.

Analysis

One of the largest and heaviest components in the EPS electronics package is the Kemet Capacitor, T210D156K075PS, mounted on the input filter printed circuit board of the filter module. This component is taken as being representative of those components in the EPS electronics package.





Component Data:

Weight = 6.3 grams (.014 lbs)

Lead Material = Tinned Nickel Wire

Ultimate Tensile Strength = 70,000 lbs/sq. ins.

Yield Strength = 40,000 lbs/sq. ins.

Endurance Limit = 28,000 lbs/sq. ins.

Lead Section Modulus,
$$Z = \frac{\pi D^3}{32} \times 2 = \frac{2\pi \times .025^3}{32} = .307 \times 10^{-5} \text{ ins}^3$$
 (for two leads)

(for conservative analysis, the supporting effect of conformal coating will be ignored.)

Acceleration

Acceleration force = 7.35 g

Induced load = $7.35 \times .014 = .103 \text{ lbs}$

Bending moment on leads, $M = .103 \times .175 = .018$ lbs - ins.

Bending stress =
$$\frac{M}{Z} = \frac{.018}{.307 \times 10^{-5}} = 5,863$$
 lbs./sq. ins.

Factor of Safety =
$$\frac{\text{U.T.S.}}{\text{Bending Stress}} = \frac{70,000}{5,863} = 11.9$$

Random Vibration

R.M.S. input to electronics package = 4.46Induced load = $4.46 \times .014 = .062$ lbs. Bending moment on leads, M = $.062 \times .175 = .011$ lbs-ins.

Bending stress = $\frac{.011}{.307 \times 10^{-5}}$ = 3583 lbs/sq. ins.

Factor of Safety =
$$\frac{\text{Endurance Limit}}{\text{Bending Stress}} = \frac{28,000}{3,583} = 7.8$$

(The above is based on the rms level. At this level, 7.35 g will be exceeded approximately 10% of the time.)

Shock

Shock input to electronics package = 24 g.

Induced load = $2 \times 24 \times .014 = .672$ lbs.

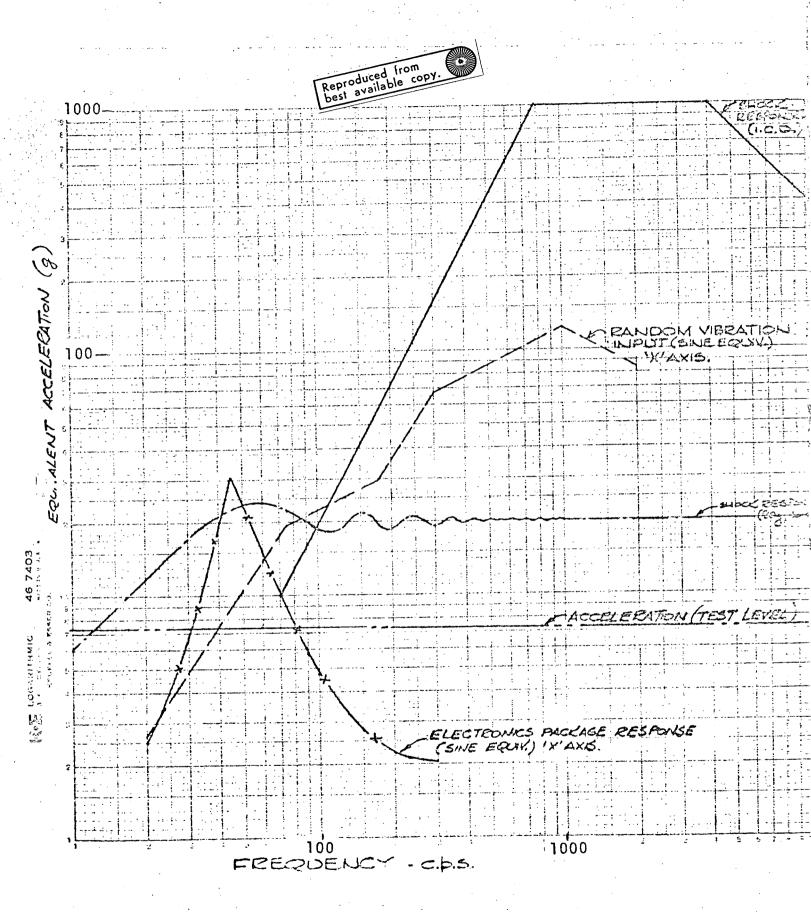
Bending moment on leads, $M = .672 \times .175 = .118$ lbs-ins.

Bending stress =
$$\frac{.118}{.307 \times 10^{-5}}$$
 = 38,436 lbs-ins.

Factor of Safety =
$$\frac{\text{U.T.S.}}{\text{Bending Stress}} = \frac{70,000}{38,436} = 1.82$$

Conclusions

It can be seen that both the random vibration and shock requirements exceed the acceleration test level by a considerable margin, even for the electronics package. The factors of safety compared to the failure level are lower for these two tests than for acceleration. It is therefore considered that these two tests adequately validate the ability of the EPS to meet the boost acceleration levels and an acceleration environment of 7.35 g.



STATEMENT OF WORK BARRY VIBRATION ISOLATORS FOR EPS

It is required that the vibration isolator design provided by the Barry Division of Barry Wright Corp. to LEC Procurement Specification EPS-356 be analyzed for the following proposed change in the 'R' Axis Random Vibration Environment:

Max. g and Lift Off Simulation

20 - 175 Hz +9 dB/octave increase

175 - 350 Hz $6.0 \text{ g}^2/\text{Hz}$

350 - 2000 Hz -3 dB/octave decrease

duration - 80 seconds.

Transonic/MACH 1 Simulation

20 - 175 Hz +9 dB/octave increase

175 - 350 Hz $10.0 \text{ g}^2/\text{Hz}$

350 - 2000 Hz -3 dB/octave decrease

duration - 10 seconds.

The analysis shall compare the 3 sigma rms acceleration and the 3 sigma rms deflection responses of the isolator for the above vibration levels with those levels given for the 'R' axis in EPS-356. Also investigate the possibility of the isolator "Bottoming Out" under the proposed vibration levels.

Additionally, provide an isolator response curve for the transonic/MACH l simulation and advise whether any standing wave effects can be anticipated.

INTERDEPARTMENTAL COMMUNICATION

B. C. Hall

DOGN. 625-40 DOGS Beta PAC. HASD

3-21-72 EPS-722

D. L. Vincent

OGGN. 625-40 MGMa Beta FAC. HASD EXT. 422

SUBJECT. Vibration Testing of the EPS Electronics

At the CDR a request for the acceptance testing of the EPS electronics by random vibration without isolators was disallowed. However, since that time, Boeing has taken over the G. E. support contract in reliability, etc., and while discussing the results of the qualification vibration testing with their representative, Mr. Dick Lopez, it became increasingly obvious that a move is afoot to have the EPS electronics tested to an acceptance random vibration level without the isolators, etc. Mr. A. J. Farkas is aware of this move.

It is presumed that such a test would be run to the levels originally given, i.e. 20-80 Hz, +3 dB/oct.: 80-350 Hz, .04 g²/Hz: 350-2000 Hz, -3 dB/oct., a composite level of 6.3 g rms. However, the qualification unit would have to be qualified at a higher level $(.067g^2/\text{Hz})$ at 80-350 Hz) giving a composite level of 9.8 g rms.

To perform such a test would require the manufacture of an adapter for the vibration test fixture by BRN, and also a solid adapter to replace the isolators on the mounting straps, so that the electronics unit could be mounted to the fixture for testing.

Some problems associated with such a test are:

- 1) The qualification test level is higher than that seen by the electronics unit in response to the high energy level in the full-blown qualification test.
- 2) The eccentric loading on the mounting straps will be approximately 50% higher than they were designed for, hence their integrity should be investigated.
- 3) With the unit hard mounted to the fixture, the transmissibility of the interface will change, and the response
 of the electronics will be considerably higher compared
 to when it is mounted on isolators. Additionally the
 peak input will be at a much higher frequency than previously
 experienced.

4) From 3), it follows that the electronics components would experience random vibration levels well in excess of those they have experienced mounted on the isolators.

The above is written to provide some idea of the impact of such a test, should a request to comply with such a requirement be forthcoming.

D. L. Vincent

cc: B. E. Curtsinger

ELECTRON - PROTON SPECTROMETER

COMBINED PRESSURE & RANDOM YIBRATION

THE STRUCTURAL INTEGRITY OF THE EPS HARDWARE
HAS BEEN DEMONSTRATED BY THE QUALIFICATION TESTING.
VISUAL AND X-RAY EXAMINATION OF THE OUTER HOUSING AND
BASEPLATE SHOW NO CRACKING OR OTHER EVIDENCE OF
FAILURE.

PRIOR ANALYSIS OF THE BASEPLATE (D.G. PROBE, 10-18-72)

AND UPDATE OF THIS ANALYSIS (D.L. VINCENT, 1-14-72) INDICATED

THAT THE BASEPLATE WAS MARSINAL UNDER THE COMBINED

RANDOM VIBRATION AND PRESSURE CRITERIA. THESE ANALYSES

WERE BASED ON AN ADMITTEDLY CONSERVATIVE APPROACH (SEE)

P.15 OF D.G.PROBE'S ANALYSIS).

THE ANALYSIS CAN NOW BE UPDATED & REFINED, UTILIZING DATA FROM THE ACCELEROMETER MOUNTED ON THE CRITICAL AREA OF THE BASEPLATE. ADDITIONALLY, THE HIGHER THAN ANTICIPATED VISRATION RESPONSE ON THE BASEPLATE JUSTIFIES UTILIZING MORE OF THE SUB-PLATE IN THE CALCULATION OF THE SECTION PROPERTIES OF THE CRITICAL BEAM.

NOTEONED WEST FROM OUAL, TEST



CEITICAL BEALT CESPONSE = 450 g CM.S. FOR 108.4 g CM.S

PEACTICAL TEST DATA HAS SHOWN THAT THE PEAK & LOAD RELATIVE TO THE 9 PMS. LEVEL FOR A RESPONSE ACCELÉROMETER 15 1.6 x g C.M.S., AND THIS IS APPLICABLE TO THE RESPONSE WHEN THE INPUT IS CLIPPED AT A BSIGNA PEAK AS IS THE CASE FOR THE QUAL, TEST.

FROM THE IT FOLLOWS THAT PEAK & LEVEL FOR COITICAL BEAM = 1.6 & 456 = 793.63.

WT. OF BASEPLATE = .53 to

UNIT LOAD = . 53 1733. 5 = 7.500 LBS/SQ.IN. -- 10.5 a 3.25

PRESSURE FACTOR = 7.599 . 2.338 3.25

: IF THE BENDING MOMENT DUE TO PRESSURE IS MULTIPLIED BY 3.338, THIS JILL GIVE MOMENT DUE TO COMBINED VIBRATION AND PRESSURE.

MAX. MOMENT DUE TO PRESSURE ONLY = 92 ths-ins.

COMBINED MAX. BENDUG MOMENT = 92 x 3.338 = 307.1 lbs. iis.

THIS OCCURS AT SECTION 7 OF BEAM

3.047

(LENGTH OF BEAM = 9.17")

BEAM & PANEL SPACING.

THE EFFECTIVE WIDTH & OF THE PLATE IS NEEDED.

95

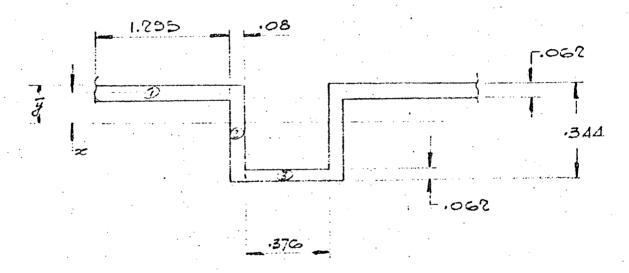
FROM ROARK, FORMULAE FOR STRESS & STRAIN, STHED, ARTICLE 37:

WHEN
$$\frac{1}{6} = \frac{9.17}{3.007} = 3.009 \approx 3.00$$

THEN b = .85, SO THAT TOTAL EFFECTIVE WIDTH OF

FLANGE = .85 x 3.047 = 7.59"

HENCE, SECTION 7:



5£C7.	AEFA A	y	Ay	Topas ars	.تح.	$A \propto^2$	INA.
/	.16058	1031	.004978	.090n51A	.060	·000578	.0006294
2	.05504	.172	.005467	.000542	.081	1000361	.0009030
3	.02331	.313	.007296	.0000075	.222	.001149	.00/1565
TOTAL	.23823		.021741	.0006007	i	.002088	.2026883

INA = .0006007 + .002088 = .0026889 INS

MAX. STRESS DUE TO COMBINED PEESSURE & VIBRATION:

$$f_b = \frac{307.1}{.01063} = 28,850 LB5/5Q.IN.$$



SO THAT :-

AND MARGIN OF SAFETY = +.21

AND MARGIN OF SAFETY = -. 03

MAX. STRESS DUE TO VIBRATION ONLY:-

$$f_6 = \frac{307.1 - 92}{.01063} = 20,235 LBS/SQ.IN.$$

SO THAT :-

M.S. ULT = +.38

THE ABOVE ANALYSIS STILL SHOWS A NEGATIVE MARGIN OF SAFET ON AN ULTIMATE LOAD CONDITION. HOWEVER, BY USING THE ACTUAL QUALITEST RESULTS IN THE AMALYSIS (WHICH REFLECT AN OVERTEST CONDITIONI) COMBINED WITH THE DIFFERENTIAL PRESSURE (WHICH IS AT 3.25 P.S.I FOR A VERY SHORT DURATION) COUPLED WITH THE INHERENT CONSERVATISM OF TREATING THE BEAM AS SIMPLY SUPPORTED, THE ABOVE MARGINS OF SAFETY ARE LOWER THAN EXIST IN PELETISE.

Vibration Test Report (Interim) on Solid State Radiation Inc's Lithium Ion Drift Detectors

Introduction:

Arrangements were made to subject the SSR detectors, of the type to be used in the EPS experiment, to several random vibration spectra representative of those given for the MDA and OWS in document MSC-01159, Rev. C, "Flight Hardware Environmental Design Requirements". Sample detectors were taken to Building 15, NASA/ MSC for testing on 12-2-70. The vibration spectra to be used were selected, in conjunction with Mr. A. Farkas (NASA/MSC), from It was intended that if the detecthe above mentioned document. tors survived these tests, the spectra would be increased in severity until a failure occurred, in an attempt to determine a maximum acceptable level of vibration.

Testing

The initial spectra selected are given in Appendix A. A diagram of a typical detector is shown in Figure 1. Two detectors, one of 2 mm size cube and the other of 3 mm (Nos. 021 and 076 respectively) were cemented with Eastman 910 adhesive to a test plate. from the header entered clearance holes in the plate. This plate was then mounted to the shake table so that the detectors would be vibrated in the X axis. The random vibration spectrum for Zone 11 on the MDA was then run. After examining the detectors, the test plate orientation was changed to the Y axis, and the test repeated. Again the detectors were examined, and then the orientation was changed to the Z axis and the test repeated. The results of this series of tests are recorded at the end of this report.

At this point in time, two more detectors were cemented to the test plate, again one 2 mm and one 3 mm (Nos. 022 and 048 respectively).

Difficulty was experienced in setting up the OWS spectrum on the test equipment. Finally, the cause of the difficulty was isolated to the cooling system for the equipment. This was apparently running hot, causing the system to overheat and cut out. No further testing could be undertaken that day (12-2-70).

The LEC engineer arrived at the test area at 9 A.M. on 12-3-70 to find that the test equipment was still out of commission. He left his phone number, so that he could be advised when the test could be recommenced.

Results

The results of the testing was as follows:

MDA Spectrum

Detector No.	021	076
"X" Axis	No visible damage	No visible damage
"Y" Axis	No visible damage	No visible damage
"Z" Axis	No visible damage	No visible

APPENDIX A

RANDOM VIBRATION SPECTRA (Extracted from MSC-01159, Rev. C)

MDA Spectrum

20 - 130 Hz @ 0.30
$$g^2/Hz$$

130 - 220 Hz @ -6dB/Oct.
220 - 800 Hz @ 0.10 g^2/Hz
800 - 1400 Hz @ -12dB/Oct.
1400 - 2000 Hz @ 0.010 g^2/Hz

Composite = 11.6 g.rms

(The above is the High Level Random criteria for the MDA Cylinder Skin - General Specification - Subzone 11-2).

OWS Spectrum

Composite = 29.1 g.rms

(The above is the Lift-off Random Vibration criteria for the OWS LH₂ Cylinder Tank Section, Stations 2970 to 3100, General Specification - Subzone 4-3.)

NOTE: The above criteria were selected, lacking any additional information, as representing the severest vibration in their respective areas. No information was available regarding Zone 1 on the OWS.

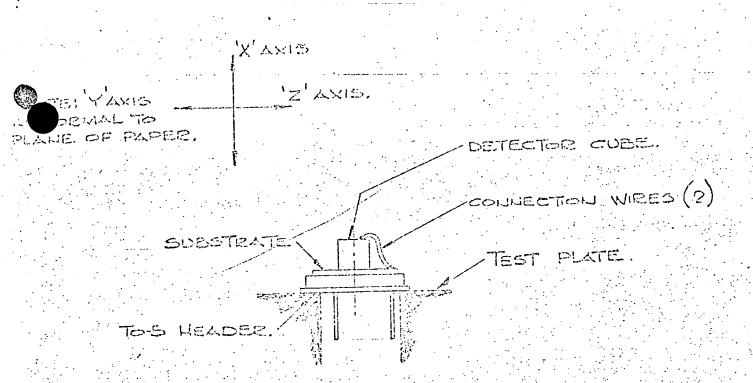


FIG. 1. DIAGRAM OF DETECTOR,

REPORT ON ACTION ITEMS (Memo, B. C. Hall to D. L. Vincent, 12-1-70)

This report contains the response to actions items 1 and 2 contained in the above memo.

Item 1

A comparison of the various environmental requirements imposed on the EPS by reason of being mounted on the Skylab Multiple Docking Adapter (MDA) or the Orbital Workshop (OWS) zone 1 was made, together with those presumed to be imposed at the Preliminary Requirements Review (Nov. 6, 1970).

The results of this comparison are tabulated below:

Environment Review (1) MDA Comparison (2 one 1) Temperature (°F) -60 to +195 -180 to +277 -200 to +300 Pressure-Launch & Ascent (mm.Hz) Orbit 10-8 (2)				
Pressure-Launch & Ascent (mm.Hz) 10-8 1086 to 10-8 (2) 10-8 760 to 10-8 (2) 10-8 Humidity (%RH) 0 to 45% 0 to 100% Acceleration 4.7g flt. axis 2.0g lateral 4.7g flt. axis 2.0g lateral Vibration (3) (3) (3) Shock ED-2002-1032 SM-56669 Meteoroid Notes IDENTICAL Radiation Light Atmospheric Comp. Air Movement (5) (5) Acoustic Noise (5) (5)	Environment	Requirements	MDA	- · · · · · · · · · · · · · · · · · · ·
(mm.Hz) Orbit 10-8 10-8 Humidity (%RH) 0 to 45% 0 to 100% Acceleration 4.7g flt. axis 2.0g lateral 2.0g lateral Vibration (3) (3) (3) Shock (4) N/A E.M.I ED-2002-1032 SM-56669 Meteoroid Notes IDENTICAL Radiation Light Atmospheric Comp. Air Movement (5) (5) Acoustic Noise (5) (5)	Temperature (°F)	-60 to +195	-180 to +277	a de la companion de la compan
Acceleration 4.7g flt. axis 2.0g lateral 2.0g lateral Vibration (3) (3) (3) (3) Shock (4) N/A E.M.I ED-2002-1032 SM-56669 Meteoroid Notes IDENTICAL Radiation Inght Atmospheric Comp. Air Movement Acoustic Noise (5) (5)	4		1086 to 10 ⁻⁸ (2)	760 to 10 ⁻⁸ (2)
2.0g lateral 2.0g	Humidity (%RH)		0 to 45%	0 to 100%
Shock (4) N/A E.M.I ED-2002-1032 SM-56669 Meteoroid Notes IDENTICAL Radiation Light Atmospheric Comp. Air Movement Acoustic Noise (5) (5)	Acceleration			4.7g flt. axis 2.0g lateral
E.M.I ED-2002-1032 SM-56669 Meteoroid Notes IDENTICAL Radiation Light Atmospheric Comp. Air Movement Acoustic Noise (5) (5)	Vibration	(3)	(3)	(3)
Meteoroid Notes IDENTICAL Radiation Light Atmospheric Comp. Air Movement Acoustic Noise (5) (5)	Shock		(4)	N/A
Radiation Light Atmospheric Comp. Air Movement Acoustic Noise (5) (5)	E.M.I		ED-2002-1032	SM-56669
Acoustic Noise —— (5) (5)	Meteoroid Notes		IDENTI	CAL
Acoustic Noise (5) (5)	Light Atmospheric Comp.		IDENTI	
Contaminants OVERBOARD DUMP MATERIAL			(5)	(5)
	Contaminants		OVERBOARD DUMP	MATERIAL

Notes:

- 1. Environmental acceptance test ground rules (Enclosure 2).
- 2. In 7 mins. max. decompression rate = 6 psi/min.
- 3. See Appendix "A".
- 4. See Appendix "B".
- 5. See Appendix "C".

It can be seen that the temperature limits on the OWS are slightly wider than for the MDA, but it is not felt that these are enough to make a significant difference.

During the launch and ascent stage, the pressure environment is initially lower on the OWS than the MDA - 1 atmosphere as opposed to 1.4 atmospheres. The OWS will see the full range of relative humidity, whereas the MDA only reaches 45% R.H.

For vibration, there is a significant difference. The OWS will give appreciably higher levels of vibration than the MDA, approximately three times the magnitude, and this may well be more severe than we can design for within the maximum allocated weight. There appears to be no significant difference between the two locations regarding acoustic noise.

At this moment, we have no information available on either of the E.M.I. documents to determine if there is any significant difference in their requirements.

Acceleration, meteoroid notes, radiation, light, atmospheric composition, air movement and contaminants criteria are the same for both MDA and OWS.

To sum up, the present design of the EPS would conform to all the environmental requirements with the exception of vibration and possibly shock. Assuming the vibration in zone 1 to be at least as severe as zone 4-3, then it is considered that it would be extremely difficult to design to meet this level of vibration within the present maximum weight allocation.

Item 2

The EPS is being presently designed to the temperature, pressure, acceleration and vibration requirements for mounting on the MDA. The vibration levels used are those for zone 11-2, being the most severe conditions.

For shock we are designing to a 20g shock for total of 11 mseconds duration.

An attempt is being made to determine the maximum vibration level that the SSR detectors can stand, and a test report on the testing conducted to date is included. This testing is incomplete, but it is anticipated that it will recommence at 10 A.M. on 12-7-70. It is not anticipated that there will be any failure of the detectors, however, as their mass is extremely small. They would therefore require extremely high g levels to cause a bond failure or failure of the connection wires.

SSR have tested slightly larger detectors up to 100g. at 2000 Hz. They agree that the normal failure mode would be for the detector cube bond to the substrate to fail.

D. L. Vincent

Appendix "A" Vibration Criteria

PRR

20	- ·	80	Ηz	9	+3dB/Oct.	Acc	ceptance	levels
30	-	350	Ηz	@	0.04g ² /Hz	· 1 n	min/axis	min.
350		2000	Ηz	9	-3dB/Oct.	5 n	min/axis	max.

(This random vibration spectrum is the only vibration criteria given in the PRR.)

MDA

Several spectra are given for different zones of the MDA. If we consider random vibration as probably being more severe that the sinusoidal inputs, the worst spectrum appears to be at zone 11-2, MDA Cylinder Skin, High Level Random Criteria.

			_					
2.0	_	130	$g^2/$	Ή:	z			
					-6dB/Oct.			
220	_	800	Hz	<u>a</u>	$0.10 \text{ g}^2/\text{Hz}$	• 1	min/axis	
					-12dB/Oct.			
1400		2000	Ηz	a	0.010g ² /Hz.			

Composite 116. g.r.m.s.

OWS

No vibration data for zone 1 on the OWS were available in MSC-01159 Rev. c, but comparison of the levels given for zone 4 shows that it can be expected that the levels could be as much as three time higher than for the most severe MDA environment.

Appendix "B" Shock Criteria

OWS

According to MSC-01159, Rev. C, shock requirements are not applicable to the OWS, with the exception of the normal MIL-STD-461 and 462 for transportation, storage and handling requirements.

MDA

As can be seen from the criteria below, the shock will vary depending upon the location of the EPS in relation to the docking post ring, reducing in severity as the distance from the ring increases.

Distance from Nearest Docking Port Ring in Inches	Shock	Spectru	ım	
0 - 12"	20 - 1600 -	1600 5000 10000	Hz 6 Hz 6 Hz 6	5.0 G's peak +9 dB/oct 3000 G's peak -4 dB/oct 1900 G's peak
13 - 49"	20 - 1600 -	1600 5000 10000	Hz (Hz (Hz (Hz (Hz (Hz (Hz (Hz (Hz (Hz (9 5.0 G's peak 9 8 dB/oct 9 1500 G's peak 9 4 dB/oct 9 950 G's peak
50 - 190"	20 - 1600 -	1600 5000 10000	Hz (Hz (Hz (Hz (Hz (Hz (Hz (Hz (Hz (Hz (9 5.0 G's peak 9 +6 dB/oct 9 380 G's peak 9 -4 dB/oct 9 240 G's peak
Greater than 190"	20 - 1600 -	1600 5000 10000	Hz (Hz (Hz (5.0 G's peak 4 dB/oct 90 G's peak 4 -4 dB/oct 57 G's peak

Present Contractual Design Criteria

MIL-STD 810B Method III, 20G for 11 msec duration.

Appendix "C" Acoustic Noise Criteria

MDA

				•
Geometric	Mean			Boundary
Frequency	(Hz)	Lift-Off		Layer
5.0		110.0	•	110.0
6.3		111.5		112.0
8.0		113.0		113.5
10.0		115.0		115.0
12.5		117.0		116.5
16.0		118.5		118.5
20.0		121.0	•	120.0
25.0		123.0		123.0
31.5		124.5	•	125.5
40.0		127.0		127.0
50.0		128.5	•	128.5
63.0	•	131.0		130.0
80.0	·	133.0		131.0
100.0		133.0		131.5
125.0		133.0		132.0
160.0		132.0		132.0
200.0		131.0		131.5
250.0		130.5		131.0
315.0		129.5		129.0
400.0		128.5		128.0
500.0		127.5		127.0
630.0		126.5	•	126.0
800.0		125.0		124.0
1,000.0	•	124.0		123.0
1,250.0		123.0	•	122.0
1,600.0		121.5		121.0
2,000.0		120.0		120.0
2,500.0		119.0		119.0
3,150.0		117.0		116.5
4,000.0		116.0		113.0
5,000.0		113.0		109.5
6,300.0		110.0	•	106.0
8,000.0	·	109.0		103.0
_ 10, 000.0		107.0		100.0
Overall SP	L ·	142.5		141.5
Duration		30.0		120.0
-				-

OWS

1

S

Geometric Mean		Boundary
Frequency (Hz)	Lift-Off	Layer
5.0	124.0	128.5
6.3	126.0	129.0
8.0	128.0	130.0
10.0	130.0	130.5
12.5	132.0	131.0
16.0	134.0	132.0
20.0	136.0	132.5
25.0	138.0	133.0
31.5	140.0	134.0
40.0	142.0	134.5
50.0	143.5	135.0
63.0	144.5	136.0
80.0	145.0	136.5
100.0	145.0	137.0
105 0	145.0	138.0
160.0	145.0	138.5
200.0	144.5	139.5
250.0	144.0	140.0
315.0	143.5	140.5
400.0	143.0	141.0
500.0	142.0	141.5
630.0	141.5	142.0
800.0	140.5	142.5
1,000.0	140.0	142.0
1,250.0	139.0	141.0
1,600.0	138.0	140.5
2,000.0	136.5	139.5
2,500.0	135.5	138.5
3,150.0	134.0	138.0
4,000.0	132.0	137.0
5,000.0	130.5	136.0
6,300.0	129.0	135.0
8,000.0	127.5	134.0
10,000.0	126.0	133.0
Overall SPL	156.0	153.5
Duration (Sec)	30.0	120.0

3.2.1.1.4 Electrical

The following are documents applicable to the assessment of the electrical requirements of the EPS.

the electrical requirements	
Subject Title	Page
EPS Pulse Amplifier Specification (EPS-3)	111
Study of the EPS Preamplifier-Amplifier Time Response when Excited by a Rectangular Pulse of Varying Width and Constant Area (EPS-140)	115
EPS Post-Amplifier Time Constant and Gain Cal- culations (EPS-138)	122
EPS Heater Circuit	127
Analog Section Specifications	128
Unipolar and Bipolar Pulse Shaping Techniques: An Evaluation (EPS-65)	131
Pole-Zero Cancellation at the Output of the Charge Sensitive Preamplifier (EPS-70)	71
Selection of Time Constants for Accelerator Testing (EPS-199)	138
Summary of Power System Performance During the EPS Engineering Test Unit Thermal- Vacuum Testing (EPS-376)	139
Power Dissipation in Data Processor Modules (EPS-198)	144

Subject Title	Page
Parts List Changes for the Dual Differential	145
Pulse Height Discriminator (EPS-197)	
Part Value Changes for R2, R5(7), R5(9), R7(8), R7(9), R7(10), R8(7), R8(9), R10(8), R10(9), R10(10) and R13 of the Dual Differential Pulse Height Discriminator (EPS-90)	146
Experimental Verification of EPS Analog Design Before Manufacturing Release (EPS-85)	147
Selection of EPS Post-Amplifier Time Constants (EPS-89)	149
Selection of EPS Post-Amplifier Time Constants (EPS-86)	150
EPS Amplifier: An Analysis of the Filter Configuration and the Optimization of Signal Shapes (EPS-103)	156
EPS Housekeeping Specification (EPS-40)	174

EPS PULSE AMPLIFIER SPECIFICATIONS

- 1. Preamplifier
 - A. Charge Gain: $29.6 \pm 0.15 \frac{\text{mv}}{\text{meV}}$
 - B. Gain Stability
 - 1. Temperature Stability: 0.02%/°C
 - Stability as a function of supply voltage variation: <0.5% for + 1.5 volt change in either or both power supplies.
 - C. Resolution (measured using a TC 202 at 0.53 µsec, bipolar):

D. Output Rise Time

- E. Output Decay Time Constant: $150.0 \pm 1.6 \mu sec$
- F. Integral Nonlinearity: 0.07% $\frac{(\Delta V_i) \text{ max}}{V_{\text{max}}} = INL$
- G. Detector Bias Polarity and Range: 0 to +500 VDC
- H. Test Input
 - 1. Resistance: $49.9 + 0.5\Omega$
 - 2. Capacitance: $1.0 \pm 0.1 pf$
- I. Permissable Load: 4990

II. Pulse Amplifier

- A. Pulse Gain: 41.6 + 2
- B. Gain Stability
 - 1. Temperature Stability: 0.01%/°C
 - 2. Stability as a function of supply voltage variation.
- C. Linear Range: 0 to +5.0 VDC
- D. Integral Nonlinearity: 0.07%
- E. Input Polarity: Positive
- F. Output Polarity: Positive
- G. Preamplifier-Amplifier Calibration: +5V = 10 mev
- H. Pulse Shaping Time Constant: 150 nsec 500 nsec
- I. Pole-Zero Cancellation: Adjustable from 50 µsec to 100 µsec.
- J. Overload Recovery: Recovers from X10 overload in ≤2 NON overloaded pulse widths.
- K. Output Noise: ≤1.0 mv (FWHM) for no input (21.7 μvolts referred to input).
- L. Average Baseline Shift with Counting Rage: < -SMV
- M. Baseline Stability
 - 1. Quiescent Value: 0.0 + 5.0 mv
 - 2. Temperature Stability: 50 uv/°C
- N. Output Coupling: Direct
- O. Permissable Load: 1 ΚΩ
- P. Power Consumption: @ +8 VDC @ -8 VDC

EPS PULSE AMPLIFIER SPECIFICATIONS.

Movember 4, 1970

Lage 3

III. Dual Pulse Height Distriminator

- A. Input Signal Pulse Height Range: 0 to +5 VDC
- B. Input Impedance: $\approx 4 \text{ K}\Omega$
- C. Input Coupling: Direct
- D. Pulse Pair Time Resolution: <100 nsec
- E. Stability of Discriminator Level
 - 1. Temperature Stability: <0.01%/°C
 - 2. Stability as a function of supply voltage variation.
- F. Output Logic Signal Shape
 - 1. Width: Variable
 - 2. Height and Polarity: +2.4 V to 0.8 V
 - 3. Drive Capability: 10 TTL Loads
- G. Power Consumption: @ +5 VDC.
 - @ -5 VDC
 - @ -8 VDC

IV. Prescaler

- A. Scale Factor: 4
 - B. Coupling: Direct
 - C. Drive Requirements:
 - 1. Logic "1" Minimum: +2.4V @ +50 μamp
 - 2. Logic "0" Maximum: +0.6V @ -2.0 Mamp
 - D. Minimum Toggle Frequency: 25 MHz

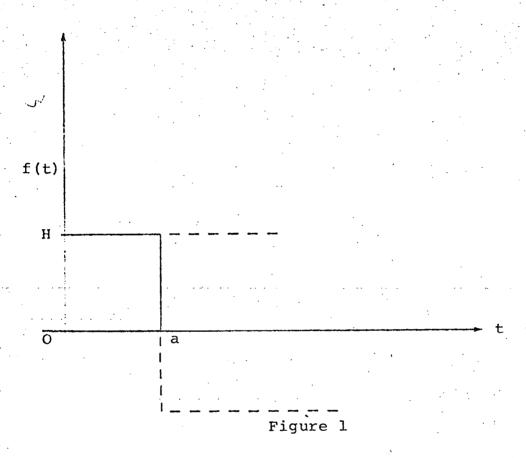
EPS PULSE AMPLIFIER SPECIFICATIONS November 4, 1970 lage 4

- E. Output
 - 1. Logic "1" Minimum: +2.4V @ 1.0 Mamp
 - 2. Logic "0" Maximum: +0.4V @ 2.0 Mamp
 - 3. Rise Time Constant/Fall Time Constant: 160 nsec
 - F. Power Consumption: 52 Mamp @ +5 VDC

STUDY OF THE EPS PREAMPLIFIER-AMPLIFIER
TIME RESPONSE WHEN EXCITED BY A RECTANGULAR
PULSE OF VARYING WIDTH AND CONSTANT AREA

EPS-140

W. A. Oliveira



f(t) can be represented as a combination of step functions:

$$f(t) = H[u(t) - u(t - a)]$$

The objective then is to obtain the output response of the preamplifier-amplifier system when f(t) as given by (1) is applied to the preamplifier input.

It is hoped that this function would represent the output current of a semiconductor nuclear particle detector, allowing for the different charge collection times which are a function of the detector thickness and reverse bias voltage.

The output response can be obtained with the aid of the system's impulse response, which has already been derived and presented in a previous report, EPS-103. This function is given by:

$$h(t) = \frac{K}{2} e^{-t/T} (t^2 - \frac{1}{3\tau} t^3)$$
 (2)

With the knowledge of f(t) and h(t), at least two different approaches can be used to derive the system's output response to f(t); 1) by using the convolution integral with f(t) and h(t) and 2) by using Laplace Transform techniques.

Just as an excercise and also as a check of the final result, let us derive the system's output response by using approach 1 and then approach 2.

Approach 1: Convolution Integral

In the field of linear systems analysis, there is a very useful theorem which states that the response of a system to a function f(t) is equal to the convolution of f(t) with the system's impulse response h(t). Thus, let y(t) be the desired response. The convolution integral is given by:

$$y(t) = \int_0^\infty f(t - \lambda) \times h(\lambda) d\lambda$$
 (3)

where λ is the new integrating variable.

Recalling expression (1) and substituting the variable t by $t-\lambda$ yields:

$$f(t - \lambda) = HU (t - \lambda) - HU [t - \lambda - a]$$
 (4)

Recalling expression (2) and substituting t by λ yields:

$$h(\lambda) = \frac{K}{2} e^{-\lambda/\tau} (\lambda^2 - \frac{1}{3\tau} \lambda^3)$$
 (5)

Substituting (4) and (5) into (3) yields:

$$y(t) = \int_0^t [HU(t-\lambda) - HU(t-\lambda - a] \times \frac{K}{2} e^{-\lambda/\tau} (\lambda^2 - \frac{1}{3\tau} \lambda^3) d\lambda$$
 (6)

by multiplying the integrand and observing the limits of integration, one has:

$$y(t) = \frac{K \times H}{2} \int_{0}^{t} U(t - \lambda) e^{-\lambda/T} (\lambda^{2} - \frac{1}{3\tau} \lambda^{3}) d\lambda$$

$$-\frac{K \times H}{2} \int_{0}^{t-a} U(t - \lambda - a) e^{-\lambda/\tau} (\lambda^{2} - \frac{1}{3\tau} \lambda^{3}) d\lambda$$
(7)

$$y(t) = \frac{KxH}{2} \left[\int_{0}^{t} U(t-\lambda) \lambda^{2} e^{-\lambda/\tau} d\lambda - \frac{1}{3\tau} \int_{0}^{t} U(t-\lambda) \lambda^{3} e^{-\lambda/\tau} d\lambda \right]$$

$$- \int_{0}^{ta} U(t-\lambda-a) \lambda^{2} e^{-\lambda/\tau} d\lambda + \frac{1}{3\tau} \int_{0}^{t-a} U(t-\lambda-a) \lambda^{3} e^{-\lambda/\tau} d\lambda$$
(8)

The integrals can be evaluated by making use of the following formulation:

$$\int \chi^{m} e^{a\chi} d\chi = \frac{\chi^{m} e^{a\chi}}{a} - \frac{m}{a} \int \chi^{m-1} e^{a\chi} d\chi$$
 (9)

from which one derives:

$$\int \chi e^{a\chi} d\chi = \frac{e^{a\chi}}{a^2} (a\chi - 1)$$
 (10)

The first term in expression (8) becomes:

$$\int_{0}^{t} U(t-\lambda) \lambda^{2} e^{-\lambda/\tau} d\lambda = \frac{\lambda^{2} e^{-\lambda/\tau}}{-\frac{1}{\tau}} \Big|_{0}^{t} - \frac{2}{(-\frac{1}{\tau})} \int_{0}^{t} \lambda e^{-\lambda/\tau} d\lambda$$

$$= \left[-\tau \lambda^{2} e^{-\frac{1}{\tau}\lambda} - 2\tau^{3} e^{-\frac{1}{\tau}\lambda} \right]_{0}^{t}$$
(11)

The second term of (8) yields:

$$-\frac{1}{3\tau} \int_{0}^{t} U(t-\lambda) \lambda^{3} e^{-\frac{1}{\tau}\lambda} d\lambda = -\frac{1}{3\tau} \left[\frac{\lambda^{3} e^{-\frac{1}{\tau}\lambda}}{(-\frac{1}{\tau})} \Big|_{0}^{t} - \frac{3}{(-\frac{1}{\tau})} \int_{0}^{t} \lambda^{2} e^{-\frac{1}{\tau}\lambda} d\lambda \right]$$

$$= -\frac{1}{3\tau} \left[-\tau \lambda^{3} e^{-\frac{1}{\tau}\lambda} + 3\tau (-\tau \lambda^{2} e^{-\frac{1}{\tau}\lambda} - 2\tau^{2} \lambda e^{-\frac{1}{\tau}\lambda} - 2\tau^{3} e^{-\frac{1}{\tau}\lambda} \right]_{0}^{t}$$

$$= \frac{1}{3}\lambda^{3} e^{-\frac{1}{\tau}\lambda} + \tau \lambda^{2} e^{-\frac{1}{\tau}\lambda} + 2\tau^{2} \lambda e^{-\frac{1}{\tau}\lambda} + 2\tau^{3} e^{-\frac{1}{\tau}\lambda} \Big|_{0}^{t}$$
(12)

By analogy with expressions (11) and (12) the third and fourth terms of expression (8) become:

$$-\int_{0}^{t-a} u(t - \lambda - a)^{2} e^{-\frac{1}{\tau}\lambda} d\lambda = \left[(\lambda^{2} + 2\tau\lambda + 2\tau^{2})\tau e^{-\frac{1}{\tau}\lambda} \right]_{0}^{(t-a)}$$
(13)

$$+\frac{1}{3\tau}\int_{0}^{t-a} U(t-\lambda-a) \lambda^{3}e^{-\frac{1}{\tau}\lambda}d\lambda$$
 (14)

$$= (-1) \left[\left(\frac{1}{3} \lambda^3 + \tau \lambda^2 + 2\tau^2 \lambda + 2\tau^3 \right) e^{-\frac{1}{\tau} \lambda} \right]_0^{(t-a)}$$

By grouping (11), (12, (13) and (14), one has:

$$y(t) = \frac{K}{2}H \left\{ \left[-(\lambda^2 + 2\tau\lambda + 2\tau^2)\tau + \frac{1}{3}\lambda^3 + \tau\lambda^2 + 2\tau^2\lambda + 2\tau^3 \right] e^{-\frac{1}{\tau}\lambda} \right\}_0^{\tau}$$

$$+ \left[(\lambda^{2} + 2\tau\lambda + 2\tau^{2})\tau - \frac{1}{3}\lambda^{3} - \tau\lambda^{2} - 2\tau^{2}\lambda - 2\tau^{3} \right] e^{\frac{1}{\tau}\lambda} \Big|_{0}^{t-a}$$

or:

$$y(t) = \frac{K \cdot H}{2} \left[\frac{1}{3} \lambda^3 e^{-\frac{1}{\tau} \lambda} \Big|_0^t - \frac{1}{3} \lambda^3 e^{-\frac{1}{\tau} \lambda} \Big|_0^{t-a} \right]$$

$$y(t) = \frac{K \cdot H}{2} \left[\frac{1}{3} t^3 e^{-\frac{1}{\tau}t} - \frac{1}{3} (t - a)^3 e^{-\frac{1}{\tau}(t - a)} \right]$$

$$y(t) = \frac{K \cdot H}{3 \times 2} \left[t^3 e^{-\frac{1}{\tau}t} - (t - a)^3 e^{-\frac{1}{\tau}t} \times e^{a/\tau} \right]$$

$$y(t) = \frac{K.H}{3 \times 2} e^{-\frac{1}{\tau}t} \left[t^3 - (t - a)^3 e^{a/\tau} \right]$$
 (15)

Thus expression (15) represents the response of the EPS preamplifier-amplifier system to an input signal function as shown in Figure 1.

Since the input signal is supposed to maintain its area invariant as the width \underline{a} is made to change, expression (15) can be modified to account for this condition:

$$y(t) = \frac{K \times A}{6a} e^{-\frac{1}{\tau}t} \left[t^3 - (t - a)^3 e^{a/\tau}\right]$$
 (16)

where A is the area under the pulse.

Approach 2: Laplace Transform

Let us now try to arrive at expression (16) by using Laplace Transform methods. The Laplace transform of Expression (1) is given by:

$$F(s) = H \times \left[\frac{1}{s} - \frac{e^{-as}}{s}\right]$$
 (17)

and for the system's impulse response one has:

$$H(s) = K \times \frac{s}{(s + \frac{1}{\tau})^4}$$
 (18)

Thus the response of the system to F(s) will be:

$$Y(s) = F(s) \times H(s)$$
 (19)

and by substitution:

$$y(s) = H\left(\frac{1 - e^{-as}}{s}\right) \times K \frac{s}{(s + \frac{1}{\tau})^4}$$

or

$$y(s) = K \times H \left[\frac{1}{(s + \frac{1}{\tau})^4} - \frac{e^{-as}}{(s + \frac{1}{\tau})^4} \right]$$
 (20)

Taking the inverse Laplace of both terms in (20), yields:

$$y(t) = K \times H \left[\frac{1}{3!} \times t^3 e^{-\frac{1}{\tau}t} - \frac{1}{3!} (t - a)^3 e^{-\frac{1}{\tau}(t-a)} \right]$$

and by rearranging terms:

$$y(t) = \frac{K \times H}{3!} \times e^{-\frac{1}{\tau}t} \left[t^3 - (t - a)^3 e^{a/\tau} \right]$$

and again making the substitution H $\frac{\lambda}{a}$ gives:

$$y(t) = \frac{K \times A}{3! \times a} e^{-\frac{1}{\tau}t} \left[t^3 - (t - a)^3 e^{a/\tau}\right]$$
 (21)

Comparison between expressions (16) and (21) shows that both approaches yielded the same result.

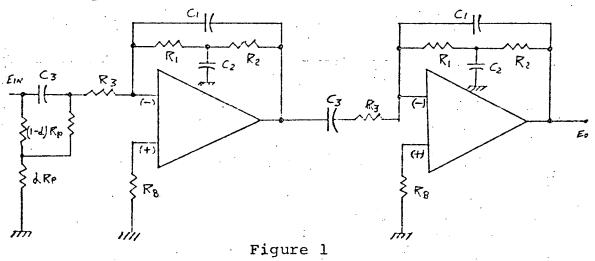
EPS POST AMPLIFIER TIME CONSTANT AND GAIN CALCULATIONS EPS-138

The impulse response of the preamplifier-amplifier system has been calculated and presented in a previous report, #EPS-103.

The expression representing the impulse response is given by:

$$h(t) = \frac{Q}{C_f} \times \frac{1}{R_3^2 \times C_1^2} \times \frac{1}{2} \times e^{-t/\tau} (t^2 - \frac{1}{3\tau} t^3)$$
 (1)

where the parameter values are defined in Figure 1 below.



The common time-constant for both stages is given by:

$$\tau = \sqrt{R_1 R_2 C_1 C_2} \tag{2}$$

In order to have the impulse response of the system in the form of expression (1), certain relationships have to hold, as detailed in Report # EPS-103. One of these relations is that:

$$R_3 \times C_3 = \frac{R_1 \times R_2}{R_1 + R_2} \times C_2$$
 (3)

Another useful information from the same report is that the system's impulse response as given by expression (1) achieves its first maximum for a value of time given by:

$$t_{(peak)} = 1.27 \times \tau \tag{4}$$

Thus this maximum of h(t) can be obtained by substituting (4) into (1):

$$h(t)_{\text{max}} = \frac{Q}{C_F} \times \frac{1}{R_3^2 C_1^2} \times \frac{1}{2} \times 1^{-1.27\tau/t}$$

$$[(1.27\tau)^2 - \frac{1}{3x\tau} (1.27\tau)^3]$$

or:

$$h(t)_{max} = \frac{Q}{C_f} \times \frac{1}{R_3^2 C_1^2} \times \frac{1}{2} \times 1^{-1.27} \times (1.27)^2 \tau^2 \left[1 - \frac{1.27}{3}\right]$$

or:

$$h(t)_{max} = \frac{Q}{C_f} \times \frac{1}{R_3^2 C_1^2} \times .1306 \tau^2$$

(5)

In Expression (5) $\frac{Q}{C_f}$ is the peak amplitude of the signal coming from the preamplifier. Thus, by rearranging expression (5), the peak gain of the post amplifier becomes:

$$\frac{h(t)_{max}}{Q/C_f} = \frac{.1306}{R_3^2 C_1^2} \times \tau^2$$

or:

$$A_{\text{Vpeak}} = \frac{.1306}{R_3^2 C_1^2} \times \tau^2$$
 (6)

Another relationship which will be used here is also previously derived in Report #EPS-103, and is given by:

$$R_2 = \frac{R_1 \times \tau}{2R_1C_2 - \tau}$$
 (7)

In order to arrive at numerical values for the six time constant determining parameters, R_1 , R_2 , R_3 , C_1 , C_2 and C_3 , one has available equations (2), (3), (6) and (7). This situation enables one to conveniently choose any two values among the original six and then solve the available expressions for the remaining four parameters.

At this point it is in order to present some clarifications about the conditions that lead to the pulse gain-time constant calculation results.

Firstly, the form of expression (1) is only valid if certain constraints are imposed on the networks of both active filter stages. These constraints are:

- 1. The poles of the input and feedback networks transadmittances must coincide, and thus cancel each other. This condition gives rise to expression (3).
- 2. The zeros of the feedback networks transadmittances for both filters must be real and coincide with each other (multiple poles in the transfer function).

3. The input network of the first filter stage must have a zero in its transfer function that coincides with the pole of the signal function at the input (preamplifier output).

Secondly, these same conditions guarantee that the damping factor of the output response be equal to one, and as a consequence no crossing of the baseline at the output of the first stage should occur, and only one crossing at the output of the second stage. In both cases, one achieves the fastest return to the baseline.

Let us now elaborate a little more on equations (2), (3), (6) and (7) in order to explicitly show the solutions for the parameters we are interested in finding numerical values.

From (6), solving for R_3 one has:

$$R_3 = \sqrt{\frac{.1306}{A_V} \times \frac{\tau}{C_1}}$$
 (8)

From (2), solving for R_1 yields:

$$R_1 = \frac{\tau^2}{R_2 C_1 C_2} \tag{9}$$

And by substituting the value of R_1 as given by (9) into equation (7) results:

$$R_2^2 - \frac{2\tau}{C_1} R_2 = \frac{\tau^2}{C_1 C_2} = 0$$
 (10)

The solutions to equation (10) are:

$$R_2 = \frac{\tau}{C_1} + \sqrt{\frac{\tau^2}{C_1^2} - \frac{\tau^2}{C_1 C_2}}$$

$$R_2 = \frac{\tau}{C_1} \left(1 + \sqrt{1 - \frac{C_1}{C_2}} \right) \tag{11}$$

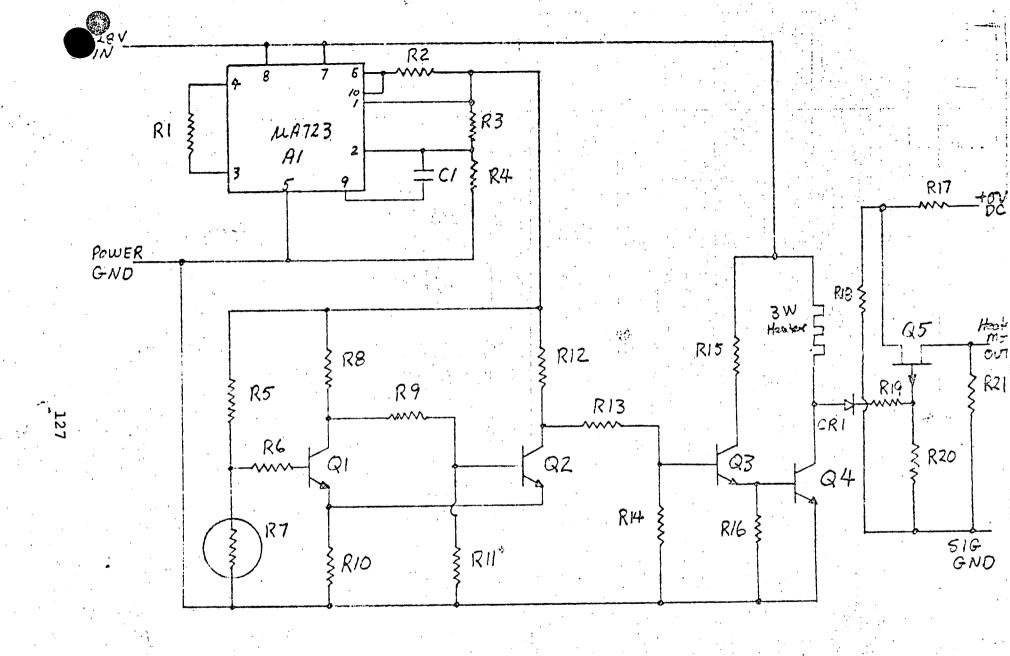
Expression (11) tells us a few things: for C_2 greater than C_1 there will be two distinct values of R_2 (and consequently R_1) that will satisfy all the requirements. For C_2 equal to C_1 , R_2 will be single valued:

$$R_2 = R_1 = \tau/C_1$$
 (12)

For C_2 smaller than C_1 , then no real value for R_2 (and R_1) will exist that will satisfy the requirements. This means that R_2 (and R_1) would have to be impedances with both real and imaginary parts. Of course, this third condition is of no practical value for the sake of network simplicity.

Expression (3) can now be solved for C_3 :

$$c_3 = \frac{R_1 \times R_2}{R_1 + R_2} \times c_2 \times \frac{1}{R_3}$$
 (13)



EPS Heater Circuit

BEC 2/17/71

ANALOG SECTION SPECIFICATIONS

- I. Preamplifier
- A. Charge Gain: $12.0 \pm 0.25 \frac{MV}{MeV}$
 - 1. Temperature Stability: 0.02%/°C
 - 2. Stability as a function of supply voltage variation
- C. Resolution (Measured using a TC202 at 0.5 usec):

Input Capacitance (pf)

	0					
Resolution	_<10keV	<10keV	<10keV	<u><</u> 10keV	<10keV	<10keV

D. Output Rise Time:

Input Capacitance

	input Capacitance					
					40	
Rise Time	<50NSec	<50NSec	<50NSec	<50NSec	<50NSec	<50NSec

- E. Output Delay Time Constant: 80.0 ± 1.6 μSec
- F. Integral Nonlinearity = $\leq 0.07\%$ $\frac{(\Delta V_i) \max}{V \max} = INL$
- G. Detector Bias Polarity and Range: 0 to +500 Vdc
- H. Test Input
 - 1. Resistance: $49.9 \pm 0.5\Omega$
 - 2. Capacitance: 2.2 ± .05pf
 - I. Permissible Load: 499Ω
- II. Pulse Amplifier
 - A. Pulse Gain: 41.6 ±2

- B. Gain Stability
 - 1. Temperature Stability: 0.01%/°C
 - 2. Stability as a function of Supply Voltage Var.
- C. Linear Range: 0 to +5.0 Vdc
- D. Integral Nonlinearity: < 0.07%.
- E. Input Polarity: Positive
- F. Output Polarity: Positive
- G. Preamplifier Amplifier Calibration: +5V = 10 MeV
- H. Pulse Shaping: 150nsec 500 nsec
- I. Pole-Zero Cancellation: Adjustable from 50 μsec to 100 μsec
- J. Overload Recovery: Recovers from X2 overload in < 2 non overloaded pulse widths
- K. Output Noise: < 1.0 mV for no input</p>
- L. Average Baseline Shift with Counting Rate
- M. Baseline Stability
 - 1. Quiescent Value: $0.0 \pm 5.0 \text{ mV}$
 - 2. Temperature Stability: 50 $\mu v/^{\circ}C$
- N. Output Coupling: Direct
 - O. Permissible Load: $1K\Omega$
 - P. Power Consumption: @ +8Vdc
 - @ -8Vdc

- III. Dual Pulse Height Discriminator
 - A. Input Signal Pulse Height Range: 0 to +5 Vdc
 - B. Input Impedance: \sim 4K Ω
 - C. Input Coupling: Direct
 - D. Pulse Pair Time Resolution: < 100 nsec
 - E. Stability of Discriminator Level
 - 1. Temperature Stability: < 0.01%/°C
 - 2. Stability as a function of Supply Voltage Variations
 - F. Output Logic Signal Shape
 - 1. Width: Variable
 - 2. Height and Polarity: +2.4V to 0.8V
 - 3. Drive Capability: 10 TTL Loads
 - G. Power Consumption @ +5Vdc
 - @ -5Vdc
 - @ -8Vdc

- IV. Prescaler
 - A. Scale Factor: 4
 - B. Coupling: Direct
 - C. Drive Requirements
 - 1. Logic "1": +2.4Vdc
 - 2. Logic "0":

B. C. Hall

DEPT./ 673-10 BLDO./Beta PLANT/HASD DATE 12-15-70 Ref: EPS-65

R. W. O'Neill

DEPT. 673-10 BLDG. Beta PLANT/HASD EXT. 481

SUBJECT. Unipolar and Bipolar Pulse Shaping Techniques: An Evaluation

An evaluation of bipolar and unipolar pulse shaping techniques, with emphasis on application in the EPS, was made. The advantages and disadvantages for a two-integrator single-differentiator system are outlined as follows.

Bipolar ·

- 1. No baseline restorer required due to symmetry of the pulses about the baseline.
- Poorer pulse-to-noise ratio (than unipolar) in a system with otherwise identical components and inputs.
- 3. Longer shaping time (than unipolar), which decreases the maximum count rate in otherwise equivalent systems.

Unipolar

- Requires a baseline restorer, which increases the component count and power by 50%.
- Less amplifier gain and bandwidth required for a given time-constant than required for bipolar.
- 3. Better pulse-to-noise ratio than bipolar in otherwise identical systems.

Breadboarding and testing has indicated that the disadvantages of the bipolar system could be overcome by proper design. The component count would be reduced, giving a bipolar system a decided advantage, which has dictated its choice over the unipolar system. The decision to use bipolar shaping in the EPS was made December 10, 1970.

Temperature Gain Stability Calculations

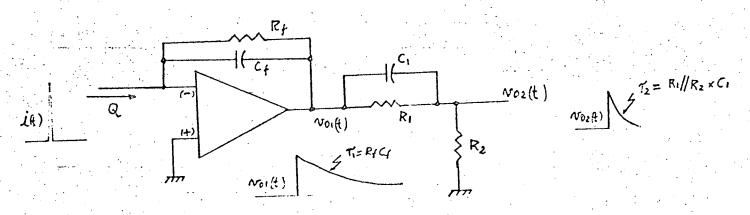
An IBM electronic circuit analysis program was run to evaluate the effect of expected temperature sensitivities of the components on the gain stability of the pulse amplifiers. A value -- 12-15-70 EPS-65 Page 2

of + 0.8% was chosen to simulate the component variations with temperature over the range from - 25°C to +25°C. This corresponds to 50 parts per million per °C for the resistors and 100 parts per million per °C for the capacitors, giving a 0.75% variation, which was rounded to 0.8% to simplify computations. The peak voltage variation was 0.2% for unipolar and 0.07% for bipolar.

The values took advantage of the inherent tracking of similar resistors and capacitors, but the combinations were such that maximum resistance was coupled with maximum capacitance and minimum resistance was combined with minimum capacitance. Resistance ratios, as well as capacitance ratios, were constant, giving maximum time-constant changes over the temperature range.

R. W. O'Neill

POLE-ZERO CANCELLATION AT THE OUTPUT OF THE CHARGE SENSITIVE PREAMPLIFIER



Due to input sensitivity considerations as well as to achieve high resolution, the feedback network elements R_f and C_f are chosen such that the product $R_f \times C_f$ is much greater than the duration of the pulse carrying the energy-amplitude relationship at the output of the shaping amplifier. Thus, it becomes necessary to interface a network between the preamplifier and postamplifier in order to shorten the pulse before amplification.

In order to achieve optimum overload recovery performance and for better high count-rate response it is mandatory that the waveform at the output of the pulse shortening network be monotonic decreasing in nature, that is, no crossing of the baseline is allowed.

This requirement can be achieved by the use of the RC network at the output of the CSA as shown in the figure above.

Suppose the CSA is excited by an impulse of current of charge Q. The time domain output voltage is given by:

$$vo_1(t) = \frac{Q}{C_f} e^{-\frac{1}{R_f C_f}} t$$
 (1)

which in the frequency domain assumes the form:

$$v_{01}(s) = \frac{Q}{C_f} \times \frac{1}{s + \frac{1}{R_f C_f}}$$
 (2)

Now, taking the transfer function of the R₁R₂C₁ network one finds:

$$\frac{V_{02}(s)}{V_{01}(s)} = \frac{s + \frac{1}{R_1 C_1}}{s + \frac{1}{(R_1//R_2)C_1}}$$
(3)

Multiplying (2) and (3) gives

$$v_{02}(s) = \frac{s + \frac{1}{R_1 C_1}}{s + \frac{1}{(R_1//R_2)C_1}} \times \frac{1}{s + \frac{1}{R_f C_f}} \times \frac{Q}{C_f}$$
(4)

If the zero of $V_{02}(s)$, $\frac{1}{R_1C_1}$, is made numerically equal to the pole of $V_{02}(s)$, $\frac{1}{R_fC_f}$, then there is what is usually called a pole-zero cancellation, and expression (4) becomes:

$$v_{02}(s) = \frac{Q}{C_f} \times \frac{1}{s + \frac{1}{(R_1//R_2)C_1}}$$
 (5)

which has the time domain expression given by

$$v_{02}(t) = \frac{Q}{C_f} \times e$$
 (6)

Page 3

Equation (6) shows that the voltage $V_{02}(t)$ is a simple exponential of time constant $(R_1//R_2)C_1$. Since $(R_1//R_2)C_1$ can be made much smaller than R_fC_f , the objective of shortening the pulse decay has been achieved, without baseline crossing.

In order to have no baseline crossing, one must have perfect pole-zero cancellation at all times. This means that $R_1C_1 = R_fC_f$ must be true under all conditions.

PULSE PILE-UP AT THE OUTPUT OF THE POLE-ZERO CANCELLATION NETWORK

In order to find the instantaneous baseline fluctuations due to pulse overlapping in high count-rate applications, Campbell's theorem can be applied:

$$\mathbf{v0}(\mathrm{rms}) = \sqrt{n \int_0^\infty |\mathbf{v}_0(t)|^2 dt}$$
 (7)

where (v0(t) is given by equation (6).

Substituting v0(t) into (7) and evaluating the integral one finds:

$$v0 \text{ (rms)} = \frac{Q}{C_f} \left[\frac{n}{2} (R_1//R_2) C_1 \right]^{1/2}$$
 (8)

POST-AMPLIFIER OUTPUT PILE-UP EFFECT

At the output of the two stage integrators with a unipolar pulse having a certain amount of undershoot due to an imperfect pole-zero cancellation of the preamplifier, the rms dispersion of the pulse amplitude can be found by applying once more Campbell's theorem.

$$v0 (rms) = \sqrt[4]{n} \int_0^\infty |f(t)|^2 dt$$
 (7)

Page 4

where, in this case:

$$f(t) = \frac{T_{j}}{T_{s}} - \frac{1}{T_{s}} t$$
(9)

and, T_{j} = resolving time of the unipolar pulse main lobe T_{s} = Time constant of the undershoot.

Substituting equation (9) into (7) one has:

[v0(rms)]_{REL} = 0.707
$$\sqrt[4]{\frac{T_{j}}{T_{s}}} n T_{j}$$
 (10)

In equation (10) the following definitions apply:

 $[v0(rms)]_{ABS} = [v0(rms)]_{REL} \times V_{peak} (normal pulse) \times 100%$

 $\frac{T_{.}}{T_{s}}$ is the fractional undershoot.

nT; is the duty cycle at the shaping amp output.

As an example of what can be expected for the instantaneous baseline fluctuations, consider the following practical parameters:

$$T_{ij} = 1 \text{ } \mu \text{sec}, T_s = 50 \text{ } \mu \text{sec}, n = 2.5 \text{ } x \text{ } 10^5 \text{ } \text{cps}.$$

Substituting these values into equation (10) yields:

$$[v0(rms)]_{REL} = .707 \frac{1}{50} \times 2.5 \times 10^{+5} z 10^{-5}$$

$$[v0(rms)]_{REL} \approx 5%$$

Note that $\frac{T_j}{T_s} = \frac{1}{50} = 2\%$ undershoot. This figure can be made smaller by carefully adjusting the P-Z cancellation network.

INTERDEPARTMENTAL COMMUNICATION

Distribution

DEPT./ 673-10 ELDO./Beta PLANT/HASD DATE 4-15-71 ORGN. Ref: EPS-199

EROM

R. S. Lindsey

DEPT./673-10 BLDG./Beta PLANT/HASD EXT. 422

SUBJECT. Selection of Time Constants for Accelerator Testing

Six EPS post amplifiers are needed for analog electronics/ detector testing presently scheduled for the NASA/MSC Van de Graaff in May. These six amplifiers will be housed in two NIM modules as follows:

1 MM Module - 150 nsec

220 nsec

290 nsec

2 MM Module - 360 nsec

430 nsec

500 nsec

Distribution:

B. C. Hall

B. L. Cash

B. E. Curtsinger

R. P. Dunn

C. L. Fletcher

P. Gleeson

T. D. Lyons

W. A. Oliveira

R. W. O'Neill

G. R. Smith

C. J. Spahn

D. L. Vincent

SUMMARY OF POWER SYSTEM PERFORMANCE DURING THE EPS ENG. TEST UNIT THERMAL-VACUUM TESTING

A. INPUT FILTER

Due to the test setup (i.e., the EPS mounted inside a vacuum chamber) and a lack of the necessary test equipment, it was not possible to perform any RFI/EMI testing on the EPS during Thermal-Vacuum testing. Therefore, it is not known whether the Input Filter met its design specifications at the temperatures encountered during this test. However, since the electronic components utilized in this subsystem do not vary significantly with temperature and are insensitive to vacuum, and since this unit had already passed an EMI test at room temperature, it is assumed that the Input Filter would have allowed the EPS to pass an EMI test at any temperature within the operating limits specified for the instrument.

Since both power supplies and the Heater Control circuit were always within specification (see below), the Input Filter could not have modified the primary power (+28 Vdc) to these circuits. Therefore, the conclusion reached is that the Input Filter performed as expected.

B. DETECTOR BIAS SUPPLY

The Detector Bias Supply met all of the performance specifications during the Thermal-Vacuum testing. A summary of its performance compared to the required specifications is given below.

Specification (Ref. EPS-41)

Peformance Thermal-Vacuum Test

 27.5 ± 2.5 Vdc Input Voltage:

Operated from 28 ± 4Vdc

 $I_{in} \leq 30 \text{ ma } 0$ Input Current:

 $I_{in} \leq 25 \text{ ma}$

+43°C

28Vdc

-25°C to Oper. Temp Range:

+25°C

Operated from -45°C to

-50°C to Surv. Temp Range:

+50°C

 $350 \pm 17.5 Vdc$ Output Voltage:

346.9 ± 0.9Vdc over Temp

range of -45°C to +43°C

LOW VOLTAGE POWER SUPPLY

The LVPS met most of the required specifications during the Eng. Test Unit Thermal-Vacuum testing. The summary below gives actual performance and the required performance.

Specification (Ref. EPS-45)

Performance Thermal-Vacuum Test

 $27.5 \pm 2.5 \text{Vdc}$ Input Voltage:

Operated from 24 to 31Vdc

 $I_{in} \leq 557 \text{ ma}$ Input Current:

 $I_{in} \leq 550 \text{ ma}$

-25°C to Oper. Temp Range:

+25°C

Operated from -45°C to

-50°C to Surv. Temp Range:

+43°C

+50°C

Outputs:

Output		
+0.2 +8 -0.0 Vdc	8.05 to 8.08 -27°	$^{\circ}$ C \leq T \leq 23 $^{\circ}$ C
+0.2 -8 -0.0 Vdc	-8.08 to -8.13	11
+5 ± 0.3 Vdc	5.00 to 5.03	n
-5 ± 0.3 Vdc	*-5.258 to -5.317	. 11
+25 ± 2.0 Vdc	25.56 to 25.64	,
-15 ± 2.0 Vdc	-16.63 to -16.73	
$3.0 \pm .01 \text{Vdc}$	3.003 to 3.009	

*Note that the -5 Vdc output was out of specification. This output was out of spec. at room temperature (V out = -5.317, spec. allows -5.300). This is a result of generating both the +5 output and the -5 output from one secondary winding on the LVPS transformer. Since the load current for the +5 is approximately 900 ma and the load current for the -5 V output is only approximately 120 ma there will be a considerable difference in the two output voltages. It was decided to set the output voltages of this winding with the +5 V output (i.e., adjust the number of turns on this winding to get a minimum of +5.00 Vdc out and take whatever comes out for the -5 V). Since the -5 V output is out of specification by only 0.3% worst case, this should be acceptable.

D. HEATER CONTROL

During the Thermal-Vacuum testing, the internal skin heaters turned on during Test Case #2 (operating during a cold orbit) when the internal package temperature had reached -0.5°C. When the additional six watts were dissipated within the EPS, the package temperature started

increasing. The temperature was monitored for an additional two hours and increased to +2.9°C during this time. It is surmised that the package temperature would have eventually reached +10°C and the heater would have turned off.

During Test Case #1 (operating during a hot orbit) the package temperature started out at -35°C. With all electronics power on and the heaters on, the package temperature increased to +9.5°C in seven hours. At this point, the heaters turned off and the package temperature immediately stabilized at +10°C where it remained for the remaining eight hours of the test.

Since during the course of the Thermal-Vacuum testing, the EPS package temperature ranged between -45°C and +43°C, it is obvious that the Heater Control Subassembly will operate over and survive this temperature range.

		• • •	_					
A. N	OT CORREC	TED FOR AL		105 37-14	+350 Volt	-15 Volt	-5 Volt	+3 Volt
Temp	+5 Volt	+8 Volt	-8 Volt	+25 Volt	+330 VOIC			
		0.114	-8.165	25.70	346.6	-16.62	-5.329	3.003
+43	5.044	8.114		25.64	346.1	-16.63	-5.317	3.009
+23	5.034	8.084	-8.131			-16.62	-5.297	2.999
+11	5.024	8.064	-8.102	25.59	345.6		-5.281	2.996
0	5.014	8.054	-8.096	25.54	345.6	-16.63		
-27	4.976	8.006	-8.038	25.43	345.6	-16.64	-5.232	2.993
	:	7.928	-7.958	25.27	346.1	-16.53	-5.142	2.987
-45 4.916 7.928 1-1.958 1 23.27 1 3.2								
В.	CORRECTED	FOR ADC				75 77-74	-5 Volt	+3 Volt
<u> </u>		+8 Volt	-8 Volt	+25 Volt	350 Volt	-15 Volt	-5 0010	
°C	1	·			346.2	-16.62	-5.329	2.999
+43	5.044	8.114	-8.165	25.65			-5.317	3.009
+23	5.034	8.084	-8.131	25.64	346.1	-16.63		3.003
+11	5.032	8.084	-8.131	25.63	346.3	-16.67	-5.317	
0	5.028	8.078	-8.117	25.62	346.8	-16.66	-5.307	3.005
	i i		-8.078	25.56	347.3	-16.73	-5.258	3.007
-27	5.000	8.046			347.8	-16.62	-5.168	3.001
-45	4.940	7.968	-7.998	25.40				

TABLE I. EPS ENG TEST UNIT PERFORMANCE DURING THERMAL-VACUUM TEST.

MITERDEPARTMENTAL COMMUNICATION

D. L. Vincent

DBFT./ 673-10 PORTS Beta PART./ HASD Ref: EPS-198

C. L. Fletcher

BEST. 673-10 SUDD. Beta FAC. HASD EXT. 481

SUBJECT: Power Dissipation in Data Processor Modules

The power dissipation for the various data processor modules was measured individually in the operating mode on the breadboard unit. Individual module power is listed below.

		5	volts	9	47	ma	 234	Wm
Counter/Memory			volts					
Sequence Control/Line	Rec.	- (
Counter Control/Clock		1-5	volts	. 9			10	
		. 5	volts	ø	36.7	ma	 184	mw
Digital Data Comp.	en e				24	ma	 120	mW
ADC Logic/MUX Cont.			volts					
Buffer/Word Sync Gen		, 5	volts	<u>a</u>	52	ma	 260	
		5	volts	9	180	ma	900	mW
Total	•••	-			2	ma	10	mW
		-5	volts	í,	2	ma		

It should be noted that ten counter/memory modules will be required for a complete unit. Thus, the total power required for a complete unit will be approximately 603 ma from the positive 5 volt supply and 2 ma from the negative 5 volt supply. If the positive supply voltage is increased to 5.1 volts, the current increases approximately 3 percent.

C. L. Fletcher

cc: B. E. Curtsinger

. B. C. Hall

R. S. Lindsey

INTERDEPARTMENTAL COMMUNICATION



G. R. Smith

orgn. 673-10zone Beta PLANT/ HASD A-12-71
Ref: EPS-197

FROM

R. S. Lindsey

DEPT./ OZON. 673-10ZONE Beta FAC. HASD 422

SUBJECT:

Parts List Change for the Dual Differential Pulse Height Discriminator

Recently completed testing conducted on the Dual Differential Pulse Height Discriminator indicates the need for several parts value changes. The new values are:

R5

R6

R7

Channel 1

RNC50H7500FR

3260H-1-201

RNC50H4640FR

R.S. Smidsey In

cc: B. E. Curtsinger

R. B. Hendrix

DEPT./673-10 BLDG./Beta PLANT/HASD DATE 12-29-70 Ref: EPS-90

DEPT. 673-10 ELDO Beta PLANT/HASD EXT. 422

FROM

, to

R. S. Lindsey

SUBJECT:

Part Value Changes for R2, R5(7), R5(9), R7(8), R7(9), R7(10), R8(7), R8(9), R10(8), R10(9), R10(10) and R13 of the Dual Differential Pulse Height Discriminator

The subject MEPCO RNC50 resistors are officially changed to the following values:

Resistor	New Value	<u>.</u>
R2	6040 Ω	
R5 (7)	576 Ω	
R5(9)	249 Ω	
R7(8)	1180 Ω	
R7(9)	1330 Ω	
R7(10)	1500 Ω	
R8(7)	576 Ω	
R8(9)	249 Ω	
R10(8)	1180 Ω	
R10(9)	1330 Ω	
R10(10)	1500 Ω	
R13	6040 Ω	

These values for R2 and R13 hold only if the input impedance of the Resolution Monitor is 4990 Ω ± 1%. If any change is made in this circuit's input impedance, please inform me so that compensating changes can be made in R2 and R3.

In addition, potentiometers R6 and R9 could possibly change to 3260 H (side screw) types.

R. S. Lindsey

cc: W. Oliveira

DEPT./ 673-10 Beta FAC. HASD Ref: EPS-85

B. C. Hall

R. S. Lindsey

DEPT. 673-10 Beta FAC. HASD EXT. 422

SUBJECT: Experimental Varification of EPS Analog Design Before Manufacturing Release

Prior to freezing the EPS analog design, a detailed attempt should be made to verify its adequacy and ferret out any shortcomings. This testing should be directed at the system performance level and should involve the detectors, preamplifier, amplifiers, pulse height discriminators, their interwiring and the overall packaging scheme. A large fraction of the testing can be accomplished at the bench. An incomplete listing of these tests is:

- 1. System gain accuracy
- 2. System gain stability
 - a. Temperature
 - b. Power supply variations
 - c. Charge collection time.
- 3. System resolution
- 4. System resolution stability
 - a. Temperature
 - b. Counting rate and spectrum
- 5. System baseline
- 6. System baseline stability
 - a. Temperature
 - b. Power Supply Variations
- 7. System Overload Recovery
- 8. System overload recovery temperature stability
- 9. System integral nonlinearity
- 10. System power requirements

Most of the required equipment necessary to accomplish the preceding list of tests is on hand or could be borrowed. One outstanding item, however, is markedly absent. This item is a fast, linear, noise free pulse stretcher capable of operation

at > 250,000/sec rates. This item will have to be developed or the (1MM)³ detector channel cannot be tested. Since EPS bases its rate performance capabilities on this channel's qualities, I feel that the need to perform adequate, well documended tests is paramount. If work is not started on this unit this week, the probability of its completion by January 15 will approach zero.

The second type of testing necessary to demonstrate the adequacy of the EPS design involves use of flight type detectors and charged particles. Due to the thickness of dead layers on SSR cubical detectors, alpha sources are of little use. In addition, the (1MM)³ detectors permit sufficient electron scattering to render the data largely useless. The only remaining form of handy charged particle is the proton. Results obtained in earlier IFS testing gave the indication that this type of particle is acceptable for resolution and gain measurements.

It is my belief that someone from the detector group should be charged with the responsibility of gathering together a group of detectors that can be used to determine the adequacy of the EPS electronics. Spahn and Cash understand the necessary ramifications involved in the selection of detectors.

It is also my recommendation that we should obtain the use of the MSC Van de Graaff. Since we have no scattering chamber, beam profile measuring apparatus, or beam monitoring equipment, the use of another facility, such as the one available at Rice, for this testing would be very painful and possibly impossible. Due to schedule and manpower limitations, we should attempt to gain access for the last two weeks in January. I have seen a NASA/MSC access for the last two weeks in January. I have seen a NASA/MSC access to the Van de Graaff to GE during this period. The Van de Graaff is scheduled to close on February 1, 1971.

R.S. Lindsey

cc: Cash
Curtsinger
Lyons
Oliveira
O'Neill
Spahn

DEPT./673-10 BLDG./Beta FLANT/HASD Ref: EPS-89

B. C. Hall

FROM R. S. Lindsey

DEPT. 673-10 BLDO. Beta PLANT/HASD EXT. 42:

SUBJECT: Selection of EPS Post Amplifier Time Constants

In IDC EPS-86 of 12-28-70, preliminary recommendations for post amplifier time constants were made. These were based upon sketchy information available at that time. On 12-28-70, Bob O'Neill repeated the data very carefully. The results are included here. Indications are that it is possible to operate the post amplifiers at time constants equal to the worst case charge collection times and suffer no ill effects so long as the worst case charge collection times are true. This would imply time constants of 110 nsec and 361 nsec for the (1 mm)³ and (2 mm)³ detector channels respectively. These time constants would produce dead times of 33% and 108% at input rates of 250K/sec. I recommend the following:

- A. Accurately breadboard time constants of 110 nsec and 361 nsec and repeat the Relative Gain Charge Collection Time Data in a manner equal in precision to that reported here. Since the curves roll off more slowly as the time constant increases it might be possible to reduce the time constants by a small amount as a result of analyzing the 110 nsec, 361 nsec data. Accurately measure the post amplifier output wave shape to assume the proper time constant.
- B. Generate counting rate information for each channel based upon the EPS boundaries and a Starfish Electron Enhancement.
 - C. Using the Random Pulser examine the behavior of the preamplifier - post amplifier - pulse height discriminator combination as a function of random input rate to determine whether or not EPS can be paralyzed by high counting rate conditions. If paralysis is possible its manner of onset and rate location are central to the quality of EPS and should be well known.

R.S. Lindsey

cc: Cash
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B. C. Hall

DEPT./673-10 Bloo./ BetaFLANT/ HASD DATE 12-28-70
Ref: EPS-86

FROM

R. S. Lindsey

DEPT./673-10 BLOG Beta FAC. HASD EXT. 422

SUBJECT. Selection of EPS Post Amplifier Time Constants

To optimize the EPS linear electronics performance for high counting rate conditions, it is necessary to minimize the time required to process each detected event. This is accomplished by minimizing the post amplifier characteristic time constant (τ). The concept of EPS requires that the post amplifier output pulse height be proportional to the total charge generated within the detector during an event. This implies that τ is long with respect to the time necessary to collect the generated charge (τ). It is apparent from a knowledge of the required counting rates and the proposed charge collection times that a conflict is possible. The facts necessitate a detailed analysis of both the charge collection time and its interaction with the post amplifier time constant.

The charge collection time for a carrier is given by:

$$T = \frac{d^2}{uV}$$

Since μ_H (the hole mobility) is approximately a factor of two less than $\mu_{\mbox{e}}$ (the electron mobility), calculations will be based upon times for holes. Now:

$$T_{H} = \frac{d^{2}}{\mu_{H}V}$$

where:

T is the hole collection time

d is the depletion depth in cm

 μ_{H} is the hole mobility in cm 2 /volt-sec

V is the depletion bias in volts.

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Additionally:

$$\mu_{\rm H} = 2.3 \times 10^9 t^{-2.7}$$

where: t is the temperature in ° Kelvin.

Energy loss requirements have already fixed the nominal values of d at 1 mm and 2 mm. The worst case value of $\mu_{\rm H}$ occurs when t is maximized. Under operational conditions this is defined as 0°C = 273°K. However, since checkout of the instrument is necessary at up to +30°C = 103°K, the true worst case value of $\mu_{\rm H}$ occurs here. These two mobility values are:

 $\mu_{\text{H}(0^{\circ}\text{C})} = 608 \text{ cm}^2/\text{volt-sec}$ $\mu_{\text{H}(+30^{\circ}\text{C})} = 459 \text{ cm}^2/\text{volt-sec}$.

Worst case initial depletion depth errors have been investigated by Spahn and Cash. Solid State Radiation, Inc. guarantees an initial error of \leq + 15% of nominal depletion depth.

Depletion depth drift as a function of oxygen impurity level, time, temperature and detector bias has been the subject of a detailed study by Spahn. He reports very little data to be available with poor agreement between authors. The worst case depletion depth drift calculations are conservative and assume an MDA mounting with the following conditions:

- A. 350° volts detector bias
- B. A .38 year active detector mission
- C. A constant 0°C detector temperature.

Spahn has proposed some additional experimental work to verify his findings.

The proposed values for detector bias were a compromise resulting from problems with voltage derating of detectors, high voltage corona effects and the complexity of dual supplies. A value of 350 volts has been selected.

Figure 1 summarizes all these effects and the resulting hole collection time.

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In parallel with this effort it is possible to measure the effect of finite charge collection time on post amplifier output pulse height to determine what τ is suitable for a known Th. This work was done by Bob O'Neill on December 24, 1970, using hypothetical values of τ near the final EPS values. These data, Figures 2 and 3, relate the post amplifier output amplitude to the ratio of charge collection time (T) to post amplifier time constant (τ). Several things are clear from these data, and are:

- 1. The $\tau=276$ nsec data should be repeated to remove several ambiguities that exist near the critical value of T/τ .
- 2. The τ = 83 nsec data should be extended on the lower side to a point where the post amplifier output amplitude shows no further increase.
- 3. If a decision must be reached from these data for maximum acceptable T/τ values the result would be < 0.5.
- -4. When preliminary values are established for τ (1 mm) and τ (2 mm) detailed precision data should be repeated for the exact values. This process should be repeated until acceptable values are found.
- 5. A computer program to predict the interaction between T, T and the output amplitude should be generated on a reduced priority basis to allow a finer analysis of the problem. The two measured boundary values should be checked to insure the program's accuracy.

To sum up, on the basis of data available now, time constants of 220 nsec for the (1 mm)³ detector and 722 nsec for (2 mm)³ detectors are necessary, resulting in pile-ups of 66% and 217% respectively at input rates of 250,000/sec. Shorter time constants could result in an inability to claim equality between instruments due to detector variations. Better information from O'Neill could possibly lower the time constants.

R. S. Lindsey

Atch: Figures 1, 2 and 3

cc: Cash Oliveira
Curtsinger O'Neill

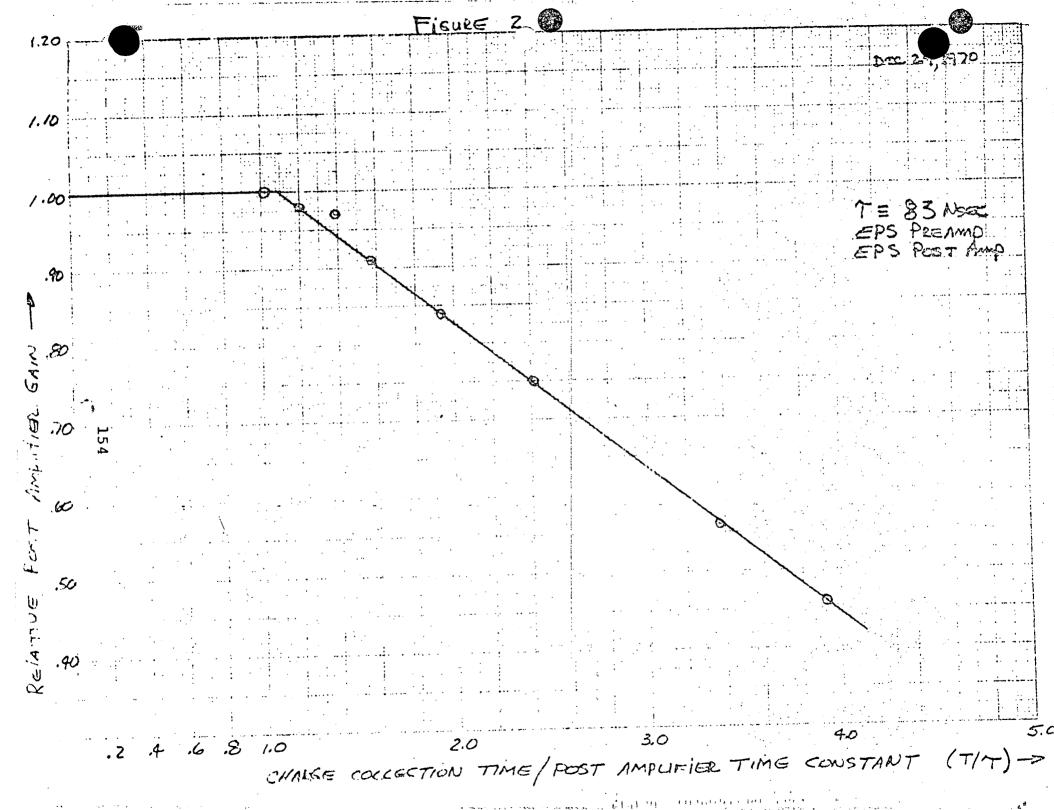
Curtsinger O'Nelll 152 Lyons Spahn

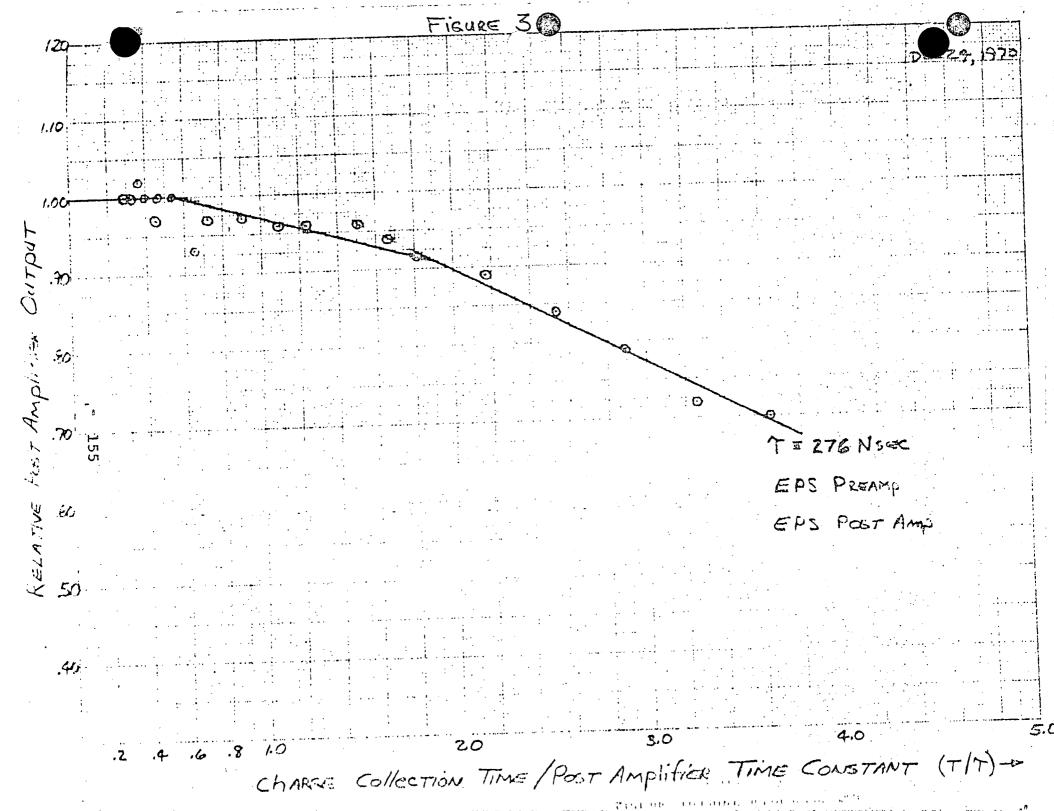
FIGURE 1 HOLE COLLECTION TIMES FOR EPS

							. (Char	ge Co Tim		tion
•							· ·.	0°	С	+30	O C
· .		Nominal	Depletio	on Depth	<i>.</i>	(1.00	mm)	48	nsec	63	nsec.
(1	mm) ³ ,	Maximum	Initial	Depletion	Depth	(1.15	mm)	63	nsec	84	nsec
•		Maximum	Drifted	Depletion	Depth	(1.32	mm)	83	nsec	110	nsec
•				* •							
	•	Nominal	Depletio	on Depth		(2.00	mm)	192	nsec	255	nsec
(2	mm) 3	Maximum	Initial	Depletion	Depth	(2.30	mm)	254	nsec	337	nsec
`-		Maximum	Drifted	Depletion	Depth	(2.38	mm)	272	nsec	361	nsec
		•									

$$T_{H} = \frac{d}{H^{V}} = \frac{d}{2.3 \times 10^{9} t^{-2.7} V}$$

- Assumptions: 1. The maximum acceptable leakage current for a 1 mm³ detector at 30°C is 1 amp resulting in a bias voltage loss of 2.22 volts
 - The maximum acceptable leakage current for a 2 mm³ detector at 30°C is 2 mamp resulting in a bias voltage loss of 4.44 volts.
 - The minimum bias voltage supply value is 347.7 volts.
 - 4. Depletion depth drift values are calculated assuming an MDA mounting with a maximum temperature of 0°C.





EPS AMPLIFIER

Church

An Analysis of the Filter Configuration and the Optimization of Signal Shapes

This report will discuss a pulse shaping amplifier composed of two sections of active filtering using two operational amplifiers connected in the inverting configuration, with bridged tee RC networks for the feedback branches. Two cases will be considered: (1) the output pulse is unipolar in nature, and (2) the output pulse is bipolar.

The design is conducted with the purpose of achieving optimum performance from the filters in regard to minimum noise contribution and predictable pulse shapes; that is, the unipolar pulse shall be near Gaussian with no undershoot, exhibiting almost perfect symmetry between the rise and fall times, and the bipolar pulse shall exhibit only one baseline crossover and its total duration being approximately equal to the unipolar pulse.

Unipolar Configuration

In order to study the response of the filter to the signal coming from the charge sensitive preamplifier, consider the circuit shown in Figure 1:

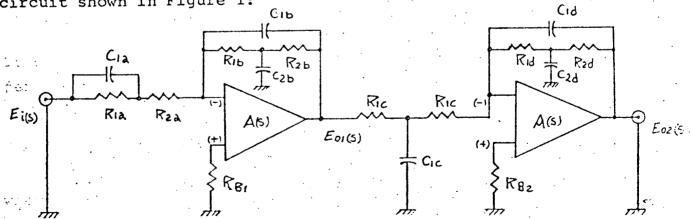


Figure 1

It will later become apparent that this configuration corresponds to unipolar shaping provided that the filter elements are chosen accordingly.

The signal coming from the preamplifier into the amplifier's input can be expressed as

$$ei(t) = \frac{Q}{C_f} e^{\frac{t}{\tau}}$$
 (1)

where:

 $Q \rightarrow \text{signal charge at the preamplifier's input.}$

C_f preamplifier's feedback capacitor.

 $\tau \rightarrow R_f \times C_f$ = preamplifier signal decay time constant and R_f is a high valued resistor connected across C_f .

In the complex frequency domain, equation (1) becomes:

$$E_{i}(s) = \frac{Q}{C_{f}} \frac{1}{s + \frac{1}{\tau}}$$
 (2)

Let us now compute the transfer function of the amplifier's first filter section. That will consist of evaluating the ratio

$$\frac{E_{01}(s)}{E_{i}(s)}$$

It can be shown by operational amplifier theory that this transfer function is given by

$$\frac{E_{01}(s)}{E_{i}(s)} = \frac{-Y_{21a}}{Y_{21b}}$$
 (3)

where Y_{2la}, Y_{2lb} are the transadmittances of the input and feed-back networks respectively.

Using standard network analysis techniques, Y 21a is found to be:

$$Y_{21a} = \frac{1}{R_{2a}} \frac{S + \frac{1}{R_{1a}C_{1a}}}{S + \frac{1}{\frac{R_{1a}R_{2a}}{R_{1a} + R_{2a}}} \times C_{1a}}$$
(4)

and:

$$-Y_{21b} = \frac{c_{1b} \left[\frac{S^2 + \left(\frac{1}{R_{1b} \times R_{2b}} c_{2b} \right)}{R_{1b} + R_{2b}} c_{2b} \right]}{\left(\frac{S + \frac{1}{R_{1b} \times R_{2b}} c_{2b}}{R_{1b} + R_{2b}} c_{2b} \right)}$$
(5)

and the transfer function is given by:
$$\frac{1}{\frac{1}{R_{2a}}} \frac{\left(S + \frac{1}{R_{1a}C_{1a}}\right)}{\left(S + \frac{1}{R_{1a}X_{2a}}C_{1a}\right)} = \frac{\frac{1}{R_{2a}} \left(S + \frac{1}{\frac{R_{1b}X_{2b}}{R_{1b} + \frac{R_{2b}}{R_{2b}}C_{2b}}}\right)}{\frac{1}{R_{1b}X_{2b}C_{2b}}S + \frac{1}{R_{1b}C_{1b}R_{2b}C_{2b}}}$$

$$\left(S + \frac{1}{\frac{R_{1b}X_{2b}}{R_{1b} + \frac{R_{2b}}{R_{2b}}C_{2b}}}\right)$$
(6)

Recalling equation (2), and establishing the condition that $\tau = R_f \times C_f$ be equal to $R_{la} \times C_{la}$, one finds that upon multiplication of the preamplifier output response to the network "a" transfer function, there is a pole-zero cancellation and the response at the output of the first amplifier is given by:

$$E_{01}(s) = -\frac{\frac{Q}{C_{f}} \times \frac{1}{\left(s + \frac{1}{R_{1a} \times R_{2a}} C_{1a}\right)}}{\frac{R_{2a}C_{1b}}{R_{2b}} \times \left(\frac{s^{2} + \left(\frac{1}{R_{1b} \times R_{2b}} C_{2b}\right)}{\frac{R_{1b}R_{2b}C_{2b}}{R_{1b} + R_{2b}} C_{2b}}\right) \times + \frac{1}{R_{1b}C_{1b}R_{2b}C_{2b}}}$$

It is desirable to have the differentiating time constant of the input network equal to the integrating time constant of the bridged tee network and thus superimpose the pole of Y_{21a} with the pole of Y_{21b} . Once this is established, $E_{01}(s)$ becomes:

$$E_{01}(s) = -\frac{Q}{C_{f}^{R} 2a^{C} 1b} \left[s^{2} + \left(\frac{1}{R_{1b} \times R_{2b}} C_{2b} \right) + \frac{1}{R_{1b}^{C} 1b^{R} 2b^{C} 2b} \right] (\epsilon)$$

Equation (8) gives the signal response at the output of the first operational amplifier.

By studying the locations of the poles of $E_1(s)$, one can determine the nature of the time response or pulse behavior. It will, of course, depend on the roots of the characteristic equation:

$$s^{2} + 2 \rho W_{0}S + W_{0}^{2} = 0 (9)$$

where the new variables are:

$$w_0^2 = \frac{1}{R_{1b}^C_{1b} \cdot R_{2b}^C_{2b}}$$
 (10)

and

$$2 \rho W_0 = \frac{1}{\frac{R_{1b} \times R_{2b}}{R_{1b} + R_{2b}}} C_{2b}$$
 (11)

Solving for ρ in equation (9) one finds:

$$\rho = \frac{1}{2 \times \frac{R_{1b} \times R_{2b}}{R_{1b} + R_{2b}} C_{2b}} \times \frac{1}{\sqrt{R_{1b}C_{1b} \cdot R_{2b}C_{2b}}}$$

$$\rho = \frac{(R_{1b} + R_{2b}) \sqrt{R_{1b}C_{1b} \cdot R_{2b}C_{2b}}}{2 R_{1b} \cdot R_{2b}C_{2b}}$$
(12)

The roots of equation (9) are:

$$s_{1,2} = \frac{-2\rho W_0 + \sqrt{4\rho^2 W_0^2 - 4W_0^2}}{2}$$

or

$$s_{1,2} = \frac{2\rho W_0 + 2W_0 \sqrt{\rho^2 - 1}}{2} \tag{13}$$

Equation (13) tells that one can expect three different kinds of solutions depending on the value of the parameter ρ .

- ρ < 1, S_{1,2} will be a pair of complex conjugates in the left half of the complex frequency plane. In this case the response of equation (8) will be underdamped and will present oscillations.
- ρ > 1, S_{1,2} will be two numbers located on the negative real axis of the complex frequency plane. In this case the response of the equation (8) will be overdamped.
- ρ = 1, S_{1,2} will be a pair of coincident real roots located on the negative real axis of the complex frequency plane. In this case, the response of equation (8) will be critically damped. This means, fastest return to the baseline with no oscillations.

In the present application, one is more interested in this third type of solution (ρ = 1) which gives for solutions the following:

$$s_{1,2} = w_0(2)$$

Under these conditions, equation (8) can be rewritten as:

$$E_{01}(s) = \frac{\frac{Q}{C_f R_{2a} C_{1b}}}{\left(s + \frac{1}{\sqrt{R_{1b} C_{1b} R_{2b} C_{2b}}}\right)^2}$$
(14)

For the second stage of filtering, the transfer function is again given by:

$$\frac{E_{02}(s)}{E_{01}(s)} = -\frac{Y_{21c}}{Y_{21d}}$$

It is easily shown that:

$$Y_{21c} = \frac{\frac{1}{(R_{1c})^2 C_{1c}}}{s + \frac{2}{(R_{1c})^2 C_{1c}}}$$
 (15)

and

$$Y_{21d} = -\frac{c_{1d} \left[s^2 + \left(\frac{R_{1d} + R_{2d}}{R_{1d} \times R_{2d}} c_{2d} \right) + \frac{1}{R_{1d} R_{2d} c_{1d} c_{2d}} \right]}{\left(s + \frac{R_{1d} + R_{2d}}{R_{1d} \times R_{2d}} c_{2d} \right)}$$
(16)

Thus:

$$\frac{E_{02}(s)}{E_{01}(s)} = -\frac{\frac{1}{(R_{1c})^2 C_{1c}} / s + \frac{2}{(R_{1c})^2 C_{1c}}}{c_{1d} \left[s^2 + \left(\frac{R_{1d} + R_{2d}}{R_{1d} \times R_{2d}} C_{2d} \right) s + \frac{1}{R_{1d}^R 2d^C 1d^C 2d} \right]}$$

$$\left(s + \frac{R_{1d} + R_{2d}}{R_{1d} \times R_{2d}} C_{2d} \right)$$
(17)

In this case, if the pole of Y_{21c} is made to coincide with the pole of Y_{21d} , one has:

$$\frac{E_{02}(s)}{E_{01}(s)} = \frac{\frac{1}{(R_{1c})^2 C_{1c}}}{c_{1d} \left[s^2 + \frac{R_{1d} + R_{2d}}{R_{1d} \times R_{2d} C_{2d}} s + \frac{1}{R_{1d} R_{2d} C_{1d} C_{2d}} \right]}$$
(18)

and the condition used to obtain (18) was:

$$\frac{R_{1c}}{2} \times C_{1c} = \frac{R_{1d} \times R_{2d}}{R_{1d} + R_{2d}} \times C_{2d}$$
 (19)

The output voltage response will be obtained by multiplying both members of equation (18) by $E_{01}(s)$ and then substituting $E_{01}(s)$ by its expression as given by equation (14). Thus:

$$E_{02}(s) = \frac{\frac{Q}{C_{f}^{R}_{2a}C_{1b}C_{1d}(R_{1c})^{2}C_{1c}}}{\left[s^{2} + \frac{R_{1d} + R_{2d}}{R_{1d} \times R_{2d}C_{2d}}s + \frac{1}{R_{1d}^{R}_{2d}C_{1d}C_{2d}}\right]\left[s + \frac{1}{\sqrt{R_{1b}C_{1b}R_{2b}C_{2c}}}\right]}$$

The second filter section can also have its elements chosen so as to guarantee critically damped response. Under these conditions, one has:

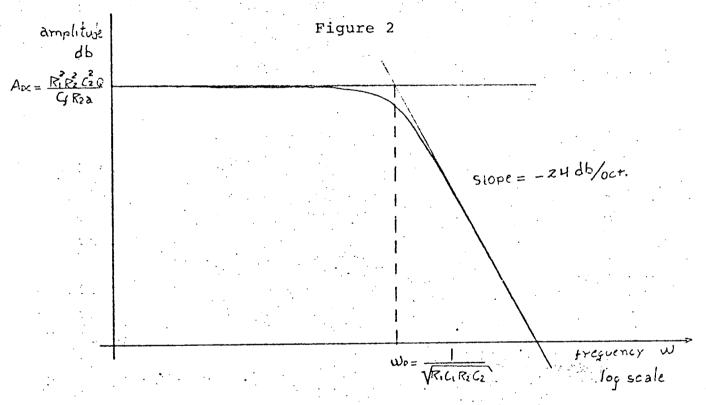
$$E_{02}(s) = \frac{\overline{c_f^{R_{2a}c_{1b}c_{1d}(R_{1c})^{2}c_{1c}}}}{\left[s + \frac{1}{\sqrt{R_{1d}^{C_{1d}R_{2d}^{C_{2d}}}}}\right]^{2} \left[s + \frac{1}{\sqrt{R_{1b}^{C_{1b}R_{2b}^{C_{2b}}}}}\right]^{2}}$$
(21)

If one goes one step further and makes the bridged tee elements for both filters correspondingly, equal, Equation (21) becomes:

$$E_{02}(s) = \frac{\frac{Q}{C_f R_{2a} C_{1d}^{2} (R_{1c})^{2} C_{1c}}}{\left[s + \frac{1}{\sqrt{R_1 C_1 R_2 C_2}}\right]^4}$$
(22)

Equation (22) gives the overall response of the pulse shaping amplifier when fed from a charge sensitive preamplifier. The filtering is arranged so that there is one early differentiation at the "front end" in the so-called "pole-zero" cancellation network, followed by two stages of active integration. In addition, the time constants were chosen to be equal as explained above.

The frequency domain amplitude response is shown in figure 2 below.



The time domain expression for equation (22) is given by:

$$e_{02}(t) = \frac{Q}{C_f^{R_{2a}C_1^{2}(R_{1c})^{2}C_{1c}}} \times \frac{1}{6} t^3 e^{\sqrt{R_1^{C_1}R_2^{C_2}}}$$
(23)

where $\sqrt{R_1C_1R_2C_2} = \tau$ is the time constant.

The time for $e_{02}(t)$ to reach its maximum amplitude can be found by taking the derivative of $e_{02}(t)$ with respect to time, equating it to zero and solving the resulting equation:

$$\frac{de_{02}(t)}{d_{+}} = K_{1} \frac{1}{6} t^{3} - \frac{1}{\tau} e^{\frac{-t}{\tau}} + K_{1} \times \frac{1}{6} e^{\frac{-t}{\tau}} \times 3t^{2} = 0$$
 (24)

thus:

$$-\frac{t}{\tau} + 3 = 0$$

and $t = 3\tau$. (25)

Expression (23) can be normalized with respect to amplitude and time constant, resulting in the following expression:

$$e_{02}(t) = t^3 e^{-t}$$
 (26)

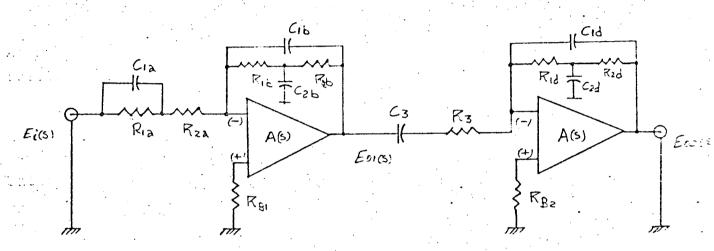
Examining expression (26) one immediately concludes that $e_{02}(t)$ has two singularities, that is, its value is zero for t=0 and also for $t=\infty$. This, of course, clearly identifies the strictly unipolar nature of this amplifier configuration.

It is desirable to know the values of $e_{02}(t)$ for many different values of t in order to have a clear understanding of the system "dead-time" and "pile-up" effects under high pulse rate excitation. The expression $e_{02}(t) = t^3t^{-t}$ was solved for t in increments of $\Delta t = .1$ from t = 0 to t = 20, using the H.P. 9100B calculator, and the results are presented in the form of a table of $e_{02}(t)$ versus t and also in the form of a polt of $e_{02}(t)$ versus t. The plot has been normalized so that maximum amplitude is made equal to 1. This allows all the other points to be immediately viewed as a direct percentage of the maximum value. The table and the plot are shown in figures 5 and 8 respectively.

Bipolar Configuration

In order to achieve a bipolar pulse response at the output of the shaping amplifier, it is necessary to differentiate the incoming pulse twice. For this particular application, and due to loading considerations, it is preferable to place the second differentiator between the two operational amplifiers. This can be made of a series R-C network at the input section of the second active filter as shown in figure 3.

Figure 3



By comparing figure 3 with figure 1, it becomes apparent that $E_{01}(s)$ still has the same expression as given by equation (14). Furthermore, the transadmittance of the second amplifier feedback network will also be maintained unchanged and equal to equation (16). Thus:

$$Y_{21d} = -\frac{c_{1d} \left[s^2 + \left(\frac{R_{1d} + R_{2d}}{R_{1d} \times R_{2d}C_{2d}} \right) s + \frac{1}{(R_{1d}C_{1d}R_{2d}C_{2d})} \right]}{\left(s + \frac{R_{1d} + R_{2d}}{R_{1d} \times R_{2d}C_{2d}} \right)}$$
(16)

The second stage input network transadmittance will be:

$$Y_{21} = \frac{1}{R_3} \times \frac{S}{S + \frac{1}{R_3 C_3}}$$
 (27)

and the second filter transfer function is given by: .

$$\frac{E_{02}(s)}{E_{01}(s)} = -\frac{\frac{1}{R_3} \frac{s}{s + \frac{1}{R_3 C_3}}}{\frac{c_1 \left[s^2 + \left(\frac{R_1 + R_2}{R_1 R_2 C_2} \right) s + \frac{1}{R_1 C_1 R_2 C_2} \right]}{\left(s + \frac{R_1 + R_2}{R_1 R_2 C_2} \right)}$$
(28)

As in the unipolar case, it is advantageous to make the following equality:

$$R_3C_3 = \frac{R_1R_2}{R_1 + R_2}C_2 \tag{29}$$

Under this condition, equation (18) becomes:

$$\frac{E_{02}(s)}{E_{01}(s)} = -\frac{s}{R_3C_1\left[s^2 + \left(\frac{R_1^{+} R_2}{R_1R_2C_2}\right) s + \frac{1}{R_1C_1R_2C_2}\right]}$$
(30)

By using $E_{01}(s)$ as given by equation (14) and considering critical damping for expression (30), the output response becomes:

$$E_{02}(s) = \left(\frac{Q}{R_3 c_f^{R_2 a_1^{C_1}}}\right) \times \frac{S}{\left[S + \frac{1}{\sqrt{R_1 c_1^{R_2 c_2}}}\right]^4}$$
(31)

By studying equation (31) it can be seen that the effect of a second differentiation is the addition of a zero located at the origin. The time domain expression for equation (31) is given by:

$$E_{02}(t) = K_1 \times \frac{1}{2} \times e^{-\frac{t}{\tau}} \left(t^2 - \frac{1}{3\tau} t^3 \right)$$
 (32)

where
$$K_1 = \frac{Q}{R_3 C_f R_{2a} C_1^2}$$

and
$$\tau = \sqrt{R_1 C_1 R_2 C_2}$$

: :

The times to reach the positive and negative peaks can be found by taking the derivative of $e_{02}(t)$ with respect to t, equating it to zero and then solving for t. After some straightforward manipulations, the following equation results:

$$t^2 - 6\tau t + 6\tau^2 = 0 ag{33}$$

for which the two solutions $t_1 = 1.27\tau$ and $t_2 = 4.73\tau$ are respectively the times of the first and second peaks of the bipolar pulse.

By substituting the values $t_1 = 1.27\tau$ and $t_2 = 4.73\tau$ into expression (32) the peak values of $e_{02}(t)$ are found to be:

$$e_{02}(first peak) = + \frac{.262 \times K_1}{2}$$
 (34)

$$e_{02}(\text{second peak}) = \frac{.114 \times K_1}{2}$$
 (35)

It is interesting to know that:

$$\frac{e_{02} \text{(second peak)}}{e_{02} \text{(first peak)}} = \frac{.114}{.262} = .435$$
 (36)

This means that the secondary lobe of the bipolar pulse has a peak that is only 43.5% as big as the primary lobe peak. However, the areas under these two lobes should be equal.

In order to find the time for the bipolar pulse to cross the baseline, one makes expression (32) equal to zero and then solve the resulting equation for t. Once that is done, the crossover point is found to be at:

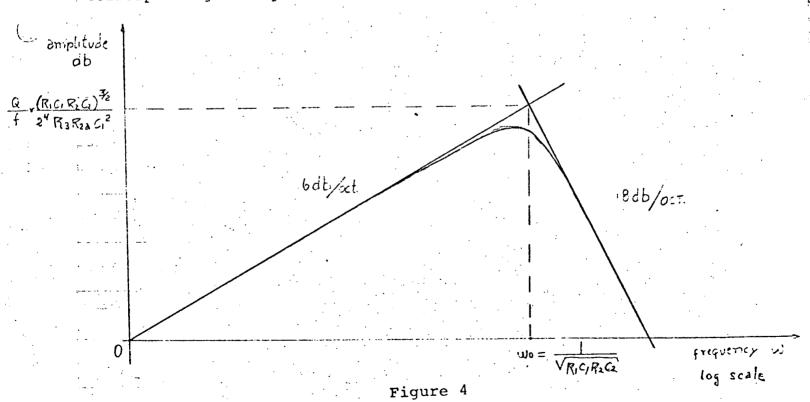
$$t = 3\tau \tag{37}$$

As in the case of the unipolar pulse analysis, expression (32) can be normalized with respect to amplitude and time constant, so that the following expression results:

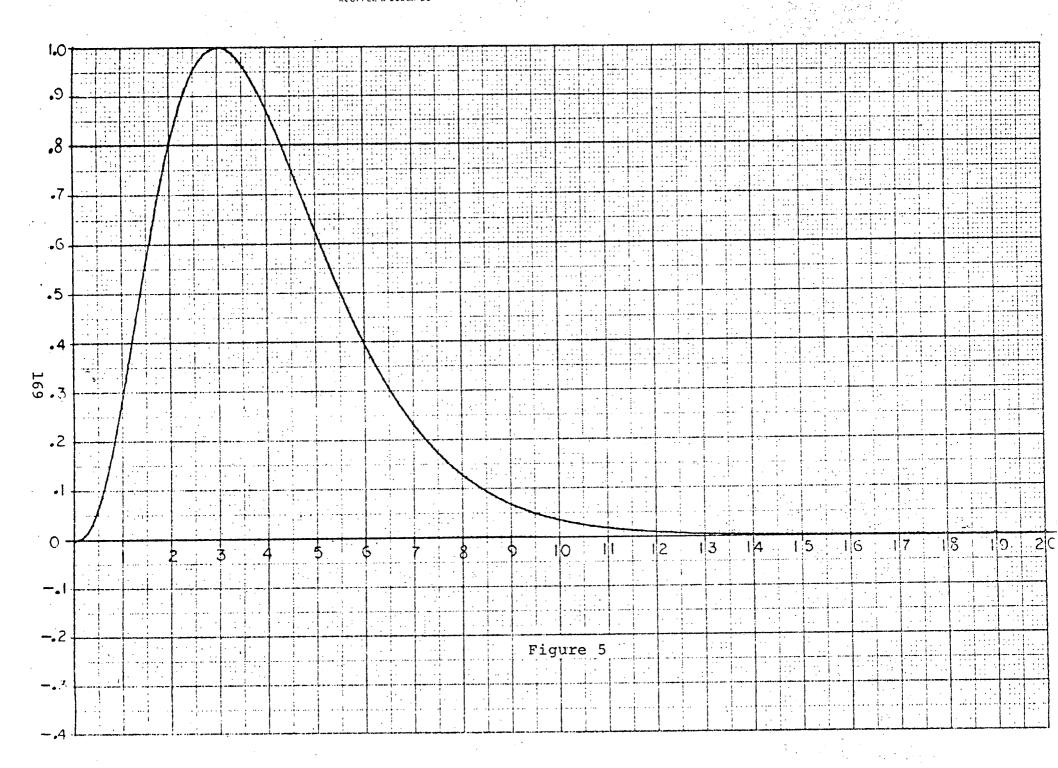
$$e_{02}(t)_{N} = e^{-t} \left(T^{2} - \frac{t^{3}}{3}\right)$$
 (38)

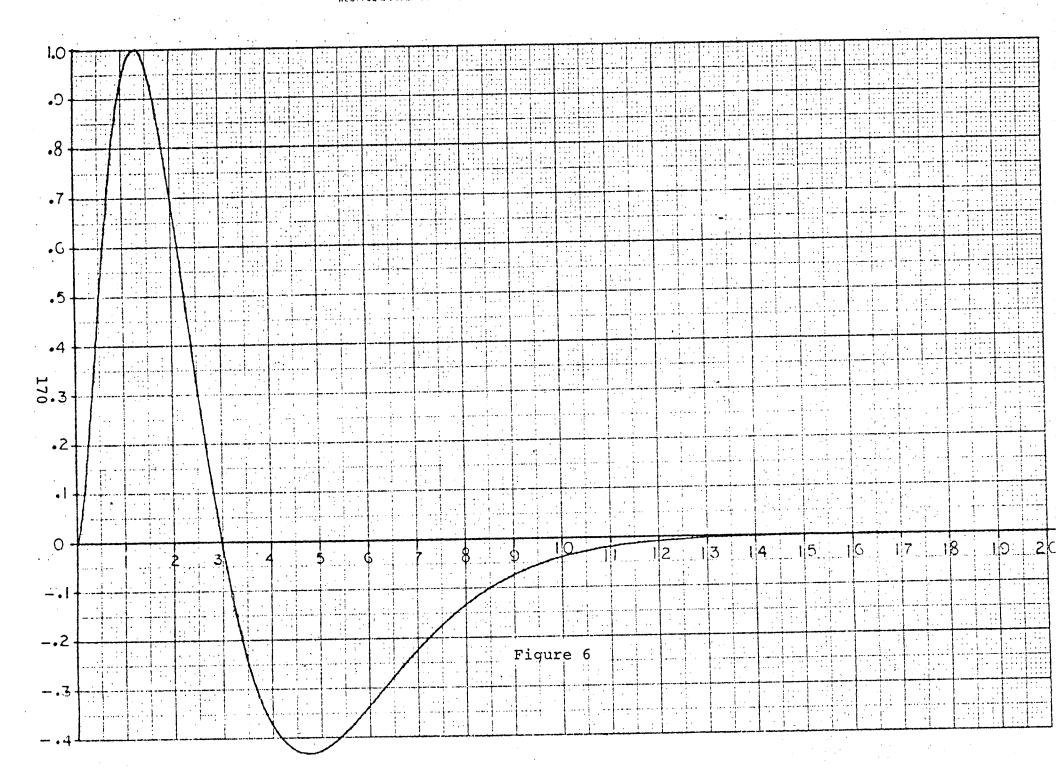
This expression was also solved for t, in increments of $\Delta t = .1$ from t = 0 to t = 20, using the H.P. 9100B calculator. The results are presented in the form of a table in figure 9 and of a plot in figure 6.

The frequency domain amplitude response for the bipolar pulse, corresponding to expression (31), is shown in the figure below.



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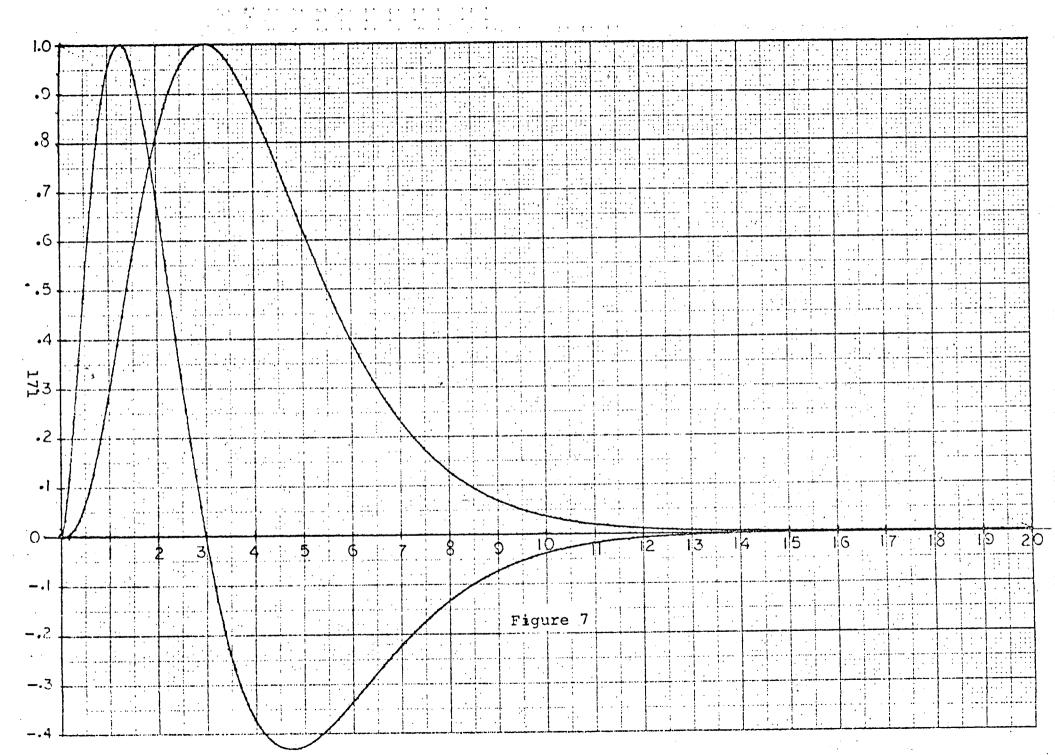


Figure 8
UNIPOLAR SHAPING

	e ₀₂ x100%		e ₀₂ x100%	٠	e ₀₂ x100%		e ₀₂ x100%		e ₀₂ x100%
t	e ₀₂ max	t	e ₀₂ max	.t	e ₀₂ max	t	e ₀₂ max	. t	e ₀₂ max
									0077
0.1	.0006	3.1	.9984	6.1	.3787	9.1	.0626	12.1	.0073
0.2	.0048	3.2	.9937	6.2	.3598	9.2	.0585	12.2	.0067
0.3	.0148	3.3	.9861	6.3	.3416	9.3	.0547	12.3	.0063
0.4	.0319	3.4	.9759	6.4	.3240	9.4	.0511	12.4	.0058
0.5	.0564	3.5	.9632	6.5	.3071	9.5	.0477	12.5	.0054
0.6	.0881	3.6	.9484	6.6	.2909	9.6	.0445	12.6	.0050
0.7	.1267	3.7	.9317	6.7	.2754	9.7	.0416	12.7	.0046
0.8	.1711	3.8	.9132	6.8	.2605	9.8	.0388	12.8	.0043
0.9	.2205	3.9	.8933	6.9	.2463	9.9	.0362	12.9	.0039
1.0	.2737	4.0	.3721	7.0	.2327	10.0	.0337	13.0	.0036
1.1	.3296	4.1	.8498	7.1	.2197	10.1	.0314	13.1	.0034
1.2	.3872	4.2	.8265	7.2	.2073	10.2	.0293	13.2	.0031
1.3	.4454	4.3	.8026	7.3	.1955	10.3	.0273	13.3	.0029
1.4	.5034	4.4	.7781	7.4	.1842	10.4	.0254	13.4	.0027
1.5	.5602	4.5	.7531	7.5	.1735	10.5	.0237	13.5	.0025
1.6	.6152	4.6	.7279	7.6	.1634	10.6	.0220	13.6	.0023
1.7	.6677	4.7	.7025	7.7	.1538	10.7	.0205	13.7	.0021
1.8	.7172	4.8	.6771	7.8	.1446	10.8	.0191	13.8	.0019
1.9	.7632	4.9	.6518	7.9	.1359	10.9	.0177	13.9	.0018
2.0	.8055	5.0	.6266	8.0	.1277	11.0	.0165	14.0	.0016
2.1	.8437	5.1	.6017	8.1	.1200	11.1	.0153	14.1	.0015
2.2	.8777	5.2	.5771	8.2	.1126	11.2	.0142	14.2	.0014
2.3	.9075	5.3	.5528	8.3	.1057	11.3	.0132	14.3	.0013
2.4	.9330	5.4	.5291	8.4	.0991	11.4		14.4	.0012
2.5	.9542	5.5	.5058	8.5	.0929	11.5	.0114	14.5	.0011
2.6		5.6	.4831	8.6	.0871	11.6	.0106	14.6	.0010
2.7	.9841	5.7	.4610	8.7	.0816	11.7	.0098	14.7	.0009
2.8	.9931	5.8	.4394	8.8	.0764	11.8	.0091	14.8	.0009
2.9	.9984	5.9	.4185	8.9	.0715	11.9	.0085	14.9	.0008
3.0	1.0001	6.0	.3983	9.0	.0669	12.0	.0078	15.0	.0007

Figure 9
BIPOLAR SHAPING

	e ₀₂ x100%		e ₀₂ x100%		e ₀₂ x100%		e ₀₂ x100%		e ₀₂ x100%
E	e ₀₂ max	t	e ₀₂ max	t	e ₀₂ max	t	e ₀₂ max	t	e ₀₂ max
				· .					
0.1	.0335	3.1	.0552	6.1	.3304	9.1	.0720	12.1	
0.2	.1171	3.2	.1066	6.2	.3188	9.2	.0677	12.2	.0087
0.3	.2299	3.3	.1539	6.3	.3072	9.3	.0636	12.3	.0081
0.4	.3561	3.4	.1971	6.4	.2955	9.4	.0597	12.4	.0076
0.5	.4842	3.5	.2362	6.5	.2839	9.5	.0560	12.5	.0070
0.6	.6056	3.6	.2713	6.6	.2724	9.6	.0526	12.6	.0065
0.7	.7148	3.7	.3026	6.7	.2611	9.7	.0493	12.7	.0060
0.8	.8081	3.8	.3300	6.8	.2499	9.8	.0462	12.8	.0056
0.9	.8833	3.9	.3539	6.9	.2390	9.9	.0433	12.9	.0052
1.0	9398	4.0	.3743	7.0	.2282	10.0	.0405	13.0	.0048
1.1	.9775	4.1	.3914	7.1	.2178	10.1	.0380	13.1	.0045
1.2	.9972	4.2	.4054	7.2	.2076	10.2	.0355	13.2	.0042
1.3	1.0001	4.3	.4165	7.3	.1977	10.3	.0332	13.3	.0038
1.4	.9877	4.4	.4250	7.4	.1881	10.4	.0311	13.4	.0036
1.5	.9619	4.5	.4310	7.5	.1788	10.5	.0290	13.5	.0033
1.6	.9242	4.6	.4346	7.6	.1698	10.6	.0271	13.6	.0031
1.7	.8766	4.7	.4362	7.7	.1611	. 10.7	.0253	13.7	.0028
1.8	.8209	4.8	.4359	7.8	.1528	10.8	.0237	13.8	.0026
1.9	.7 586	4.9	.4339	7.9	.1448	10.9	.0221	13.9	.0024
2.0	.6914	5.0	.4303	8.0	.1371	11.0	.0206	14.0	.0022
2.1	.6208	5.1	.4253	8.1	.1297	11.1	.0192	14.1	.0021
2.2	.5480	5.2	.4191	8.2	.1226	11.2	.0179	14.2	0019
2.3	.4742	5.3	.4119	8.3	.1159	11.3	.0167	14.3	.0018
2.4	.4004	5.4	.4037	8.4	.1094	11.4	.0156	14.4	.0016
2.5	.3276	5.5	.3947	8.5	.1032	11.5	.0145	14.5	.0015
2.6	.2565	5.6	.3851	8.6	.0973	11.6	.0135	14.6	.0014
2.7	.1877	5.7	.3749	8.7	.0918	11.7	.0126	14.7	.0013
2.8	.1217	5.8	.3642	8.8	.0864	11.8	.0117	14.8	.0012
2.9	.0591	5.9	.3532	8.9	.0814	11.9	.0109	14.9	.0011
3.0	.0000	6.0	.3419	9.0	.0766	12.0	.0101	15.0	.0010

EPS HOUSEKEEPING SPECIFICATION

General: To insure proper operation and maintenance of the EPS hardware a total of twenty (20) parameters must be monitored using two (2) spacecraft high level, low rate analog FM channels. Since the detectors' temperature controls the spectrometer's operating mode, a wide range detector temperature sensor will be monitored on one channel singularly. The other nineteen (19) monitors and two sync channels will be multiplexed onto the second TM channel.

The total complement of monitors is:

Parameter	Quantity
	•
+8	1
-8	1
+28	1
+5	. 1
- 5	1
-5 (reference)	1
+350 (bias)	1
Electronic Package Temperature	1
Wide Range Detector Temperature	1
Narrow Range Detector Temp. Monitor	1
Detector Leakage Current Monito	r 5
Electronic Noise Monitor	_5
Total	20

TM Interface: Each of the analog TM channels assigned to the EPS has the following characteristics:

Input Range	0 to +5 VDC
Input Impedance	≥ 1 MΩ
Input Shunt Capacitance	< 2.2 µf
Sample Rate	1.25/second
Sample Interval	< 20 µseconds
Sync Availability	None
Required Source Impedance	< 10ΚΩ
Keduited pource impedance	

Detailed Specifications: The analog multiplexer/buffer system will have the following end to end characteristics:

MT	output	range
----	--------	-------

Output Impedance

Short Circuit Duration
Integral Nonlinearity
Gain Stability

Zero Stability

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Tolerance to induced noise in signal line

Buffer Amplifier Input Bias Current

Power Requirement

Power Supply Rejection

Operating Temperature Range Survival Temperature Range 0.000 to +5.000 volts into 1 $M\Omega$

1.00 K Ω ± 0.1 Ω orig. temp. range

œ

<0.1%

<0.1% over the allowable package temperature</pre>

<5.0 mvolts over the
allowable package temp.</pre>

Must meet or exceed the requirements of tests CE02, CE04, RE01, RE02 and RS03 of MIL-STD 461A.

<10 nAmps over the allowable temperature range.

@ +8 VDC

@ -8 VDC

@ +5 VDC

No loss in monitor characteristics for a + 1 volt variation in any supply voltage.

-25°C < T < +25°C

-50°C < T < +50°C

Design Responsibility: The housekeeping subsystem engineer will have the responsibility of designing all components of the analog system with the exception of:

- A. The five leakage current monitors
- B. The noise monitor and its associated input multiplex circuitry.

However, in these two cases the housekeeping subsystem engineer will determine output specifications necessary to properly interface with the ensuing multiplexer.

Location: The entire housekeeping subsystem with the exception of the five leakage current monitors and the multiplexed noise monitor will be located in the Data Processor module.

Detailed Sensor Specifications

A. Wide range detector temperature sensor

1. Range -100°C to +100°C

2. Accuracy* ±5°C

B. Electronics Package Temperature Sensor

1. Range -100°C to +100°C

2. Accuracy* +5°C

C. Narrow Range Detector Temperature Sensor

1. Range -25°C to +30°C

2. Accuracy* ± 0.5 °C

D. Leakage Current Monitors

1. Range 0 amp to 5 amp

2. Accuracy* ± 5 namp

E. Resolution Monitor

1. Range 0 Kev (FWHM) to 100 Kev (FWHM)

2. Accuracy* ± 1 Kev (FWHM)

F. Voltage Monitors

1. Range +5.00 +4.50 volts maximum +3.75V Nominal vin

2. Accuracy

+0.5%

G. Positive Analog Sync

1. D.C. Output*

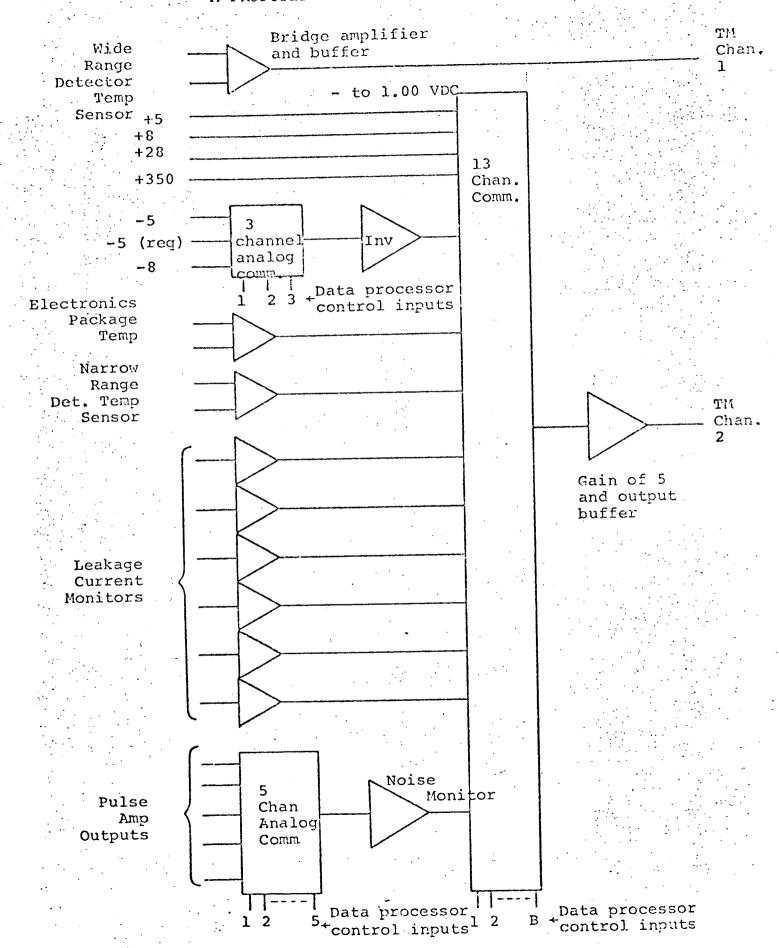
 $+5.000 \pm 0.01 \text{ volt}$

H. Ground Analog Sync

1. D.C. Output*

 $0.000 \pm 0.01 \text{ volt}$

*Indicates accuracy over the entire environmental range.



3.2.1.5.C Mission Interface (Times of Hardware Operation)
The determination of mission profiles are defined by the Skylab Program Office. Certain requirements of the mission total times are defined by the ICD. The ability of the EPS to meet these requirements and to operate in hostile environment for more than the required mission times is reflected by the FMEA and the Qualification Test Report. A mean-time-between-failure analysis of the original concept of an operation time of two years is met. A worse case rough analysis of the entire system estimates a mean-time-to-failure (MTTF) of 21,500 hours. This MTTF does not include the detectors.

3.3.1.7.1 Structural Factors of Safety

The original design of the EPS incorporated factors of safety as required to meet this requirement. After the higher test levels were received, there was some doubt as to whether the design had a sufficient factor of safety. A computer calculation performed very recently indicates that the EPS design continues to meet this requirement even when stressed to the higher test levels.

3.3.2.4 Electrical Connectors - Pin Assignment and Pin or Socket Selection

All electrical connectors used in the EPS were analyzed during the Single Point Failure Analysis and the Failure Mode Effects Analysis (FMEA). The requirements of paragraph 3.3.24 of MSC-KA-69-44 were met with emphasis on mishaps due to design, operational and procedural deficiencies, environmental conditions, personnel error, and normal equipment operation.

a. All connectors in slices are keyed and cannot be mated wrong. Also connectors (slices) cannot be de-mated with power on instrument. Hence, no hazard.

\$2.1

b. A statement indicating 'power must be off' during installation in spacecraft will be added to installation and handling procedures. 3.3.2.6 Material Detrimental to Electrical Connectors

Non-metallic materials used on the EPS program were surveyed
by LEC R&QA for compatibility. The source of this analysis
is the non-metallic manual and NASA/MSC personnel. No
material used on the EPS program is considered detrimental
to electrical connectors. No metallic materials report is
required by the contract; therefore, this effort is not
documented.

No materials are used adjacent to exposed electrical contact surfaces. The only material used on or near the connector (but not near exposed contact surfaces) is PR 1538 polyurethane conformal coating on leads and rear of connector bodies. The only fluids used in cleaning are isopropyl alcohol and freon.

3.3.2.7 Electrical and Electronic Piece Parts

A fully documented parts program is available for review. This includes procurement specifications, screening specifications, EEE Parts list, and procurement requirements. The documentation meets all the requirements of this paragraph. These documents have been reviewed by NASA/MSC Reliability and Quality Assurance with no comments. The referenced documents are available for review.

3.3.2.9 Protection of Electrical and Electronic Devices
Electrical and electronic devices used on the EPS have protection against reverse polarity. Adequate diodes have been installed for circuit protection. A protection circuit has been designed to protect the instrument from spurious voltages from the spacecraft as well as protection from feedback voltages into the spacecraft from the instrument.

3.3.4 Debris Protection

a. Electrical circuitry - prevent unwanted current path being produced by debris

The EPS consist of an inner subassembly containing four "slices" (modular aluminum housings containing printed wiring boards and electronic subassemblies encapsulated in their own aluminum housings), which is shock-mounted within an outer mechanical housing. The top plate containing the detector assemblies is mounted onto the inner assembly leaving a gap around the upper edge of the outer housing to allow any movement due to the vibration isolators. This gap is concealed by a flexible silicone skirt to prevent open access to the inner assembly and act as a reflective shield for thermal control yet not affecting the controlled thermal conduction between the outer housing and the top plate/inner electronics assembly. contaminants and/or debris could penetrate the outer housing only through this gap and reflective shield. When the four slices are mated, there are covers between each printed wiring board and its mating printed wiring board. This results in an assembly which is sealed except for access holes to test point jacks in two ends of the upper three slices. access hole presents access to only one cavity and printed wiring board. The printed wiring boards are conformally coated with PR 1538, a polyurethane, on both sides as protection against moisture, contaminants, etc. Each printed wiring board was designed to mount in a separate cavity shielded from any other cards or electronic subassembly. All wire or contact terminations are conformally coated or encapsulated.

b. Critical mechanical items covers and containers

The eight vibration isolators are contained within the EPS outer housing in pockets with access when required through covers. The detectors are enclosed within hermetically-sealed housings for protection and selection of energy levels. The EPS is supplied with a protective glass fiber cover over the upper half of the experiment which is secured in a shipping and testing stand for protection until installation in spacecraft where a boost cover is employed. All electronic subassemblies are mounted in compartments in slice assembly configurations, which makes any subassembly inaccessible without dismantling the inner assembly.

d. Threaded fittings and fasteners

All fasteners used in the EPS are used with heli-coil screwlock inserts to positively secure threaded members against loosening caused by vibration and shock and to protect tapped threads against wear and damage in use. All mechanical and electro-mechanical assemblies are cleaned per MSC C-8, Class A. All mechanical parts are packaged per MSC-SPEC-C-12A or MSC10M01836 Paragraph 5.1 and 5.2 (for parts with thermal control coatings) until assembly in a controlled access area or clean room. Upon final assembly all subassemblies are cleaned per MSC C-8, Class A. This cleaning prevents contaminants and/or debris in tapped holes or other limited access areas which could loosen and contaminate areas of the EPS. No self-tapping screws, bolts, or quick-acting fasteners are used. In all four slices, where tapped holes are not blind, they are open outside the hardware so that debris will not be released inside.

3.3.6.1 Test Points

1

During the early phase of the development of the EPS it was established that there would not be any testing of the EPS after it was installed on the spacecraft other than observing the output of the instrument thru the normal telemetry system. Therefore, all test points contained within the EPS are for laboratory use only.

3.3.6.2 Test Equipment

Development analysis of the Bench Test Equipment (BTE) was made based on the ICD and EPS requirements. The approach was to make the overall acceptance test procedures as simple as possible. The BTE simulates the spacecraft interface such that all inputs/outputs to the EPS are tested in such a way to guarantee proper minimum/maximum level signals. The BTE has been designed and proved by tests and operation.

There are three sources of power in the BTE which are used to power the various interfaces as well as the EPS itself. The computers internal 6 volt supply powers all logic used in the BTE, the ±15 volt dual supply powers the input interface board and the 8 channel digital to analog converter, and the 25 to 30 volt supply is used exclusively to power the EPS. All power supplies have internal current limiting and over voltage protection to completely protect the EPS and the various subassemblies of the BTE from damage due to power supply malfunction.

3.3.7 Single Point Failure

The "Electron-Proton Spectrometer Single-Point Failure Report", EPS-424 is presented to satisfy this requirement.

ELECTRON-PROTON SPECTROMETER SINGLE-POINT FAILURE REPORT

LEC Document Number EPS-424

Prepared by

Lockheed Electronics Company, Inc.
Houston Aerospace Systems Division
Houston, Texas

Under Contract NAS 9-11373

For .

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

August 1971

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SINGLE-POINT FAILURE REPORT

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SINGLE-POINT FAILURE ELECTRON-PROTON SPECTROMETER

1. PURPOSE

A single point failure summary identifies the critical areas that will, as a result of a single assembly failure, cause a complete or partial loss of the experiment, questionable data, or complete loss of data acquisition. The following information must be delineated:

Corrective action taken

Experiment objective and,

Justification for retaining a single point failure

2.0 CORRECTIVE ACTION

The requirements of the Electron-Proton Spectrometer (EPS), such as weight to power limitations, logic, and electronic circuit packaging, limit redundant circuits and components. As a result, corrective action to reduce the possibility of critical failures is applied through careful selection of the best available high-reliability components, screen and burn-in tests, and derating of components used in the circuits.

3.0 JUSTIFICATION FOR RETAINING SINGLE POINT FAILURES

Space and weight are important factors in the EPS; consequently, there are no redundant logic and electronic circuits. Most of the components used have a long life expectancy. Hi-Rel micro circuits have a predicted Mean-Time-To-Failure (MTTF) rate of five to ten years.

Discrete components have been selected to the high reliability requirements of MIL-STD 883, MIL-STD 202, established reliability programs, or have been screened to Hi-Rel requirements. Component derating further increases the life span. Worst case analysis of the entire system estimates a MTTF of 21,500 hours. This is several times the hours required by mission objectives. The above MTTF does not include the detectors.

4.0 MISSION OBJECTIVE

To measure electron and proton radiation the instrument accepts charge pulses from the detectors. These pulses are shaped and amplified and trigger discriminators at different energy levels. The discriminators outputs are fed into the data processor for telemetry processing.

5.0 SINGLE-POINT FAILURE ANALYSIS

5.1 DATA PROCESSOR

5.1.1 Counter Memory

Ten channels of input information from the discriminators are processed and shifted to the Sequence Control and Digital Data Compressor. The data consists of 4 channels of electron and 6 channels of proton information. A failure of any one channel would result in 10 percent loss of data critical to the mission.

5.1.2 Sequence Control

A failure of the Sequence Control could result in no data output from the Data Processor, including housekeeping events. All common Digital Data Output, Column Sync, Word Sync, Multiplexer Address Advance, housekeeping gates, A/D Converter Start, etc., are dependent on the Sequence Control.

5.1.3 Digital Data Compressor

Failures in the Digital Data Compressor could result in no output data from the Word Sync Generator and Output Buffer, resulting in no data readout to telemetry.

.5.1.4 Multiplexer A/D Analog Section

This section of the Data Processor handles housekeeping events. A failure in any part of the Multiplexer would have very little effect on the mission critical data.

5.1.5 Multiplexer A/D Converter Logic

A failure in this section would not effect mission critical data.

5.1.6 Word Sync Generator and Output Buffer

Failure in this section of the Data Processor could result in complete loss of output to telemetry.

5.1.7 Filter Module

This module contains one Output Filter for each telemetry data channel. Failure of a data point filter would result in no data out on one telemetry data channel.

5.1.8 Voltage Monitor

A failure of the Voltage Monitor would have negligible effect on the mission critical data of the EPS.

5.2 LOW VOLTAGE POWER SUPPLY

5.2.1 Preregulator

Failure of the Preregulator could result in erratic output or no output from Preregulator with a possible loss of power to the EPS.

5.2.2 Core Driver

A failure of this driver would result in erratic operation, loss of switching or possible loss of power to the EPS.

5.2.3 Transformer Assembly

A failure of the Transformer Assembly could result in possible loss of a portion of the power to the EPS or possible loss of all low voltage power.

5.2.4 Discriminator Reference Regulator

A failure of the Regulator could result in reduced power input to the Transformer Assembly, power loss to transformer, or possible loss of all low voltage functions.

5.2.5 Inductor Assemblies

Failure in an Inductor Assembly could result in erratic output or loss of one or more of the power supply outputs.

5.3 DETECTOR BIAS POWER SUPPLY

Loss of Detector Bias would result in no primary data.

Detectors would not function. Secondary data (housekeeping information would still be obtained).

5.4 HEATER

5.4.1 Heater Control

Loss of the Heater Control Circuit would result in a possible temperature variation that could cause loss of or erroroneous data.

5.4.2 Heater Circuit

The Heater Circuit is not normally on during EPS operation. During down or storage time the effect of failure in the Heater Circuit would depend on orbit mode. At Beta 0° no effect would be noticed. At Beta 73° the EPS survival could be effected.

5.5 NOISE MONITOR (5 each)

Failure of the Noise Monitor function would result in a loss of housekeeping events. Effect on the operational data of the EPS would be minor.

5.6 LEAKAGE CURRENT MONITOR (5 each)

Failure of the Leakage Current Monitor would cause a loss of housekeeping events. This event would have minor effects on the primary data received from the EPS.

5.7 PREAMPLIFIER (5 each)

Failure of any one Preamplifier would cause a loss of 20 percent of the primary data inputs to the Data Processor.

5.8 PULSE AMPLIFIER (5 each)

Failure of any one Pulse Amplifier would result in the loss of 20 percent of the primary data to the data processor.

5.9 PULSE HEIGHTS DISCRIMINATOR (5 each)

Failure of any one of the Pulse Height Discriminators would result in 20 percent loss of primary data to the Data Processor.

5.10 INPUT FILTER

Failure of the Input Filter would cause the loss of either all data, primary data only, or Heater Control only.

5.11 DETECTORS

If one of the Detectors failed, two channels of information would be lost (1 Electron, 1 Proton). Twenty percent of mission critical data would be lost.

5.12 CONNECTORS

5.12.1 1 PPS

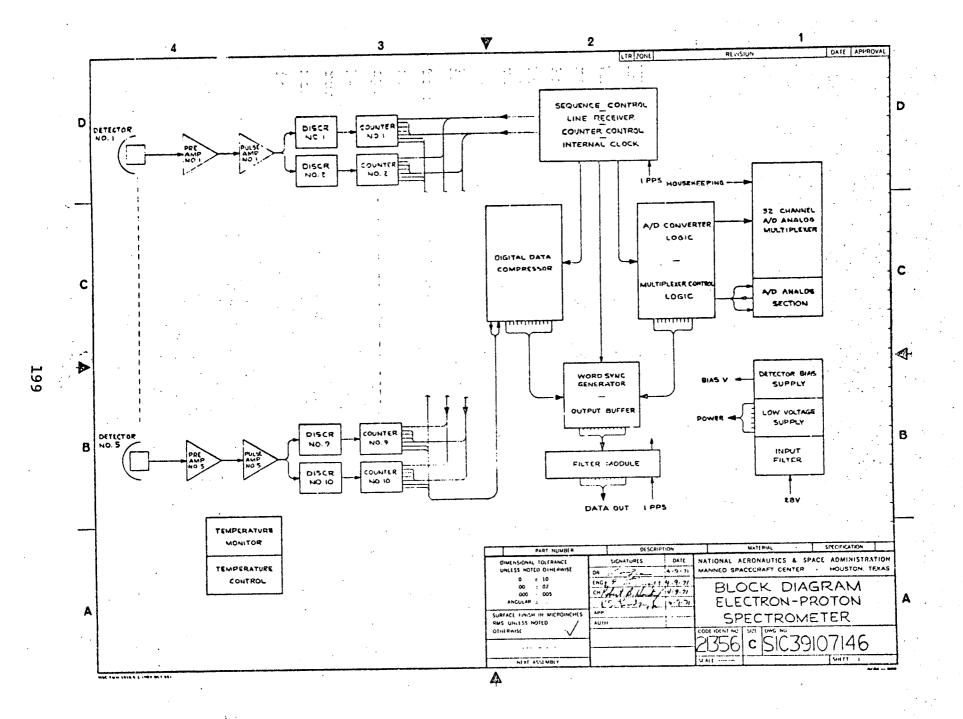
Clock Sync Pulse for cycling data and timing for data processor. Failure of 1 PPS would result in loss of all data.

5.12.2 Input, Detector Bias Supply

Failure of input to bias supply would result in loss of detector operation.

5.12.3 Input 28 Vdc To Instruments

A failure of input power would result in loss of all power to instrument.



3.3.9 Selection of Specifications and Standards:

Parts and material conforming to various Government specifications were selected in the precedence required. Certain parts required for the EPS were not available as Established Reliability Parts. Procurement of these parts was handled in three different ways, i.e.

Vendors Specifications,
Procurement Specifications, and
Screen and Burn-In.

VENDORS SPECIFICATIONS

When vendors specifications were available, they were reviewed. If the specifications complied with NASA Reliability Requirements for flight hardware, parts were procured on this basis. Specification Test Sheets are available on request on these parts.

PROCUREMENT SPECIFICATIONS

To meet the requirements for High Reliability Parts when suitable vendors specifications were not available, procurement specifications were written to ensure that vendors' testing programs would be upgraded to qualify their parts under NASA requirements for High Reliability Flight parts. The Procurement Specifications were published in EPS-239, a copy of which is attached.

SCREEN AND BURN-IN SPECIFICATIONS

Some parts did not lend themselves to these approaches and were purchased as commercial and JAN parts and subjected to a Screen and Burn-In to qualify them as Hi-Rel Parts. The Screen and Burn-In was conducted at the NASA White Sands Test Facility. These tests were designed to meet Specification for Semiconductors, MIL-S-19500; Test Requirements for Semiconductors, MIL-STD-750; Test Methods for Electronic Parts, MIL-STD-202D; and MSC Reliability Parts Program Requirements, MSC-3515. The Screen and Burn-In Specification are included as a part of EPS-239.

EPS FLIGHT UNIT PROCUREMENT AND RELIABILITY REQUIREMENTS

LEC Document Number EPS-239

Revision A. Added EPS-356 and page 2-9
Revised pages 2-5, 2-6, and
2-7

Prepared by
Lockheed Electronics Company
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for

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EPS FLIGHT UNIT PROCUREMENT AND RELIABILITY REQUIREMENTS

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EPS FLIGHT UNIT PROCUREMENT AND RELIABILITY REQUIREMENTS

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SECTION 1

EPS FLIGHT UNIT PROCUREMENT AND RELIABILITY REQUIREMENTS

INTRODUCTION

This document brings together a compilation of the reliability requirements for parts/components for use in (procurred for) the Electron/Proton Spectrometer (EPS) Qualification and three flight units. The reliability data contained herein provides a visibility of parts selection and reliability requirements for the EPS to insure a parts program that will meet the extended life criteria of the EPS, and to meet the NASA/MSC reliability requirements.

A few parts, which meet the design requirements of certain aspects of the instrument, could not be obtained in the quality grade of established reliability parts. For these particular parts, which require screening and extra testing, applicable procurement and screen and burn-in specifications are included in this document.

Cognizant personnel associated with the reliability and quality assurance aspects of the EPS program are urged to bring to the attention of the LEC Reliability Engineer any errors or omissions in, or modifications of any statements or requirements contained herein so that appropriate corrective action can be made in a timely manner.

SECTION 2

EPS FLIGHT UNIT COMPONENTS RELIABILITY REQUIREMENTS

The following list provides a visibility of the parts selection and the reliability requirements required for the procurement of parts/components for the EPS.

EPS FLIGHT UNIT COMPONENTS RELIABILITY REQUIREMENTS

	t	1			•	•					
	PR #	Description	Mfr. Number	Source	Federal Spec./ Mil Spec	LEC Spec	Mfr. Spec	Other Specs	Gov't Source Insp.	Lot Trace- ability	C of C require
•	U055	Solder	44	Kester	QQ-S-571D					х	х
	U153	Detectors, 20-505		SSR		EPS-125				x	х
	U154	Detectors, 20-606		SSR		EPS-125 .				x	x
	U155	Detectors, 20-707		ssr .		EPS-125				х	х
	U156	Detectors, 25-808		SSR		EPS-125				x	x
	U157	Detectors, 25-909		SSR		EPS-125				x	х
	บ158	Detectors, 20-404	•	SSR		EPS-125 .				x	x
	U159	Drift measurements silicon ingot, de- tectors for 30-404		SSR '		EPS-125				x	x
	U166	Connector, 20-505	ME414-0120 -0021	Kierulf	Not used		MC414- -365,		х	x	x
•	U167	Connector, 20-606	ME414-0120 -0021	Kierulf	Not used		Rev. C & PDC- la,-2,		х	x	x
	U168	Connector, 20-707	ME414-0120 -0021	Kierulf	Not used		-3A &		х	x	х
-	บ175	Connector, Coax Receptacle	CX-RB-M-0	ITT Cannon Greymar				100% visual inspection; insulation resistance, dielectric withstanding voltage tested		x	x
	. ,										

EPS FLIGHT UNIT COMPONENTS RELIABILITY REQUIREMENTS

			•						,		t
		Description	Mfr.	. 1	Federal Spec/ MIL Spec	LEC Spec	Mfr Spec	Other Specifications	Gov't Source Insp	Lot Trace- ability	C of C require
-	-	Connector, Coax Receptable	CX-RB-M-0	ITT Cannon Greymar				100% visual inspection; insulation resistance, dielectric withstanding voltage tested		x	x .
	U177	Connector, Coax Receptacle	ск-пв-м-0	ITT Cannon Greymar				100% visual inspection; insulation resistance, dielectric withstanding voltage tested		x	x
	ບ178	Connector; Coax Receptacle	CX-RB-M-0	ITT Cannon Greymar				100% visual inspection; insulation resistance, dielectric withstanding voltage tested		х	x
	U179.	Connector, Coax Receptacle	CX-RB-M-0	ITT Cannon Greymar		•		100% visual inspection; insulation resistance, dielectric withstanding voltage tested		x	x
;	U180	Connector	ME414-0120 -0021	Kierulf Elect.	Not used		MC414- 0365, Rev. C		х	X	x
	U161	Connector	ME414-0120 -0021	Kierulf Elect.	Not used		& PDC- 1a,-2, -3A&-4		X	x .	X
	U218	Thermistor, 4.7K +5% @ 25°C	RTH06BS472J	Victory Eng.	MIL-T- 23648			168 hour burn-in @ 0.2W, @ 85°C: 100% elect. test req. after burn-in: all units must meet prior eselectrical & temperature parameters	st.	x	x
	U219	Potentiometer	3260H-1-XXX	Bourns	MIL-R- 27208 (RT26 MIL-R- 22097 (RT27					x	X

EPS FLIGHT UNIT COMPONENTS RELIABILITY REQUIREMENTS

				١٠.					•		
	20.		Mfr. Number		Federal Spec/ MIL Spec	LEC Spec	Mfr Spec		Gov't Source Insp	Lot Trac- ability	C of C required
	PR #	Description Amplifier	SE526K/883		MIL-STD883			X-ray U-221-1 893- Level A testing		x	х.
	U221	Amplifier	HA2-2520-2	Harris	MIL-STD883					×	Х,
		Multiplexer, 16 ch	HS9-1000-2	Harris -	MIL-STD883	\$				x	X
	U222	Inductor, 20 mh	526-2930-130	Collins	MIL-T-27B			168 hr burn-in at rated power & 125°C		x	X
	U223	Transistor, PNP	2N5333	Texas Inst				Screen and Burn-in at W.		x	x
	U224	Transistor	2N4878	Intersil				Screen and Burn-in at W.		Х	. x
	υ 22 5	FET	JAN2N2609	Teledyne	MIL-S- 19500					×	X
	U226	Transistor	SS3520	Motorola	MIL-S 19500			h _{fe} >100@2ma, 1kHz & 15V; h _{FE} =min 25; f _T >500mHz@1M	P	х	x
)	ບ226	Transistor	JAN2N3811	Motorola	MIL- 19500			Screen and Burn at W.S. h >10002ma, lkHz & 15V; hfe=min 25; f _T >500mHz9lM	A	x	x
	U231	Capacitor, Var- iable 0.8-2.5 pf	RVC-12	JFD		EPS-232		Screen and Burn at W.S.		x	x
	บ232	Transistor	JANTX2N	Texas Inst	MIL-S- 19500					x	х
	U232	Diode	JANTXIN	Texas Inst	MIL-S- 19500	·				x	X

EPS FLIGHT UNIT COMPONENTS

, RELIABILITY REQUIREMENTS

			•					•			
P	R#	Description	Mfr. Number		Federal Spec/ MIL Spec	LEC Spec	Mfr. Spec	Other Specifications	Gov't Source Insp.	Lot Trace- ability	C of C required
υ	233	Diode, 1N4567A	1N4567A 1N4901A	Dickson	MIL-S- 19500/159, 127			To satisfy TX requirements		x	х
ប	234	Diode	JANTX1N 4942,UT4010	Unitrode	MIL-S- 19500	·		To satisfy TX require-		х	x
U	235	Amplifier	LM108/883 µA723/883	Adv. Micro	MIL-Std883	3				x	x
ט	236	Inductor, 100µhy	PD-100	Nytronics		EPS-167		ORDER CANCELLED.		х	x .
U	1237	Filter	8332-125, 126, 201	Potter	MIL-F- 15733		8000	Environmental & burn-in (Potter spec dated 1970)		x	x
	1246	Capacitor	828-1KV- X5T-103M	Erie	MIL-C- 11015D	EPS-121	·	Cap - offset leads - ant. corona undercoating - no to be dipped in wax, 100 visual. Corona start vol- tage to be measured.		x	х
ָט	247	Diode	5082-2123	Hewlett Packard	MIL-S- 19500, MIL-STD 750			To be tested to Hewlett Packard's specification sheet for Hi-Rel appli- cation		x	x
U	1248	Connector	MCDM1	Microdot	MIL-C- 24308, MIL-C- 83848		,			x	x
U	249	Magnetic Cores	52002-1A 52134-1A 55037-W4 55040-W4 55051-W4 55121-W4 80530-1A	Magnetics, Inc.	NASA QA Accept- ance					x	x
i	:					٠.,	. ,				

EPS FLIGHT UNIT COMPONENTS RELIABILITY REQUIREMENTS

į	·		Mfr.		Federal Spec/ MIL Spec	LEC Spec	Mfr.	Other Specifications	Gov't Source Insp.	Lot Trace- ability	C of C required
į	PR#	Description	Number		MIL Spec	nac spec	- Disco			х	x
1	J250	Magnet Wire	80XX	Belden						x	x
1	U251	Resistor, Film	MK132	Caddock	MIL-R- 55182	EPS-116	i	Reliability and QA Data required.			
	U 25 2	Resistor, Carbon	RCR07, RCR20	Allen- Bradley	MIL-R- 39008		; ;	Established Reliability		X	x
	U253	Capacitor	CKR05, CKR06	Kemet	MIL-C- 39014			Established Reliability		X	X
	U254	Integrated Circuits (TTL)	SNC54, SNH54	Texas Inst	MIL-STD 883, Level A		! !			×	X
	U257	Connector	NBH16-26PH	Deutsch	NASA 40M 39569		1	Hermetic seal jam nut mounting, environmental resisting 200°C		х	x
	u261	Resistor	1712-100 meg	Caddock	MIL-R- 55182	EPS-168		Reliability and QA Data required.			
	U262	Transistor	SS3515	Motorola	MIL-S- 19500			Selected from JANTX2N 3251A. hfe=150 min @ Ic=lma: VCE=10V & f=		x	X
								1KHz; FT=35-mHz min @ IC=-3mA: VCE=10V & f= 100 mHz: Cob=5pfmax @ V =8V:IE=0mA and f=100kHz	cb •		
	U262	Transistor	SS2638H	Motorola	MIL-S- 19500,			Selected from MM4261H: BVCEO=20Vmin @ I _C +10mA hfe=55 min & 150 max		x	x
					MIL-STD 883, Level A			@ I _C =4mA DC and V _C E=5V C _{Cb} =2 pf max V _{CB} =1VDC			
							!				

'EPS FLIGHT UNIT COMPONENTS 'RELIABILITY REQUIREMENTS

1263 R	Resistor Capacitor	RNC50, RNC55 RC33, RC12,	Mepco	MIL Spec MIL-R- 55182C		Established Reliability,		х	х
1264 C	Capacitor				1	F tolerance, R or S failure rate			
	į	RC37		MIL-C- 39014		 Temp. Cycling, 100 hr burn-in @ 200% rated power, DR, IR, Dissi- pation factor		x	x
J269 T	Fransistor	JANTX2N2484		MIL-S- 19500/376				x	. x
J270 V	Voltage Comparator	LM111/883	Advance Micro	MIL-STD 883, Not.B		MIL-STD 883 level A & X-ray		X	X
0271 S	Switch	DAS2132	Dickson	MIL-STD 883, Not 2 Met. 5004				x	Х
U279 C	Connector (Coax)	031-0070 -001	Microdot			Insulation Resistance, Dielectric Withstanding Voltage, Contact Resis- tance and Vibration to be performed 100%.		x	x
	Capacitor, Polycarbonate	x483W4	TRW	MIL-C- 18312, MIL-C- 19978B		Hi-Rel testing - tempera ture & imersion cycling, 240 hour burn-in-@ 125°C		x	х
บ287 ร	Sensistor	TG51	Texas Inst	MIL-T- 23648		Temp Cycling, Leak Test & 48 hour burn-in @ 150°	q	x	x
-	Thermal heater Dissipator	TXP0508ND TX0561ND	Int'l Elec Int's Elec			Temp Cycling, 168 hr burn-in		x x	x x

EPS FLIGHT UNIT COMPONENTS RELIABILITY REQUIREMENTS

DR #	Description	Mfr.	•	Federal Spec/ MIL Spec	LEC Spec	Mfr. Spec	Other Specifications	Gov't Source Insp.	Lot Trace- ability	C of C required
U303	Transistor	SSC6113	Texas Inst	MIL-S- 19500/ 1385			Selected from JAN TX 2N4858. Gm(min)=18000 micro-mhos: VGS Range =.3V to .6V @ IDS=10mA & VDS=4V.		х	х
U318	Capacitor	Т210	Kemet	MIL-C- 39003	:		Established Reliability		х	х
U324	Inductor	MS90538-12	J.W. Miller Co.	MIL-C- 15305			Temp. Cycling & 168 hr burn-in at rated power.		X	х
บ320	Chromel A Wire	242-594 424-610	Curtin Scien. Co.	Not used					x	x
บ327	Socket	332223	Amp Inc						х	x
U332	BEO Mounting Disc	D-350-19	Thermalloy						x	x
U333	Resistor	RWR-81S R500-FR RWR-81S 1R-300FR	Dale	MIL-R- 39007B			R failure rate		X	х
บ337	Gold Dumet Leads				ļ.				x	x
บ356	Resistors	RCR05	Allen- Bradley	MIL-R- 39008	,		Established Reliability		x	x
บ357	Resistor	RNC50,RNC55	Мерсо	MIL-R- 55182C	·		R or S Failure Rate		x	×
U358	Capacitor	RC10C	uscc	MIL-C- 39014			Temp Cycling, 168 hour burn-in, dissipation factor, insulation resistance, dielectric withstanding voltage.		x	x

EPS FLIGHT UNIT COMPONENTS RELIABILITY REQUIREMENTS

	PR	Description	Mfr. Number	Source	Federal Spec./ Mil Spec	LEC Spec	Mfr.	Other Specification	Gov't Source Insp.	Lot Trace- ability	C of C Required
İ	No. U429	Carbon Resistor	RCR07G130JP	Allen Bradley	MIL-R- 39008		•	Established Reliability		. · x	x
	ช375	Capacitor	CKR05BX	Kemet	MIL-C- 39014			Established Reliability		x	·x
	U510	Capacitor	T210D	Kemet	MIL-C- 39003			Established Reliability		x	х
	U497		RC33	uscc	MIL-C- 39014	:		High Rel. Testing		х	· x
	บ450	Transistor	JAN2N3811	Motorola	MIL-S- 19500	EPS-129		Screen & Burn-in White Sands Test Facility Replacement for failed		X	X
717	บ 4 6 2	Transistor	2n4848	Intersil		EPS-175		parts on screen & burn-in High Reliability pre seal inspect tested to - EPS-175 (screen and burn- Replacement of commercial version	in) -	x	x
	บ372	Integrated Circuit	U4L96L 051/883	Advance Micro	MIL-STD- 883/Level	A		High Reliability Tested		x	x
	U480	Inductor	8336-001	Potter	MIL-C- 15305			High Reliability Tested		х	x
	U511	Inductor	8336-001	Potter	MIL-C- 15303			High Reliability Tested		x	x

PROCUREMENT SPECIFICATION

FOR

LITHIUM-DRIFTED SILICON DETECTORS

Document Number EPS-819
7-26-72

Prepared by

Lockheed Electronics Company, Inc.
Houston Aerospace Systems Division
Houston, Texas

Under Contract NAS 9-11373

For

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

PROCUREMENT SPECIFICATION

FOR

LITHIUM-DRIFTED SILICON DETECTORS

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1.0 SCOPE

This document defines the electrical, mechanical and environmental specifications and initial acceptance tests for the procurement of lithium-drifted silicon detectors for use on the Electron-Proton Spectrometer (EPS) being developed by Lockheed Electronics Company for NASA/MSC under Contract NAS 9-11373.

2.0 APPLICABLE DOCUMENTS

MIL-STD 750A, Test Methods for Semiconductor Devices

MIL-STD 202D, Test Methods for Electronic and Electrical Component Parts

MSCM 8080, Manned Spacecraft Criteria and Standards

3.0 COMPONENT SPECIFICATIONS

3.1 Mechanical

3.1.1 General

The detector elements shall be cubical in shape. They shall be manufactured of lithium-drifted silicon.

3.1.2 Physical Mounting

The silicon cube shall be bonded to an aluminum oxide substrate which in turn is bonded to a TO-5 transistor header as shown in Figures 1 and 2. The header shall be supplied with a steel can (unsealed)

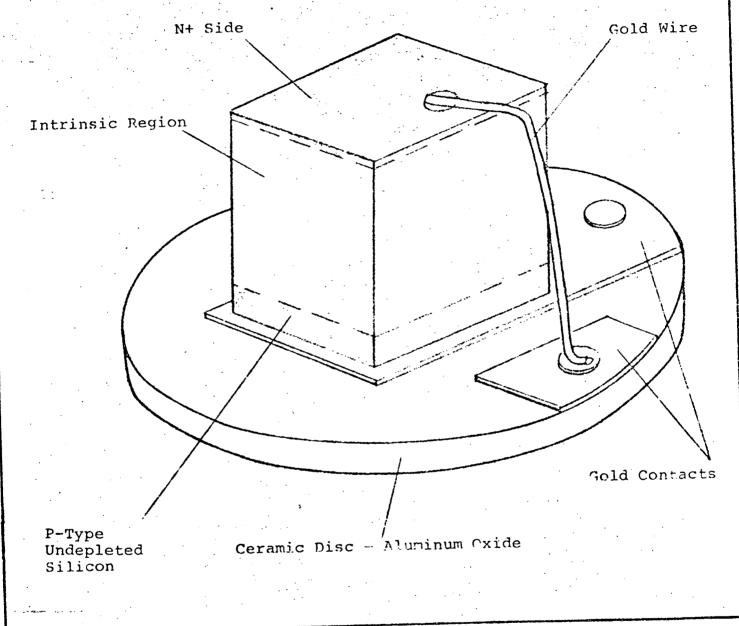


Fig. 1. View of Detector Mounting

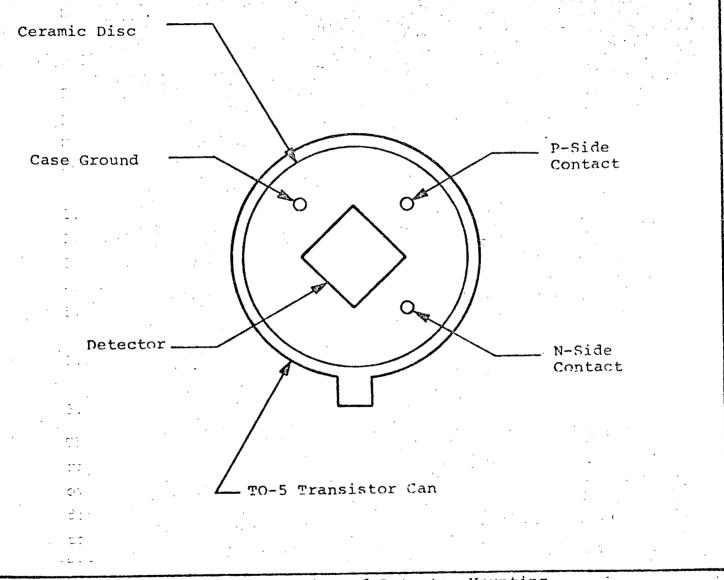


Fig. 2. Top View of Detector Mounting

3.1.3 Dimensions and Dead Layers

The dimensions of the silicon cube shall be as shown in figure 3. The five exposed sides of the detectors shall have dead layers of .0050 cm or less equivalent of silicon. The p+ (unexposed) side shall have a dead layer of nominal thickness .05 cm.

3.1.4 Identification

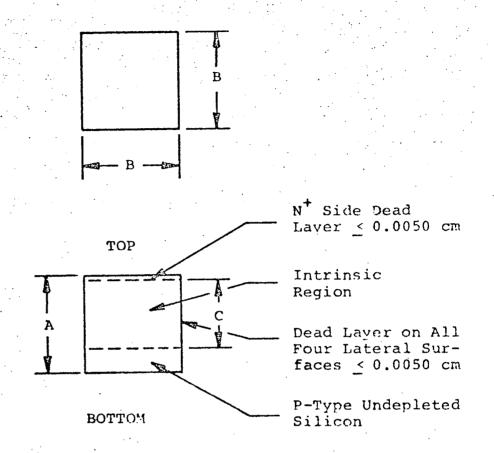
Each detector shall have a four-digit identification number painted or inscribed on its base. If painted, the paint must be vacuum compatible. The most significant digit shall be "2". Each number shall be unique and referenced to:

- 1. The silicon ingot used in fabrication
- 2. The date of detector fabrication
- 3. The lot number
- 4. The dates of testing
- 5. The data supplied with each detector

3.2 Environmental

3.2.1 Temperature

The detectors shall operate within specifications over the range -50°C to +25°C. They shall be capable of being cycled over the range -50°C to +60°C at 1°C/minute. No permanent deterioration of the detector shall be incurred by exposure to a 60°C environment for a period of 24 hours providing bias is not applied during this period.



Symbol	Dimensions	
A	0.255±0.0050	cm
B*	0.200:0.0025	cm
С	0.210±0.010	CM

*Not Counting Dead Layers on Lateral Surfaces

Fig. 3. Schematic Drawing of Lithium-Drifted Silicon Detector

3.2.2 Pressure

The detectors shall operate within specifications in a dry environment of either air or nitrogen from 1000mm Hg to 350mm Hg and also over the range from 20 \times 10⁻³ torr to less than 10⁻⁵ torr.

3.2.3 Vibration

The detectors shall be capable of withstanding the following vibration criteria without suffering any physical damage or degradation:

RANDOM VIBRATION CRITERIA

20 - 175 Hz @ +6 dB/Octave

 $175 - 350 \text{ Hz} @ 6.0 \text{ g}^2/\text{Hz}$

350 - 2000 Hz @ -3 dB/Octave

≈85.99 g r.m.s..

3.3 Electrical and Nuclear

3.3.1 Extended Bias

The detectors shall be capable of operation at an extended bias voltage of 500 volts dc over the warranty period without suffering electrical damage.

3.3.2 Leakage Current

The detectors shall have a leakage current not to exceed 2.5 microamperes at 350 volts bias at 25°C ± 1°C, and 4.0 microamperes at 500 volts bias at 25°C ± 1°C. The temperature coefficient of the leakage current shall be such that the current increases by no more than a factor of two (2) for each 8°C temperature rise above 25°C. The leakage current shall increase by not more than 25 percent per month of the value measured on the first acceptance test, referred to 25°C ± 1°C.

3.3.3 Noise

The detectors shall have a FWHM noise of $\leq 30~\rm{keV}^*$ at a bias of 350 volts at 25°C \pm 1°C, utilizing a shaping amplifier with double differentiation and double integration time constants of 0.36 microseconds.* The temperature coefficient of the noise shall be such that it increases by no more than a factor of 1.41 for each 8°C rise above 25°C.

The detectors shall be free of "contact" and "microplasma" noise and shall exhibit a count rate of < .05 ct above a 200 keV discriminator level due either to noise of any kind or radioactive contamination, all at temperatures from -50°C to 25°C, utilizing a shaping amplifier with double differentiation and double integration time constants of 0.36 microseconds.

Furthermore the noise of the detector shall increase by no more than 15 percent per month of the value measured on the first acceptance test, referred to 25°C ± 1°C.

3.3.4 Electron Resolution and Spectral Characteristics

The detectors shall exhibit a FWHM resolution of < 45 keV*

for the 972 keV conversion electron line of Bi-207 when

the electrons impinge on the entire lithium face (uncollimated)

of the detector.

^{*} Including electronic noise

^{**} See 3.3.7

3.3.4 Continued

The ratio of the number of counts in the <u>peak channel</u> of the 972 keV line to the number of counts in the <u>peak channel</u> of the 482 keV line of the Bi-207 spectrum shall be ≥ 1.3 (with background not subtracted). These tests are to be carried out at 350 volts bias, $25^{\circ}\text{C} \pm 1^{\circ}\text{C}$, with double differentiation, and double integration shaping amplifier time constants of 0.36 microseconds.**

During these tests a pulser shall be fed into the test input of the preamplifier and a pulser peak accumulated with the electron spectrum.

3.3.5 Bias Tabulation

Data shall be tabulated on the total time that bias was applied to the detectors, including the temperature and the bias voltage. The time shall be tabulated to within ± 15 percent, and the temperature to within $\pm 2^{\circ}$ C.

3.3.6 Calibration

The electronic system used for the tests of 3.3.3 and 3.3.4 shall be calibrated using a high quality detector of known characteristics. Namely:

- 1. Entrance window < 1 micron equivalent of silicon.
- 2. Active area \geq 50 mm².

^{**} See 3.3.7

3.3.6 Continued

- 3. Depletion depth ≤ 2 mm.
- 4. Electron resolution:

< 23 keV for 972 keV Bismuth-207 electrons</pre>

All measurements shall be performed using a preamplifier with a noise of \leq (7 keV + 0.1 $\frac{\text{keV}}{\text{pf}}$) and a shaping amplifier with double differentiation and double integration time constants of 0.36 microseconds** with the calibration detector biased for full charge collection.

During these tests a pulser shall be fed into the test input of the preamplifier and a pulser peak accumulated with the electron spectrum.

3.3.7 Shaping Time Constants

Although the detector parameters must be warranted with the specified shaping time constants, the vendor may, at his option, measure the pertinent parameters with double differentiation, single integration time constants of 0.4 microseconds.

3.3.8 Silicon Reserves

The remnants of the silicon ingot(s) from which the detectors are fabricated shall be reserved for LEC for possible future fabrication of EPS detectors for a period of 24 months from the beginning of the contract.

^{**} See 3.3.7

3.3.9 Lithium Drift Rate

The lithium drift rate in the silicon ingot(s) used for the EPS detectors shall be measured and specified at $25^{\circ}C \pm 1^{\circ}C$. The accuracy of the measurement shall be within ± 25 percent.

4.0 ACCEPTANCE TESTS

4.1 Initial Acceptance Tests (performed by Vendor)

The detector shall undergo the following initial acceptance tests performed by the vendor at the place of manufacture. Lockheed Electronics Company reserves the right to have its engineers present at any or all of these tests.

4.1.1 Thermal Cycle

The detectors shall undergo one thermal cycle, from 25°C to 25°C, with the temperature remaining at the extremes for one hour.

4.1.2 Detector Biasing

After the thermal cycle the detectors shall be biased for at least two weeks at 350 volts at 23°C ± 2°C.

#4.1.3 Leakage and Noise

During the biasing period, leakage, noise, and detector temperature shall be measured and recorded for each detector every seventy-two hours ± 2 hours.

4.1.4 Electron Response

At the end of the two weeks biasing period, leakage current, noise, and response to a Bismuth-207 source shall be measured and recorded.

4.1.5 Stability

If, at the end of the two week biasing period, the leakage current and/or noise of a particular detector have increased by more than 20 percent (referred to 25°C) above their initial values as measured within 24 hours after the beginning of the two week period, that detector shall be rejected although it might still satisfy the requirements of 3.3.2 and 3.3.3.

4.2 Final Acceptance Tests

Final acceptance of the detectors will occur approximately six weeks after their delivery to Lockheed Electronics Company and will be based upon tests performed by Lockheed engineers.

5.0 RELIABILITY AND QUALITY ASSURANCE PROVISIONS

5.1 Certificate of Compliance

A certificate of compliance signed by the Quality Control manager shall be included with each detector shipment. The certificate shall verify that the detectors were processed in accordance with this specification and that all requirements have been met.

5.2 Traceability

The contractor shall assure that traceability required by Standard No. 86 in MSCM 8080 can be provided for all parts delivered. All traceability identification to the parts manufacturer's production, assembly, or test lot shall be made available in a timely manner on request from LEC and/or NASA/MSC. This traceability requirement is a one way, backward traceability by part or lot code.

5.3 Record Retention

All records assembled as a result of this specification shall be retained by the manufacturer for at least two years following completion of the order.

5.4 Test Data

Test data encompassing the items of paragraphs 3.1.4, 3.3.2 through 3.3.6, and 3.3.9 shall be supplied with each detector. The data of 3.3.4 and 3.3.6 shall include plots of the spectra involved.

5.5 Preparation for Delivery

5.5.1 Unit Preparation and Packaging

Each unit procured to this specification shall be clean, dry, and packaged individually. The manner of packaging will afford adequate protection against corrosion, deterioration, and physical damage during shipment from supply source to the first receiving activity.

5.5.2 Packing

The packaged units shall be packed in a manner that will afford adequate protection against damage during direct shipment from the supply source to the first receiving activity. This pack shall conform to the applicable carrier rules and regulations.

5.5.3 Marking

Each shipping container will be marked with the supplier's name and the part number.

5.5.4 Delivery

Unless otherwise specified, the supplier shall use his own delivery facilities if delivery is local, and air express if the distance is greater than 100 miles.

6.0 WARRANTY

The manufacturer shall guarantee the operation of the detectors to the specification herein, when subjected to any combination of the conditions specified herein, for a period of one year.

PROCUREMENT SPECIFICATION FOR BOURNS POTENTIOMETER 3260 (RT26) and 3262 (RJ26)

Document Number EPS-124

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

PROCUREMENT SPECIFICATION FOR

BOURNS POTENTIOMETER RJ 26 AND RT 26

Prepared by:

P. Gleeson

Reliability and Quality

Assurance Engineer

Approved by:

B. E. Curtsinger

Engineering Supervisor

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Program Manager

Electron-Proton Spectrometer Program
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Lockheed Electronics Company
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1.0 SCOPE

This document defines the detailed high reliability requirements for Bourns potentiometer models 3260 (RT26) and 3262 (RJ26) for use on the Electron-Proton Spectrometer (EPS). Various resistance values and lead configurations will be used and are covered by this specification.

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of application shall form a part of this specification to the extent specified.

MIL-R-27208, Variable Resistor General Specifications

MIL-R-22097, Variable Resistor, Non-Wire Wound

MSCM-8080, Manned Spacecraft Criteria and Standards

MIL-STD 202D, Test Methods for Electrical and Electronic Parts

3.0 RELIABILITY AND QUALITY ASSURANCE REQUIREMENTS

3.1 Certificate of Compliance

A certificate of compliance signed by the Quality Control Manager shall be included with the device(s)

3.1 (continued)

shipment. It shall verify that the potentiometers were processed in accordance with this specification, and that all requirements have been met.

3.2 Retention of Records

The part supplier shall maintain and preserve records of evidence of compliance for a period of one year from the date of acceptance of the item by LEC. The supplier shall make his records available upon request from LEC or NASA/MSC.

3.3 Traceability

The vendor shall assure that traceability required by Standard No. 86 in MSCM 8080 can be provided. Identification to the part production, assembly and test lot shall be recorded. All traceability information shall be supplied on request of LEC or NASA/MSC. This traceability requirement is for a one-way, backward traceability by part or lot code.

3.4 Preparation for Delivery

The potentiometers shall be packed in a suitable container which will protect the body and leads of the device during shipment.

4 0 TESTS AND INSPECTIONS

All components procured to this specification shall be subjected to the following tests on a 100% basis and in the sequence specified.

4.1 Resistance Measurement

Each potentiometer shall be tested in accordance with MIL-STD-202D, Method 303. The following details shall apply.

4.1.1 Test Voltage

Measurement of resistance shall be made by using the test voltage in Table 1. This same voltage shall be used whenever a subsequent resistance measurement is made.

TABLE 1

Total Resistance, Nominal	Maximum Test Voltage		
Ohms	Volts		
10 to 100	1.0		
100 to 1,000	3.0		
1,000 to 10,000	10.0		
10,000 to 0.1 megohm	30.0		

4.1.2 Total Resistance

Total resistance shall be measured between the resistance-end elements, with the contact arm positioned against a stop. The positioning of the contact arm and terminal shall be the same for all subsequent measurements of the total resistance. The total resistance shall not deviate from the specified nominal by more than + 1%.

4.2 Temperature Cycling

Each potentiometer shall be tested in accordance with Method 102A, Condition C, MIL-STD 202D.

Resistance measurements shall be made at the conclusion of the final cycle. The resistance measurement shall be within + 1% of specified values.

4.3 Vibration

Each potentiometer shall be tested in accordance with Method 204, MIL-STD 202D. The following details shall apply.

a. Test leads - Test leads used during this test shall be no larger than AWG 22 stranded wire, so that the influence of the test leads on the potentiometer shall be held to a minimum.

4.3 (continued)

- b. Measurements before vibration Total resistance and setting stability shall be measured as specified in 4.6.2.1 and 4.6.9.1 respectively, MIL-R-27208C.
- c. Test condition D
- d. Measurements during vibration Each potentiometer shall be monitored to determine electrical discontinuity of the resistance element, and between the contact arm and element, by a method that shall at least be sensitive enough to monitor or register, automatically, any electrical discontinuity of 0.1 millisecond or greater duration.
- e. Measurements after vibration Setting stability and total resistance shall be measured as specified in 4.6.9.1 and 4.6.2.1 respectively of MIL-R-27208C.
- f. Examination after vibration Potentiometers shall be examined for evidence of mechanical damage.

4.3.1 Vibration Test Requirements

When potentiometers are tested as specified, there shall be no electrical discontinuity, and potentiometers shall meet the following requirements.

4.3.1 (continued)

Setting stability - Change shall not exceed + 1%.

Total Resistance - Change shall not exceed + 1%.

Operating Torque - Shall not exceed 150% of specified operating torque.

Visual Examination - There shall be no evidence of mechanical damage.

4.4 High Temperature Burn-In

4.4.1 Total Resistance and Setting Stability

Total resistance and setting stability shall be measured as specified in 4.6.2.1 and 4.6.9.1 respectively of MIL-R-27208C. The potentiometers shall then be exposed to an ambient temperature of 150°C ±5°C with power off, for a period of 168 hours. Not less than 2 hours after the end of the exposure time, the total resistance and setting stability shall be measured. Torque shall be measured as specified in 4.6.8.1 of MIL-R-27208C. Dielectric withstanding voltage and insulation resistance shall be measured as specified in 4.6.6.1 and 4.6.7 respectively of MIL-R-27208C.

4.4.2 Burn-In Test Requirements

When tested as specified, potentiometers shall meet the following requirements:

4.4.2 (continued)

- a. Setting Stability Change shall not exceed + 1%.
- b. Total Resistance Change shall not exceed + 1%.
- c. Operating Torque Shall not exceed 150% of specified torque.
- d. Dielectric Withstanding Voltage There shall be no evidence of damage, arcing, or breakdown. The leakage current shall not exceed 1 milliampere.
- e. Insulation Resistance Shall not be less than 1,000 megohms.
- f. Visual Examination There shall be no evidence of mechanical damage.

TABLE 1

ELECTRICAL AND ENVIRONMENTAL TESTS

	Paragraph
Electrical	
Total Resistance	4.1
Environmental	
Temperature Cycle	4.2
Vibration	4.3
Burn-In	4.4.2

PROCUREMENT SPECIFICATION

FOR

ERIE CAPACITOR TYPE

838-1KV-X5T-103M

Document Number EPS-121

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

PROCUREMENT SPECIFICATION

FOR

ERIE CAPACITOR TYPE 828-1KV-X5T-103M

Prepared by:

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Approved by:

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1.0 SCOPE

This specification defines the high reliability requirements of capacitors for the Electron-Proton Spectrometer. The components shall be subjected to the specified tests in the order given.

2.0 APPLICABLE DOCUMENTS

MIL-STD-202D, Test Methods for Electronic and Electrical Parts

MSCM 8080, Manned Spacecraft Center Criteria and Standards

OUALITY ASSURANCE

3.1 Certificate of Compliance

A certificate of compliance signed by the quality control manager shall be included with all units shipped. It shall verify that the units were manufactured in accordance with this specification and that all requirements have been met.

3.2 Traceability

The Manufacturer will assure that traceability required by Std. 86 in MSCM 8080 can be provided. In addition, provisions will be made to record information relating to the specific tests performed and

3.2 (continued)

processes on each lot of parts. All traceability information will be supplied to LEC and/or NASA/MSC upon request.

3.3 Record Retention

The part supplier shall maintain and preserve records of evidence of compliance and traceability for a period of one year from date of acceptance by LEC. The supplier shall make his records available upon request.

4.0 PREPARATION FOR DELIVERY

4.1 Unit Preparation and Packaging

Each unit procured to this specification shall be clean, dry and packaged individually. The manner of packaging will afford adequate protection against corrosion, deterioration and physical damage during shipment from supply source to the first receiving activity.

4.2 Packing

The packaged units shall be packed in a manner that will afford adequate protection against damage during direct shipment from the supply source to the first receiving activity. This pack shall conform to the applicable carrier rules and regulations.

4.3 Marking

Each shipping container will be marked with the supplier's name and the part number.

4.4 Shipping Method

Unless otherwise specified, the supplier shall use his own delivery facilities if delivery is local, and air express if the distance is greater than 100 miles.

5.0 ELECTRICAL AND ENVIRONMENTAL TESTS

5.1 Capacitance

Capacitors shall be tested in accordance with Method 302 of MIL-STD 202D. The following details shall apply.

- a. Test frequency 1 MHz + 100 kHz.
- b. Limit of accuracy + 10%.

5.2 <u>Dissipation Factor</u>

The dissipation factor of capacitors shall be measured with a capacitance bridge or other suitable method at the frequency and temperature specified. The inherent accuracy of the measurement shall be ±2% of the reading plus 0.1% dissipation factor unless otherwise specified. Suitable measurement techniques shall be used to minimize errors due to connections between the measuring apparatus and the specimen. The AC voltage actually

5.2 (continued)

impressed across the specimen shall be as low as practicable. When a DC polarizing voltage is required, it shall be as specified and shall exceed the peak AC voltage impressed across the specimen; however the sum of the peak AC and the DC voltages shall not exceed the voltage rating of the specimen.

The following details shall apply.

- a. Test frequencies 60 cps, 120 cps, 1 KC, 100 KC and 1 megacycle.
- b. Test temperature 25°C.

The dissipation factor shall be not greater than the percent indicated in the applicable specification sheet.

5.3 Temperature Cycling

Capacitors shall be tested in accordance with Method 102 of MIL-STD 202D. The following details shall apply.

a. Conditioning prior to first cycle - 15 minutes at standard temperature.

5.4 Burn-In

Capacitors shall be tested in accordance with Method 108A of MIL-STD 202D. The following details shall apply:

- a. Test temperature 85°C + 3°C
- b. Length of test minimum of 168, +16, -0 hours.

5.4.1 Operating Conditions

Capacitors tested shall be subjected to the dc rated voltage. The surge current shall be not less than $30\,\mathrm{ma}$ nor more than $50\,\mathrm{ma}$.

5.4.2 Measurements During and After Exposure

At the conclusion of this test and while the capacitors are at the applicable test temperature, the insulation resistance shall be measured in accordance with Method 302, MIL-STD 202D, Condition C. The insulation resistance shall not be less than 10,000 megohms. The specimens shall be returned to 25°C and Paragraph 5.1 and 5.2 shall be repeated.

5.4.3 Corona Start Voltage

The capacitors shall be tested in acordance with Method 105C, MIL-STD 202D. The following details shall apply.

- a. Corona start voltage measured and recorded.
- b. Minimum acceptable value of corona start voltage for any unit is 1000 volts RMS.

PROCUREMENT SPECIFICATION FOR CADDOCK RESISTORS TYPE MK, MG AND MS

Document Number EPS-116
January 28, 1971

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

PROCUREMENT SPECIFICATION FOR

CADDOCK RESISTORS TYPE MK, MG AND MS

Prepared by

Senior Aerospace Engineer

Approved by

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1.0 SCOPE

This specification defines the high reliability requirements of resistors for the Electron-Proton Spectrometer. The components shall be subjected to the specified tests in the order given.

2.0 APPLICABLE DOCUMENTS

MIL-STD 202D, Test Methods for Electronic and Electrical Component Parts

MIL-R-10509-F, Resistor Fixed Film, General Specification For

MSCM 8080, Manned Spacecraft Center Standards and Criteria

3.0 QUALITY ASSURANCE REQUIREMENTS

3.1 Certificate of Compliance

A certificate of compliance signed by the Quality Control Manager shall be included with the device(s) shipment. It shall verify that the resistors were processed in accordance with this specification, and that all requirements have been met.

3.2 Retention of Records

The part supplier shall maintain and preserve records of evidence of compliance for a period of one year

3.2 (continued)

from the date of acceptance of the item by LEC. The supplier shall make his records available upon request from LEC or NASA/MSC.

3.3 Traceability

The vendor shall assure that traceability required by Standard No. 86 in MSCM 8080 can be provided. Identification to the part production, assembly, and test lot shall be recorded. All traceability information shall be supplied on request of LEC or NASA/MSC. This traceability requirement is for a one-way, backward traceability by part or lot code.

3.4 Preparation for Delivery

The resistors shall be packed in a suitable container which will protect the body and leads of the device during shipment.

4.0 ELECTRICAL TESTS

4.1 <u>Electrical Parameters</u>

Measure the following parameters and record the results on an appropriate data sheet beside the applicable serial number. Reject devices exceeding the limits shown.

4.1 (continued)

- a. R (resistance) per method 302 of MIL-STD-202D.
 Limit = ± 1% of designated value.
- b. IR (insulation resistance) per method 302 of MIL-STD 202D. VR = 200 V, limit = 1000 megohm minimum.

4.2 Resistance Value by Type

Type	R in ohms	Tolerance
MK 132	800 K	± 1%
MK 650	50 K	± 1%
MG 660	10 M	± 1%
MG 650	100 K	± 1%
MG 650	4.99 M	± 1%
MG 650	2.49 M	± 1%
MG 650	2.0 M	± 1%
MS 126	1.33 K	± 18

5.0 ENVIRONMENTAL

5.1 Temperature Cycle

Temperature cycle per MIL-STD-202D, Method 102A, Test Condition C, and MIL-R-10509F, Paragraph 4.6.4.

5.2 Burn-In

Subject each resistor to a burn-in test for 168 hours under the following conditions:

Temperature - 125°C

Operate at rated power.

The resistance change shall not be more than 0.5% from initial measured value, or out of initial tolerance, before and after burn-in.

6.0 FINAL SCREEN

Measure and record resistance. Resistance shall be within \pm 1% of nominal and shall not change greater than \pm 0.5% from initial reading.

TABLE 1

ELECTRICAL AND ENVIRONMENTAL TESTS

Paragraph Electrical 4.1 Environmental Temperature Cycle 5.1 Burn-in 5.2 Final Screen 6.0

PROCUREMENT SPECIFICATION

FOR

CADDOCK RESISTORS

TYPE 1712-100 MEG

Document Number EPS-168

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

PROCUREMENT SPECIFICATION

FOR DESTRUCT

CADDOCK RESISTORS
TYPE 1712-100 MEG

Prepared by:

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1.0 SCOPE

This specification defines the high reliability requirements of resistors for the Electron-Proton Spectrometer. The components shall be subjected to the specified tests in the order given.

2.0 APPLICABLE DOCUMENTS

MIL-STD 202D, Test Methods for Electronic and Electrical Component Parts

MIL-R-10509F, Resistor Fixed Film, General Specification For

MSCM 8080, Manned Spacecraft Center Standards and Criteria

3.0 QUALITY ASSURANCE REQUIREMENTS

3.1 Certificate of Compliance

A certificate of compliance signed by the Quality Control Manager shall be included with the device(s) shipment. It shall verify that the resistors were processed in accordance with this specification, and that all requirements have been met.

3.2 Retention of Records

The part supplier shall maintain and preserve records of evidence of compliance for a period of one year from the date of acceptance of the item by LEC. The supplier shall make his records available upon request from LEC or NASA/MSC.

3.3 Traceability

The vendor shall assure that traceability required by Standard No. 86 in MSCM 8080 can be provided. Identification to the part production, assembly and test lot shall be recorded. All traceability information shall be supplied on request of LEC or NASA/MSC. This traceability requirement is for a one-way, backward traceability by part or lot code.

3.4 Preparation for Delivery

The resistors shall be packed in a suitable container which will protect the body and leads of the device during shipment.

4.0 ELECTRICAL TESTS

4.1 Electrical Parameters

Measure the following parameters and record the results on an appropriate data sheet beside the applicable serial number. Reject devices exceeding the limits shown.

- a. R (resistance) per method 302 of MIL-STD 202D. Limit = +1% of designated value.
- b. IR (insulation resistance) per method 302 of MIL-STD 202D. VR = 200V, limit = 100,000 megohm minimum.

5.0 ENVIRONMENTAL

5.1 Temperature Cycle

Temperature cycle per MIL-STD 202D, Method 102A, Test Condition C, and MIL-R-10509F, Paragraph 4.6.4.

The parameters specified in Paragraph 4.1 shall be monitored. Any unit failing the electrical parameters shall be rejected.

5.2 Burn-In

Subject each resistor to a burn-in test for 168 hours under the following conditions:

Temperature - 125°C Operate at rated power.

The resistance change shall not be more than 0.5% from initial measured value, or out of initial tolerance, before and after burn-in.

6.0 FINAL SCREEN

Measure and record resistance. Resistance shall be within +1% of nominal and shall not change greater than +0.5% from initial reading.

TABLE 1

ELECTRICAL AND ENVIRONMENTAL TESTS

	•	Paragraph
Electrical		4.1
Environmental		
Temperature Cycle		5.1
Burn-In		5.2
Final Screen		6.0

PROCUREMENT SPECIFICATION FOR CAPACITOR (VARIABLE) RVC 12

Document Number EPS-232

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

PROCUREMENT SPECIFICATION

FOR

CAPACITOR (VARIABLE) RVC 12

Prepared by:

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L.O SCOPE

This specification defines the high reliability requirements of variable capacitors for the Electron-Proton Spectrometer. The components shall be subjected to the specified tests in the order given.

2.0 APPLICABLE DOCUMENTS

MIL-STD 202D, Test Methods for Electronic and Electrical Parts

MSCM 8080, Manned Spacecraft Center Criteria and Standards

3.0 RELIABILITY AND QUALITY ASSUFANCE REQUIREMENTS

3.1 Certificate of Compliance

A certificate of compliance signed by the quality control manager shall be included with all units shipped. It shall verify that the units were manufactured in accordance with this specification and that all requirements have been met.

3.2 Traceability

The manufacturer will assure that traceability can be traced to the lot date and/or code of the lot the parts procured to this specification was taken from. All traceability information will be supplied to LEC and/or NASA/MSC upon request.

3.3 Record Retention

The part supplier shall maintain and preserve records of evidence of compliance and traceability for a period of one year from date of acceptance by LEC. The supplier shall make his records available upon request from LEC or NASA/MSC.

4.0 PREPARATION FOR DELIVERY

4.1 Unit Preparation and Packaging

Each unit procured to this specification shall be clean, dry and packaged individually. The manner of packaging will afford adequate protection against corrosion, deterioration and physical damage during shipment from supply source to the first receiving activity.

4.2 Packing

The packaged units shall be packed in a manner that will afford adequate protection against damage during direct shipment from the supply source to the first receiving activity. This pack shall conform to the applicable carrier rules and regulations.

4.3 Marking

Each shipping container will be marked with the supplier's name and the part number.

5.0 ELECTRICAL AND ENVIRONMENTAL TESTS

5.1 Capacitance

Capacitors shall be tested in accordance with Method 305 of MIL-STD 202D. The following details shall apply.

- a. Test frequency 1 mHz + 100 kHz.
- b. Limit of accuracy + 2% or 0.5 picofarad, whichever is greater.

5.2 Dissipation Factor

The dissipation factor of the capacitors shall be measured at both maximum and minimum capacitance setting at a frequency of 1 mHz \pm 100 kHz. The accuracy of the measurement shall be at least 0.2%.

5.3 Dielectric Withstanding Voltage

Terminal to Terminal - Capacitors shall be tested in accordance with Method 30l of MIL-STD 202D. The following details shall apply:

- a. Magnitude of test voltage 2.2 times applicable rated dc voltage.
- b. Duration of application of test voltage 3, ±2 seconds.
- c. Points of application of test voltage between terminals.
- d. Limiting value of surge current 50 milliamps.

5.3 (continued)

When measured as specified, capacitors shall withstand the dc current potential without damage, breakdown or flashover.

5.4 Temperature Cycling

Capacitors shall be tested in accordance with Method 102A, Test Condition C, MIL-STD 202D. Examination and measurements shall be made after final cycle.

Capacitors shall be examined visually for evidence of mechanical damage; dielectric withstanding voltage (paragraph 5.3), capacitance (paragraph 5.1) and dissipation factor (paragraph 5.2) shall be measured as specified in the referenced paragraphs.

5.5 Vibration

The capacitors shall be tested in accordance with MIL-STD 202D, Method 204, Condition B, one sweep from 15 to 2000 cycles, with a time duration of 10 minutes. The following details shall apply.

a. Capacitors shall be rigidly mounted on a mounting fixture by normal mounting means. The mounting fixture shall be so constructed as to preclude any resonances within the test range.

5.5 (continued)

, · *.

- b. Measurements prior to vibration Capacitors shall be set at approximately 90% to 95% of maximum rated capacitance, and capacitance shall be measured to four places.
- c. Electrical-load conditions During the test a potential of 125% of rated dc voltage shall be applied between the terminals of the capacitor.
- d. Test Condition Letter B.
- e. Measurement during vibration During the last cycle in each direction, an electrical measurement shall be made to determine intermittent contacts.

 Intermittent contacts of 0.5 ms or greater, or open or short circuiting shall be considered a failure.
- f. Examination after vibration Capacitors shall be visually examined for evidence of mechanical damage.
- g. Final Measurements After the final vibration cycle, the initial capacitance setting shall not be disturbed. The change in the initial setting as defined in paragraph 5.5b shall not exceed .03%. Dielectric withstanding voltage, capacitance and dissipation factor shall be measured as specified in paragraph 5.3, 5.1 and 5.2 respectively.

5.6 Burn-in

The capacitors shall be subjected to burn-in temperature of 125°C for 168 hours +16, -0 hours. The following operating conditions shall apply:

- a. The capacitors shall be subjected to the maximum rated voltage. The surge current shall not exceed 50 ma.
- b. Measurement during and after exposure: At the conclusion of this test and while the capacitors are still held at the maximum rated temperature, the dielectric withstanding voltage and capacitance shall be measured as specified in Paragraph 5.3 and 5.1 respectively. The capacitors shall be returned to normal temperature and visually examined for evidence of mechanical damage. The capacitance and dissipation factor shall be measured as specified in Paragraph 5.1 and 5.2 respectively.

5.7 External Visual

The dimensions of each device shall conform to the configuration shown in Figure 1.

ELECTRICAL AND ENVIRONMENTAL TESTS

The property of the ${f P}_{i}$	Paragraph	
Capacitance	5.1	
Dissipation Factor	5.2	
Dielectric Withstanding Voltage	5.3	
Temperature Cycling	5.4	
Vibration	5.5	
Burn-in	5.6	
External Visual	5.7	

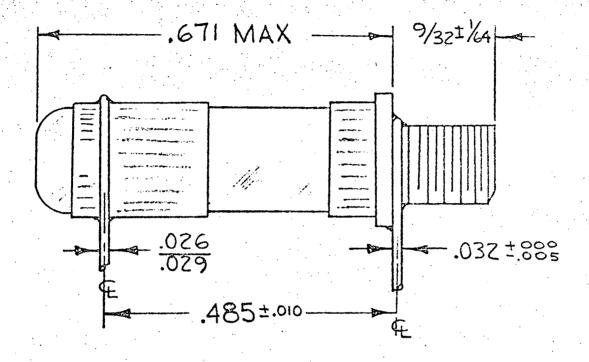


FIGURE 1. LEAD CONFIGURATION OF RVC 12

PROCUREMENT SPECIFICATION

FOR

NYTRONICS INDUCTOR

PD-100

Document Number EPS-167

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

PROCUREMENT SPECIFICATION

FOR

NYTRONICS INDUCTOR

PD-100

Prepared by:

Gleeson

Reliability and Quality

Assurance Engineer

Approved by:

ī:.

Staff Engineer

B. E. Curtsinger Engineering Supervisor

Program Manager

Electron-Proton Spectrometer Program Advanced Programs Department Lockheed Electronics Company Houston Aerospace Systems Division

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1.0 SCOPE

This specification defines the high reliability requirements of Inductors for the Electron-Proton Spectrometer.

The components shall be subjected to the specified tests in the order given.

2.0 APPLICABLE DOCUMENTS

MIL-STD 202D, Test Methods for Electronic and Electrical Parts

MSCM 8080, Manned Spacecraft Center Criteria and Standards

MIL-C-15305D, Coils, Fixed and Variable, General Specifications For

3.0 QUALITY ASSURANCE

3.1 Certificate of Compliance

A certificate of compliance signed by the quality control manager shall be included with all units shipped. It shall verify that the units were manufactured in accordance with this specification and that all requirements have been met.

3.2 Traceability

4:3

The Manufacturer will assure that traceability required by Standard 86 in MSCM 8080 can be provided. In addition, provisions will be made to record information relating to the specific tests performed and processes on each lot of parts. All traceability information will be supplied to LEC and/or NASA/MSC upon request.

3.3 Record Retention

The part supplier shall maintain and preserve records of evidence of compliance and traceability for a period of one year from date of acceptance by LEC. The supplier shall make his records available upon request.

4.0 PREPARATION FOR DELIVERY

4.1 Unit Preparation and Packaging

Each unit procured to this specification shall be clean, dry and packaged individually. The manner of packaging will afford adequate protection against corrosion, deterioration and physical damage during shipment from supply source to the first receiving activity.

4.2 Packing

The packaged units shall be packed in a manner that will afford adequate protection against damage during direct shipment from the supply source to the first receiving activity. This pack shall conform to the applicable carrier rules and regulations.

4.3 Marking

Each shipping container will be marked with the supplier's name and the part number.

4.4 Shipping Method

Unless otherwise specified, the supplier shall use his own delivery facilities if delivery is local, and air express if the distance is greater than 100 miles.

5.0 ELECTRICAL AND ENVIRONMENTAL TESTS

5.1 Dielectric Withstanding Voltage

The inductors shall be tested in accordance with Paragraph 4.8.2, MIL-C-15305D. There shall be no arcing, flashover, breakdown, or other damage.

5.2 Insulation Resistance

The inductors shall be tested in accordance with Paragraph 4.8.4, MIL-C-15305D. The insulation resistance shall be not less than 1000 megohms.

5.3 "O" of Inductors

The test shall be performed using a Q meter such as Boonton RCA Model 260A, or equivalent, and Boonton RCA Q-standard, type 513A or equivalent. The tests shall be performed in accordance with Paragraph 4.8.8.3 of MIL-C-15305D. The "Q" of the inductors shall be 55 minimum at a frequency of 2.5 mHz.

5.4 DC Resistance (DCR)

Direct Current Resistance of the inductors shall be measured in accordance with Method 303, MIL-STD 202D. Test Current (I_T) = 110 mA. The unit shall be considered failed if the DCR is greater than 11.5 ohms.

5.5 <u>Temperature Cycling</u>

Inductors shall be tested in accordance with Method 102 of MIL-STD 202D. The following details shall apply:

a. Conditioning prior to first cycle - 15 minutes at standard temperature.

5.6 Burn-In

Inductors shall be tested in accordance with Method 108A of MIL-STD 202D. The following details shall apply:

- a. Test temperature 125°C + 3°C
- b. Length of Test minimum of 168, +16, -0 hours

5.6.1 Operating Conditions

Inductors tested shall be subjected to the DC rated voltage. The rated current shall not be greater than 110 mA.

5.6.2 Measurements During and After Exposure

At the conclusion of this test and while the inductors are at the applicable test temperature, the insulation resistance shall be measured in accordance with Method 302, MIL-STD 202D, Condition C. The insulation resistance shall not be less than 1,000 megohms. The specimens shall be returned to 25°C and paragraph 5.1 through 5.4 shall be repeated.

PROCUREMENT SPECIFICATION

FOR

BARRY CONTROL VIBRATION ISOLATORS

LEC Document Number EPS-356

Revision A 5.2.1 (6.0 to 6.2)
Revision B 6.2 (by to to)

Prepared by
Lockheed Electronics Company, Inc.
Houston Aerospace Systems Division
Houston, Texas

Under Contract NAS 9-11373

for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

PROCUREMENT SPECIFICATION

FOR

BARRY CONTROLS VIBRATION ISOLATOR

Prepared by

Donald Vincent

Sr. Mech. Engineer

Approved by:

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Reliability & Quality

Assurance

B. C. Hall

Program Manager

PROCUREMENT SPECIFICATION FOR BARRY CONTROLS VIBRATION ISOLATORS

1.0 SCOPE

1.1 Scope

This specification defines necessary procurement requirements for the Barrymount 6300 Series Isolator, to satisfy design requirements and NASA Reliability and Quality Assurance provisions for the Electron-Proton Spectrometer.

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of application should form a part of this specification to the extent specified herein.

NBH 5300.4(1B) Reliability and Quality Assurance Provisions for Aeronautical and Space System Contractors.

3.0 QUALITY ASSURANCE REQUIREMENTS

3.1 Inspection, Measuring and Test Equipment

The vendor shall maintain and control inspection, measuring and test equipment in accordance with paragraph 1B705 of NHB 5300.4(1B).

3.2 Inspection and Test Records

Inspection and test records shall include part number, identification of each mount and each set of isolators, number of defects found, kind of defects, and acceptance number. Records of inspection and tests shall be delivered to Lockheed.

3.3 Certificate of Compliance

A certificate of compliance signed by the Quality Control manager shall be included with the device shipment. It shall verify that the isolators were processed in accordance with this specification and that all requirements have been met.

3.4 Retention of Records

The part supplier shall maintain and preserve records of evidence of compliance for a period of one year from the date of acceptance of the item by LEC. The supplier shall make his records available upon request from LEC or NASA/MSC.

3.5 Traceability

The vendor shall assure that traceability required by Standard No. 86 in MSCM 8080 can be provided. Identification to the part production, assembly and test lot shall be recorded. All traceability information shall be supplied on request of LEC or NASA/MSC. This traceability requirement is for a one-way, backward traceability by part or lot code.

3.6 Preparation for Delivery

The isolators shall be packaged in a suitable container which will protect the body of the device during shipment.

4.1 Physical Requirements

4.1.1 The vibration isolator required shall be of the proportions of the Barrymount 6300 series isolator. However, the mounting flanges shall be modified to the dimensions shown in Fig. 4. Also, the spacer end plates shall be of the dimensions shown in Fig. 4A.

4.1.2 Material

The vibration isolators shall be made from silicone material which is 'Hi-Damp' Elastomer. Material shall be compatible with orbital vacuum (as low as 1×10^{-8} Torr). Maximum Mission duration is 56 days.

4.1.3 Package Format

The EPS electronics package as supported on the isolators will weigh 15.5 lbs. MAX., and be supported by 8 isolators. The location of the isolators, together with the size and C. G. position of the package is shown in Fig. 5.

4.1.4 Dynamic Envelope

Maximum permissable dynamic envelope for the package is shown in Fig. 6.

4.1.5 System (Mount) Natural Frequency

The system natural frequency shall be designed for 40 Hz and must fall in the frequency range of 35 - 50 Hz.

4.1.6 Damping Ratio

Desired Damping Ratio is .15, and shall not be less than .12.

4.1.7 Central Bush

The Centre Bush shall be capable of withstanding a load of 1700 lbs. (induced by the mounting screw tightening torque) without failure or affecting mount properties.

4.1.8 Matching

The mounts shall be provided in matched sets of (8) eight to eliminate as far as possible 'rocking' induced by variations in mount stiffness.

4.1.9 Mounts shall be marked and identified individually.

5.0 TESTING

5.1 All vibration isolation mounts shall be tested to determine their natural frequency and damping ratio in both vertical and horizontal axes, and this information provided to LEC.

5.2 Dynamic Testing

5.2.1 Isolation mounts shall be dynamically tested to the environmental requirements of 6.2. This test data shall be used to select the location of individual isolators within each matched set. Location of mounts and test data to be provided to LEC with matched sets of mounts.

5.3 Temperature Testing

- 5.3.1 The mounts must meet or exceed a temperature environment of -55° C to +125° C. The mounts shall be tested or available data analyzed to show that the mounts meet this requirement. Supporting data shall be furnished to LEC.
- 6.0 ENVIRONMENTAL REQUIREMENTS
- 6.1 Vibration

6.1.1 Random Vibration

The Random Vibration Criteria imposed on the EPS are as follows:

QUALIFICATION

R-Axis

20 to 125 Hz

125 to 500 Hz

500 to 670 Hz

670 to 1100 Hz

1100 to 2000 Hz

+12 dB/oct increase

 $2.0 \, g^2/Hz$

-9 dB/oct decrease

 $0.8 \text{ g}^2/\text{Hz}$

-9 dB/oct decrease

X-Axis

20 to 75 Hz

75 to 175 Hz

175 to 300 Hz

300 to 1000 Hz

1000 to 2000 Hz

+6 dB/oct increase

 $0.085 \text{ g}^2/\text{Hz}$

+6 dB/oct increase

 $0.25 \, \mathrm{g}^2/\mathrm{Hz}$

-6 dB/oct decrease

T-Axis

20 to 100 Hz 100 to 440 Hz

440 to 600 Hz 660 to 900 Hz

900 to 2000 Hz

+6 dB/oct increase

 $0.04 \text{ g}^2/\text{Hz}$

+18 dB/oct increase

 $0.3 \text{ g}^2/\text{Hz}$

-12 dB/oct decrease

The excitation shall act along each of the above axes for a duration of 140 seconds per axis. In addition, the spectral density shall be increased by 4 dB above the nominal for a duration of 10 seconds per axis. (See Fig. 1 for Instrument Axes)

One isolator shall be subjected to the dynamic response of the listed vibration criteria. The remaining isolators shall be qualified by similarity. The data from the analysis shall be sent to LEC.

Total Duration +3 dB/octave 6.1.2 Flight: 20 - 100 Hz -12 1/2 mins/Axis.(increasing) Constant at 0.15 g^2/Hz . 100 - 2000 Hz

6.2 Sinusoidal

5-35 Hz @ .25 G peak along each of three orthogonal axes as follows: Sweep at 3 octaves per minute from 5 to 35 to 5 Hz.

The sinusoidal vibration test shall be accomplished on 100% of the isolators furnished to LEC.

6.3 Acceleration

The EPS is subjected to a gradually increasing acceleration load in the +X Axis for 140 seconds after lift-off. Fig. 2 shows the acceleration level versus time. The 10 second, 4 dB above nominal, burst occurs just prior to achieving Mach. 1, and its location relative to the acceleration level is also shown in Fig. 2.

One isolator shall be subjected to the dynamic response of the listed acceleration tests. The remaining isolators shall be qualified by similarity. The results of the analysis will be sent to LEC.

6.4 Shock

6.4.1 Test Shock

The EPS Shock Test is in accordance with MIL-STD-810B, Method 516, Procedures I and V. The shock pulse shape for Procedure I shall be as shown in Fig. 516 -1 of MIL-STD-810B. The peak value for Procedure I shall be 20 g. and the nominal duration of the pulse shall be 11 milliseconds.

Procedure I consists of three shocks in each direction applied along three mutually perpendicular axes of the test item (total of 18 shocks). The shock pulse shall be of a saw tooth shape with an amplitude of 20 g's and a duration of 11 milliseconds. The unit shall be operated after the test and the results compared with functional test results obtained before the shock test.

Procedure V consists of placing the unit on a wooden bench top at least 1 5/8 inches thick and performing the following: With the unit resting on its one flat surface lift one edge of the unit four inches and allow the unit to drop back freely to the horizontal bench top. Repeat using the other three edges as pivot points for a total of four drops. Functionally test unit and compare with previous test results.

One isolator shall be subjected to the dynamic response of the shock criteria listed below. The remaining isolators shall be qualified by similarity. The results of the analysis shall be sent to LEC.

6.4.2 Flight Shock

In addition to the Test Shock conditions of Para. C.1, the EPS is mounted in the command and service module fairing area. The pyrotechnic separation of the (SLA) from the CSM provides a shock response spectrum as shown in Fig. 3.

The Flight Shock shall be proven by analysis. A summary of the resulting data shall be sent to LEC.

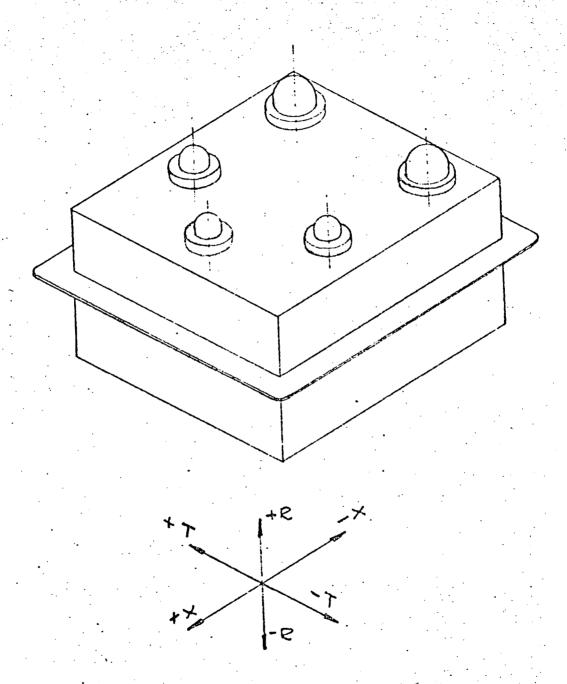
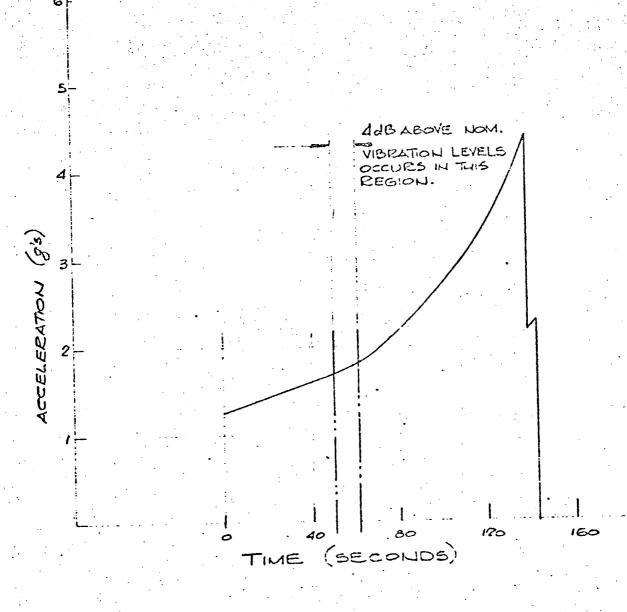


FIG. 1 E.P.S. YIBRATION AXES.



FIG? ACCELERATION V TIME.

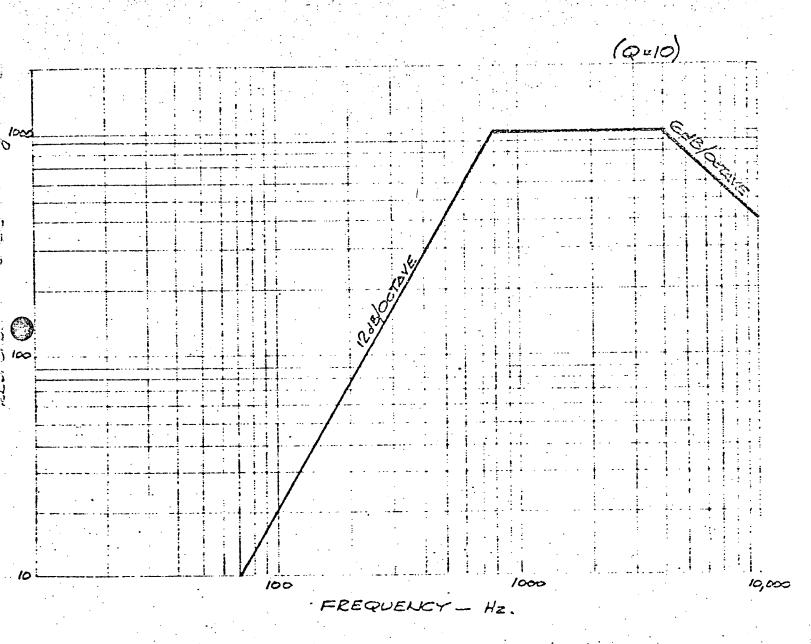


FIG.3. CSM FAIRING-SHOCK RESPONSE SPECTRUM.

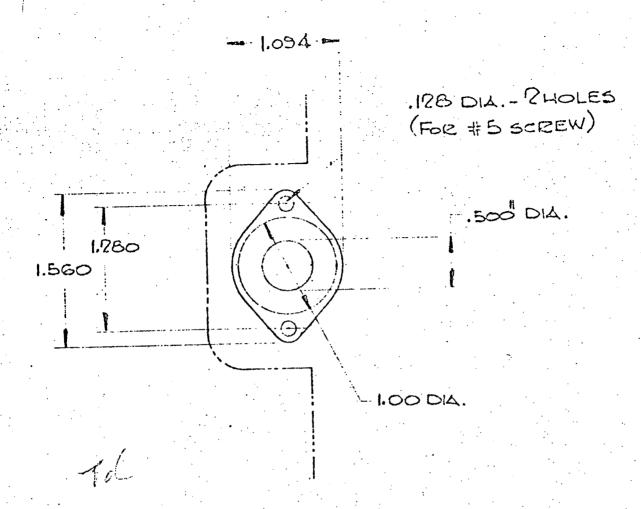


FIG.4. REQUIRED VIBRATION ISOLATOR
PROFILE - ELECTRON-PROTON
SPECTROMETER.

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LOCKHEED ELECTRONICS :

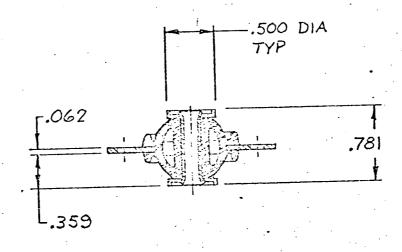


FIG. 1a - REQUIRED HEIGHT AND
FLANGE POSITION FOR
ISOLATOR - ELECTRON-PROTON
SPECTROMETER.

45 A 25

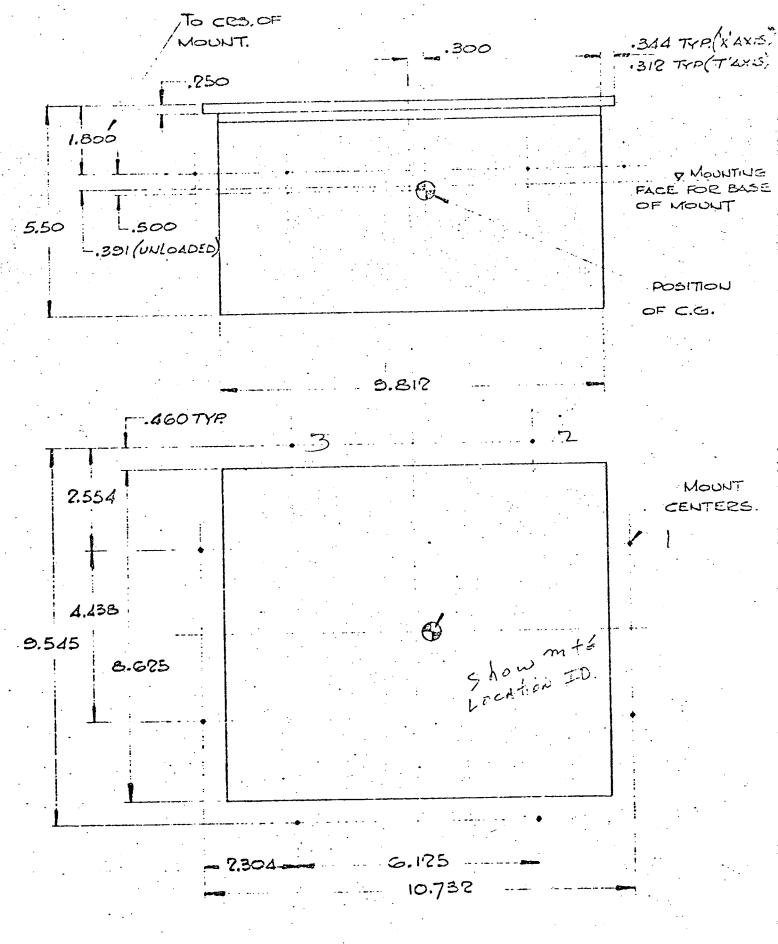
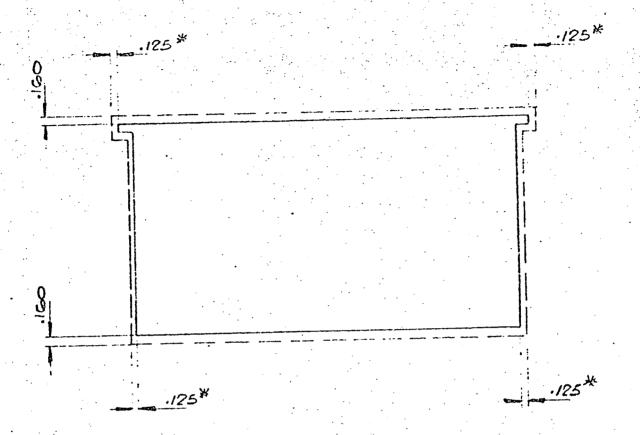


FIG.5 VIBRATION, MOUNT LOCATION.

64 8-12-7



* DIMS. APPLY TO X & T AXES

FIG. 6 MAXIMUM ALLOWABLE DYNAMIC ENVELOPE.

SCREENING SPECIFICATION FOR TRANSISTOR SS3520

Document Number EPS-128

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
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Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

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SCREENING SPECIFICATION FOR TRANSISTOR SS 3520

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1.0 SCOPE

This document defines the necessary requirements for the screening of transistor SS3520 to satisfy NASA high reliability requirements for the Electron-Proton Spectrometer (EPS).

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of application shall form a part of this specification to the extent specified herein.

MIL-STD 202D, Test Methods for Electronic and Electrical component parts

MIL-STD 750A, Test Methods for Semiconductor Devices MIL-STD 883, Test Methods and Procedures for Micro-electronics

NHB 5300.4(1A), Reliability Program Provisions for Aeronautical and Space Systems Contractors

3.0 REQUIREMENTS FOR TEST LABORATORY SUBCONTRACTORS

3.1 Facilities

The subcontractor shall provide and maintain adequate facilities for inspecting and testing electronic components described in this specification.

3.2 Inspection, Measuring and Test Equipment

The subcontractor shall maintain and control inspection, measuring and test equipment in accordance with

3.2 (continued)

NHB 5300.4 (1A). Upon request, the subcontractor shall submit to Lockheed Electronics Company (LEC) for approval, a listing of equipment and their intended usage.

3.3 Calibration Records

The subcontractor shall prepare and have available for review by LEC, a written procedure and schedule for the maintenance and calibration of such equipment based on type, accuracy, purpose and degree of usage. Records of calibration shall be maintained and the calibration due date, or other identification attesting the due date of the next calibration, shall be displayed on each item of this equipment.

3.4 Calibration Traceability

Standards used for calibration shall be traceable to the National Bureau of Standards (NBS). No more than five steps shall be used to establish traceability from actual inspection and test equipment to the NBS.

RELIABILITY AND QUALITY ASSURANCE PROVISIONS

4.1 General

4.0

The procedures and methods of testing the transistors in accordance with this specification shall meet the general requirements of MIL-STD-202D.

4.2 Screening Inspections and Tests

Each transistor supplied shall be submitted in the sequence specified to the inspections and tests of Table 1.

4.3 Inspection and Test Data

A summary of the transistor data obtained during each inspection or test shall be prepared and submitted with the transistors to LEC. This summary shall list all transistors that failed electrical tests and the number that failed each parameter. The raw test data shall also be delivered to LEC with the transistors.

4.4 Inspection and Test Records

Inspection and test records shall include part number, serial number, inspection or test number, number of defects found, kinds of defects, acceptance number and the disposition inspector's identity. Records of all inspections and tests shall be delivered to LEC along with the transistors.

4.5 Serialization

4.3

All transistors shall be serialized in a manner that will be permanent during use and testing periods.

4.6 Reject Disposition

Each transistor that fails the inspections and tests of Table 1 shall be marked with a red dot and placed in a reject bag, and tagged to note unit part number, serial number and inspection or test failed. These units shall also be delivered to LEC. Use 3M-401-5D paint for marking of parts.

4.7 Marking of Acceptable Parts

Transistors which meet the requirements of this specification shall be identified with a permanent green dot placed on the body of the transistor. The dot shall be placed on the body at a point which will not interfere with reading the manufacturers part number or date code identification. Use 3M-401-G3 paint for marking of parts.

4.8 Acceptance

Preliminary inspection for compliance with the requirements of this specification may be performed at origin by an authorized representative of the Government. Final acceptance for the Contracting Officer shall be performed by the assigned project engineer.

4.9 Certificate of Compliance

A certificate of compliance signed by the Quality Control manager shall be included with the device shipment. It shall verify that the transistors

4.9 (continued)

were processed in accordance with this specification and that all requirements have been met.

4.10 Notification of Government Source Inspector

The Government Representative who has been delegated quality assurance function at your test facility shall be notified immediately upon receipt of this order.

5.0 PREPARATION FOR DELIVERY

5.1 Type of Packaging

Each transistor shall be packaged in a suitable container which will protect the body and leads of the device during shipment. The rejected parts shall be identified and packaged separately from the acceptable items.

5.2 Packaging for Shipment

The transistors packaged in accordance with paragraph 5.1 shall be packed to afford protection against damage during direct shipment from the test laboratory to the receiving activity. Containers will comply with the carrier's rules and regulations applicable to the mode of transportation.

6.0 INSPECTION AND TEST METHODS

6.1 External Visual

The transistors shall be examined to verify that the materials, design, construction, marking and workmanship are in accordance with the applicable requirements.

6.2 Electrical

All electrical tests shall be performed at an ambient temperature of 25°C unless otherwise noted.

6.2.1 Collector-Base Cutoff Current

$$v_{CB} = 15 \text{ VDC}$$

$$I_{E} = 0$$

The collector-base cutoff current shall be tested in accordance with Method 3036, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $I_{\mbox{CBO}}$ is greater than 10 nA dc.

6.2.2 Collector - Base Breakdown Voltage

$$I_C = 1.0 \mu A dc$$

6.2.2 (continued)

$$I_E = 0$$

The collector - base breakdown voltage shall be tested in accordance with Method 3001.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if ${\ensuremath{\mathsf{BV}}}_{\ensuremath{\mathsf{CBO}}}$ is less than 35 VDC.

6.2.3 Emitter - Base Breakdown Voltage

$$I_E = 10 \mu A dc$$

$$I_C = 0$$

The emitter - base breakdown voltage shall be tested in accordance with Method 3026.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if the ${\rm BV}_{\rm EBO}$ is less than 3.0 VDC.

6.2.4 Collector - Emitter Breakdown Voltage

$$I_C = 3.0 \text{ mA dc}$$
 (pulsed)

$$I_B = 0$$

Pulse width ≤ 300 µs

Duty Cycle = 1%

6.2.4 (continued)

The collector - emitter breakdown voltage shall be tested in accordance with Method 3011.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if the ${\ensuremath{\mathsf{BV}}}_{\ensuremath{\mathsf{CEO}}}$ is less than 20 VDC.

6.2.5 Forward Current Ratio (hfe)

 $v_{CE} = 15 \text{ VDC}$

 $I_C = 2.0 \text{ mA dc}$

f = 1.0 kHz

The forward transfer ratio shall be tested in accordance with Method 3206, MIL-STD 750A.

The unit shall be considered failed if the $h_{\mbox{\scriptsize fe}}$ is less than 100.

6.2.6 Base - Emitter Saturation Voltage

 $I_C = 10 \text{ mA dc}$

 $I_{B} = 1.0 \text{ mA dc}$

The base-emitter saturation voltage shall be tested in accordance with Method 3066.1, MIL-STD 750A.

6.2.6 (continued)

The unit shall be considered failed if the $V_{\mbox{\footnotesize{BE}}}(\mbox{Sat})$ is greater than 1.0 VDC.

6.2.7 Collector - Emitter Saturation Voltage

$$I_{C} = 10 \text{ mA dc}$$

$$I_B = 1.0 \text{ mA dc}$$

The collector - emitter saturation voltage shall be tested in accordance with Method 3071.1, MIL-STD 75CA.

The unit shall be considered failed if the $V_{CE}^{}(Sat)$ is greater than 0.4 VDC.

6.2.8 Unity Gain Frequency

$$v_{CE} = 15 \text{ VDC}$$

$$I_C = 1 \text{ mA}$$

$$f = 100 \text{ MHz}$$

The Unity Gain (f_t) shall be tested in accordance with Method 3261, Use, Method 3306.1, Condition A to determine the magnitude of the common emitter small-signal short-circuit transfer ratio. The unit shall be considered failed if the f_t is less than 500 MHz.

6.3 Electrical Intermediate

6.3.1 Forward - Current Transfer Ratio (h_{FE})

$$V_{CE} = 2.0 \text{ VDC}$$

$$I_C = 2.0 \text{ mA dc (pulsed)}$$

Pulse Width = $300 \mu s$

6.3.1 (continued)

Duty Cycle = 1%.

The forward current transfer ratio (h_{FE}) shall be tested in accordance with Method 3076.1, MIL-STD 750A.

The unit shall be considered failed if the $h_{\mbox{\scriptsize FE}}$ is less than 75.

6.4 Environmental

6.4.1 High Temperature Storage

The transistor shall be exposed to a temperature of 200°C, +0°C, -10°C, for a period of 48 hours, +24 hours, -0 hours.

6.4.2 Temperature Cycling

The transistor shall be tested in accordance with MIL-STD 202D, Method 102, Condition C. The transistor shall be subjected to five cycles performed continuously.

6.4.3 Acceleration

The transistor shall be tested in accordance with MIL-STD 750A, Method 2006. The transistor shall be accelerated for one minute in the Y_1 plane at a level of 20,000 g's.

6.4.4 Fine Leak

The transistor shall be tested in accordance with MIL-STD 202D, Method 112, Condition C. The units shall be subjected to a pressure of 60 psig, + 10 psig, in a helium atmosphere for a minimum period of four hours.

6.4.4 (continued)

The units shall then be placed in a mass spectrometer to measure helium leakage. Units exhibiting leak rates in excess of 10⁻⁸ atm-cc/sec shall be considered failed.

6.4.5 Gross Leak

The transistor shall be tested in accordance with MIL-STD 883D, Method 1014, Condition C, at a temperature of 125°C ± 10°C. The unit shall be submerged to a minimum of one inch into the hot liquid and observed for a minimum of one minute. Any unit emitting a continuous stream of bubbles shall be considered failed.

6.4.6 Vibration

Each transistor shall be tested in accordance with MIL-STD 202D, Method 204A, Cond. C. The following shall apply:

- 1. Non-operating
- Perform 2.4.2 part 2 only. The entire frequency range of 55 to 2000 cycles (no return sweep) shall be traversed in 10 ± 3 minutes.
- 3. Paragraph 6.3, Electrical Intermediate, shall be run after completion of vibration testing.

6.5 Burn-In

6.0.

6.5.1 Heat Sink

The transistor shall be mounted on a heat sink whose temperature will be maintained at 70°C, +15°C, -5°C.

6.5.2 Test Conditions

The collector to emitter voltage V_{CE} shall be set at 10 volts. The collector current I_{C} shall be set to 15 mA dc.

6.5.3 Test Length

The test shall be run for 168 hours, +12, -0 hours. Section 6.2 of this specification shall be rerun, and any transistor failing any portion of Section 6.2 shall be considered failed. Prior to the testing of Section 6.2, the transistor shall be allowed to return to ambient temperature (25°C).

6.6 Radiographic Examination

6.6.1 Procedure

The transistor shall be X-rayed in two mutually perpendicular planes. Maintain unit identity between units and film position.

6.6.2 Acceptance

Examine film, using 100X minimum magnification, and reject units having the following defects or characteristics:

- a. Poor chip mounting: any unit displaying less than 50% contact between chip and mounting base.
- b. Extraneous material: any unit displaying extraneous or foreign material that is not a normal portion of the product.

6.6.2 (continued)

- c. Bonds and bond wires: any bond or bond wires that are misplaced, loose or extra. Bond wires that are within 0.005 inch of any area not electrically common with the bond wire.
- d. Miscellaneous: any anomaly which, in the opinion of the inspector, will degrade performance or reliability of the unit.

TABLE I ELECTRICAL AND ENVIRONMENTAL REQUIREMENTS

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SCREENING SPECIFICATION FOR TRANSISTOR 2N2609

Document Number EPS-214

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

SCREENING SPECIFICATION FOR TRANSISTOR 2N2609

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Electron-Proton Spectrometer Program
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1.0 SCOPE

This document defines the necessary requirements for the screening of transistor 2N2609 to satisfy NASA high reliability requirements for the Electron-Proton Spectrometer (EPS).

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of application shall form a part of this specification to the extent specified herein.

MIL-STD 750A, Test Methods for Semiconductor Devices

MIL-STD 202D, Test Methods for Electronic and Electrical Component Parts

NHB5300.4(1A), Reliability Program Provisions for Aeronautical and Space Systems Contractors

3.0 REQUIREMENTS FOR TEST LABORATORY SUBCONTRACTORS

3.1 Facilities

The subcontractor shall provide and maintain adequate facilities for inspecting and testing electronic components described in this specification.

3.2 Inspection, Measuring and Test Equipment

The subcontractor shall maintain and control inspection, measuring and test equipment in accordance with NHB5300.4 (lA). Upon request, the subcontractor shall submit to

3.2 (continued)

Lockheed Electronics Company (LEC) for approval, a listing of equipment and their intended usage.

3.3 Calibration Records

The subcontractor shall prepare and have available for review by LEC, a written procedure and schedule for the maintenance and calibration of such equipment based on type, accuracy, purpose and degree of usage. Records of calibration shall be maintained and the calibration due date, or other identification attesting the due date of the next calibration shall be displayed on each item of this equipment.

3.4 Calibration Traceability

Standards used for calibration shall be traceable to the National Bureau of Standards (NBS). No more than five steps shall be used to establish traceability from actual inspection and test equipment to the NBS.

4.0 RELIABILITY AND QUALITY ASSURANCE PROVISIONS

4.1 General

The procedures and methods of testing the transistors in accordance with this specification shall meet the general requirements of MIL-STD 202D.

4.2 Screening Inspections and Tests

Each transistor supplied shall be submitted in the sequence specified to the inspections and tests of Table 1.

4.3 Inspection and Test Data

A summary of the transistor data obtained during each inspection or test shall be prepared and submitted with the transistors to LEC. This summary shall list all transistors that failed electrical tests and the number that failed each parameter. The raw test data shall also be delivered to LEC with the transistors.

4.4 Inspection and Test Records

Inspection and test records shall include part number, serial number, inspection or test number, number of defects found, kinds of defects, acceptance number and the disposition inspector's identity. Records of all inspections and tests shall be delivered to LEC along with the transistors.

4.5 Serialization

All transistors shall be serialized in a manner that will be permanent during use and testing periods.

4.6 Reject Disposition

Each transistor that fails the inspections and tests of Table 1 shall be marked with a red dot and placed in a reject bag, and tagged to note unit part number, serial number and inspection or test failed. These units shall also be delivered to LEC. Use 3M Company's 3M-401-5D paint for marking of parts.

4.7 Marking of Acceptable Parts

Transistors which meet the requirements of this specification shall be identified with a permanent green dot placed on the body of the transistor. The dot shall be placed on the body at a point which will not interfere with reading the manufacturer's part number or date code identification. Use 3M Company's 3M-401-G3 paint for marking of parts.

4.8 Acceptance

Preliminary inspection for compliance with the requirements of this specification may be performed at origin by an authorized representative of the Government. Final acceptance for the Contracting Officer shall be performed by the assigned project engineer.

4.9 Certificate of Compliance

A certificate of compliance signed by the Quality Control manager shall be included with the device shipment. It shall verify that the transistors were processed in accordance with this specification and that all requirements have been met.

4.10 Notification of Government Source Inspector

The Government Representative who has been delegated quality assurance function at your test facility shall be notified immediately upon receipt of this order.

5.0 PREPARATION FOR DELIVERY

5.1 Type of Packaging

Each transistor shall be packaged in a suitable container which will protect the body and leads of the device during shipment. The rejected parts shall be identified and packaged separately from the acceptable items.

5.2 Packaging for Shipment

The transistors packaged in accordance with paragraph 5.1 shall be packed to afford protection against damage during direct shipment from the test laboratory to the receiving activity. Containers will comply with the carrier's rules and regulations applicable to the mode of transportation.

6.0 INSPECTION AND TEST METHODS

6.1 External Visual

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The transistors shall be examined to verify that the materials, design, construction, marking and workman-ship are in accordance with the applicable requirements.

6.2 Electrical

All electrical tests shall be performed at an ambient temperature of 25°C unless otherwise noted.

6.2.1 Gate-Source Reverse Current

$$v_{DS} = 0$$

 $v_{GS} = -5 \text{ V}$

6.2.1 (continued)

Connect the transistor as shown in Figure 1. The specified DC voltage shall be applied between the gate and the source with the drain connected to the source.

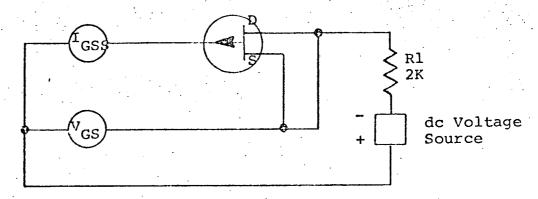


FIGURE 1

The unit shall be considered failed if the $I_{\mbox{GSS}}$ is greater than 30 nA.

6.2.2 Gate-Drain Breakdown Voltage

$$I_G = 1 \mu A$$
 $V_{DS} = 0$

Connect the transistor as shown in Figure 2.

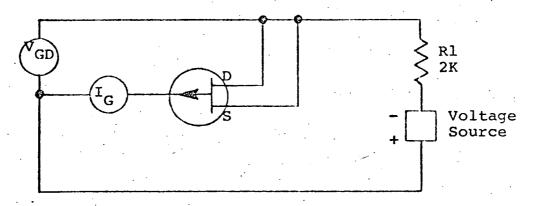


FIGURE 2

6.2.2 (continued)

The voltage shall be gradually increased from zero to the specified minimum value of $\mathrm{BV}_{\mathrm{GDS}}=30\mathrm{V}$ or until the specified gate current is reached. The device is acceptable if the specified limit for $\mathrm{BV}_{\mathrm{GDS}}$ is reached before the current reaches the specified value. If the specified current is reached first, the device is rejected.

6.2.3 Drain Current at Zero Gate Voltage

$$v_{DS} = -5v$$

$$v_{GS} = 0$$

Connect the transistor as shown in Figure 3.

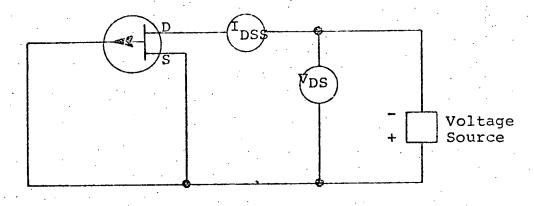


FIGURE 3

The specified drain to source voltage is applied. The device is accepted if the drain current I_{DSS} falls between the following values:

$$I_{DSS}$$
 (min) = 2.0 mA
 I_{DSS} (max) = 10.0 mA

6.2.4 Gate-Source Pinch-Off Voltage

$$V_{DS} = -5V$$

$$I_{D} = 1 \mu A$$

Connect the transistor as shown in Figure 4.

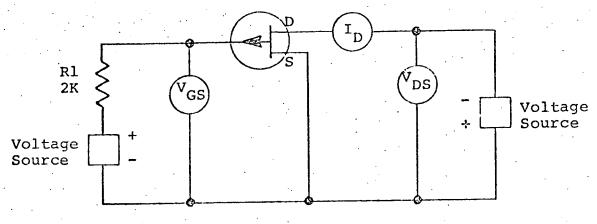


FIGURE 4

The drain-to-source voltage is applied and the gate-to-source voltage increased until the drain current reads 1 μ A, for $V_p(min)=lV$, $V_p(max)=4V$. The device is acceptable if the gate-to-source voltage (V_p) falls within the specified limits.

6.3 <u>Intermediate Electrical</u>

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6.3.1 Drain-Current at Zero-Gate Voltage

$$V_{DS} = -5V$$

 $V_{GS} = 0$

6.3.1 (continued)

Connect the transistors as shown in Figure 3. The specified $V_{\rm DS}$ is applied. The device is acceptable if the drain current ($I_{\rm DSS}$) falls between $I_{\rm DSS}$ (min) = 2.0 mA and $I_{\rm DSS}$ (max) = 10.0 mA.

6.3.2 Gate-Source Reverse Current

$$V_{GS} = 5 V$$

$$V_{DS} = 0$$

Connect transistor as shown in Figure 1. The specified DC voltage shall be applied between the gate and the source with the drain connected to the source. The device is considered failed if the $I_{\rm GSS}$ is greater than 30 nA.

6.4 Environmental

6.4.1 High Temperature Storage

The transistor shall be exposed to a temperature of 200°C +0°C, -10°C for a period of 48 hours, +24 hours, -0 hours.

6.4.2 Temperature Cycling

The transistor shall be tested in accordance with MIL-STD 202D, Method 102, Condition C. The transistor shall be subjected to five cycles performed continuously.

6.4.3 Acceleration

The transistor shall be tested in accordance with MIL-STD 750A, Method 2006. The transistor shall be accelerated for one minute in the Y_1 plane at a level of 20,000 g's.

6.4.4 Fine Leak

The transistor shall be tested in accordance with MIL-STD 202D, Method 112, Condition C. The units shall be subjected to a pressure of 60 psig ± 10 psig, in a helium atmosphere for a minimum period of four hours. The units shall then be placed in a mass spectrometer to measure helium leakage. Units exhibiting leak rates in excess of 10⁻⁸ atm-cc/sec shall be considered failed.

6.4.5 Gross Leak

The transistor shall be tested in accordance with MIL-STD 202D, Method 112, Condition A, using ethylene glycol at a temperature of 125°C, ± 10°C. The unit shall be submerged to a minimum of one inch into the hot liquid and observed for a minimum of one minute. Any unit emitting a continuous stream of bubbles shall be considered failed.

6.4.6 Vibration

Each device shall be tested in accordance with MIL-STD 202D, Method 204A, Condition C. The following shall apply.

- 1. Non-operating
- 2. Perform 2.4.2, Part 2 only
 - (a) The entire frequency range of 55 to 2000 cycles (no return sweep) shall be traversed in 10 ± 3 minutes

6.4.6 (Continued)

3. Paragraph 6.3, Electrical Intermediate, shall be run after completion of vibration testing.

6.5 Burn-In

6.5.1 Heat Sink

The transistor shall be mounted on a heat sink whose temperature will be maintained at 70°C, +15°C, -5°C.

6.5.2 Test Conditions

$$v_{DS} = -5V$$

$$I_D = I_{DSS}$$

6.5.3 Test Length

The test shall be run for 168 hours, +12 hours, -0 hours. Section 6.2 of this specification shall be rerun, and any transistor failing any portion of Section 6.2 shall be considered failed.

6.6 Radiographic Examination

6.6.1 Procedure

The transistor shall be X-rayed in two mutually perpendicular planes. Maintain unit identity between units and film position.

6.6.2 Acceptance

Examine film, using 100X minimum magnification, and reject units having the following defects or characteristics.

- a. Poor chip mounting: any unit displaying less than 50% contact between chip and mounting base.
- b. Extraneous material: any unit displaying extraneous or foreign material that is not a normal portion of the product.
- c. Bonds and bond wires: any bond or bond wires that are misplaced, loose or extra. Bond wires that are within 0.005 inch of any area not electrically common with the bond wire.
- d. Miscellaneous: any anomaly which, in the opinion of the inspector, will degrade performance or reliability of the unit.

TABLE I

ELECTRICAL AND ENVIRONMENTAL REQUIREMENTS

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SCREENING SPECIFICATION
FOR
TRANSISTOR 2N5333

Document Number EPS-179

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

SCREENING SPECIFICATION FOR TRANSISTOR 2N5333

Prepared by:

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4.5

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1.0 SCOPE

This document defines the necessary requirements for the screening of Transistor 2N5333 to satisfy NASA high reliability requirements for the Electron-Proton Spectrometer (EPS).

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of application shall form a part of this specification to the extent specified herein.

MIL-STD 202D, Test Methods for Electronic and Electrical Component Parts

MIL-STD 750A, Test Methods for Semiconductor Devices

MIL-STD 883, Test Methods and Procedures for Microelectronics

NHB53-0.4(lA), Reliability Program Provisions for Aeronautical and Space Systems Contractors

3.0 REQUIREMENTS FOR TEST LABORATORY SUBCONTRACTORS

3.1 Facilities

The subcontractor shall provide and maintain adequate facilities for inspecting and testing electronic components described in this specification.

3.2 Inspection, Measuring and Test Equipment

The subcontractor shall maintain and control inspection, measuring and test equipment in accordance with NHB5300.4(1A). Upon request, the subcontractor shall submit to Lockheed Electronics Company (LEC) for approval, a listing of equipment and their intended usage.

3.3 Calibration Records

The subcontractor shall prepare and have available for review by LEC, a written procedure and schedule for the maintenance and calibration of such equipment based on type, accuracy, purpose and degree of usage. Records of calibration shall be maintained and the calibration due date, or other identification attesting the due date of the next calibration, shall be displayed on each item of this equipment.

3.4 Calibration Traceability

Standards used for calibration shall be traceable to the National Bureau of Standards (NBS). No more than five steps shall be used to establish traceability from actual inspection and test equipment to the NBS.

4.0 RELIABILITY AND QUALITY ASSURANCE PROVISIONS

4.1 General

4.1

The procedures and methods of testing the transistors in accordance with this specification shall meet the general requirements of MIL-STD 202D.

4.2 Screening Inspections and Tests

Each transistor supplied shall be submitted in the sequence specified to the inspections and tests of Table 1.

4.3 Inspection and Test Data

A summary of the transistor data obtained during each inspection or test shall be prepared and submitted with

4.3 (continued)

the transistors to LEC. This summary shall list all transistors that failed electrical tests and the number that failed each parameter. The raw test data shall also be delivered to LEC with the transistors.

4.4 Inspection and Test Records

Inspection and test records shall include part number, serial number, inspection or test number, number of defects found, kinds of defects, acceptance number, and the disposition inspector's identity. Records of all inspections and tests shall be dleivered to LEC along with the transistors.

4.5 Serialization

All transistors shall be serialized in a manner that will be permanent during use and testing periods.

4.6 Reject Disposition

Each transistor that fails the inspections and tests of Table 1 shall be marked with a red dot and placed in a reject bag, and tagged to note unit part number, serial number and inspection or test failed. These units shall also be delivered to LEC. Use Minnesota Mining and Manufacturing Co's 3M-401-5D paint for marking of parts. Mixing and application should be done in accordance with manufacturer's specification sheet.

4.7 Marking of Acceptable Parts

Transistors which meet the requirements of this specification shall be identified with a permanent green dot placed on the body of the transistor. The dot shall be placed

4.7 (continued)

on the body at a point which will not interfere with reading the manufacturer's part number or date code identification. Use Minnesota Mining and Manufacturing Co's 3M-401-G3 paint for marking of parts. Mixing and application should be done in accordance with manufacturer's specification sheet.

4.8 Acceptance

6.6

6.2

Preliminary inspection for compliance with the requirements of this specification may be performed at origin by an authorized representative of the Government. Final acceptance for the Contracting Officer shall be performed by the assigned project engineer.

4.9 Certificate of Compliance

A certificate of compliance signed by the Quality Control Manager shall be included with the device shipment. It shall verify that the transistors were processed in accordance with this specification and that all requirements have been met.

4.10 Notification of Government Source Inspector

The Government Representative who has been delegated quality assurance function at your test facility shall be notified immediately upon receipt of this order.

5.0 PREPARATION FOR DELIVERY

5.1 Type of Packaging

Each transistor shall be packaged in a suitable container which will protect the body and leads of the device during shipment. The rejected parts shall be identified and packaged separately from the acceptable items.

5.2 Packaging for Shipment

The transistors packaged in accordance with Paragraph 5.1 shall be packed to afford protection against damage during direct shipment from the test laboratory to the receiving activity. Containers will comply with the carrier's rules and regulations applicable to the mode of transportation.

6.0 INSPECTION AND TEST METHODS

6.1 External Visual

The transistors shall be examined to verify that the materials, design, construction, marking and workmanship are in accordance with the applicable requirements.

6.2 Electrical

All electrical tests shall be performed at an ambient temperature of 25°C unless otherwise noted.

6.2.1 Collector Cutoff Current

$$V_{CE} = -40 \text{ VDC}$$

$$I_{B} = 0$$

6.2.1 (continued)

The collector cutoff current shall be tested in accordance with Method 3036, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $I_{\mbox{\footnotesize CEO}}$ is greater than -50 μA dc.

6.2.2 Collector-Emitter Breakdown Voltage

$$I_C = -30$$
 mA (pulsed)
 $I_B = 0$
Pulse Width = 300 μ s
Duty Cycle = 1%

The collector-emitter breakdown voltage shall be tested in accordance with Method 3001.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if ${\ensuremath{\mathsf{BV}}}_{\ensuremath{\mathsf{CEO}}}$ is less than -80 VDC.

6.2.3 Emitter-Base Voltage

$$V_{CE} = -4 \text{ VDC}$$
 $I_{C} = -2A$

Pulse Width = 300 μ sec
Duty Cycle = 1%

The emitter-base voltage shall be tested in accordance with Method 3026.1, Condition D, MIL-STD 750A. The unit shall be considered failed if the $V_{\rm BE}$ is greater

than -1.5 VDC.

6.2.4 Emitter Cutoff Current

$$V_{EB} = -4V$$
 $I_{C} = 0$

The emitter cutoff current shall be tested in accordance with Method 3061.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $\boldsymbol{J}_{\mbox{EBO}}$ is greater than -1 $\mu A_{\mbox{\tiny \star}}$

6.2.5 Forward-Current Transfer Ratio (h_{FE})

$$V_{CE} = -4 \text{ VDC}$$
 $I_{C} = -1 \text{ ADC (pulsed)}$
 $Pulse Length = 300 \mu s$
 $Pulse Cycle = 1%$

The forward current transfer ratio shall be tested in accordance with Method 3076.1, MIL-STD 750A.

The unit shall be considered failed if the $h_{\mbox{\scriptsize FE}}$ is less than 30.

6.2.6 Collector-Emitter Saturation Voltage

$$I_C = -1.0$$
 ADC (pulsed) $I_B = -0.1$ ADC (pulsed) Pulse Width = 300 μ s Duty Cycle = 1%

6.2.6 (continued)

The collector-emitter saturation voltage shall be tested in accordance with Method 3071.1, MIL-STD 750A.

The unit shall be considered failed if the V_{CE} (sat) is greater than -0.45 VDC.

6.3 Electrical Intermediate

6.3.1 Forward-Current Rransfer Ratio (h FE)

 $V_{CE} = -4 \text{ VDC}$ $I_{C} = -1 \text{ ADC (pulsed)}$ $Pulse Width = 300 \mu s$ Puty Cycle = 1%

The forward current transfer ratio $(h_{\rm FE})$ shall be tested in accordance with Method 3076.1, MIL-STD 750A.

The unit shall be considered failed if the $h_{\mbox{\scriptsize FE}}$ is less than 30.

6.4 Environmental

6.6.4.1 High Temperature Storage

The transistor shall be exposed to a temperature of 200°C, +0°C, -10°C, for a period of 48 hours, +24 hours, -0 hours.

6.4.2 Temperature Cycling

The transistor shall be tested in accordance with MIL-STD 202D, Method 102, Condition C. The transistor shall be subjected to five cycles performed continuously.

6.4.3 Acceleration

The transistor shall be tested in accordance with MIL-STD 750A, Method 2006. The transistor shall be accelerated for one minute in the Y_1 plane at a level of 20,000 g's.

6.4.4 Fine Leak

The transistor shall be tested in accordance with MIL-STD 202D, Method 112, Condition C. The units shall be subjected to a pressure of 60 psig + 10 psig, in a helium atmosphere for a minimum period of four hours. The units shall then be placed in a mass spectrometer to measure helium leakage. Units exhibiting leak rates in excess of 10⁻⁸ atm-cc/sec shall be considered failed.

6.4.5 Gross Leak

The transistor shall be tested in accordance with MIL-STD 883D, Method 1014, Condition C, at a temperature of 125°C ± 10°C. The unit shall be submerged to a minimum of one inch into the hot liquid and observed for a minimum of one minute. Any unit emitting a continuous stream of bubbles shall be considered failed.

6.4.6 Vibration

Each device shall be tested in accordance with MIL-STD 202D, Method 204A, Condition C. The following shall apply.

Non-operating

6.4.6 (Continued)

- 2. Perform 2.4.2 Part 2 only
 - (a) The entire frequency range of 55 to 2000 cycles (no return sweep) shall be traversed in 10 ± 3 minutes
- Paragraph 6.3, Electrical Intermediate, shall be run after completion of vibration testing.

6.5 Burn-In

6.5.1 Heat Sink

The transistor shall be mounted on a heat sink whose temperature will be maintained at 70°C, +15°C, -5°C.

6.5.2 Test Conditions

The collector to emitter voltage $V_{\rm CE}$ shall be set at -10V. The collector current $I_{\rm C}$ shall be set at -1 ADC.

6.5.3 Test Length

The test shall be run for 168 hours, +12 hours, -0 hours. Section 6.2 of this specification shall be rerun, and any transistor failing any portion of Section 6.2 shall be considered failed. Prior to the testing of Section 6.2, the transistor shall be allowed to return to ambient temperature (25°C).

6.6 Radiographic Examination

6.6.1 Procedure

The transistor shall be X-rayed in two mutually perpendicular planes. Maintain unit identity between units and film position.

6.6.2 Acceptance

Examine film, using 10X minimum magnification, and reject units having the following defects or characteristics:

- a. Poor chip mounting: any unit displaying less than 50% contact between chip and mounting base.
- b. Extraneous material: Any unit displaying extraneous or foreign material that is not a normal portion of the product.
- c. Bonds and bond wires: any bond or bond wires that are misplaced, loose or extra. Bond wires that are within 0.005 inch of any area not electrically common with the bond wire.
- d. Miscellaneous: any anomaly which, in the opinion of the inspector, will degrade performance or reliability of the unit.

TABLE 1

ELECTRICAL AND ENVIRONMENTAL REQUIREMENTS

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SCREENING SPECIFICATION
FOR
TRANSISTOR JAN2N3811

Document Number EPS-129

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas
Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

SCREENING SPECIFICATION FOR TRANSISTOR 2N3811

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0 SCOPE

This document defines the necessary requirements for screening of Transistor 2N3811 to satisfy NASA High Reliability requirements for the Electron-Proton Spectrometer (EPS).

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of application shall form a part of this specification to the extent specified herein.

MIL-STD 202D, Test Methods for Electronic and Electrical component parts

MIL-STD 750A, Test Methods for Semiconductor Devices MIL-STD 883, Test Methods and Procedures for Micro-electronics

NHB 5300.4(1A), Reliability Program Provisions for Aeronautical and Space Systems Contractors

3.0 REQUIREMENTS FOR TEST LABORATORY SUBCONTRACTORS

3.1 Facilities

The subcontractor shall provide and maintain adequate facilities for inspecting and testing electronic components described in this specification.

3.2 Inspection, Measuring and Test Equipment

The subcontractor shall maintain and control inspection, measuring and test equipment in accordance with NHB 5300.4(1A). Upon request, the subcontractor shall submit to Lockheed Electronics Co. (LEC) for approval, a listing of equipment and their intended usage.

3.3 Calibration Records

The subcontractor shall prepare and have available for review by LEC, a written procedure and schedule for the maintenance and calibration of such equipment based on type, accuracy, purpose and degree of usage. Records of calibration shall be maintained and the calibration due date, or other identification attesting the due date of the next calibration, shall be displayed on each item of this equipment.

3.4 Calibration Traceability

Standards used for calibration shall be traceable to the National Bureau of Standards (NBS). No more than five steps shall be used to establish traceability from actual inspection and test equipment to the NBS.

4.0 QUALITY ASSURANCE PROVISIONS

4.1 General

The procedures and methods of testing the transistors in accordance with this specification shall meet the general requirements of MIL-STD 202D.

4.2 Screening Inspections and Tests

Each transistor supplied shall be submitted in the sequence specified to the inspections and tests of Table I.

4.3 Inspection and Test Data

A summary of the transistor data obtained during each inspection or test shall be prepared and submitted along with the transistors to LEC. This summary shall list all transistors that failed electrical tests and the number that failed each parameter. The raw test data shall also be delivered to LEC with the transistors.

4.4 Inspection and Test Records

Inspection and test records shall include part number, serial number, inspection or test number, number of defects found, kinds of defects, acceptance number and the disposition inspector's identity. Records of all inspections and tests shall be delivered to LEC along with the transistors.

4.5 <u>Serialization</u>

All transistors shall be serialized in a manner that will be permanent during the testing period.

4.6 Reject Disposition

Each transistor that fails the inspections and tests of Table I shall be marked with a red dot and placed in a

4.6 (continued)

reject bag and tagged to note unit part number, serial number and inspection or test failed. These units shall also be delivered to LEC. Use 3M-401-5D paint for marking of parts.

4.7 Marking of Acceptable Parts

Transistors which meet the requirements of this specfication shall be identified with a permanent green dot placed on the body of the transistor. The dot shall be placed on the body at a point which will not interfere with reading the manufacturer's part number or date code identification. Use 3M-401-G3 paint for marking of parts.

:4:8 Acceptance

Preliminary inspection for compliance with the requirements of this specification may be performed at origin by an authorized representative of the Government.

Final acceptance for the Contracting Officer shall be performed by the assigned project engineer.

4.9 Certificate of Compliance

A certificate of compliance signed by the Quality Control manager shall be included with the device shipment. It shall verify that the transistors were processed in accordance with this specification and that all requirements have been met.

1.10 Notification of Government Source Inspector

The Government Representative who has been delegated quality assurance function at your test facility shall be notified immediately upon receipt of this order.

5.0 PREPARATION FOR DELIVERY

5.1 Type of Packaging

Each transistor shall be packaged in a suitable container which will protect the body and leads of the device during shipment. The rejected parts shall be identified and packaged separately from the acceptable items.

5.2 Packing for Shipment

The transistors packaged in accordance with Paragraph 5.1 shall be packed to afford protection against damage during direct shipment from the test laboratory to the receiving activity. Containers will comply with the carriers rules and regulations applicable to the mode of transportation.

6.0 INSPECTION AND TEST METHODS

6.1 External Visual

The transistors shall be examined to verify that the materials, design, construction, marking and workmanship are in accordance with the applicable requirements.

6.2 Electrical

6.2.5

All electrical tests shall be performed at an ambient temperature of 25°C unless otherwise noted. Both sections of the dual device shall be tested separately as defined in paragraphs 6.2 and 6.3.

6.2.1 Collector-Base Cutoff Current

$$V_{CB} = 50 \text{ VDC}$$
 $I_{E} = 0$

The collector-base cutoff current shall be tested in accordance with Method 3036, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $I_{\mbox{CBO}}$ is greater than 0.01 $\mu\mbox{Adc}$.

6.2.2 Collector-Base Breakdown Voltage

$$I_C - 10 \mu Adc$$
 $I_E = 0$

The collector-base breakdown voltage shall be tested in accordance with Method 3001.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if $\ensuremath{\text{BV}}_{\ensuremath{\text{CBO}}}$ is less than 60 VDC.

6.2.3 Emitter-Base Breakdown Voltage

$$I_E = 10 \mu Adc$$
 $I_C = 0$

.2.3 (continued)

The emitter-base breakdown voltage shall be tested in accordance with Method 3026.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if the ${}^{\mathrm{BV}}_{\mathrm{EBO}}$ is less than 5.0 VDC.

6.2.4 Collector-Emitter Breakdown Voltage

 $I_C = 10 \text{ mAdc}$ $I_B = 0 \text{ (pulsed)}$ Pulse Width = 300 μ s
Duty Cycle = 1%

The collector-emitter breakdown voltage shall be tested in accordance with Method 3011.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $^{\mathrm{BV}}_{\mathrm{CEO}}$ is less than 60 VDC.

6.2.5 Forward Current Transfer Ratio (H_{FE})

V_{CE} = 5.0 VDC I_C = 100 μAdc Pulse Length = 300 μs Duty Cycle = 1%

The forward current transfer ratio shall be tested in accordance with Method 3076.1, MIL-STD 750A.

6.2.5 (continued)

The unit shall be considered failed if the $h_{\mbox{\scriptsize FE}}$ is less than 300.

6.2.6 Base-Emitter Saturation Voltage

$$I_C = 100 \mu Adc$$

 $I_B = 10 \mu Adc$

The base-emitter saturation voltage shall be tested in accordance with Method 3066.1, MIL-STD 750A.

The unit shall be considered failed if the $V_{\mbox{\footnotesize BE}}$ (Sat) is greater than 0.7 VDC.

6.2.7 Collector-Emitter Saturation Voltage

$$I_C = 100 \mu Adc$$

 $I_B = 10 \mu Adc$

The collector-emitter saturation voltage shall be tested in accordance with Method 3071.1, MIL-STD 750A.

The unit shall be considered failed if the $V_{\hbox{\footnotesize CE}}$ (Sat) is greater than 0.2 VDC.

- 6.3 Electrical Intermediate
- 6.3.1 Forward Current Transfer Ratio (h_{FE})

$$V_{CE} = 5.0 \text{ VDC}$$
 $I_{C} = 100 \text{ µAdc (pulsed)}$

6.3.1 (continued)

Pulse Width = 300 μ s Duty Cycle = 1%

The forward current transfer ratio ($h_{\rm FE}$) shall be tested in accordance with Method 3076.1, MIL-STD 750A.

The unit shall be considered failed if the $h_{\mbox{\scriptsize FE}}$ is less than 300.

6.4 Environmental

6.4.1 High Temperature Storage

The transistor shall be exposed to a temperature of 200°C, +0°, -10°, for a period of 48 hours, +24 hours, -0 hours.

6.4.2 Temperature Cycling

The transistor shall be tested in accordance with MIL-STD 202D, Method 102, Condition C. The transistor shall be subjected to five (5) cycles performed continuously.

6.4.3 Acceleration

The transistor shall be tested in accordance with MIL-STD 750A, Method 2006. The transistor shall be accelerated for one minute in the Y₁ plane at a level of 20,000 g's.

6.4.4 Fine Leak

The transistor shall be tested in accordance with MIL-STD 202D, Method 112, Condition C. The units shall be subjected to a pressure of 60 psig ± 10 psig, in a helium atmosphere for a minimum period of four hours. The units shall then be placed in a mass spectrometer to measure helium leakage. Units exhibiting leak rates in excess of 10⁻⁸ atm-cc/sec shall be considered failed.

6.4.5 Gross Leak

The transistor shall be tested in accordance with MIL-STD 883D, Method 1014, Condition C, at a temperature of 125°C ±10°C. The unit shall be submerged to a minimum of one inch into the hot liquid and observed for a minimum of one minute. Any unit emitting a continuous stream of bubbles shall be considered failed.

6.4.6 Vibration

Each device shall be tested in accordance with MIL-STD-202D, Method 204A, Condition C. The following shall apply:

- Non-operating
- 2. Perform 2.4.2 Part 2 only
 - (a) The entire frequency range of 55 to 2000 cycles (no return sweep) shall be traversed in 10±3 minutes

6.4.6 (continued)

3. Paragraph 6.3 Electrical Intermediate shall be run after Completion of Vibration Testing.

6.5 Burn-In

6.5.1 Heat Sink

The transistor shall be mounted on a heat sink whose temperature will be maintained at 70°C, +15°C, -5°C.

6.5.2 Test Conditions

The collector to emitter voltage V_{CE} shall be set at 34 volts. The collector current I_{C} shall be set to 3 mAdc each portion.

6.5.3 Test Length

The test shall be run for 168 hours, +12 hours, -0 hours. Section 6.2 of this specification shall be rerun, and any transistor failing any portion of Section 6.2 shall be considered failed. Prior to the testing of Section 6.2, the transistor shall be allowed to return to ambient temperature (25°C).

6.6 Radiographic Examination

6.6.1 Procedure

The transistors shall be X-rayed in two mutually perpendicular planes. Maintain unit identity between units and film position.

6.6.2 Acceptance

Examine film, using 100X minimum magnification, and reject units having the following defects or characteristics.

- a. Poor chip mounting: any unit displaying less than 50% contact between chip and mounting base.
- b. Extraneous material: any unit displaying extraneous or foreign material that is not a normal portion of the product.
- that are misplaced, loose or extra. Bond wires that are within 0.005 inch of any area not electrically common with the bond wire.
- d. Miscellaneous: any anomaly which, in the opinion of the inspector, will degrade performance or reliability of the unit.

TABLE 1 ELECTRICAL AND ENVIRONMENTAL REQUIREMENTS

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SCREENING SPECIFICATION FOR TRANSISTOR 2N4878

Document Number EPS-175

Prepared by
Lockheed Electronics Company
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Under Contract NAS 9-11373
for

National Aeronautics and Space Administration

Manned Spacecraft Center

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SCREENING SPECIFICATION FOR TRANSISTOR 2N4878

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1.0 SCOPE

This document defines the necessary requirements for the screening of Transistor 2N4878 to satisfy NASA high reliability requirements for the Electron-Proton Spectrometer (EPS).

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of application shall form a part of this specification to the extent specified herein.

MIL-STD 202D, Test Methods for Electronic and Electrical Component Parts

MIL-STD 750A, Test Methods for Semiconductor Devices
MIL-STD 883, Test Methods and Procedures for Microelectronics

NHB 5300.4(1A), Reliability Program Provisions for Aeronautical and Space Systems Contractors

3.0 REQUIREMENTS FOR TEST LABORATORY SUBCONTRACTORS

3.1 Facilities

The subcontractor shall provide and maintain adequate facilities for inspecting and testing electronic components described in this specification.

3.2 Inspection, Measuring and Test Equipment

The subcontractor shall maintain and control inspection, measuring and test equipment in accordance with NHB 5300.4(1A). Upon request, the subcontractor shall submit

3.2 (continued)

to Lockheed Electronics Company (LEC) for approval, a listing of equipment and their intended usage.

3.3 Calibration Records

The subcontractor shall prepare and have available for review by LEC, a written procedure and schedule for the maintenance and calibration of such equipment based on type, accuracy, purpose and degree of usage. Records of calibration shall be maintained and the calibration due date, or other identification attesting the due date of the next calibration, shall be displayed on each item of this equipment.

3.4 Calibration Traceability

Standards used for calibration shall be traceable to the National Bureau of Standards (NBS). No more than five steps shall be used to establish traceability from actual inspection and test equipment to the NBS.

4.0 RELIABILITY AND QUALITY ASSURANCE PROVISIONS

4.1 General

The procedures and methods of testing the transistors in accordance with this specification shall meet the general requirements of MIL-STD 202D.

4.2 Screening Inspections and Tests

Each transistor supplied shall be submitted in the sequence specified to the inspections and tests of Table 1.

4.3 Inspection and Test Data

A summary of the transistor data obtained during each inspection or test shall be prepared and submitted with the transistors to LEC. This summary shall list all transistors that failed electrical tests and the number that failed each parameter. The raw test data shall also be delivered to LEC with the transistors.

4.4 Inspection and Test Records

Inspection and test records shall include part number, serial number, inspection or test number, number of defects found, kinds of defects, acceptance number, and the disposition inspector's identity. Records of all inspections and tests shall be delivered to LEC along with the transistors.

4.5 Serialization

All transistors shall be serialized in a manner that will be permanent during use and testing periods.

4.6 Reject Disposition

Each transistor that fails the inspections and tests of Table 1 shall be marked with a red dot and placed in a reject bag, and tagged to note unit part number, serial number and inspection or test failed. These units shall also be delivered to LEC. Use Minnesota Mining and Manufacturing Co.'s 3M-401-5D paint for marking of parts.

Mixing and application should be done in accordance with manufacturer's specification sheet.

4.7 Marking of Acceptable Parts

Transistors which meet the requirements of this specification shall be identified with a permanent green dot placed on the body of the transistor. The dot shall be placed on the body at a point which will not interfere with reading the manufacturer's part number or date code identification. Use Minnesota Mining and Manufacturing Co.'s 3M-401-G3 paint for marking of parts. Mixing and application should be done in accordance with manufacturer's specification sheet.

4.8 Acceptance

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Preliminary inspection for compliance with the requirements of this specification may be performed at origin by an authorized representative of the Government. Final acceptance for the Contracting Officer shall be performed by the assigned project engineer.

4.9 Certificate of Compliance

A certificate of compliance signed by the Quality Control Manager shall be included with the device shipment. It shall verify that the transistors were processed in accordance with this specification and that all requirements have been met.

4.10 Notification of Government Source Inspector

The Government Representative who has been delegated quality assurance function at your test facility shall be notified immediately upon receipt of this order.

5.0 PREPARATION FOR DELIVERY

5.1 Type of Packaging

Each transistor shall be packaged in a suitable container which will protect the body and leads of the device during shipment. The rejected parts shall be identified and packaged separately from the acceptable items.

5.2 Packaging for Shipment

The transistors packaged in accordance with Paragraph 5.1 shall be packed to afford protection against damage during direct shipment from the test laboratory to the receiving activity. Containers will comply with the carrier's rules and regulations applicable to the mode of transportation.

6.0 INSPECTION AND TEST METHODS

6.1 External Visual

The transistors shall be examined to verify that the materials, design, construction, marking and workmanship are in accordance with the applicable requirements.

6.2 Electrical

All electrical tests shall be performed at an ambient temperature of 25°C unless otherwise noted.

Note: All tests shall be performed on both transistors (dual package).

6.2.1 Collector Cutoff Current

$$V_{CB} = 45 \text{ VDC}$$

$$I_E = 0$$

The collector cutoff current shall be tested in accordance with Method 3036, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $I_{\mbox{CB0}}$ is greater than 0.1 nA dc.

6.2.2 Collector-Base Breakdown Voltage

$$I_C = 10 \mu A dc$$
 $I_E = 0$

The collector-base breakdown voltage shall be tested in accordance with Method 3001.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if BV_{CB0} is less than 60 VDC.

6.2.3 Emitter-Base Breakdown Voltage

$$I_E = 10 \mu A dc$$

 $I_C = 0$

The emitter-base breakdown voltage shall be tested in accordance with Method 3026.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if the ${\rm BV}_{\rm EB0}$ is less than 7.0 VDC.

6.2.4 Matching Characteristics

6.2.4.1 DC Current Gain Ratio

$$I_{C1} = 10 \mu A$$
 $I_{C2} = 10 \mu A$
 $V_{CE1} = 5.0 V$
 $V_{CE2} = 5.0 V$

The forward current transfer ratio shall be tested in accordance with Method 3076.1, MIL-STD 750A.

The DC Current Gain Ratio $h_{\text{FE}_1}/h_{\text{FE}_2}$ shall have the following characteristics:

$$Min = 0.9$$
 $Max = 1.0$

Note: Lower of two h_{FE} is defined as h_{FE} .

6.2.4.2 Base-Emitter Voltage Differential

$$I_{C1} = 10 \mu A$$
 $I_{C2} = 10 \mu A$
 $V_{CE1} = 5.0 V$
 $V_{CE2} = 5.0 V$

€.2.

The base-emitter voltage shall be tested in accordance with Method 3066.1, Test Condition B, MIL-STD 750A.

Base Emitter Voltage Differential $V_{BE_1} - V_{BE_2}$ shall be = 3.0 mV maximum.

6.2.5 Forward Current Gain (h_{FE})

$$V_{CE} = 5 \text{ VDC}$$

$$I_{C} = 10 \text{ } \mu \text{A dc}$$

The forward current gain shall be tested in accordance with Method 3076.1, MIL-STD 750A.

The unit shall be considered failed if the $h_{\mbox{\scriptsize FE}}$ is less than 200.

6.2.6 Emitter Cutoff Current

$$I_C = 0$$
 $V_{EB} = 5.0 V$

The emitter cutoff current shall be tested in accordance with Method 3061.1, MIL-STD 750A.

The unit shall be considered failed if the $I_{\mbox{EB0}}$ is greater than 0.1 nA.

6.2.7 Collector Saturation Voltage

$$I_C = 1.0 \text{ MA dc}$$
 $I_B = 0.1 \text{ MA dc}$

The collector saturation voltage shall be tested in accordance with Method 3071.1, MIL-STD 750A.

6.2.7 (continued)

The unit shall be considered failed if the $V_{\mbox{\footnotesize{CE}}}(\mbox{\footnotesize{sat}})$ is greater than 0.35 VDC.

6.3 Electrical Intermediate

Note: All tests shall be performed on both transistors (dual package).

6.3.1 Forward Current Cain (h_{FE})

$$V_{CE} = 5.0 \text{ VDC}$$

$$I_{C} = 10 \text{ } \mu\text{A dc}$$

The forward current gain (h_{FE}) shall be tested in accordance with Method 3076.1, MIL-STD 750A.

The unit shall be considered failed if the $h_{\mbox{\scriptsize FE}}$ is less than 200.

6.4 Environmental

Note: All tests shall be performed on both transistors (dual package).

6.4.1 High Temperature Storage

The transistor shall be exposed to a temperature of 200°C +0°C, -10°C, for a period of 48 hours, +24 hours, -0 hours.

6.4.2 Temperature Cycling

The transistor shall be tested in accordance with MIL-STD 202D, Method 102, Condition C. The transistor shall be subjected to five cycles performed continuously.

6.4.3 Acceleration

The transistor shall be tested in accordance with MIL-STD 750A, Method 2006. The transistor shall be accelerated for one minute in the Y_1 plane at a level of 20,000 g's.

6.4.4 Fine Leak

The transistor shall be tested in accordance with MIL-STD 202D, Method 112, Condition C. The units shall be subjected to a pressure of 60 psig ± 10 psig, in a helium atmosphere for a minimum period of four hours. The units shall then be placed in a mass spectrometer to measure helium leakage. Units exhibiting leak ranges in excess of 10⁻⁸ atm-cc/sec shall be considered failed.

6.4.5 Gross Leak

é .E

The transistor shall be tested in accordance with MIL-STD 883D, Method 1014, Condition C, at a temperature of 125°C ± 10°C. The unit shall be submerged to a minimum of one inch into the hot liquid and observed for a minimum of one minute. Any unit emitting a continuous stream of bubbles shall be considered failed.

6.4.6 Vibration

Each device shall be tested in accordance with MIL-STD-202D Method 204A Condition C. The following shall apply

- Non-operating
- 2. Perform 2.4.2 Part 2 only
 - (a) The entire frequency range of 55 to 2000 cycles (no return sweep) shall be traversed in 10±3 minutes
- 3. Paragraph 6.3 Electrical Intermediate shall be run after completion of vibration testing.

6.5 Burn-In

Note: All tests shall be performed on both transistors (dual package).

6.5.1 Heat Sink

The transistor shall be mounted on a heat sink. The transistor case temperature will be maintained at 70° C, $\pm 5^{\circ}$ C.

6.5.2 Test Conditions

The collector to emitter voltage $V_{\rm CE}$ shall be set at 30 volts. The collector current I shall be set to 5 ma each collector.

6.5.3 Test Length

The test shall be run for 168 hours, +12 hours, -0 hours. Section 6.2 of this specification shall be rerun, and any transistor failing any portion of Section 6.2 shall be considered failed. Prior to the testing of Section 6.2, the transistor shall be allowed to return to ambient temperature (25°C).

6.6 Radiographic Examination

Note: All tests shall be performed on both transistors (dual package).

6.6.1 Procedure

The transistor shall be X-rayed in two mutually perpendicular planes. Maintain unit identity between units and film position.

6.6.2 Acceptance

Examine film, using 100X minimum magnification, and reject units having the following defects or characteristics.

- a. Poor chip mounting: any unit displaying less than50% contact between chip and mounting base.
- b. Extraneous material: any unit displaying extraneous or foreign material that is not a normal portion of the product.

6.6.2 (Continued)

- c. Bonds and bond wires: any bond or bond wires that are misplaced, loose or extra. Bond wires that are within 0.005 inch of any area not electrically common with the bond wire.
- d. Miscellaneous: any anomaly which, in the opinion of the inspector, will degrade performance or reliability of the unit.

Table 1 ELECTRICAL AND ENVIRONMENTAL REQUIREMENTS

	Electrical					6.2
2.0	Environmental			•	•	
2.1	High Temperature	S orag	е.	• •	Para.	6.4.1
2.2	Electrical	• • •	• • •		Para.	6.3
2.3	Temperature Cycli	ng	• •	• •	Para.	6.4.2
2.4	Electrical				Para.	6.3
2.5	Fine Leak				Para.	6.4.4
2.6	Gross Leak	• • •		• • •	Para.	6.4.5
2.7	Electrical			• •	Para.	6.3
2.8	Vibration				Para.	6.4.6
2.9	Burn-In		• • .		Para.	6.5
2.10	Radiographic Exam	inatio	n		Para.	6.6

SCREENING SPECIFICATION FOR TRANSISTOR SS3520

Document Number EPS-128

Prepared by

Lockheed Electronics Company

Houston Aerospace Systems Division

Houston, Texas

Under Contract NAS 9-11373

for

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

SCREENING SPECIFICATION FOR TRANSISTOR SS 3520

Prepared by:

Reliability and Quality Assurance Engineer

Approved by:

4

T. D. Lyons / Senior Aerospace Engineer

E. Curtsinger

Engineering Supervisor

C. Hall

Program Manager

Electron/Proton Spectrometer Program Advanced Programs Department Lockheed Electronics Company Houston Aerospace Systems Division

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6.5	Burn-In			-	11
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Page

1.0 SCOPE

2 . 3

3 . 2

This document defines the necessary requirements for the screening of transistor SS3520 to satisfy NASA high reliability requirements for the Electron-Proton Spectrometer (EPS).

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of application shall form a part of this specification to the extent specified herein.

MIL-STD 202D, Test Methods for Electronic and Electrical component parts

MIL-STD 750A, Test Methods for Semiconductor Devices MIL-STD 883, Test Methods and Procedures for Microelectronics

NHB 5300.4(1A), Reliability Program Provisions for Aeronautical and Space Systems Contractors

3.0 REQUIREMENTS FOR TEST LABORATORY SUBCONTRACTORS

3.1 <u>Facilities</u>

The subcontractor shall provide and maintain adequate facilities for inspecting and testing electronic components described in this specification.

3.2 Inspection, Measuring and Test Equipment

The subcontractor shall maintain and control inspection, measuring and test equipment in accordance with

3.2 (continued)

NHB 5300.4 (1A). Upon request, the subcontractor shall submit to Lockheed Electronics Company (LEC) for approval, a listing of equipment and their intended usage.

3.3 Calibration Records

The subcontractor shall prepare and have available for review by LEC, a written procedure and schedule for the maintenance and calibration of such equipment based on type, accuracy, purpose and degree of usage. Records of calibration shall be maintained and the calibration due date, or other identification attesting the due date of the next calibration, shall be displayed on each item of this equipment.

3.4 Calibration Traceability

Standards used for calibration shall be traceable to the National Bureau of Standards (NBS). No more than five steps shall be used to establish traceability from actual inspection and test equipment to the NBS.

4.0 RELIABILITY AND QUALITY ASSURANCE PROVISIONS

4.1 General

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The procedures and methods of testing the transistors in accordance with this specification shall meet the general requirements of MIL-STD-202D.

4.2 Screening Inspections and Tests

Each transistor supplied shall be submitted in the sequence specified to the inspections and tests of Table 1.

4.3 Inspection and Test Data

A summary of the transistor data obtained during each inspection or test shall be prepared and submitted with the transistors to LEC. This summary shall list all transistors that failed electrical tests and the number that failed each parameter. The raw test data shall also be delivered to LEC with the transistors.

4.4 Inspection and Test Records

Inspection and test records shall include part number, serial number, inspection or test number, number of defects found, kinds of defects, acceptance number and the disposition inspector's identity. Records of all inspections and tests shall be delivered to LEC along with the transistors.

4.5 Serialization

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All transistors shall be serialized in a manner that will be permanent during use and testing periods.

4.6 Reject Disposition

Each transistor that fails the inspections and tests of Table 1 shall be marked with a red dot and placed in a reject bag, and tagged to note unit part number, serial number and inspection or test failed. These units shall also be delivered to LEC. Use 3M-401-5D paint for marking of parts.

4.7 Marking of Acceptable Parts

Transistors which meet the requirements of this specification shall be identified with a permanent green dot placed on the body of the transistor. The dot shall be placed on the body at a point which will not interfere with reading the manufacturers part number or date code identification. Use 3M-401-G3 paint for marking of parts.

4.8 Acceptance

Preliminary inspection for compliance with the requirements of this specification may be performed at origin by an authorized representative of the Government. Final acceptance for the Contracting Officer shall be performed by the assigned project engineer.

4.9 Certificate of Compliance

A certificate of compliance signed by the Quality Control manager shall be included with the device shipment. It shall verify that the transistors

4.9 (continued)

were processed in accordance with this specification and that all requirements have been met.

4.10 Notification of Government Source Inspector

The Government Representative who has been delegated quality assurance function at your test facility shall be notified immediately upon receipt of this order.

5.0 PREPARATION FOR DELIVERY

5.1 Type of Packaging

Each transistor shall be packaged in a suitable container which will protect the body and leads of the device during shipment. The rejected parts shall be identified and packaged separately from the acceptable items.

5.2 Packaging for Shipment

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The transistors packaged in accordance with paragraph 5.1 shall be packed to afford protection against damage during direct shipment from the test laboratory to the receiving activity. Containers will comply with the carrier's rules and regulations applicable to the mode of transportation.

6.0 INSPECTION AND TEST METHODS

6.1 External Visual

The transistors shall be examined to verify that the materials, design, construction, marking and workmanship are in accordance with the applicable requirements.

6.2 <u>Electrical</u>

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All electrical tests shall be performed at an ambient temperature of 25°C unless otherwise noted.

6.2.1 Collector-Base Cutoff Current

$$v_{CB} = 15 \text{ VDC}$$

$$I_E = 0$$

The collector-base cutoff current shall be tested in accordance with Method 3036, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $I_{\mbox{CBO}}$ is greater than 10 nA dc.

6.2.2 Collector - Base Breakdown Voltage

$$I_C = 1.0 \mu A dc$$

6.2.2 (continued)

$$I_E = 0$$

The collector - base breakdown voltage shall be tested in accordance with Method 3001.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if ${}^{\mathrm{BV}}_{\mathrm{CBO}}$ is less than 35 VDC.

6.2.3 Emitter - Base Breakdown Voltage

$$I_E = 10 \mu A dc$$

$$I_C = 0$$

The emitter - base breakdown voltage shall be tested in accordance with Method 3026.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $\mathrm{BV}_{\mathrm{EBO}}$ is less than 3.0 VDC.

6.2.4 Collector - Emitter Breakdown Voltage

$$I_C = 3.0 \text{ mA dc}$$
 (pulsed)

$$I_B = 0$$

Pulse width ≤ 300 µs

Duty Cycle = 1%

6.2.4 (continued)

The collector - emitter breakdown voltage shall be tested in accordance with Method 3011.1, Condition D, MIL-STD 750A.

The unit shall be considered failed if the $^{\mathrm{BV}}_{\mathrm{CEO}}$ is less than 20 VDC.

6.2.5 Forward Current Ratio (hfe)

 $v_{CE} = 15 \text{ VDC}$

 $I_C = 2.0 \text{ mA dc}$

f = 1.0 kHz

The forward transfer ratio shall be tested in accordance with Method 3206, MIL-STD 750A.

The unit shall be considered failed if the $h_{ extstyle fe}$ is less than 100.

6.2.6 Base - Emitter Saturation Voltage

 $I_C = 10 \text{ mA dc}$

 $I_{R} = 1.0 \text{ mA dc}$

The base-emitter saturation voltage shall be tested in accordance with Method 3066.1, MIL-STD 750A.

6.2.6 (continued)

The unit shall be considered failed if the $V_{\mbox{\footnotesize BE}}$ (Sat) is greater than 1.0 VDC.

6.2.7 Collector - Emitter Saturation Voltage

 $I_C = 10 \text{ mA dc}$

 $I_B = 1.0 \text{ mA dc}$

The collector - emitter saturation voltage shall be tested in accordance with Method 3071.1, MIL-STD 750A.

The unit shall be considered failed if the $V_{CE}^{}(\text{Sat})$ is greater than 0.4 VDC.

6.2.8 Unity Gain Frequency

 $v_{CE} = 15 \text{ VDC}$

 $I_C = 1 \text{ mA}$

f = 100 MHz

The Unity Gain (f_t) shall be tested in accordance with Method 3261, Use, Method 3306.1, Condition A to determine the magnitude of the common emitter small-signal short-circuit transfer ratio. The unit shall be considered failed if the f_t is less than 500 MHz.

- 6.3 Electrical Intermediate
- 6.3.1 Forward Current Transfer Ratio (h_{FE})

 $v_{CE} = 2.0 \text{ VDC}$

 $I_C = 2.0 \text{ mA dc (pulsed)}$

Pulse Width = 300 μs

6.3.1 (continued)

Duty Cycle = 1%.

The forward current transfer ratio (h_{FE}) shall be tested in accordance with Method 3076.1, MIL-STD 750A.

The unit shall be considered failed if the ${\rm h}_{\rm FE}$ is less than 75.

6.4 Environmental

6.4.1 High Temperature Storage

The transistor shall be exposed to a temperature of 200°C, +0°C, -10°C, for a period of 48 hours, +24 hours, -0 hours.

6.4.2 Temperature Cycling

The transistor shall be tested in accordance with MIL-STD 202D, Method 102, Condition C. The transistor shall be subjected to five cycles performed continuously.

6.4.3 Acceleration

The transistor shall be tested in accordance with MIL-STD 750A, Method 2006. The transistor shall be accelerated for one minute in the Y_1 plane at a level of 20,000 g's.

6.4.4 Fine Leak

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The transistor shall be tested in accordance with MIL-STD 202D, Method 112, Condition C. The units shall be subjected to a pressure of 60 psig, ± 10 psig, in a helium atmosphere for a minimum period of four hours.

6.4.4 (continued)

The units shall then be placed in a mass spectrometer to measure helium leakage. Units exhibiting leak rates in excess of 10^{-8} atm-cc/sec shall be considered failed.

6.4.5 Gross Leak

The transistor shall be tested in accordance with MIL-STD 883D, Method 1014, Condition C, at a temperature of 125°C ± 10°C. The unit shall be submerged to a minimum of one inch into the hot liquid and observed for a minimum of one minute. Any unit emitting a continuous stream of bubbles shall be considered failed.

6.4.6 Vibration

Each transistor shall be tested in accordance with MIL-STD 202D, Method 204A, Cond. C. The following shall apply:

- 1. Non-operating
- Perform 2.4.2 part 2 only. The entire frequency range of 55 to 2000 cycles (no return sweep) shall be traversed in 10 ± 3 minutes.
- 3. Paragraph 6.3, Electrical Intermediate, shall be run after completion of vibration testing.

6.5 Burn-In

6.5.1 Heat Sink

The transistor shall be mounted on a heat sink whose temperature will be maintained at 70°C, +15°C, -5°C.

6.5.2 Test Conditions

The collector to emitter voltage V_{CE} shall be set at 10 volts. The collector current I_{C} shall be set to 15 mA dc.

6.5.3 Test Length

The test shall be run for 168 hours, +12, -0 hours. Section 6.2 of this specification shall be rerun, and any transistor failing any portion of Section 6.2 shall be considered failed. Prior to the testing of Section 6.2, the transistor shall be allowed to return to ambient temperature (25°C).

6.6 Radiographic Examination

6.6.1 Procedure

The transistor shall be X-rayed in two mutually perpendicular planes. Maintain unit identity between units and film position.

6.6.2 Acceptance

Examine film, using 100X minimum magnification, and reject units having the following defects or characteristics:

- a. Poor chip mounting: any unit displaying less than 50% contact between chip and mounting base.
- b. Extraneous material: any unit displaying extraneous or foreign material that is not a normal portion of the product.

6.6.2 (continued)

- c. Bonds and bond wires: any bond or bond wires that are misplaced, loose or extra. Bond wires that are within 0.005 inch of any area not electrically common with the bond wire.
- d. Miscellaneous: any anomaly which, in the opinion of the inspector, will degrade performance or reliability of the unit.

TABLE I
ELECTRICAL AND ENVIRONMENTAL REQUIREMENTS

•	Electrical	Para. 6.2
1.		Para. 6.4
2.	Environmental	•
2.1	High Temperature Storage	Para. 6.4.1
2.2	Electrical	Para. 6.3
2.3	Temperature Cycling	Para. 6.4.2
4	Electrical	Para. 6.3
2.4		Para. 6.4.4
2.5	Fine Leak	Para. 6.4.5
2.6	Gross Leak	
2.7	Electrical	Para. 6.3
2.8	Vibration	Para. 6.4.6
2.9	Burn-In	Para. 6.5
2.9		Para. 6.6
2.10	Radiographic Examination	1414. 0.0

3.3.10.2 Restriction on Use of Transistors and Capacitors. None of the restricted parts are used in the EPS.

3.3.10.3 Soldering NBH5300.4(3A)

The soldering techniques and requirements are imposed by the Quality Assurance Plan, Reliability Plan and Inspection during assembly. The requirements of NBH5300.4(3A) are by definition and implementation rather than by analysis.

3.3.10.4 Welding and Brazing

The welded techniques and requirements are imposed by the Quality Assurance Plan, Reliability Plan and Inspection during assembly. The requirements of MIL-W-6858 are by definition and implementation rather than by analysis.

3.3.10.7 Adhesive Bonding

The adhesive was selected on the basis of satisfactory performance in prior applications. The only area using adhesive is the strip heaters. All operations connected with bonding, were conducted in a dust free area. Specific materials are described in the fabrication procedures. Bonding was accomplished according to manufacturer's recommended procedures. The specification used in this process is MIL-A-9067C.

3.3.10.9 Parts and Material Selection.
Refer to paragraph 3.3.9

3.3.10.9.1 Controlled Electrical, Electronic and Electromechanical (EEE) Parts

See EEE Parts List attached.

ELECTRON-PROTON SPECTROMETER EEE PARTS LIST

LEC Document Number EPS-469

Prepared by
Lockheed Electronics Company
Houston Aerospace Systems Division
Houston, Texas

Under Contract NAS 9-11373

for the

National Aeronautics and Space Administration

Manned Spacecraft Center

Houston, Texas

June, 1971

EEE PARTS LIST

Prepared by:

Reliability and Quality Assurance Engineer

Approved by:

Curtsinger

Engineering Supervisor

Program Manager

Electron-Proton Spectrometer Program Advanced Programs Department

Lockheed Electronics Company, Inc. Houston Aerospace Systems Division Houston, Texas

ELECTRON-PROTON SPECTROMETER

The Electron-Proton Spectrometer EEE Parts List catalogs the electrical, electronic, and electromechanical (EEE) parts used in the EPS. The list is divided into sections each representing a particular assembly. The parts of each assembly are grouped by their generic name. Parts are identified by size, rating, material, and part numbers as applicable. Drawing designation, manufacture, specification number, method of qualification, qualification status, and number required are also shown.

Parts used on the EPS are procured to user's specifications that include reliability and quality assurance for each application. Electronic parts have been derated to obtain the best operating levels for prolonged reliability.

REVISION	LETTER _	CICVIA	D ELECTO	ON DO	TON SPEC	CTDOMET	ED					PAGE		. OF _	
		SKILA		EEE PART		CIROMEI	LIX	. •		OUA	NTIT	Y PE	R SUI	B ASSEN	ASLY
•	SSEMBLY: N	NAME <u>ELECTRON-PROTON SPECTROME</u>	TER		EC39107185 PREAMPLIFIER	•	_ /	45,508 1104,902	102.185					707.4	7
ITEM NO.	DRAWING DESIGNATION	DESCRIPTION AND/OR DRAWING TITLE	MFG.	MFG'S PART NO. OR DRAWING NO.	SPECIFICATION	METHOD OF QUALIFICATION	QUAL. STATUS				//		//	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
	Rl	RESISTOR - Selected	Мерсо		MIL-R-55182	Established Reliability	Q	1						5	
	R2	RESISTOR - 7.87k Ω , 1%, 1/20W, Film	Mepco	RNC50 K7871FR	MIL-R-55182	Established Reliability	Q	1						5	
'	R3	Metal RESISTOR - 7.15kΩ, 1%, 1/20W, Film		RIIC50 K7151FR	•	Established Reliability	Q	1						5	
ľ	R4	Metal RESISTOR - 2550, 1%, 1/20W, Film		RNC55 K2550FR		Established Reliability	Q	1	'					5	
	R5	Metal RESISTOR - 604Ω, 1%, 1/20W, Film	, ,	RNC50 K6040FR		Established Reliability	Q	1	.					5	
	R6	RESISTOR - 1.21kΩ, 1%, 1/20W, Film		RNC50 K1211FR		Established Reliability	Ω	1						5	
- 1	R7	RESISTOR - 100MΩ, 5%	Caddock	1712- 100 Meg.		LEC Spec	Q	1						. 5	
	R8	RESISTOR = 2.55k Ω , 1%, 1/20W, Film	Mepco	RNC55 K2551FR		Established Reliability	٥	1						5	
	R9	Metal RESISTOR - 93.1Ω, 1%, 1/10W, Film		RNC50 K93R1FR	•	Established Reliability	Q.	1						5	
	R10	Metal RESISTOR -49.90, 1%, 1/10W, Film		RNC55 K49R9FR	•	Established Reliability	Ω	1						5	
	R11,	Metal RESISTOR - 49.9kn, 1%, 1/20W, Film	•	RNC50H 4991FS		Established Reliability	Ω	2						10	
	R16 R12	RESISTOR - 4.99kΩ, 1%, 1/20W, Film		RIC50H 4991FS	•	Established Reliability	Q	1						5	
	R13	RESISTOR - Selected	Caddock		•	LEC Spec #168	Q	1						5	
	R14,	Metal RESISTOR - 2.67kΩ, 1%, 1/20W, Film	MEPCO	RNC50H 2671FS	•	Established Reliability	Q	2						10	
1	1164	· Metal	4	RNCSOH	1	Established		1 1	- 1		•	1 1	· 1	1 1	

RNC50H 8062FS

3260W

1-501

Bourns

Metal RESISTOR - 80.6kΩ, 13, 1/20, Film

POTENTIOMETER - 5000

R15,

R17

Established Reliability

Q

LEC Spec

NEXT ASSEMBLY: NUMBER

SKYLAB	ELECTRON-FROTON SPECTROMETER
	EEE PARTS LIST

TOP ASSEMBLY: NUMBER

REVISION LETTER

NAME

ELECTRON-PROTON SPECTROMETER

SEC39107190 .

SEC39106425

NAME

PREAMPLIFIER SLICE

ASSEMBLY:

NUMBER SEC39107185

NAME PREAMPLIFIER

PAGE

QUANTITY PER SUB ASSEMBLY

ITEM NO.	DRAWING DESIGNATION	DESCRIPTION AND/OR DRAWING TITLE	MFG.	MFG'S PART NO. OR DRAWING NO.	SPECIFICATION	METHOD OF QUALIFICATION	QUAL. STATUS		5/	/	/	//	1	//	<u>/</u>	4	70.7 P. 2.7 P. 2
	R18,	. Metal RESISTOR - 30.1Ω, 1%, 1/20W, Film	Мер со	RNC50H 30R1FS	MIL-R-55182	Established Reliability	Q	1									5
	R19 Cl ·	CAPACITOR-Variable, .6-1.8pF, 750V	JFD	RVC-12	LEC Spec EPS-232	Screen and Burn-in	Q	1									5
. 1	C2	CAPACITOR - NPO, 1.0pF, 25%, 50V	usćc	RC33C1ROD	MIL-C-39003	Screen and Burn-in	Q	1									5
	C'3	Solid CAPACITOR -47µF, 10%, 6V, Tantalum	Kemet	T2105476 K006RS	MIL-C-39003	Established Reliability	Q	1									5
	C4	Solid CAPACITOR-3.3µF, 10%, 15V, Tantalum	Kemet	T210A335 K015RS		Established Reliability	Q	1									5
	C5, C6,	CAPACITOR01µF, 10%, 200V,	Kemet	CKR06BX 103KR		Established Reliability	Q	3									15
	C8 C7, C9	ceramic CAPACITOR - 15µF, 10%	Kemet	T210B156 K020R5	n	Established Reliability	Q	2									10
	C10	CAPACITOR01µF, 10%	Kemet	CKR06BX 103MR		Established Reliability	Q	1							•	ŀ	5
	C11	CAPACITOR - 100pF, 10%	Kemet	CKR05BX 101KR		Established Reliability	Q.	1									5
	01	TRANSISTOR - FET	Texas Instrument	(JANTX- 2N4858) Selected SSC6113	MIL-S-19500/ 385 .	Established Reliability		1		•							5
	Q2, Q4	TRANSISTOR - PNP, Fast Switching, Silicon	Motorola	JAN-TX 2N-3251A	MIL-S-19500/ 323	Established Reliability		2									10
	Q3	TRANSISTOR - NPN, Low Power, Silicon	Motorola	JANTX 2N-2708	MIL-S-19500/	Hi-Rel Testing	Q	1									5
	CRI	DIODE - General Purpose, Silicon	Texas Instrument	JANTX 1N649	MIL-S-19500/ 240	Reliability		1									5
	CR2, CR3	DIODE - Silicon	Dickson	104567A	Dickson Hi- Rel Spec.	Hi-Rel Testing	Q	2	,								10

REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER NAME ELECTRON-PROTON SPECTROMETER ASSEMBLY : SEC39107185 NUMBER SEC39107196 · NEXT ASSEMBLY: NUMBER PREAMPLIFIER NAME PREAMPLIFIER SLICE MFG'S DESCRIPTION PART NO OR SPECIFICATION METHOD OF QUAL AND/OR MFG. ITEM DRAWING QUALIFICATION STATUS DRAWING NO. DESIGNATION DRAWING TITLE NO. Hi-Rel J. W. 15 MIL-C-15305 Testing Ō. 3 9210-76 Miller L1, L2, INDUCTOR - 100µH L4 Established 526-2930-5 1 MIL-C-15305 Reliability Q Collins . 130 L3 · INDUCTOR - 20mil Microdot MCDM1-5 MIL-C-38300A Hi-Rel Tests 1 Q Microdot 15P4L4-0.5 CONNECTOR - Screw Mount MIL-STD-202D 031-0070-5 MIL-C-38300A Microdot Microdot .001 CONNECTOR - Receptacle Hi-Rel Tests MIL-STD-2020 Q 1

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PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST REVISION A (UPDATE) QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME NUMBER SEC39107185-303 NEXT ASSEMBLY: NUMBER NAME DETECTOR LEAKAGE MONITOR NAME MFG'S DESCRIPTION METHOD OF QUAL PART NO. OR SPECIFICATION . MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS DRAWING NO DESIGNATION DRAWING TITLE NO. High-Rel MIL-S-Component Q 19500 1N4567A CR2 DIODE - 6.4V. 1 1 Update: Part Deleted High-Rel Q MIL-S-Component 19500 1N4567A 1 1 DIODE - 6.4V. CR3 Update: Part Deleted Established RNC5011 MIL-R-Reliability Q 55182 2671FR Mepco RESISTOR - 2.67k, 18 R14, R21 2 2 Update: Parts Deleted Established RNC50H MIL-R-Q Reliability 30RIFR 55182 Мерсо RESISTOR - 30.1 Ω , 1% R18 1 Update: Part Deleted Established RNC50H MIL-R-Q 55182 Reliability Mepco 30R1FR RESISTOR - 30.1 Ω , 18 R19 1 1 Update: Replaced with .020 Dumet Lead Established MIL-R-RNC50H Reliability Q 55182 8062FR RESISTOR - 80.6k, 1% Мерсо R15, R20 2 2 Update: Part Deleted MIL-R-Established RNC59H Reliability Q 55182 4992FR R11 RESISTOR - 49.9k, 18 Mepco Established RNC50II MIL-R-Reliability Q 1 1003FR 55182 Changed to 100k, 18 Mepco Established RNC50H MIL-R-Reliability 4992FR 55182 Мерсо RESISTOR - 49.9k, 18 R16 RNC50H MIL-R-Established 1 55182 Reliability 6982FR Mepco Changed to 69.8k, 18

PAGE _2 OF REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST REVISION A (UPDATE) QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: SEC39107185-303 NUMBÉR NEXT ASSEMBLY: NUMBER DETECTOR LEAKAGE MONITOR MFG'S DESCRIPTION METHOD OF QUAL. QUAL PART NO. OR SPECIFICATION METHOD OF DRAWING AND/OR , MFG. ITEM DRAWING NO. DESIGNATION DRAWING TITLE Hi-Rel MIL-R-Testing Q 55182 MK132 Caddock RESISTOR - 5 Meg, 1% R13 Hi-Rel MIL-R-Q Testing 55182 Caddock MK100k Changed to 100k

REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39107184 NUMBER SEC39107190 NEXT ASSEMBLY: NUMBER DETECTOR BIAS-SUPPLY NAME PREAMPLIFIER SLICE NAME MFG'S DESCRIPTION METHOD OF QUAL SPECIFICATION PART NO OR MFG. AND/OR QUALIFICATION STATUS DRAWING ITEM DRAWING NO DRAWING TITLE DESIGNATION NO. 1 Established Q MIL-R-55182 RNC50H Mepco RESISTOR - $14k\Omega$, 1%, 1/20W Reliability Rl 1402FR 1 Established Q MIL-R-39008 RCR07G Allen RESISTOR - 13Ω , 5%, 1/4WReliability R2 130JP Bradley 1 Q Established 3 MIL-R-55182 RNC50H RESISTOR - 34.8k Ω , 1%, 1/20W. Mepco R3 Reliability 3482FR 1 Established Q RNC50H Mepco RESISTOR - 22.1kΩ, 1%, 1/20W Reliability 2212FR 1 1 Q 3262WH MIL-R-27208 Hi-Rel Bourns POTENTIOMETER - 10kn, 5% R5 Testing 39103 1 Established Q RNC50II MIL-R-55182 RESISTOR - 1.0k Ω , 1%, 1/20W Mepco R6 Reliability 1001FR 1 Q 1 RNC50H Menco RESISTOR - 13kΩ, 1%, 1/20W R7 1302FR . 1 Q CKR05BX MIL-C-39014 Kemet CAPACITOR - 100pf, 200V, 10% Cl 101KP Q 1 1 CKR06BX CAPACITOR - 3300pf, 200V, 10% Kemet C2 332KP Q 1 1 MIL-C-39003 T210C186 CAPACITOR - 18µf, 50V, 10% Kemet C3 K050PS 2 0 2 CKR050BX MIL-C-39014 Kemet CAPACITOR - 1000pf, 200V, 10% C9, C10 102KP Q 1 ŀ CKR06BX CAPACITOR - Selected Kemet Cll 2 Q MIL-S-19500 JAN-TX-Texas CR1, CR2 DIODE 1N914 Instruments 2 2 Q JAN-TX-Texas Q1, Q2 TRANSISTOR 2N3421 Instruments 1 MIL-STD-11A723/ Established Advance VOLTAGE REGULATOR 21 863/Level A Reliability 883 Micro 2 2

MCDM1-

9041.-0.5

Microdot

CONNECTOR

P1, P2

MIL-C-38300X

Hi-Rel

Tested

OF

PAGE

Q

OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY TOP ASSEMBLY: NUMBER SEC39106425 FLECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39106694 NUMBER SEC39107184 NEXT ASSEMBLY: NUMBER DETECTOR RECTIFIER & FILTER NAME DETECTOR BIAS SUPPLY NAME MFG'S DESCRIPTION METHOD OF QUAL PART NO. OR SPECIFICATION MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS DRAWING NO DRAWING TITLE DESIGNATION NO. 1 Hi-Rel Q MIL-R-55182 Caddock MK-132-50K RESISTOR - 50kΩ, 1%, 3/4W R8 Testing 3 Hi-Rel Q 3 MG660-Caddock RESISTOR - $10M\Omega$, 1%, 1/2Wk9, R11, Testing 10MEG R12 1 Q 1 Hi-Rel Caddock MK-132-RESISTOR - 100kΩ, 1%, 3/4W R10 Testing 100K Q MIL-C-39014 Hi-Rel 828-1KV÷ Erie CAPACITOR - .01µf, 1000V C4 - C7 Testing X5T-103M 1 Established Q MIL-C-39014 CKR05BX Kemet CAPACITOR - 1000pf, 200V C8 Reliability 102KP Established JAN-TX-MIL-S-19500 Texas DIODE CR3 - CR8 Reliability Instruments 1NG49

PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY : NUMBÉR SEC39107187 SEC39106670 NEXT ASSEMBLY: NUMBER NAME PULSE AMPLIFIER PULSE AMPLIFIER SLICE NAME MFG'S DESCRIPTION METHOD OF QUAL SPECIFICATION PART NO. OR . MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS) DRAWING NO. DRAWING TITLE DESIGNATION NO. Hi-Rel 3260HH 5 1 1 MIL-R-27208 Testing 0 39103 Bourns POTENTIONETER - 10k0, 5% Rl Hi-Rel 1 Q 1 MIL-R-55182 Caddock MK132 RESISTOR - 44.2kΩ, 18, 3/4W Testing R2 Hi-Rel 1 . • Caddock MK132 RFSISTOR - $140k\Omega$, 18, 3/4WTesting R2 RNC5011 Established 1 1650FR RESISTOR - 1650, 1%, 1/20W Mepco Reliability R3 RNC50H 10 2 2 3240FR RESISTOR - 3240, 1%, 1/20W R4, R28 RNC50H 10 2 2 0 2670FR RESISTOR - 2670, 1%, 1/20W R4, R28 RNC50H 2 1690FR RESISTOR - 169Ω , 1%, 1/20WR4; R28 RNC50H 20 7872FR RESISTOR - 78.7kΩ, 18, 1/20W R5, R8 R29, R33 RNC50II 10 2 2 8062FR RESISTOR - 80.6kΩ, 1%, 1/20W R6, R30 RNC50H 2 10 2 5902FR RESISTOR - 59kΩ, 18, 1/20W R7, R31 RNC50H 10 2 2 4871FR RESISTOR - 4.87kn, 1%, 1/20W R9, R32 Established RNC50H Reliability 4 4 2431FR RESISTOR - 2.43kΩ, 18, 1/20W R10, R11 R34, R35

SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY : NAME NUMBER SEC39107187 SEC39106670 NEXT ASSEMBLY: NUMBER NAME PULSE AMPLIFIER PULSE AMPLIFIER SLICE NAME MFG'S DESCRIPTION METHOD OF QUAL PART NO. OR SPECIFICATION . MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS DRAWING NO. DRAWING TITLE DESIGNATION NO. Established RMC50H 10 2 2 MIL-R-55182 Reliability 2741FR Menco RESISTOR - 2.74kΩ, 1%, 1/20W R12, R36 RNC50H 10 2 Q 2 3741FR RESISTOR - 3.74kΩ, 18, 1/20W R13, R37 RNC50H 20 4 4 R14, R15 2552FR RESISTOR - 25.5k Ω , 1%, 1/20W R38, R39 RNC50H 10 2 2 8252FR RESISTOR - 8.25kn, 18, 1/20W R16, R40 RNC50H 10 2 2 1132FR RESISTOR - 1.13kn, 18, 1/20W R17, R41 RNC50K 20 4 Q R18, R19 43R2FR RESISTOR - 43.20, 1%, 1/20W R42, R43 RNC5011 10 2 2 2000FR RESISTOR - 2000, 1%, 1/20W R20, R44 RNC50K 4 0 R21, R24 10R0FR RESISTOR - 100, 1%, 1/20W R45, R51 RNC50K 20 4 R22, R23 40R2FR RESISTOR - 40.2Ω , 1%, 1/20W R47, R49 RNC50K 4 R25, R26 4 32R4FR RESISTOR - 32.40, 1%, 1/20WR46, R52 Established RNC50H 1 Reliability 1 2150FR RESISTOR - 2150, 1%, 1/20W R27

REVISION LETTER

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ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39107187 SEC39106670 NUMBER NEXT ASSEMBLY: NUMBER NAME PULSE AMPLIFIER PULSE AMPLIFIER SLICE NAME MFG'S DESCRIPTION METHOD OF QUAL PART NO. OR SPECIFICATION . MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS DRAWING NO DESIGNATION DRAWING TITLE NO. Established RNC50K Reliability Q 49R9FR MIL-R-55182 Мерсо RESISTOR - 49.9Ω, 1%, 1/20W R48 Established RNC50II 1 1 Reliability Q 1000FR RESISTOR - 100Ω, 1%, 1/20W R50 Hi-Rel RC37C 2 MIL-C-39014 Testing USCC 851F CAPACITOR - 850pf, 50V C1, C16 Hi-Rel RC37C Testing 516F CAPACITOR - 51pf, 50V C1, C16 Established T2100A 2 2 MIL-C-39003 Reliability 184K050RS Kemet CAPACITOR - .18µf, 50V C2, C17 C3, C7, C13, C18 Established CKRO6BX C24, C28 8 8 MIL-C-39014 Reliability 103KP Kemet CAPACITOR - .01µf, 200V C31, C32 Hi-Rel Tests RC37C5 2 Oual. MIL-C-39014 ROD USCC CAPACITOR - 5.0pf, 50V C4, C19 RC12C2 2 R2D CAPACITOR - 2.2pf, 50V C4, C19 RC37C 2 220J C5, C20 CAPACITOR - 22pf, 50V Hi-Rel Test: RC37C 2 Qual. 100J CAPACITOR - 10pf, 50V C5, C20 Established T210A335-

Kemet

USCC

SKYLAB ELECTRON-PROTON SPECTROMETER
EEE PARTS LIST

MIL-C-39003

MIL-C-39014

MIL-C-39014

K015RS

CKROGBX

RC37151P

333KP

Reliability

Established

Reliability

Hi-Rel Test

Qual.

PAGE

QUANTITY PER SUB ASSEMBLY

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4

REVISION LETTER

TOP ASSEMBLY: NUMBER

C6, C9

C22, C23

C8, C21

C10, C11

C25, C26

SEC39106425

CAPACITOR - 3.3µf, 200V

CAPACITOR - .033µf, 100V

CAPACITOR - 150pf, 50V

REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER NAME ASSEMBLY : SEC39107187 NUMBER SEC39106670. NEXT ASSEMBLY: NUMBER NAME PULSE AMPLIFIER PULSE AMPLIFIER SLICE NAME MFG'S DESCRIPTION SPECIFICATION METHOD OF PART NO OR MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS DRAWING NO. DRAWING TITLE DESIGNATION NO. Hi-Rel Test C10, C11 RC37C910F MIL-C-39014 Qual CAPACITOR - 91pf, 50V USCC C25, C26 RC12C3R3D CAPACITOR - 3.3pf, 50V C12, C27 2 RC12C3R9D CAPACITOR - 3.9pf, 50V C12, C27 2 RC12C1R5D CAPACITOR - 1.5pf, 50V C12, C27 RC12C2R7D CAPACITOR - 2.7pf, 50V C12, C27 2 RC12C1ROD CAPACITOR - 1.0pf, 50V C12, C27 RC37C680J CAPACITOR - 68pf, 50V C14, C29 RC37C270J CAPACITOR - 27pf, 50V C14, C29 10 2 2 USCC RC37C181J CAPACITOR - 180pf C15, C30 RC37C680J CAPACITOR - 68pf C15, C30 Hi-Rel Test 2 RC37C101J Qual CAPACITOR - 100pf. C15, C30

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OF PAGE SKYLAB ELECTRON-PROTON SPECTROMETER REVISION LETTER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER FLECTRON-PROTON SPECTROMETER ASSEMBLY: NAME NUMBER SEC39107187 SEC39106670 NEXT ASSEMBLY: NUMBER NAME PULSE AMPLIFIER PULSE AMPLIFIER SLICE NAME MFG'S DESCRIPTION QUAL METHOD OF SPECIFICATION PART NO. OR MFG. AND/OR QUALIFICATION STATUS DRAWING ITEM DRAWING NO. DRAWING TITLE DESIGNATION NO. LEC Hi-Rel 20 Test Qual Q 4 4 MIL-S-19500 2N4878 Intersil TRANSISTOR - Dual 01 Thru SS2638II Motorola 04 20 4 MIL-S-19500 MIL-STD-883 Q Motorola (2N4261) TRANSISTOR 05 Thru Motorola SS 3520 20 4 Hi-Rel Tests MIL-S-19500 (2N2708) Motorola 09 Thru TRANSISTOR Established Q12 JANTX-Texas . 90 18 18 Reliability Q MIL-S-19500 1N4153 Instruments CR1 Thru DIODE Hi-Rel MCDMI-CR18 5 1 1 15P-4L4-0.5 MIL-C-38300A Test Qual Q Microdot P1 CONNECTOR Hi-Rel MCDMI-5 0 1 MIL-C-388300 Test Qual 15S-4L40.5 Microdot CONNECTOR Sl

OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY TOP ASSEMBLY: NUMBER SEC39106425 ASSEMBLY: ELECTRON-PROTON SPECTROMETER NAME NUMBER SEC39107189 SEC39106670 NEXT ASSEMBLY: NUMBER NAME TEMPERATURE MONITOR PULSE AMPLIFIER SLICE NAME MFG'S DESCRIPTION METHOD OF QUAL PART NO. OR SPECIFICATION MFG. AND/OR QUALIFICATION STATUS DRAWING ITEM DRAWING NO DRAWING TITLE DESIGNATION NO. Hi-Rel Test MK132 1 Q Qual Selected MIL-R-55182 Caddock RESISTOR - Selected Value Rl Established RNC50II 2 2 Reliability Q 3920FR RESISTOR - 3920, 1%, 1/20W Mepco R2, R9 Hi-Rel 3260WM 2 2 Testing MIL-R-22097 39500 Bourns POTENTIOMETER - 500 R3, R10 Established RNC55H4 2 12 Reliability 0 MIL-R-55182 Selected Mepco RESISTOR - Selected Value R4, R11 Established RNC50H 2 2 Reliability 5490FR RESISTOR - 549 Ω , 1%, 1/20W R5, R12 3260WM Hi-Rel 2 39501 MIL-R-22097 Testing POTENTIOMETER - 500Ω Bourns R6, R13 RNC50H Established 2 2 MIL-R-55182 Reliability 1372FR RESISTOR - 13.7kΩ, 1%, 1/2-W Мерсо R7, R14 Established RNC50H 1 Reliability Q Selected Mepco RESISTOR - Selected Value R8 Hi-Rel 1 Testing MIL-S-19500 DT710415D Dickson DIODE - Zener (1N4901A) VRl Hi-Rel 1 Q DT710415C MIL-S-19500 Testing Dickson DIODE - Zener (1N4567A) VR2

REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC391066425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39106675 NUMBÉR SEC39106664 NEXT ASSEMBLY: NUMBER PULSE HEIGHT DISCRIMINATOR DISCRIMINATOR SLICE NAME MFG'S DESCRIPTION METHOD OF QUAL PART NO. OR SPECIFICATION MFG. DRAWING AND/OR ITEM QUALIFICATION STATUS DRAWING NO. DRAWING TITLE DESIGNATION NO. Established RNC50H 10 2 2 2 2 2 Reliability 4531FR MIL-R-55182 RESISTOR - 4.53kΩ, 1%, 1/20W Мерсо R1, R12 RNC50H 2 2 2 2 10 2 3161FR RESISTOR - 3160 Ω , 1%, 1/20W R2, R13 RNC50H 1 1 1541FR RESISTOR - 15400, 1%, 1/20W R3 RNC50H 1 1471FR RESISTOR - 1470Ω, 18, 1/20W R3 Established RNC50H 1 Reliability 1501FR RESISTOR - 1500Ω, 1%, 1/20W R3 Hi-Rel 1 1 Testing Q MK132 Caddock RESISTOR - $580k\Omega$, 1%, 3/4W R4 Hi-Rel 1 1 Q Testing RESISTOR - 550kΩ, 1%, 3/4W R4' Hi-Rel 1 1 0 Testing RESISTOR - 480kΩ; 18, 3/4W . R4 !!i-Rel 1 0 Testing RESISTOR - 440kΩ, 18, 3/4W R4 Hi-Rel Testing Q MK132 RESISTOR - 500kn, 18, 3/4W R4 Established RNC50H Reliability Mepco 7500FR R5 (1) RESISTOR - 750Ω , 1%, 1/20WRNC5011 1 7150FR R5 (2) RESISTOR - 7150, 18, 1/20W RNC50H 7870FR RESISTOR - 7870, 1%, 1/20W R5 (3) RNC50H 1 Q 1 1001FR RESISTOR - $1k\Omega$, 18, 1/20WR5 (4) RNC5011 Established 1 1131FR Reliability RESISTOR - 1.13kΩ, 1%, 1/20W R5 (5)

OF

PAGE

OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME NUMBER SEC39106664 SEC39106675 NEXT ASSEMBLY: NUMBER NAME PULSE HEIGHT DISCRIMINATOR DISCRIMINATOR SLICE NAME MFG'S 15/5/ DESCRIPTION METHOD OF QUAL. SPECIFICATION PART NO. OR MFG. AND/OR ITEM DRAWING QUALIFICATION STATUSY DRAWING NO. DRAWING TITLE DESIGNATION NO. Hi-Rel 32601111 1 Q 1 MIL-R-22097 Testing 39101 POTENTIONETER - 1000, 5% Bourns R6 Hi-Rel 3260IIM 1 1 HIL-R-22097 Testing 39201 POTENTIOMETER - 5%, 200Ω R6 Established RNC50H Reliability MIL-R-55182 4640FR RESISTOR - 464Ω , 1%, 1/20W Hepco R7 (1) RNC50H 6040FR RESISTOR - 604Ω , 1%, 1/20W R7 (2) RMC5011 1 2940FR RESISTOR - 4870, 1%, 1/20W R7 (3) RNC50H 1 2670FR R7 (4) RESISTOR - 267Ω , 1%, 1/20W RNC50H 1 2940FR RESISTOR - 2940, 1%, 1/20WR7. Established Rt:C5011 1 Reliability 2101FR MIL-R-55182 RESISTOR - 2.10kΩ, 18, 1/20W R8 Established RNC50H 1 1 Reliability 1691FR RESISTOR - 1.69k Ω , 1%, 1/20W R8 Hi-Rel 3260HM 1 MIL-R-22097 Testing 39201 Bourns POTENTIOMETER - 2000, 5% R9 Hi-Rel 3260HM 11 1 Testing 39500 MIL-R-22097 POTENTIOMETER - 500, 5% R9 10 2 2 12 2 RESISTOR - 0000, Shorting Wire R10. Established R25 RNC50H 1 Reliability 1821FR MIL-R-55182 Mepco RESISTOR - 1.82k Ω , 1%, 1/20W R11 Established RNC5011 1 Q Reliability 1781FR RESISTOR - 1.78kΩ, 1%, 1/20W Hepco R11 Established 1 1 Q MK132 MIL-R-55182 Reliability

Caddock

RESISTOR - 725kg, 18, 3/4W

R14

PAGE OF REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST PER SUB ASSEMBLY OUANTITY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME NUMBER SEC39106664 SEC39106675 NEXT ASSEMBLY: NUMBER NAME PULSE HEIGHT DISCRIMINATOR DISCRIMINATOR SLICE NAME MFG'S DESCRIPTION METHOD OF SPECIFICATION PART NO. OR MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS DRAWING NO DRAWING TITLE DESIGNATION NO. Hi-Rel 1 Testing Q MIL-R-55182 MK 132 Caddock RESISTOR - 750kΩ, 1%, 3/4W R14 Established RNC50H 10 2 2 2 2 2 Reliability 1690FR RESISTOR - 169Ω, 18, 1/20W Menco R15. R16 RNC50H 5 1 1 1 1 1001FR RESISTOR - 1.0kΩ, 1%, 1/20W R17 RNC50H 10 2 2 2 2 1000FR RESISTOR - 100Ω , 18, 1/20WR18. R19 RNC50H 15 3 3 3 3 4992FR RESISTOR - 49.9kn, 1%, 1/20W R20. R21 R22 R23, R24 RNC50K 20 4. 33R2FR RESISTOR - 33.20, 1%, 1/20W R29 ,. R30 RNC50H 10 2 2 2 2 1003FR RESISTOR - 100kΩ, 18, 1/20W R26, R27 Established RNC50H 1 1 1 Reliability 4021FR RESISTOR - 4.02kn, 18, 1/20W R28 Hi-Rel 3262WM 1 1 1 MIL-R-22097 Testing 39104 Bourns POTENTIOMETER - 100kg, 5% R31 RIC50H Established 5 1.11 MIL-R-55182 Reliability 3652FR RESISTOR - 36.5kn, 1%, 1/20W Мерсо R32 Established RHC50H 1 1 Reliability 1583FR RESISTOR - 158kΩ, 1%, 1/20W R33 Established RNC50H 5 1 1 1 1 Reliability 3012FR RESISTOR = 30.1kΩ, 1%, 1/20W R34 Established RHC50H 1 5 1 1 0 Reliability 97R6FR RESISTOR - 97.60, 18, 1/20WR35

3260HM

39103

Bourns

POTENTIOMETER - 10k, 5%

R36

Hi-Rel

Testing

MIL-R-22097

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SKYLAB	ELECTRON-PROTON SPECTROME	TER
	FFE PARTS LIST	,

TOP ASSEMBLY: NUMBER

NAME

SEC39106425

ELECTRON-PROTON SPECTROMETER

ASSEMBLY :

NEXT ASSEMBLY: NUMBER

REVISION LETTER

NAME

SEC39106675

DISCRIMINATOR SLICE

NUMBER SEC39106664 PULSE HEIGHT DISCRIMINATOR PAGE

QUANTITY PER SUB ASSEMBLY,

S.C. 39.206.67.39.1 S.C. 39.06.66.4.30.1 S.C. 39.06.67.30.3 MFG'S DESCRIPTION PART NO. OR SPECIFICATION METHOD OF QUAL. MFG. AND/OR DRAWING ITEM QUALIFICATION STATUS DRAWING NO. DRAWING TITLE DESIGNATION NO. Established CKR06 35 7 7 7 7 MIL-C-19014 Reliability Q BX104KR CAPACITOR - 1µf, 10%, 100V Kemet Cl thru C7 CKR05 10 2 2 2 2 BX221KR CAPACITOR - 220pf, 10%, 200V Kemet C8, C9 T210C68 1 1 MIL-C-39003 6K015RS CAPACITOR - 68µf, 10%, 15V C10 CKR06 20 4 4 4 4 Q BX103KP MIL-C-19014 C11, C12 CAPACITOR - .01uf, 10%, 200V C14, C15 CKR05 10 2 2 2 2 BX101KP C13, C18 CAPACITOR - 100pf, 10%, 200V Established T210A225 5 1 1 Reliability 1 1 K020FS MIL-C-39003 CAPACITOR - 2.2µf, 10%, 20V C17 J. W. Miller J. W. 20 MIL-C-15305 Hi-Rel Spec Q 9210-76 Miller INDUCTOR - 100µH Ll·thru MIL-STD Established L4 LM108/ Advance 5 1 1 Reliability Q 883-Level A Micro 883 AMPLIFIER Z6 · JAN-TX XT-NAL MIL-S-Texas : 10 2 2 Q 2 Instruments 1N914 Hi-Rel 19500/116 DIODE - Silicon, Switching CR1, Hi-Rel CR2 Hewlett 5 1 Q 1 1 Special Test MIL-S-19500 SN5473T Packard DIODE - Silicon Hot Carrier CR3, MIL-STD. Established CR4 10 2 2 2 Q 883/Level A Reliability SE526K Signetics AMPLIFIER Z1, Z2 Established MIL-STD Texas 5 1 1 Q Reliability Instruments SN5473S 883/Level A JK Flip-Flop **Z** 3 Established MIL-STD Harris 10 2 2 2 Q 2 Reliability Semiconduc- IIA-2-2520-2 883/Level A Z4, Z5 AMPLIFIER : tor MII.-C-Hi-Rel 031-0070-10 2 2 Q 001 38300A Testing CONNECTOR - PCB Receptacle Microdot P3, P4 Hi-Rel MCDM1+ 5 1 1 Q MIL-C-38300A Testing 15041.4-.5 Microdot CONNECTOR - Screw Mount S2 ni,-ne l MCDMI~ BIL-C-38300A Tonting 0 21041.4 . . 5 tti crodot. commeron - Serew Mount

REVISION LETTER _____

SKYLAB ELECTRON-PROTON SPECTROMETER

EEE PARTS LIST REVISION A (UPDATE)

TOP ASSEMBLY: NUMBER

NEXT ASSEMBLY: NUMBER

NAME

NAME

SEC39106425
ELECTRON-PROTON SPECTROMETER

SEC39106675 .

DISCRIMINATOR SLICE

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ASSEMBLY:

NUMBER SEC39106664

NAME PULSE HEIGHT DISCRIMINATOR

PAGE _1_

QUANTITY PER SUB ASSEMBLY

ITEM NO.	DRAWING DESIGNATION	DESCRIPTION AND/OR DRAWING TITLE	MFG.	MFG'S PART NO. OR DRAWING NO.	SPECIFICATION	METHOD OF QUALIFICATION	QUAL. STATUS	1 2	1. () 1. ()	\(\frac{\epsilon_{\text{i}}}{\text{c}}\)		<u>:</u> 	_{_{}}	//	4	10 2 4 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
		RESISTOR - 7500, 1%	Мерсо	RNC50H 7500FR	MIL-R- 55182	Established Reliability	Q .	1								
	R-5	Changed to 1.18k, 1%	Мерсо	RNC50H 1181FR	MIL-R- 55182	Established Reliability	Q	1								
	<u> </u>	RESISTOR - 4640. 18	Mepco	RNC50H 4640FR	MIL-R- 55182	Established Reliability	Q ,									
	R7	Changed to 69.80, 18	Мерсо	RNC50H 69R8FR	MIL-R- 55182	Established Reliability	Q	1								· i
•	į	RESISTOR - 500k, 1%	Caddock	MK132- 500k	MIL-R- 55182	Hi-Rel resting	o									
	.R4	Changed to 100k, 18	Caddock	MK132- 100k	MIL-R- 55182	Hi-Rel Testing	Ω	1								. •
		RESISTOR - 1.47k, 18	Мерсо	RNC50H 1471FR	MIL-R- 55182	Established Reliability	٥									
	R3	Changed to 1.54k, 1%	Мерсо	RNC50H 1541FR	MIL-R- 55182	Established Reliability	Q		1							
		RESISTOR - 7150, 18	Мерсо	RNC50H 7150FR	MIL-R- 55182	Established Reliability	Q .									
	R5	Changed to 1.18k, 18	Mepc o	RNC50H 1181FR	MIL-R- 55182	Established Reliability	Q		1	•						
		RESISTOR - 6040, 18	Мерсо	RNC50H 6040FR	MIL-R- 55182	Established Reliability	Q				1					
	R7	Changed to 69.80	Mepc o	RNC50H 69R8FR	MIL-R+ 55182	Established Reliability	Ω.		1							l
		RESISTOR - 440k, 18	Caddock	MK132- 440k	MIL-R- 55182.	Hi-Rel Testing	Q									
	R4	Changed to 100k, 1%	Caddock	MK132 100k	MIL-R- 55182	Hi-Rel Testing	Q		1							
l		Changed to 100ky #4														

2 OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST REVISION A (UPDATE) QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39106664 NUMBER SEC39106675 NEXT ASSEMBLY: NUMBER PULSE HEIGHT DISCRIMINATOR NAME DISCRIMINATOR SLICE NAME MFG'S DESCRIPTION QUAL METHOD OF SPECIFICATION PART NO. OR MFG. AND/OR DRAWING ITEM QUALIFICATION STATUS DRAWING NO DRAWING TITLE DESIGNATION NO. istablished RNC5011 MIL-R-Reliability 0 55182 1501FR Mepco RESISTOR - 1.50k, 1% R3 Established RNC50H MIL-R-Q 55182 Reliability 1541 Mepco Changed to 1.54k, 1% Established MIL-R-RNC50H 3 Reliability 55182 7870FR Megco RESISTOR - 787Ω , 1% R5 Established MIL-R-PNC50H 1 Q Reliability 1181FR 55182. Mepco Changed to 1.18k, 1% established MIL-R-RUCSOH Q Reliability 55182 4870FR Mepco ' RESISTOR - 487Ω, 1% R7 istablished MIL-R-RNC50H Q Reliability 55182 69R8FR Mepco Changed to 69.80, 1% li-Rel :1K132-MIL-R-55182 resting Caddock 480k RESISTOR - 480k, 18 R4. li-Rel MIL-R-MK132resting 55182 Caddock 100k Changed to 100k, 18 Established MIL-R-RNC50H Reliability 55182 1001FR Mepco RESISTOR - 1.00k, 18 R5 Established MIL-R-RNC50H Reliability 55182 1181FR Мерсо Changed to 1.18k, 18 istablished RNC50H MIL-R-Reliability 55182 2940FR Mepco RESISTOR - 294 Ω , 18 R7 Established MIL-R-RNC5011 Reliability 55182 69R8FR Мерсо Changed to 69.8Ω , 1% stablished 11K132~ MIL-R-Reliability 55182 550k Caddock RESISTOR - 550k, 1% R4 Established MK132-MIL-R-Reliability 55182 1.00k Caddock Changed to 100k, 18 Established MIL-R-RNCSOH 55182 Reliability 1131FR RESISTOR - 1.13k, 18 Mepco R5 Entablished MIL-R-Barcs OH

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1181FR

Mepco

Changed to 1.18k, 18

PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST REVISION A (UPDATE) QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: SEC39106664 SEC39106675 NUMBER NEXT ASSEMBLY: NUMBER PULSE HEIGHT DISCRIMINATOR DISCRIMINATOR SLICE NAME MFG'S DESCRIPTION STATUS LA METHOD OF SPECIFICATION PART NO. OR MFG. AND/OR DRAWING ITEM QUALIFICATION DRAWING NO. DRAWING TITLE DESIGNATION Established MIL-R-RNC50H Reliability 55182 Mepco 2670FR RESISTOR - 267Ω , 1% R7 Established MIL-R-RNC50H Reliability 55182 69R8FR Mepco Changed to 69.8Ω , 1% Hi-Rel мк132-MIL-R-3 Testing 55182 580k Caddock RESISTOR - 580k, 18 R4 -Hi-Rel MK132→ MIL-R-55182 Testing Caddock 100k Changed to 100k, 1% Hi-Rel 3260IIM MIL-R-22097 Testing 39101 Bourns POTENTIOMETER - 1000, 18 R6 Hi-Rel MIL-R-3260HM Testing 22097 39201 Bourns Changed to 2000, 1%

PAGE 1 OF REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST REVISION A (UPDATE) QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY : SEC39106664 NUMBER SEC39106695 NEXT ASSEMBLY: NUMBER NAME DETECTOR RESOLUTION MONITOR DISCRIMINATOR SLICE MFG'S DESCRIPTION METHOD OF QUAL 5/5 PART NO OR SPECIFICATION MFG. ITEM DRAWING AND/OR DRAWING NO. DRAWING TITLE DESIGNATION NO. RNC50H 4992FR RESISTOR - 49.9k, 1% Мерсо R20 RNC50H 111111 4991FR Changed to 4.99k, 1% Mepco RNC50H 1.003FR RECISTOR - 100k, 18 Mepco R28 1 | 1 | 1 | 1 | 1 Changed to On

SKYLAB ELECTRON-PROTON SPECTROMETER **EEE PARTS LIST** QUANTITY PER SUB ASSEMBLY TOP ASSEMBLY: NUMBER SEC39106425 ELECTRON-PROTON SPECTROMETER ASSEMBLY : NAME NUMBER SEC39106669 SEC39106675 NEXT ASSEMBLY: NUMBER NAME HEATER CONTROL DISCRIMINATOR SLICE NAME MFG'S DESCRIPTION SPECIFICATION QUALIFICATION STATUS METHOD OF QUAL PART NO. OR , MFG. AND/OR ITEM DRAWING DRAWING NO. DRAWING TITLE NO. DESIGNATION Established RNC50H 1 MIL-R-55182 1372FR Reliability Q RESISTOR - $13k\Omega$, 1%, 1/20W Mepco R1 Allen RCR07G 1 MIL-R-39008 0 RESISTOR - 33Ω , 5%, 1/4WBradley 330JP R2 RNC5011 1 0 1 MIL-R-55182 RESISTOR - 19.1kΩ, 1%, 1/20W Mepco 1912FR **R3** RNC50H 1 4752FR Q R4 RESISTOR - $47.5k\Omega$, 18, 1/20W RMC50H 1 4532FR R5 RESISTOR - $45.3k\Omega$, 1%, 1/20W RNC50H 1 4992FR R6 RESISTOR - $49.9k\Omega$, 1%, 1/20WRNC50H 4991FR R8 RESISTOR - 4.99k Ω , 1%, 1/20W RNC50H 6650FR R9 RESISTOR - 66Ω, 1%, 1/20W ' RNC50II 1 6190FR Q R10 RESISTOR - 6190, 18, 1/20W RNC5011 1 1 0 Rli RESISTOR - 1.91kΩ, 1%, 1/20W 1911FR RNC50H RESISTOR - 2.61k Ω , 1%, 1/20W 2611FR R12 RNC50H 0 RESISTOR - 10k0, 18, 1/20W 1002FR R13 RNC50II 1 7681FR 0 RESISTOR - 7.68kΩ, 1%, 1/20W R14 RCR07G MIL-R-39008 R15 RESISTOR - 3.0kn, 1%, 1/20W 302JS Allen RCR07G Established R16 RESISTOR - 100kΩ, 5%, 1/4W

Bradley

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RELIABILITY

REVISION LETTER

OF

PAGE

QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME NUMBER SEC39106669 SEC39106675 . NEXT ASSEMBLY: NUMBER HEATER CONTROL NAME DISCRIMINATOR SLICE NAME MFG'S DESCRIPTION QUAL METHOD OF SPECIFICATION PART NO. OR MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS DRAWING NO DRAWING TITLE DESIGNATION NO. Established RNC5011 1 Q MIL-R-55182 Reliability 4991FR Mepco RESISTOR - 4.99kΩ, 1%, 1/20W. R17 RIIC50H 1 2002FR RESISTOR - 20.0kΩ, 1%, 1/20W R18 · RCR07G Allen 1 1 MIL-R-39008 Bradley 225JR RESISTOR - 2.2110, 5%, 1/4W R19 RCR07G 1 125JR RESISTOR - 1.2M Ω , 5%, 1/4W R20 RCR07G 1 104JR RESISTOR - 100kΩ, 5%, 1/4W R21 CKR05 1 Q MIL-C-39014 BX101KR CAPACITOR - 100pF, 10%, 200V Kemet C1 CSR13G 1 MIL-C-39003 186KR CAPACITOR - 10µF, 10%, 75V C2 MIL-S-JAN-TX 2 19500/376 2N2484 Teledyne TRANSISTOR - NPN, Amplifier Q1, Q2 Established MIL-S JAN-TX Texas 0 Reliability 19500/393 3421 Instruments Q3, Q4 TRANSISTOR - NPN, Power MIL-S LEC Spec MAL Texas Q 19500/296 #214 2N2609 Instrument TRANSISTOR - FET, Silicon Q5 MIL-STD-Established uA723 Advance Reliability 883/Level A 1883 Micro Al AMPLIFIER Established MIL-S XT-MAL Texas 1 Q 1 19500/116 Reliability 1N914 Instruments DIODE - Switching, Silicon CRI

SKYLAB ELECTRON-PROTON SPECTROMETER
EEE PARTS LIST

OF

PAGE

4

REVISION LETTER

	LETTER _		SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST REVISION A (UPDATE) 106425 RON-PROTON SPECTROMETER ASSEMBLY:						PAGE 1 OF 1						
XT AS	SEMBLY: N	DESCRIPTION AND/OR	MFG.	NUMBER NAME MEG'S PART NO. OR DRAWING NO.	N/A SPECIFICATION	METHOD OF Q	UAL TATUS	///		1014 104 104 104 104 104 104 104					
NO.	DESIGNATION	DRAWING TITLE	Electro Film	112558-1	Manuf. Specification	LEC EPS Specification									
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TOP A	SSEMBLY: N			EEE PAR						QUA	ITITY	PER :	SUS ASS	SEME
NEXT A	SSEMBLY: N	NAME ELECTRON-PROTON SPECTRO SEC39106690 NAME DATA PROCESSOR LVPS SLI			SEC39106980 LOW VOLTAGE PM	R SUPPLY	- /	45,50,8	106980-30:		///	///		
ITEM NO.	DRAWING DESIGNATION	DESCRIPTION AND/OR DRAWING TITLE	MFG.	MFG'S PART NO. OR DRAWING NO.	SPECIFICATION	METHOD OF QUALIFICATION	QUAL.	18		///	///			PER ACOUNT
	FL4	FILTER	Potter	8332-126	MIL-C-15305	• Hi-Rel Testing	Ω.	1					1	\neg
	FL2, FL3, FL5 - FL8	FILTER	Potter	8332-125	MIL-C-15305	Hi-Rel Testing	Q	6					6	
:	Q3	TRANSISTOR	Motorola	2N5333	MIL-S-19500	LEC Spec EPS-179	Q	1					1	
	C20, C21	CAPACITOR - 15pf, 75V	Kemet	T210P156K 075PS	MIL-C-39014	Established Reliability	Q	2					1	
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OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39106671 NUMBER SEC39106980 NEXT ASSEMBLY: NUMBER NAME PRIMARY SIDE LOW VOLTAGE POWER SUPPLY NAME MFG'S DESCRIPTION QUALIFICATION STATUS METHOD OF QUAL PART NO. OR SPECIFICATION MFG. AND/OR ITEM DRAWING ' DRAWING NO. DESIGNATION DRAWING TITLE CR1, Hi-Rel CR12-CR15 9 MIL-S-19500 Testing Q UT4010 Unitrode CR17-CR20 DIODE

OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39106676. SEC39106671 NUMBER NEXT ASSEMBLY: NUMBER PREREGULATOR MODULE NAME PRIMARY SIDE NAME MFG'S DESCRIPTION QUAL METHOD OF PART NO. OR SPECIFICATION MFG. AND/OR DRAWING ITEM QUALIFICATION STATUS DRAWING NO DRAWING TITLE DESIGNATION MIL-R-55182 Established RNC55H-RESISTOR - 33.2k Ω , 1%, 1/10W Mepco Rl Reliability 1 Q 3322FR RCR20G Allen R2A, R2B RESISTOR - 3.9k Ω , 5%, 1/2W 12 2 MIL-R-39008 Q Bradley 392SP Mepco RNC55H R3 RESISTOR - $4.75k\Omega$, 1%, 1/10W1 Q MIL-R-55182 4751FR Q 1 MIL-R-39008 Allen RCR07G RESISTOR - 100Ω , 5%, 1/4WŘ4 Bradley 101JP MIL-R-39008 0 1 Allen RCR07G RESISTOR - 10Ω , 5%, 1/4WR5 Bradley 100JP MIL-R-55182 0 1 RNC50H RESISTOR - $39.2k\Omega$, 1%, 1/20WMepco R6 3922FR 0 1 RNC50II RESISTOR - $5.62k\Omega$, 1%, 1/10WMepco R7 5621FR 0 RNC50H Mepco R8, R9 RESISTOR - 2.21k Ω , 1%, 1/20W 2211FR 1 0 RNC50H RESISTOR - 18.2k Ω , 18, 1/20W Mepco R10 1822FR 1 0 RNC50H RESISTOR - To Be Determined R11 Mepco 1 RNC50H RESISTOR - To Be Determined Mepco R12 2 MIL-C-39003 T210D226 CAPACITOR - 22µf ' Kemet C1. C8 K050PS MIL-C-39014 0 1 CKR06 CAPACITOR - 3300pf Kemet C2 BX332KP 1 MIL-S-19500 Texas JAN TX Q Ql TRANSISTOR Instruments 2N2222A 1 Q JAN TX Q2 TRANSISTOR Texas Instrument 203421

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Instruments

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TRANSISTOR

OF PAGE SKYLAB ELECTRON-PROTON SPECTROMETER REVISION LETTER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ASSEMBLÝ: ELECTRON-PROTON SPECTROMETER NAME SEC39106676. NUMBER SEC39106671 NEXT ASSEMBLY: NUMBER NAME PRERECULATOR MODULE PRIMARY SIDE NAME MFG'S DESCRIPTION METHOD OF QUAL SPECIFICATION PART NO. OR MFG. AND/OR QUALIFICATION STATUS DRAWING ITEM DRAWING NO. DRAWING TITLE **DESIGNATION** NO. 2 0 MIL-S-19500 Established JAN TX Texas TRANSISTOR Q5. Q6 Reliability 2N2907A Instruments 1 Established MIL-S-19500 JAN TX Teledyne TRANSISTOR Reliability 2N2484 Hi-Rel 1 MIL-S-19500 UT4010 Unitrode DIODE CRI Spec. Tests Established JAN TX MIL-S-19500 Texas DIODE CR2, CR3 Reliability 1N914 Instruments CR5, CR6 Hi-Rel 1N4567A MIL-S-19500 Dickson DIODE - Zener CR4 Spec. Tests

PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER FLECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39106677 NUMBER SEC39106671 NEXT ASSEMBLY: NUMBER CORE DRIVER MODULE NAME PRIMARY SIDE NAME MFG'S DESCRIPTION QUAL METHOD OF PART NO OR SPECIFICATION MFG. AND/OR QUALIFICATION STATUS ITEM DRAWING DRAWING NO. DRAWING TITLE DESIGNATION NO. 1 0 Established MIL-R-39008 RCR07G Dale RESISTOR - $4.7k\Omega$, 5%, 1/4WR14 Reliability 472JP 1 1 Q MIL-R-39008 RCR07G RESISTOR - 100Ω, 5%, 1/4W Dale R15 101JP Q 1 MIL-R-39008 RCR07G Dale RESISTOR - 47Ω , 5%, 1/4WR16 470JP Q 1 1 MIL-R-55182 RNC50H Mepco RESISTOR - 28kn, 1%, 1/20W R17 283FR Q 1 RNC50H Мерсо RESISTOR - $10k\Omega$, 1%, 1/20WR38 103FR Q T2100226 MIL-C-39003 Kemet CAPACITOR - 22uf, 50V C3 K050PS T210A475 Kemet CAPACITOR - 4.7µf, 10V C4 K010RS 1 IAH-TX-MIL-S-19500 Texas CR7 DIODE 1N746A Instruments 2 Q 2 JAN-TX-Texas CR8, CR9 DIODE 1N914 Instruments 2 JAN-TX-Texas DIODE CR10 1N645 Instruments 3 JAN-TX-Texas Q8, Q9 TRANSISTOR 2N3421 Instruments Q10 Established JAN-TX-TRANSISTOR 011 Reliability 0 1 2N2484. Instruments

PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME NUMBER SEC39106678 SEC39106671 NEXT ASSEMBLY: NUMBER RECTIFIER-FILTER MODULE PRIMARY SIDE NAME MFG'S DESCRIPTION QUAL METHOD OF SPECIFICATION PART NO. OR MFG. AND/OR DRAWING ITEM QUALIFICATION STATUS DRAWING NO. DRAWING TITLE DESIGNATION NO. 2 Q 2 Established T210C476 MIL-C-39008 Kemet CAPACITOR - 47µf, 20V C7, C10 Reliability K020RS 2 2 Established T210B395 Kemet CAPACITOR - 3.9µf, 75V C16, C18 Reliability KO75PS 2 Established 2 T210CG86 Kemet CAPACITOR - 68µf, 15V C12, C14 Reliability K015RS . 2 MIL-S-19500 Established Texas JAN TX DIODE CR22, CR23 Reliability Instruments 1N645

OF PAGE SKYLAB ELECTRON-PROTON SPECTROMETER REVISION LETTER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ASSEMBLY: ELECTRON-PROTON SPECTROMETER NAME SEC39106672 NUMBER SEC 39 106980 NEXT ASSEMBLY: NUMBER SECONDARY SIDE NAME LOW VOLTAGE POWER SUPPLY NAME MFG'S DESCRIPTION METHOD OF QUAL PART NO. OR SPECIFICATION MFG. AND/OR DRAWING QUALIFICATION STATUS ITEM DRAWING NO. DRAWING TITLE DESIGNATION NO. Hi-Rel Q 1 MIL-R-27208 3262W-POTENTIOMETER - 10k Bourns R19 Testing 1-103 1 Established Ó µ723 MIL-STD-Fairchild VOLTAGE REGULATOR 21 Reliability 883/Level A

PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME SEC39106688 NUMBER SEC39106672 NEXT ASSEMBLY: NUMBER DISCRIMINATOR REG. MODULE NAME SECONDARY SIDE NAME QUALIFICATION STATUS MFG'S DESCRIPTION SPECIFICATION PART NO. OR MFG. AND/OR DRAWING ITEM DRAWING NO. DRAWING TITLE DESIGNATION NO. 1 Established Q. MIL-R-55182 PMC50H Мерсо RESISTOR - 11.5kΩ, 1%, 1/20W R18 Reliability 1152FR 2 0 RNC50H Mepco RESISTOR - 5.98kn, 18, 1/20W R20, R22 6981FR Q MIL-R-39008 Allen RCR07G RESISTOR - 130, 5%, 1/4W R21 130JP Bradley 1 Q 1 MIL-R-55182 RNC50H RESISTOR - $15k\Omega$, 1%, 1/20W Mepco R39 153FR 1 1 MIL-C-39014 CKR05BX Kemet CAPACITOR - 1000pf, 200V C5 102KP 1 1 MIL-C-39014 CKR05BX Kemet CAPACITOR - 100pf, 200V Ç6 101KP 2 2 MIL-C-39003 T210B156 Kemet CAPACITOR - 15µf, 20V C9, C11 K020RS 2 2 T210B226 Kemet CAPACITOR - 22µf, 15V C13, C15 K015RS 2 2 T210B395 Kemet CAPACITOR - 3.9µf, 75V C17, C19 K075PS 1 Established MIL-S-19500 JAN TX Texas DIODE - Zener CR24 Reliability 1N758A Instruments

PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: NAME NUMBER SEC39107473 NEXT ASSEMBLY: NUMBER SEC39106690-NAME INPUT FILTER MODULE DATA PROCESSOR LYPS SLICE NAME MFGS DESCRIPTION PART NO. OR SPECIFICATION METHOD OF QUAL MFG. DRAWING AND/OR ITEM QUALIFICATION STATUS DRAWING NO. DRAWING TITLE DESIGNATION NO. MIL-C-15305 Hi-Rel Q. 2 Potter 8336-001 FILTER Testing Hi-Rel Q MIL-C-15305 Potter 8332-125 FILTER Testing

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PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ASSEMBLY : ELECTRON-PROTON SPECTROMETER NAME NUMBER SEC39107014 SEC39107473 NEXT ASSEMBLY: NUMBER NAME INPUT FILTER INPUT FILTER MODULE NAME MFG'S DESCRIPTION SPECIFICATION METHOD OF PART NO. OR MFG. AND/OR DRAWING ITEM QUALIFICATION STATUS DRAWING NO DRAWING TITLE DESIGNATION NO. 1 Established MIL-R-39008 RCR05G Allen RESISTOR - 2.70, 1%, 1/8W Reliability R3 2R7JS Bradley 5 Established MIL-C-39003 T210D156 Kemet CAPACITOR - 15pf, 75V C1, C3 -Reliability K075PS Established MIL-C-39014 CKR06 Kemet CAPACITOR - .luf, 100V C2, C7 Reliability BX104KP

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OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST OUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ASSEMBLY : ELECTRON-PROTON SPECTROMETER NAME NUMBER SEC39107016 NEXT ASSEMBLY: NUMBER SEC39107473 NAME FILTER SURGE LIMITERS INPUT FILTER MODULE NAME MFG'S DESCRIPTION SPECIFICATION METHOD OF PART NO. OR MFG. AND/OR DRAWING ITEM QUALIFICATION STATUS DRAWING . NO. DRAWING TITLE DESIGNATION NO. Hi-Rel Q MIL-S-19500 Unitrode 1N4942 DIODE CR1, CR2 Testing Hi-Rel MIL-S-19500 UT4010 Unitrode DIODE CR3 - CR6 Testing MIL-R-39008 Established RCR05G RESISTOR - 4.70, 1%, 1/8W Allen P.1 Reliability 4P.7JS Bradley Established RWR81S Dale · RESISTOR - .50, 1%, 1W R2 Reliability R500FR Established RWR81S Dale . RESISTOR - 1.30, 18, 1W R4. Reliability 1R300FR

OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER FLECTPON-PROTON SPECTPOMETER ASSEMBLY: NAME SEC39106991 NUMBÉR SEC39106673 NEXT ASSEMBLY: NUMBER MULTIPLEXER MODULE NAME DATA PROCESSOR NAME MFG'S DESCRIPTION PART NO. OR SPECIFICATION METHOD OF QUAL , MFG. AND/OR DRAWING ITEM QUALIFICATION STATUS DRAWING NO. DESIGNATION DRAWING TITLE NO. 2 2 MIL-STD-MIL-STD-HS-9-1000-Harris MULTIPLEXER - 16-Channel 21, 22 883 883 Level A Semi-2 Conductor Hi-Rel MIL-C-15305 Q J. W. 9210-76 INDUCTOR - 100µH L1, L2 Testing Miller MIL-C-39014 Established CKROGBK Union CAPACITOR - .1µf, 100V C1 - C2 Reliability 104KP Carbide MIL-R-39008 Established Allen RCR05G : RESISTOR - 1kn, 10%, 1/8W Rl Reliability Bradley 102JS 12 12 Hi-Rel MIL-S-19500 Texas JAN-TX DIODE CR1 -Testing 1N914 Instruments CR12

SKYLAB ELECTRON-PROTON SPECTROMETER FFF PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY : NAME NUMBER SSEC39107003. NEXT ASSEMBLY: NUMBER SEC39106673 A/D CONVERTER NAME DATA PROCESSOR MFG'S DESCRIPTION METHOD OF QUAL . MFG. PART NO. OR SPECIFICATION ITEM DRAWING AND/OR STATUS QUALIFICATION DRAWING NO DRAWING TITLE NO. DESIGNATION 3 Established MIL-R-55182 RNC50II Mepco RESISTOR - $4.99k\Omega$, 18 R3, R9, Reliability 4992FR R14 Established 1 RNC 50H Mepco RESISTOR - 9.53k Ω , 1% R5 Reliability 9532FR Established Q 1 Mepco RNC5011 RESISTOR - Selected R8 Reliability Hi-Rel 1 3260HM MIL-R-27208 Bourns R7 POTENTIOMETER - 10kn Testing 39103 Established MIL-R-55182 RNC 50H RESISTOR - 11.3k Ω , 18 Мерсо R4 Reliability 1132FR 2 Hi-Rel MG660 MIL-R-55182 Caddock R2, R10 RESISTOR - $10M\Omega$, 1% Testing Established RNC50H RESISTOR - $47.5k\Omega$, 18 Mepco R6 . Reliability 4752FR Established 49922FR Mepco RESISTOR - $49.9k\Omega$, 1% R11. R12. Reliability R13 3 Hi-Rel Q MIL-STD-LM108/ INTEGRATED CIRCUIT Advance 21 thru 883 . 883/Level A Testing Micro 23 Q MIL-STD-Ni-Rel Advance LM 111/ 24 INTEGRATED CIRCUIT 883/Level A Testing 883/Level Micro Q MIL-STD-Hi-Rel DAS 2132 INTEGRATED CIRCUIT Dickson 25 . Testing 883/Level A Hi-Rel 0 1N4567A MIL-S-19500 Dickson VR1. DIODE - Zener Testing Established 2 JANTX

Texas

Miller

TRW

Instrument

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MS90538-

TX Testing

Established

Reliability

Hi-Rel

Testing

MIL-C-15305

MIL-C-39014

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REVISION LETTER

DIODE

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CAPACITOR - 2µf

CR2. CR3

L1, L2

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REVISION LETTER PAGE OF SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER NAME ELECTRON-PROTON SPECTROMETE ASSEMBLY: SEC39107003 SEC39106673 NUMBER NEXT ASSEMBLY: NUMBER DATA PROCESSOR A/D CONVERTER NAME MFG'S DESCRIPTION ITEM PART NO. OR DRAWING AND/OR MFG. SPECIFICATION METHOD OF QUAL DESIGNATION DRAWING NO. DRAWING TITLE QUALIFICATION STATUS CKR06BX MIL-C-39014 Established Q CAPACITOR - .luf Kemet C3, C4, Reliability 104KP C6, C7, C9, C10 C11, C13, C14 ž. C12 CAPACITOR - .01µf CKR06BX MIL-C-39014 Established Q 1 Kemet 103KP Reliability C5, C8, CAPACITOR - 100pf Kemet : CKR05BX MIL+C-39014 Established Q 101KP Reliability

OF PAGE REVISION LETTER SKYLAB ELECTRON-PROTON SPECTROMETER EEE PARTS LIST QUANTITY PER SUB ASSEMBLY SEC39106425 TOP ASSEMBLY: NUMBER ELECTRON-PROTON SPECTROMETER ASSEMBLY: SEC39107005 NUMBER NEXT ASSEMBLY: NUMBER SEC39106673 A/D LOGIC MODULE NAME DATA PROCESSOR MFG'S DESCRIPTION METHOD OF QUAL PART NO. OR SPECIFICATION MFG. AND/OR ITEM DRAWING QUALIFICATION STATUS DRAWING NO NO. DESIGNATION DRAWING TITLE MIL-STD-Hi-Rel 0 4 SNH54L INTEGRATED CIRCUIT Texas 21, 26, 01-02 883 Level H Testing Instrument 28, 216 3 MIL-STD-0 3 SNH54L Texas 22, 27, 883 Level H 93T-02 Instruments 29 4 MIL-STD-0 SNH54L Texas 23, 213. 883 Level H Instrument: 00T-02 215, 218 Q 2 MIL-STD-2 Texas SNH54L 24, 214 883 Level H 73T-02 Instruments U4196L MIL-STD-0 Advance 25 0251 883 Level H Micro MIL-STD-Q 1 SMH54L Texas Z10 30T-02 883 Level H Instruments Q 1 MIL-STD-SNH54L 1 Texas Z11 ' 20T-02 Instruments 883 Level H 2 SNH54L MIL-STD-Hi-Rel 0 2 Texas 212, 217 04T-02 883 Level H Testing Instrument 1 Established MIL-R-55182 RNC50H 1 RI RESISTOR - $22k\Omega$, 1%, 1/20WMepco Reliability 2202FR 2 RNC50H RESISTOR - 1.0k Ω , 1%, 1/20W R2, R4 1001FR 1 Q RNC50H RESISTOR - 10kn, 1%, 1/20W R3 1002FR 1 RC10G MIL-C-39014 Q USCC 1 CAPACITOR - 100pf Cl 101J 1 CKR06BX 1 C2 CAPACITOR - .luf Kemet 1.04KP T210A335 MIL-C-39003 Established 1 Kemet C3 CAPACITOR - 3.3µf K015R3 Reliability

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3.3.11 Standard Parts

Refer to paragraph 3.3.10.9.1

3.3.13 Fungus Resistance

The parts and materials used on the EPS were selected to resist fungus by the elimination of nutrients which could support such fungus. The electronic assemblies are conformal coated to further prevent surface and component exposure to fungus. Humidity tests have proved that the electronics and mechanical packaging are free of nutrients for fungus. The exposed surfaces of the baseplate has been chemically treated to prevent fungus and corrosion. All other components used on the EPS are sealed or otherwise free of fungus nutrients.

3.3.13 Corrosion Prevention

Metal and mechanical parts used in the EPS are of the corrosion resistant type. Areas that are exposed to possible corrosion has been suitably treated to prevent corrosion.

3.3.14 Interchangeability and Replaceability

The EPS was designed, as a total unit, to be replaceable on any flight of Skylab. Each subassembly was designed so a like assembly will have interchangeability and replaceability. It becomes necessary to calibrate the EPS after replacement of certain modules, however, this is expected in any equipment of this type. Spare subassemblies are designed to replace those in the EPS if it becomes necessary.

3.3.18 Storage

Ancillary hardware has a storage life of five years. The only parts or materials which are sensitive to age or storage environments are the EPS detectors which are not to be installed in the EPS instrument until approximately three weeks before launch. Control is maintained on these items by historical record card.